Honeywell

H316 **CIRCUIT MODULES AND PARTS INSTRUCTION MANUAL**

Doc. No. 70130072166AV Order No. M-494

Honeywell

SERIES 16

H316 CIRCUIT MODULES AND PARTS INSTRUCTION MANUAL

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PREFACE

This instruction manual provides complete descriptive and reference material for the circuit modules and parts used in the H316 General Purpose Computer manufactured by Honeywell Inc., Framingham, Massachusetts. Three types of H316 computers are manufactured: Types 316-01, 316-0100, and 316-0110. The differences among the three are, for the most part, mechanical and, unless specifically stated, the parts for the three are the same. Options are documented in separate manuals.

This manual is divided into four chapters: Chapter I contains technical specifications, microcircuit characteristics, and individual assembly illustrations and parts listings for the logic modules. Chapters II and III provide instructions for proper operation and maintenance of the CSM-160 and CSM-150 core memories, respectively, and associated PAC logic modules. A detailed illustrated parts breakdown is presented in Chapter IV as an aid to service personnel in identification and procurement of replaceable parts including assemblies and components.

NOTICE

All H316 power supply information, formerly presented in this publication as Chapters IV and V, now appears as Appendices A and B in this document for this printing only. The power supply information will appear in Document Number 70130072759, Order Number M-1532, as of January 1974.

CHAPTER I PLUG-IN CIRCUIT MODULES

This chapter contains specifications for integrated circuit plug-in devices used throughout the H316 General Purpose Computer. Section 1 contains the information pertinent to integrated circuit characteristics associated with the logic module subassemblies. Section 2 contains detailed assembly and schematic drawings and parts listings for each logic circuit module type.

SECTION 1 INTEGRATED CIRCUIT CHARACTERISTICS

This section contains general specifications and detailed technical data for the integrated circuits used on the H316 logic modules.

SPECIFICATIONS

All performance specifications are guaranteed based on worst-case tolerances.

Actual performance will invariably exceed these specifications. The following specifications apply to all circuit types.

Input Switching Thresholds

The following definitions apply to all electronic signals. A "passive" signal is defined as a signal that denotes voltage potential between +2.5 volts and +V_{cc}. An "active" signal is defined as a signal that denotes potential between 0 volt and +0.95 volts. Figure 1-1-1 defines the switching thresholds of the circuits. An "active" input applied to a gate will guarantee a "passive" output. If a "passive" signal is simultaneously applied to all inputs of a NAND gate, the output is guaranteed to be "active."

Output Logic Levels (for all circuit types)

Active Levels: 0 to 0.5 volts
Passive Levels: 3.5 to 6.3 volts

Temperature Range

Operating (case temperature): 0°C to +80°C

Storage: -65°C to +150°C

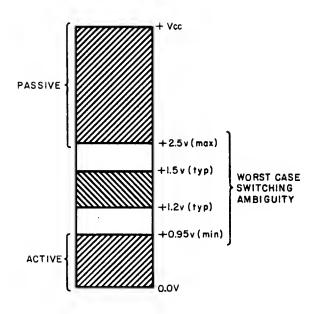


Figure 1-1-1. Switching Thresholds

Power Supply Requirements

Nominal: +5.5V to +6.0V

Operating Range: +5.1 to +6.3V

Absolute Maximum Rating: +8.0V

Fan-In Expansion Using Nodes

Many of the integrated circuits have expansion nodes available on gate inputs allowing input gating expansion by connecting discrete diodes. As many as twenty silicon diodes may be connected to one node without degrading dc performance. However, there is degradation in the turn-on delay as the stray capacitance on the node point is increased. This delay increase amounts to 1.5 nanoseconds per picofarad of added capacitance.

Loading

Loading and drive specifications are expressed in terms of current (milliamperes). Input load current is the amount of current that the driving source must sink when the source is active. A passive drive source is not required to sink or supply current except for minor amounts of leakage.

Basic NAND Circuit

All NAND gates are ground-emitter, inverter amplifiers. All inputs are diodebuffered, and the output is the voltage of a saturated transistor when it is in the active state. The following circuits have an internal resistor to V_{CC} connected to the collector of each output: 930, 961, 946, 949, 936, 937, 962, 963, and F-19 (excluding circuit C). The F-04 flip-flops also have resistors to V_{CC} . The following contain total pole circuits which provide a low drive impedance when the circuits go from the active to passive state: F-03, F-09, 932, F-19 (circuit C only). The following circuits have open collectors: F-01, 944, and 032. All outputs are protected so that accidental grounding of an output will not cause circuit damage.

When all inputs to a NAND gate have passive signals applied, the output will be active. If any one input to a NAND gate is active, the output will be passive.

TYPE F-01 NAND GATE (CCD 70 950 100 001)

The F-01 dual NAND gate (Figure 1-1-2) has two 3-input gates, each with an input node and a separate kilohm load resistor which is connected to $\pm V_{CC}$.

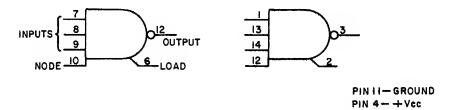


Figure 1-1-2. F-01 Dual NAND Gate

Specifications

Input Loading: 2.0 mA
Output Drive: 23.0 mA

Circuit Delay: 30 ns (max) measured at 1.5V level with 75 pF

stray capacitance

TYPE F-03 POWER AMPLIFIER (CCD 70 950 100 003)

The F-03 power amplifier microcircuit (Figure 1-1-3) has two 3-input inverter amplifiers with nodes for input gating expansion. The power amplifier circuit is logically equivalent to the F-01 gate but has twice the dc drive and three times the ac drive capability.

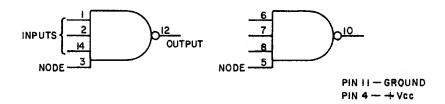


Figure 1-1-3. F-03 Power Amplifier

Specifications

Input Loading:

4.0 mA

Output Drive:

50.0 mA

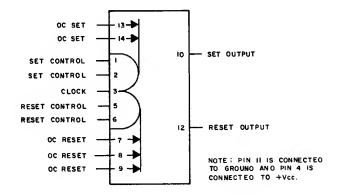
Circuit Delay:

30 ns (max) measured at 1.5V level with 250 pF

stray capacitance

TYPE F-04 FLIP-FLOP (CCD 70 950 100 004)

The standard μ -PAC integrated circuit flip-flop, type F-04, is a double-rank, J-K flip-flop with dc set and reset capability. Figure 1-1-4 shows the logic symbol and equivalent logic circuit.



A. LOGIC SYMBOL

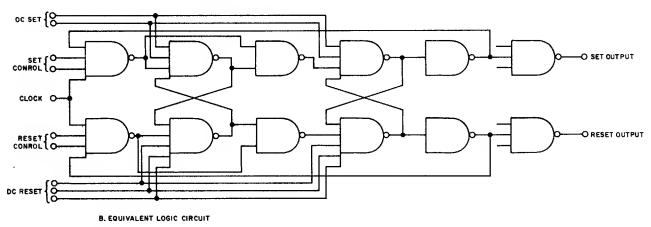


Figure 1-1-4. Type F-04 Flip-Flop Logic Symbol and Equivalent Logic Circuit

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The clock gate portion of the flip-flop is composed of the clock and the set and reset control inputs. The control inputs are energized by passive signals. A positive pulse on the clock will cause the flip-flop to assume the state determined by the condition of the control inputs. With J-K circuitry, no combination of the control input signals can cause an ambiguous state.

The set and reset control inputs may be used as follows.

- a. To gate clock pulses
- b. As direct set and reset inputs
- c. As another clock input when a set and a reset control are tied together.

For dc operation, voltage levels are used on the dc inputs. Signals applied to the dc set and reset inputs take precedence over any ac gating. However, output spikes may occur when the reset clock gate is activated during a dc set, or vice-versa. Such spikes can be eliminated by tying the dc set input to a reset control input and tying the dc reset input to a set control input.

Pulse Dodging

The flip-flop utilizes the double-rank technique of pulse dodging (Figure 1-1-5). When the clock input makes the positive transition, the state of the input flip-flop is fixed and data transfer from the input flip-flop to the input of the output flip-flop is inhibited. On the negative transition of the clock input, data from the input flip-flop is shifted to the output flip-flop and the inputs to the input flip-flop are inhibited. Thus the clock provides intrinsic pulse dodging by means of trailing edge triggering. This feature permits strobing of the flip-flop output with input triggering signals.

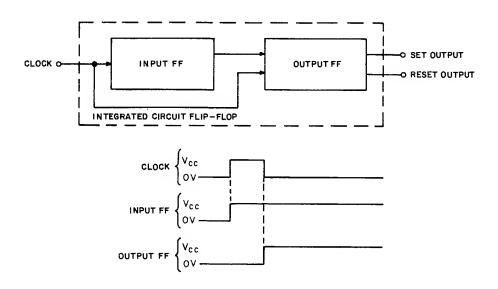
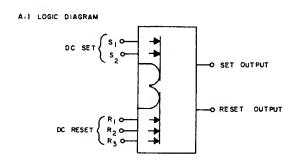


Figure 1-1-5. Double-Rank Flip-Flop Pulse Dodging, Timing Diagram

DC Operation

If either dc set goes to ground, the flip-flop will assume the set state; if any dc reset goes to ground, the flip-flop will assume the reset state. If both a dc set and a dc reset go to ground at the same time, both the set and the reset outputs will be ambiguous. Figure 1-1-6 contains diagrams and equations describing this mode of flip-flop operation.



B) Truth Table and Boolean Equations

$$S_D$$
- AND result of the dc set inputs. $S_D = S_1 \cdot S_2$
 R_D - AND result of the dc reset inputs. $R_D = R_1 \cdot R_2 \cdot R_3$

F - state of the flip-flop (set output)

 $F^{\,\prime}$ - previous state of the flip-flop

$s_{_{ m D}}$	R _D	F
0 V		(Condition not allowed. Output will be ambiguous.)
ov	V _{cc}	Set Reset
V _{cc}	0 V	Reset
Vcc	Vcc	F' (no change) $F = R_D (\overline{S}_D + F')$
		$F = R_D (\overline{S}_D + F')$

C) TIMING DIAGRAM

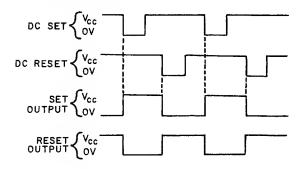
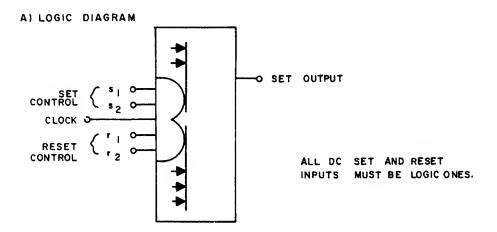


Figure 1-1-6. DC Operation

Control Inputs Used to Steer Clock Pulses

If Vcc is applied to both the set controls (S_C) and the reset controls (R_C) , the flip-flop will be complemented by the application of a clock pulse. If only S_C or R_C is at Vcc, the state of the flip-flop will be a set or reset, respectively, after the clock is energized. If both S_C and R_C are at ground, the flip-flop will remain in its previous state. One restriction is that when a control input is used to gate the clock, the control input cannot make a negative transition while the clock is a ONE. Figure 1-1-7 contains diagrams and equations describing this mode of flip-flop operation.



B) Truth Table and Boolean Equations

 S_C - AND result of the set control inputs, $S_C = s_1 \cdot s_2$

 R_C - AND result of the reset control inputs, $R_C = r_1 \cdot r_2$

F' - previous state of the flip-flop

F - state of the flip-flop after the clock pulse

s	R	F'	F		
ov ov	0V 0V	ov Vcc	0 V V _{CC}	NO CHANGE	
ov ov	V _{cc}	ov V _{cc}	0V 0V	RESET	
V _{CC}	0V 0	ov _{Vcc}	V _{cc}	SET	
V _{cc}	V _{cc} V _{cc}	ov _{Vcc}	∨ ₆ c	COMPLEMENT	

$$F = S_C \overline{F'} + \overline{R}_C F'$$

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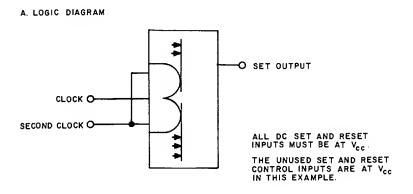
Figure 1-1-7. Control Inputs Used to Gate Clock Pulses (Sheet 1 of 2)

(C) TIMING DIAGRAMS (1) COMPLEMENTING SET CONTROL RESET CONTROL (°cc ______ CLOCK SET OUTPUT (2) SET SET CONTROL RESET CONTROL CLOCK SET OUTPUT RESET (3) SET CONTROL RESET CONTROL (VCC SET OUTPUT (4) NO CHANGE CONDITION I CONDITION 2 SET CONTROL RESET CONTROL CLOCK { Vc c-SET OUTPUT 558

Figure 1-1-7. Control Inputs Used to Gate Clock Pulses (Sheet 2 of 2)

Control Inputs Used as a Second Clock

A set and a reset control can be tied together and used as another clock input. In this case, the resultant clock is the ANDed result of both clocks. Figure 1-1-8 contains diagrams describing this mode of flip-flop operation.



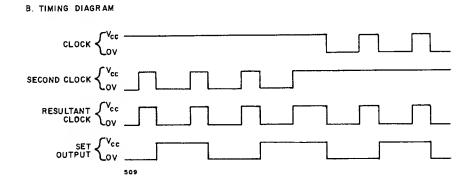
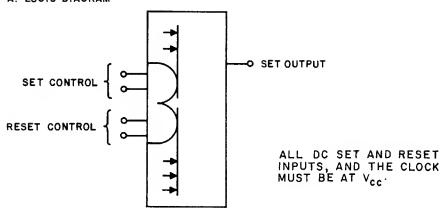


Figure 1-1-8. Control Inputs Used As a Second Clock

Control Inputs Used Directly to Set or Reset

The set and the reset control inputs can also be used separately to change the state of the flip-flop. When the clock is at $V_{\rm CC}$, the first control input that goes from $V_{\rm CC}$ to ground acts as the clock input. After a set control changes from Vcc to ground, the flip-flop will be in the set state. After a reset control changes from Vcc to ground, the flip-flop will be in the reset state. Figure 1-1-9 contains diagrams and equations describing this mode of flip-flop operation.

A. LOGIC DIAGRAM



B) Boolean Equations

 S_{C} - AND result of the set control inputs

 R_{C} - AND result of the reset control inputs

F - state of the flip-flop

primes (') - previous state of a signal

$$F = S'_C \cdot \overline{S}_C$$
 (setting operation)
 $\overline{F} = R'_C \cdot \overline{R}_C$ (resetting operation)

C. TIMING DIAGRAM

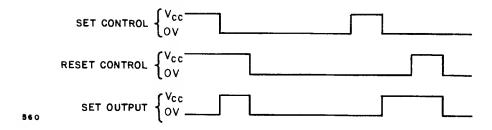


Figure 1-1-9. Control Inputs Used Directly to Set or Reset

Input Loading

DC inputs: 1.33 mA
Clock input: 2.0 mA
Control inputs: 2.0 mA

Output Drive Capability

8 unit loads (both outputs)

(Capable of also driving 75 pF total capacitance with delays as specified.)

Circuit Delay

The following circuit delays are specified from the +1.5V level of the input signal to the +1.5V level of the output signal.

Clock input (negative transition)	$\int 45 \text{ ns (typ)}$
to latest output	$\begin{cases} 45 \text{ ns (typ)} \\ 60 \text{ ns (max)} \end{cases}$
DC set input to set output or	$\begin{cases} 65 \text{ ns (typ)} \\ 80 \text{ ns (max)} \end{cases}$
DC reset input to reset output	•
DC set input to reset output or	$\begin{cases} 45 \text{ ns (typ)} \\ 60 \text{ ns (max)} \end{cases}$
DC reset input to set output	60 ns (max)

Clock and Control Input Timing Requirements

To trigger the flip-flop at the clock or control inputs, pulses must meet the requirements shown in Figure 1-1-10.

DC Input Timing Requirements

To activate a dc input, signals must meet the requirements of Figure 1-1-11.

Control Inputs

Figure 1-1-12 shows the timing requirements of the set and reset control inputs when they are being used to steer the triggering clock input to set the flip-flop. The reset control input must be completely switched to ground before the clock starts positive. No control input should go from Vcc to ground while the clock is positive. The set control input must be switched to Vcc at least 40 ns before the clock starts towards ground. The clock must be a positive pulse of 40 ns minimum duration. The flip-flop changes state on the trailing edge of the positive clock pulse. Reset timing is the same, except that the time relations and logic levels of the set and reset input must be interchanged.

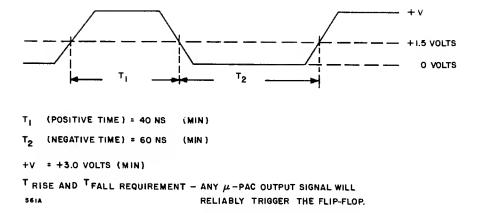


Figure 1-1-10. Flip-Flop Input Pulse Requirements

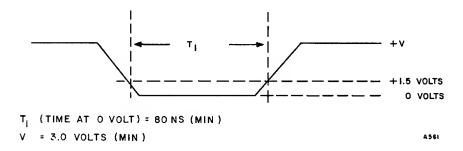


Figure 1-1-11. DC Set and Reset Input Signal Requirements

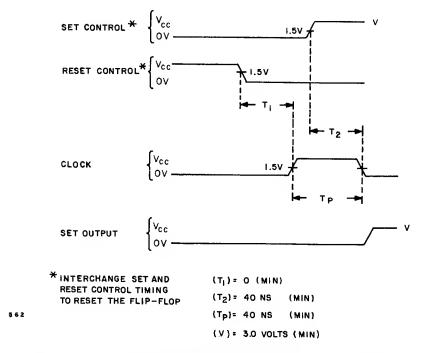


Figure 1-1-12. Timing Requirements for Control Inputs, Using Clock Triggering

Maximum Allowable Clock Skew

In cases where a register is being driven by clock (shift) signals from different sources, the output of one stage may arrive at the next stage before late clock signal. If the delay between the early and late clock signals is more than 30 ns, erroneous data transfer may occur. To guarantee proper operation the allowable clock skew must be as shown in Figure 1-1-13. Note that the triggering signal to flip-flop B is S_A rather than C_B . This situation is not detrimental to the operation of the shift register. Either S_A or C_B may trigger flip-flop B, depending on which occurs first.

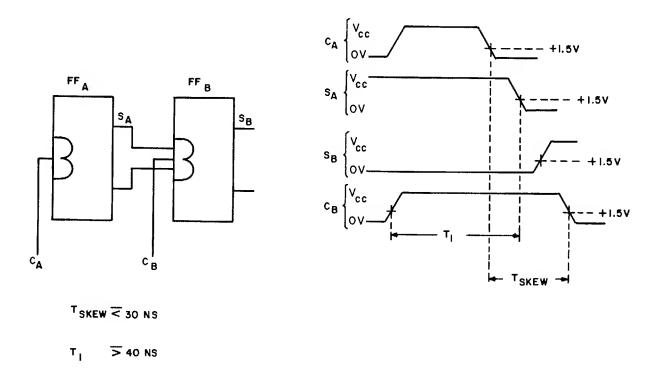


Figure 1-1-13. Allowable Clock Skew, Logic and Timing

TYPE F-09 POWER AMPLIFIER (CCD 70 950 100 009)

The type F-09 high speed power amplifier microcircuit has two 4-input inverter amplifiers with nodes for input gating expansion. (See Figure 1-1-14.) The power amplifier circuit is logically equivalent to the F-01 gate but has about twice the output drive capability. It has a short circuit protection network such that accidental grounding of the output will not damage the circuit.

Specifications

Input Loading: 4.0 mA
Output Drive: 50 mA

Circuit Delay: 15 ns with 70 pF of stray capacitance

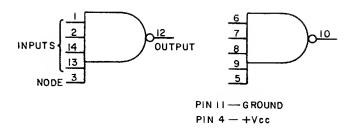


Figure 1-1-14. Type F-09 Power Amplifier Equivalent Logic Symbol

TYPE F-19 FUNCTIONAL LOGIC GATE (CCD 70 950 100 019)

The F-19 (Figure 1-1-15) has five NAND gates interconnected as a functional gating circuit. The outputs of A and B are connected together and can be used to perform the logic OR operation. This output is connected as an input to the power amplifier inverter (gate C). Gates B, D and E have input nodes (pins 2, 6 and 7) to facilitate input gate expansion by connecting discrete diodes to them.

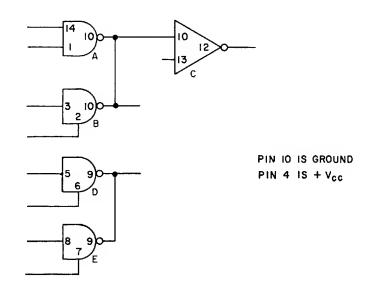


Figure 1-1-15. F-19 Logic Symbol

Specifications

Input Load:

2.0 mA

Output Drive:

Circuit A-B, D-E - 23.5 mA

Circuit C

- 40.0 mA

Circuit Delay:

20 ns per gate with 70 pF stray capacitance

TYPE 930/961 NAND GATES (CCD 70 950 105 001/009)

The 930 and 961 (Figure 1-1-16) dual 4-input NAND circuits are logically similar to the F-01 gate. The 930 has a 6 kilohm resistor connected between the output collector and $+V_{cc}$ while the 961 has a 2 kilohm resistor. Otherwise, the two are identical.

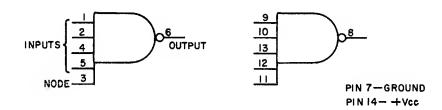


Figure 1-1-16. 930/961 Dual NAND Gates

Specifications

Input Loading: 1.6 mA

12.8 mA

Output Drive: Circuit Delay:

930-75 ns averaged over two stages

961-50 ns averaged over two stages

TYPE 946/949 NAND GATES (CCD 70 950 105 002/010)

The 946 and 949 (Figure 1-1-17) quad 2-input NAND circuits are similar to each other in all respects except for the value of the resistor which connects between the output collector and +V_{cc}. The 946 has a 6 kilohm resistor while the 949 has a 2 kilohm. The AND-OR-INVERT operation can be performed with the 6 kilohm version by connecting the output of two gates together. This can be done without substantial reduction in output drive capability.

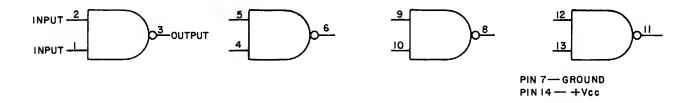


Figure 1-1-17. 946/949 Quad NAND Gates

Specifications

Input Loading: 1.6 mA
Output Drive: 12.8 mA

Circuit Delay: 946-75 ns averaged over two stages

961-50 ns averaged over two stages

TYPE 936/937 HEX INVERTER (CCD 70 950 105 004/011)

The 936 and 937 (Figure 1-1-18) contain six inverter circuits. The 936 has a 6-kilohm resistor while the 937 has a 2 kilohm.

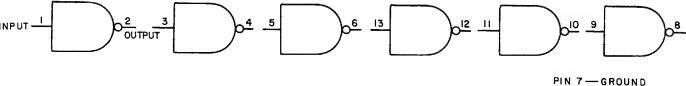


Figure 1-1-18. 936/937 Hex Inverter

PIN 14 — +Vcc

Specifications

Input Load: 1.6 mA
Output Drive: 12.8 mA

Circuit Delay: 936-75 ns averaged over two stages 937-50 ns averaged over two stages

TYPE 932 POWER AMPLIFIER (CCD 70 950 105 005)

The type 932 power amplifier has two 4-input inverter amplifiers with nodes for input gating expansion (see Figure 1-1-19). The circuit is logically equivalent to the 930 gate but has twice the output drive capability. The 932 output cannot be connected to other outputs to perform the AND-OR-INVERT logic function.

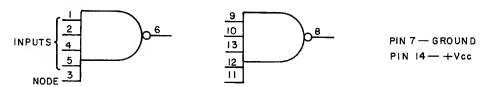


Figure 1-1-19. 932/944 Power Amplifiers

Specifications

Input Load: 1.6 mA
Output Drive: 36.0 mA

Circuit Delay: 80 ns averaged over two stages driving 500 pF of

stray capacitance

TYPE 944 POWER AMPLIFIER (CCD 70 950 105 008)

The 944 (Figure 1-1-19) dual 4-input power amplifier differs from the 932 only in that it has an open collector for OR operations. The turn-on delay is 40 nanoseconds when driving 120 picofarads of stray capacitance. The turn-off delay is dependent on the amount of external current that is supplied to charge the stray capacitance. The input loading and output drive specifications are similar to the 932.

TYPE 962/963 TRIP NAND GATES (CCD 70 950 105 006/012)

The 962 and 963 (Figure 1-1-20) triple 3-input NAND gates are similar to each other in all respects except for the value of resistance between the collectors and $+V_{CC}$. The 962 has a 6 kilohm resistor while the 963 has a 2 kilohm resistor.

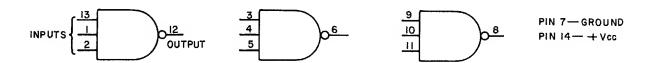


Figure 1-1-20. 962/963 Trip NAND Gates

Specifications

Input Load:

1.6 mA

Output Drive:

12.8 mA

Circuit Delay:

962-75 ns averaged delay over two stages

963-50 ns averaged delay over two stages

TYPE 032 QUAD NAND GATE (CCD 70 950 100 032)

The 032 quad 2-input NAND gate (Figure 1-1-21) is logically similar to the 930 but it does not have a resistor between the collector and $\pm V_{cc}$. This feature allows many of these gates to be collector ORed without degrading the dc drive capability.

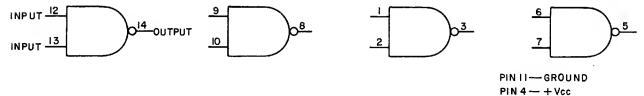


Figure 1-1-21. 032 Quad NAND Gate

Specifications

Input Load:

1.6 mA

Output Drive:

20.0 mA

Circuit Delay:

45 ns averaged over two stages

SECTION 2 MODULE DESCRIPTIONS

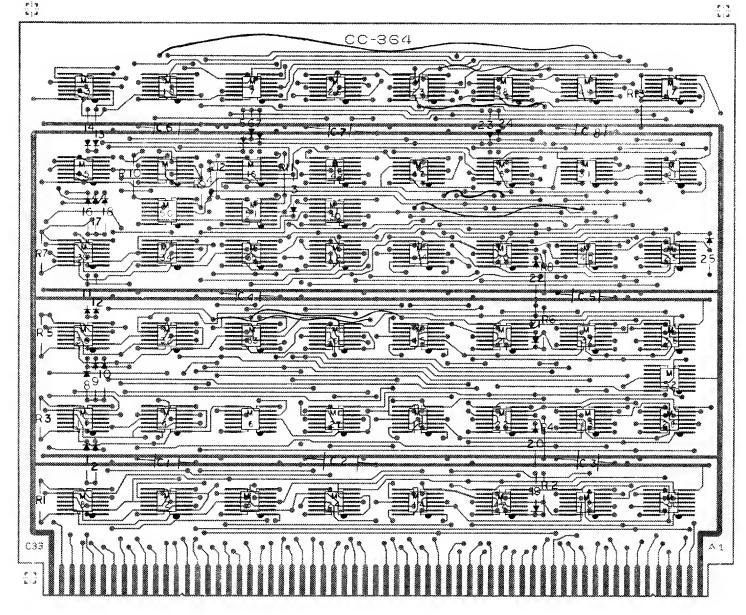
This section contains detailed assembly and schematic diagrams, and parts listings for the following logic circuit modules.

€C-364A	Columns 1-4 Module
CC-365A	Columns A-D Module
CC-366A	Columns 9-12 Module
CC-367	Address Bus Module
CC-368	Shift Register Module
CC-369B	Lamp Driver Module
CC-370	M Register Module
CC-371	Clock Module
CC-372	Regulator Counter Module
CC-373/CC-899	Memory Timing Module
₩CC-374	ASR Interface Module
CC-375	High Speed A-U No. 1 Module
CC-401	High Speed A-U No. 2 Module
CC-510A/CC-869	Extended Address Module
CC-558/CC-621	Memory Parity Board
CC-672	Cable PAC
CC-681	Cable PAC

COLUMNS 1-4 MODULE, MODEL CC-364A

Electrical Parts List

D. C		
Ref. Desig.	Description	Part No.
Cl-C8	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 µF ±20%, 50 Vdc	70 930 313 016
CR1-CR14, CR16-CR18, CR23-CR25	DIODE: Replacement type 1N914	70 943 083 002
CR19-CR22	DIODE: Replacement type 882	70 943 024 002
M1-M4, M6 M9, M25, M28-M30, M32-M35, M38	MICROCIRCUIT: 946, quad NAND gate integrated circuit	70 950 105 002
M5	MICROCIRCUIT: 962, triple NAND gate integrated circuit	70 950 105 006
M7, M8, M11 M16, M17, M19, M31, M36, M39, M41, M43, M45, M48, M50, M51	MICROCIRCUIT: Power amplifier integrated circuit	70 950 105 008
M10, M13 M37, M40	MICROCIRCUIT: 963, triple NAND gate integrated circuit	70 950 105 012
M12, M2 4 , M27, M46	MICROCIRCUIT: F-01, Dual NAND gate integrated circuit	70 950 100 001
M14, M15, M18, M20-M22, M42, M44, M52	MICROCIRCUIT: 032, quad NAND gate integrated circuit	70 950 100 032
M23, M26	MICROCIRCUIT: 936, hex inverter integrated circuit	70 950 105 004
M47, M49	MICROCIRCUIT: 930, dual NAND gate integrated circuit	70 950 105 001
R1, R3, R5, R7	RESISTOR, FIXED, COMPOSITION: 2K ±5%, 1/4W	70 932 007 056
R2, R4, R6, R8	RESISTOR, FIXED, COMPOSITION: 510 ohms ±5%, 1/4W	70 932 007 042
R9-R13	RESISTOR, FIXED, COMPOSITION: 1K ±5%, 1/4W	70 932 007 049



COMPONENT VIEW

Figure 1-2-1. Columns 1-4 Module Parts Location

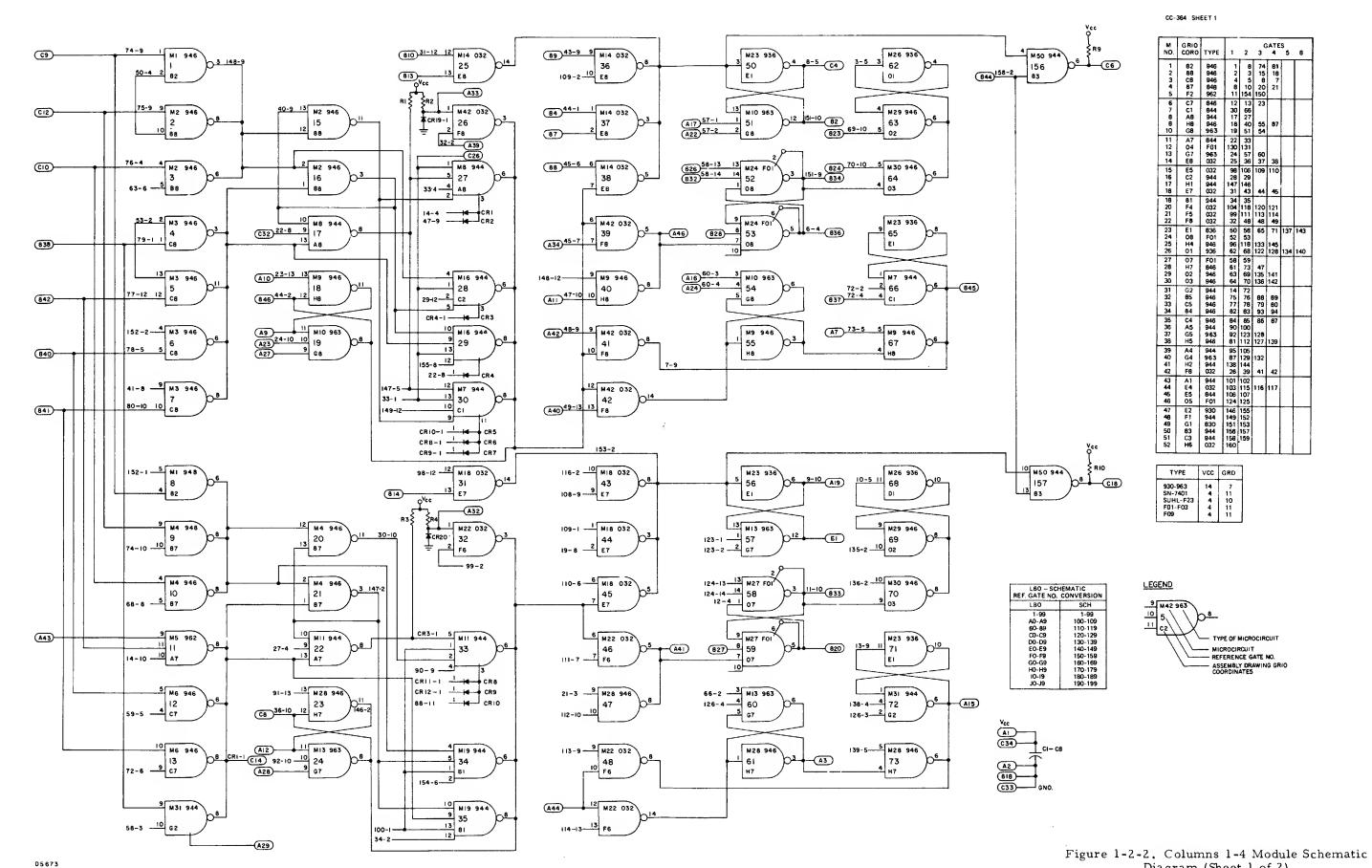
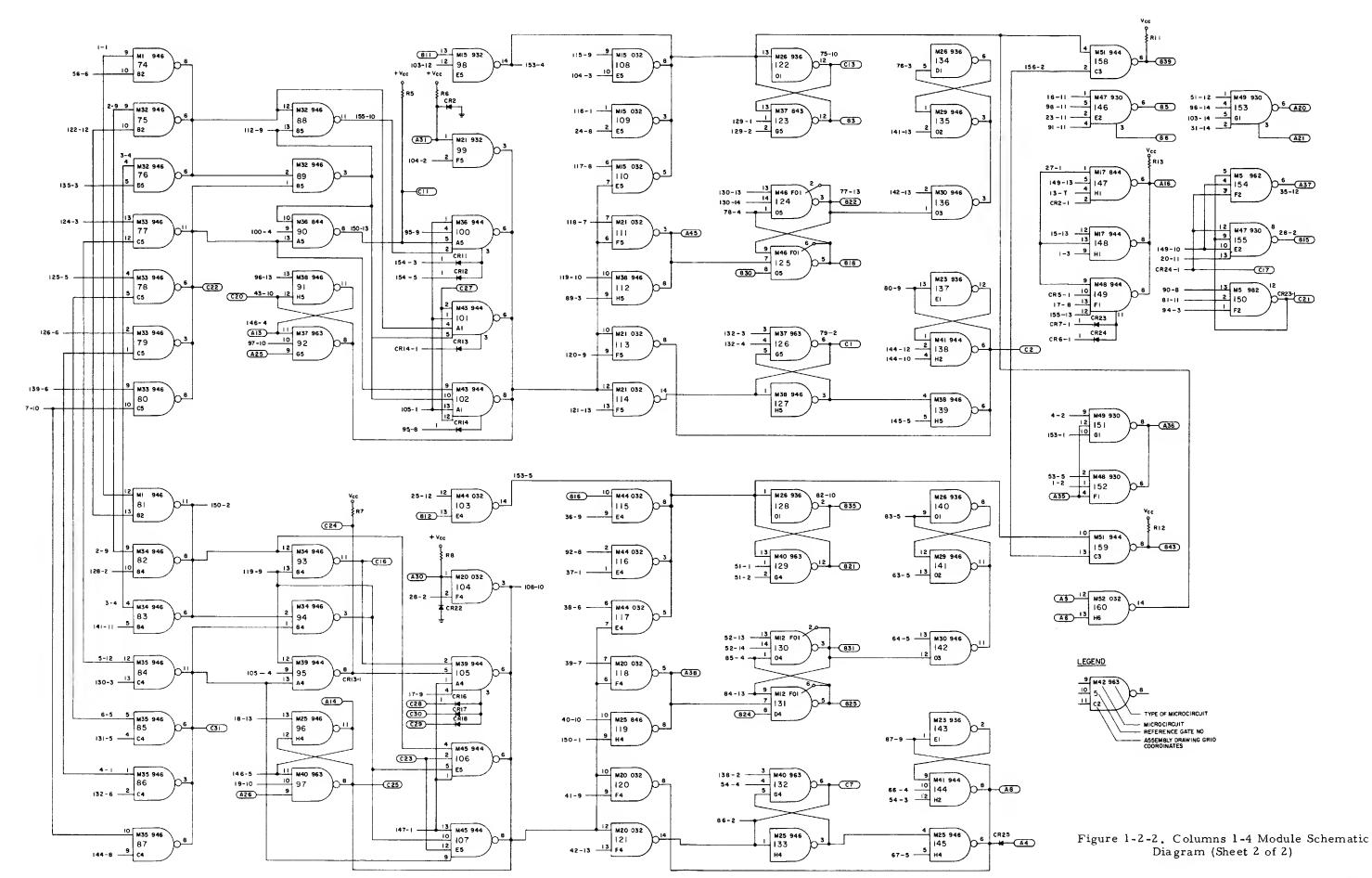


Diagram (Sheet 1 of 2)



COLUMNS A-D MODULE, MODEL CC-365A

Ref. Desig.	Description	Part No.
C1-C8	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 µF ±20%, 50 Vdc	70 930 313 016
CR1, CR2, CR13, CR14	DIODE: Replacement type 882	70 943 024 002
CR3-CR12, CR15-CR38	DIODE: Replacement type 1N914	70 943 083 002
M1, M6, M7, M20, M21, M30, M31, M41	MICROCIRCUIT: 032, quad NAND gate integrated circuit	70 950 100 032
M2, M5, M9, M12, M15, M16, M19, M23, M26, M29, M33, M36, M39, M43, M49	MICROCIRCUIT: 946, quad NAND gate integrated circuit	70 950 105 002
M3, M4, M13, M14, M17, M18, M27, M28, M37, M38, M45, M46	MICROCIRCUIT: 944, power amplifier integrated circuit	70 950 105 008
M8, M22, M42, M32	MICROCIRCUIT: 963, triple NAND gate integrated circuit	70 950 105 012
M35, M48	MICROCIRCUIT: 962, triple NAND gate integrated circuit	70 950 105 006
M10, M25	MICROCIRCUIT: 936, hex inverter integrated circuit	70 950 105 004
M11, M24, M34, M44	MICROCIRCUIT: F-01, dual NAND gate integrated circuit	70 950 100 001
M40, M47, M50	MICROCIRCUIT: 930, dual NAND gate integrated circuit	70 950 105 001
R1, R2, R7 R8	RESISTOR, FIXED, COMPOSITION: 510 ohm ±5%, 1/4W	70 932 007 042
R3-R6	RESISTOR, FIXED, COMPOSITION: 2K ±5%, 1/4W	70 932 007 056

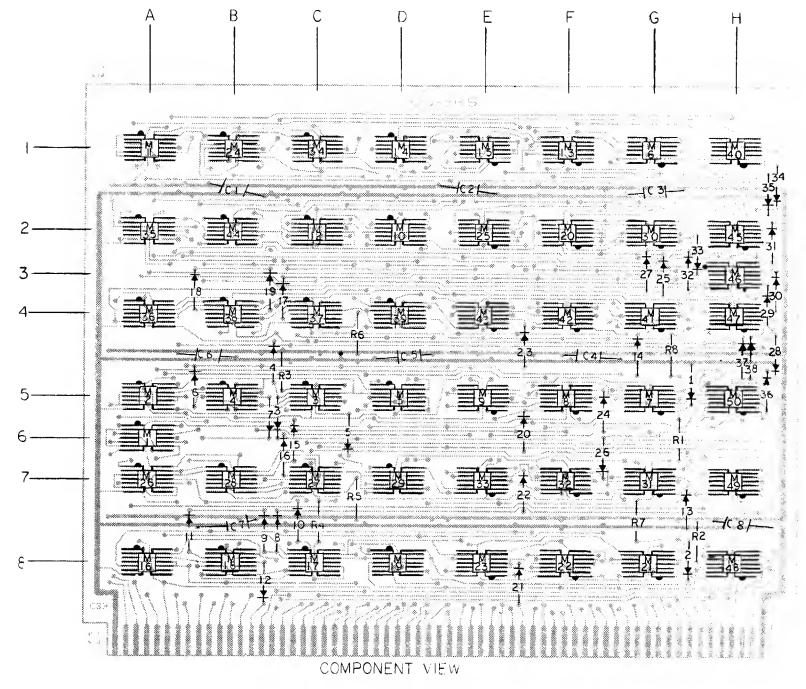
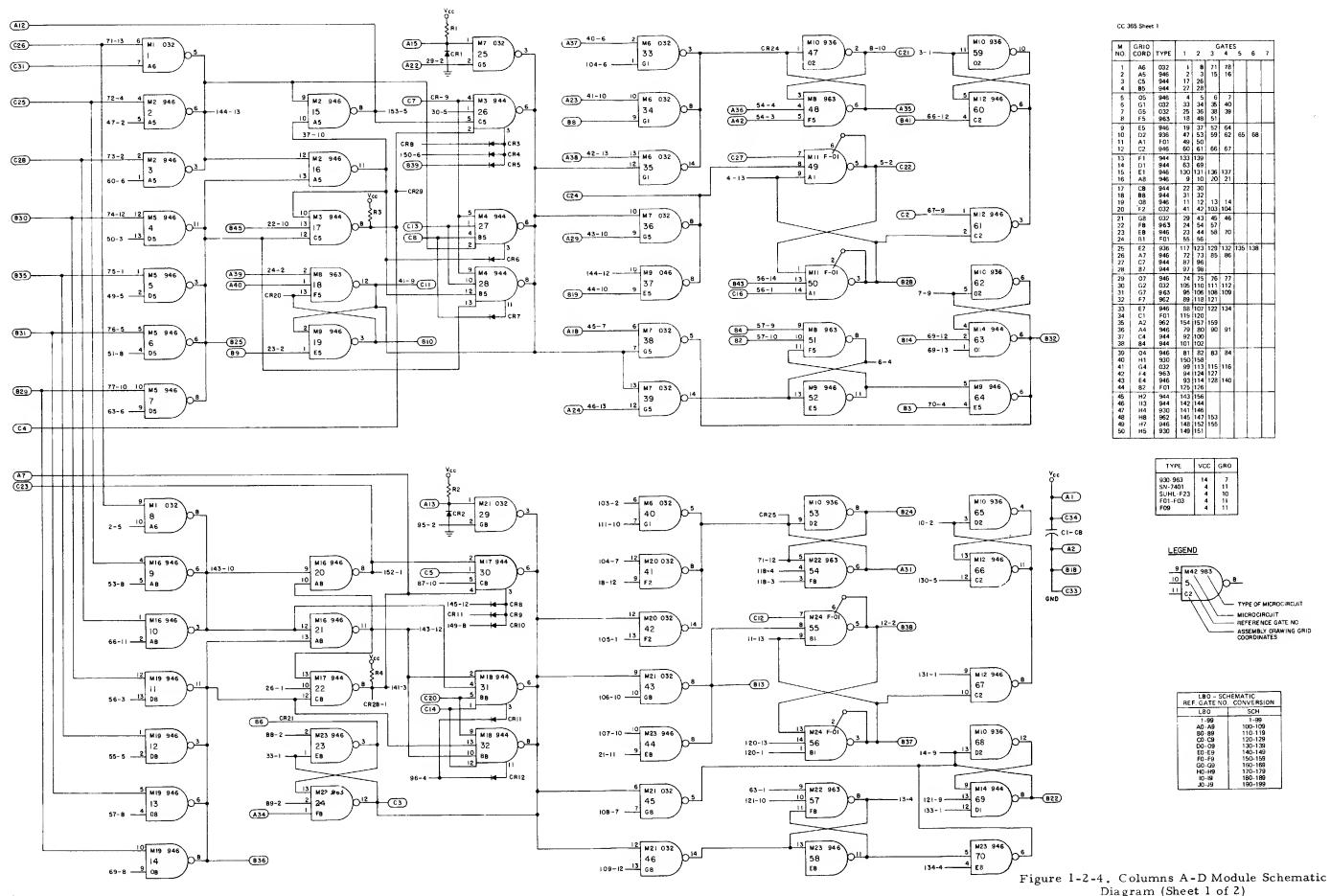
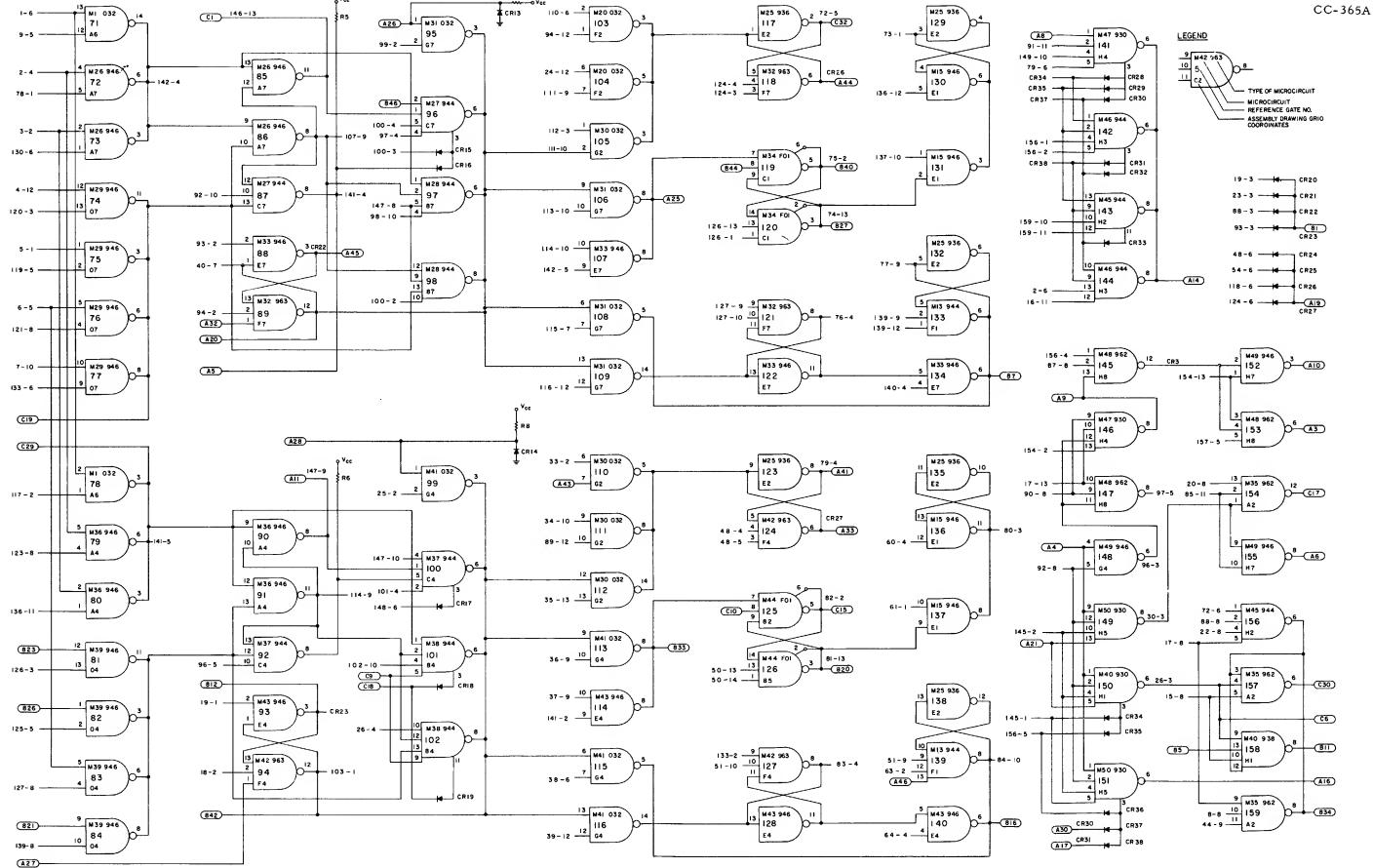


Figure 1-2-3. Columns A-D Module Parts Location





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Figure 1-2-4. Columns A-D Module Schematic Diagram (Sheet 2 of 2)

COLUMNS 9-12 MODULE, MODEL CC-366A

Ref. Desig.	Description	Part No.
C1-C8	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.33 µF ±20%, 50 Vdc	70 930 313 016
CR1, CR4, CR8, CR10	DIODE: Replacement type 882	70 943 024 002
CR2, CR3, CR5-7, CR9, CR11-CR31	DIODE: Replacement type 1N914	70 943 083 002
M1, M2, M5, M9, M12, M15 M16, M19, M23, M26, M29, M33, M36, M39, M43, M49	MICROCIRCUIT: 946, quad NAND gate integrated circuit	70 950 105 002
M6, M7, M30, M41	MICROCIRCUIT: 032, quad NAND gate integrated circuit	70 950 100 032
M3, M4, M13, M14, M17, M18, M27, M28, M35, M37, M38, M45	MICROCIRCUIT: 944, power amplifier integrated circuit	70 950 105 008
M8, M22, M31, M32, M42	MICROCIRCUIT: 963, triple NAND gate integrated circuit	70 950 105 012
M48	MICROCIRCUIT 962, triple NAND gate integrated circuit	70 950 105 006
M10, M25	MICROCIRCUIT: 936, hex inverter integrated circuit	70 950 105 004
M11, M24, M34, M44	MICROCIRCUIT: F-01, dual NAND gate integrated circuit	70 950 100 001
M46, M47, M40	MICROCIRCUIT: 930, dual NAND gate integrated circuit	70 950 105 001
R1, R3, R5, R7	RESISTOR, FIXED, COMPOSITION: $2K \pm 5\%$, $1/4W$	70 932 007 056
R2, R4, R6, R 8	RESISTOR, FIXED COMPOSITION: 510 ohms $\pm 5\%$, $1/4W$	70 932 007 042

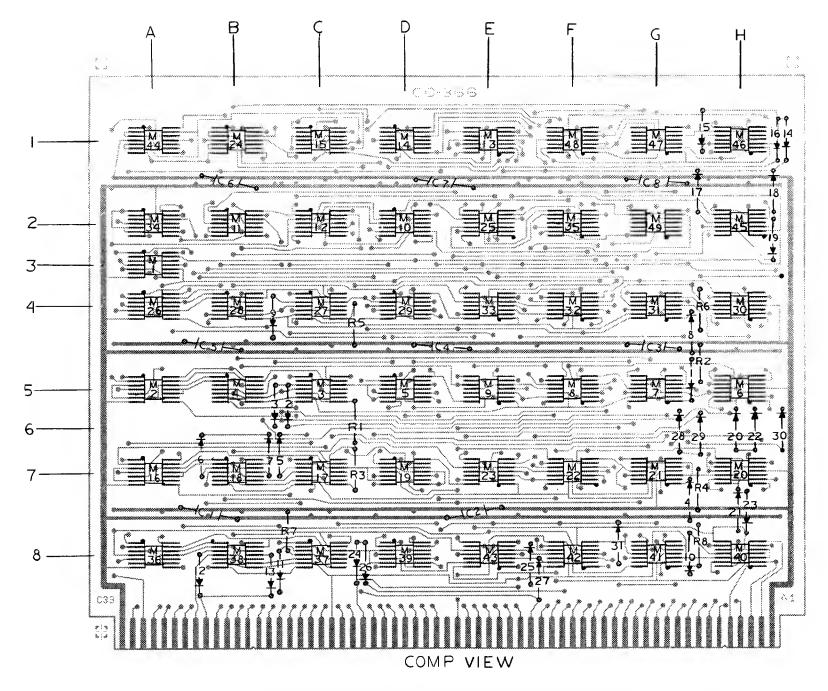


Figure 1-2-5. Columns 9-12 Module Parts Location

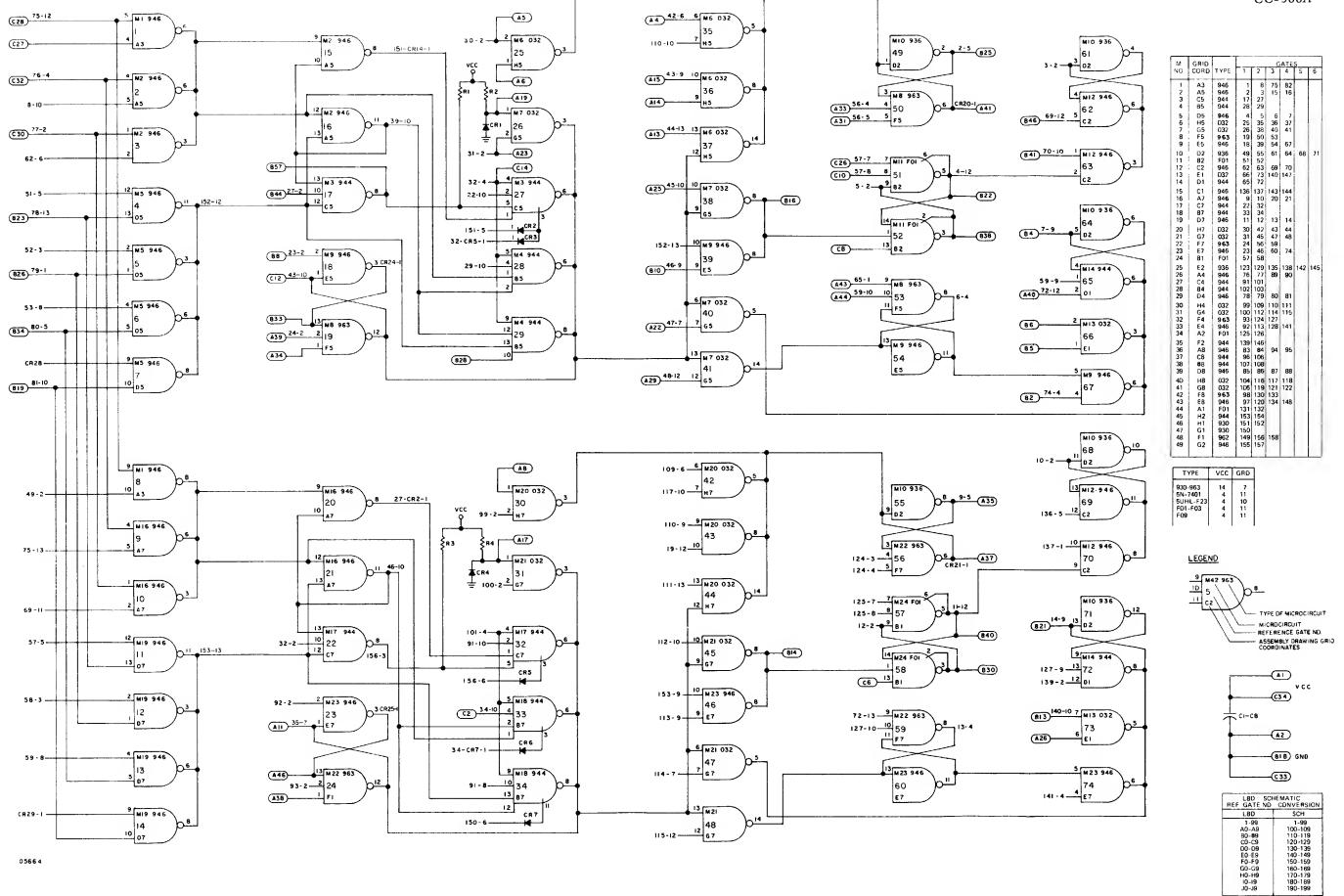


Figure 1-2-6. Columns 9-12 Module Schematic Diagram (Sheet 1 of 2)

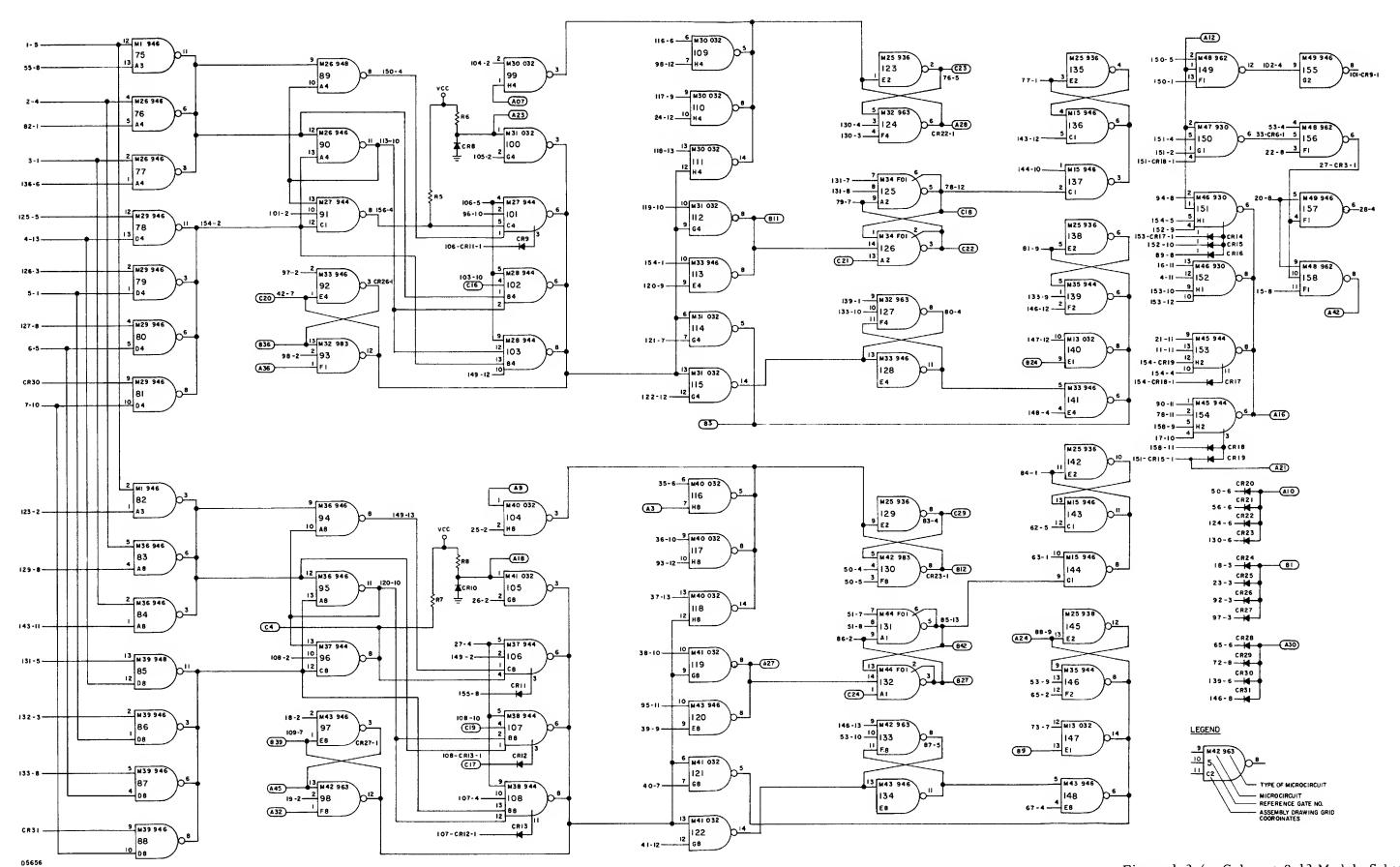
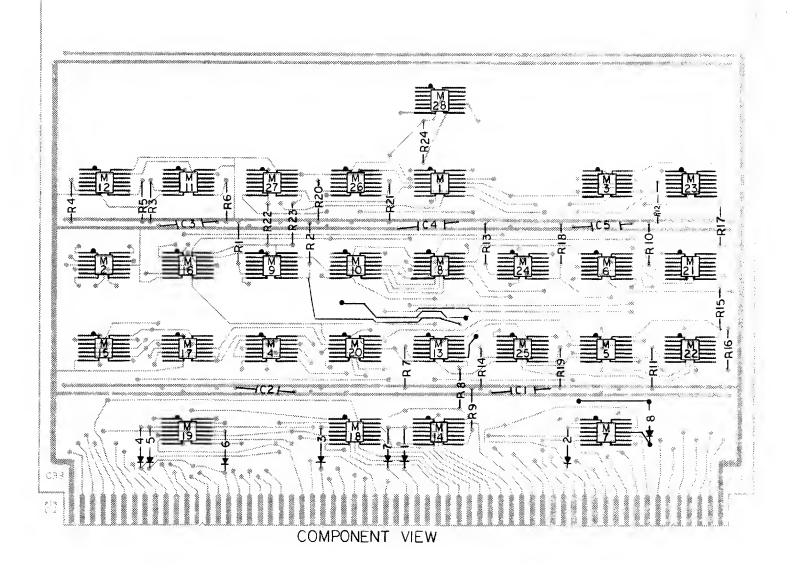


Figure 1-2-6. Columns 9-12 Module Schematic Diagram (Sheet 2 of 2)

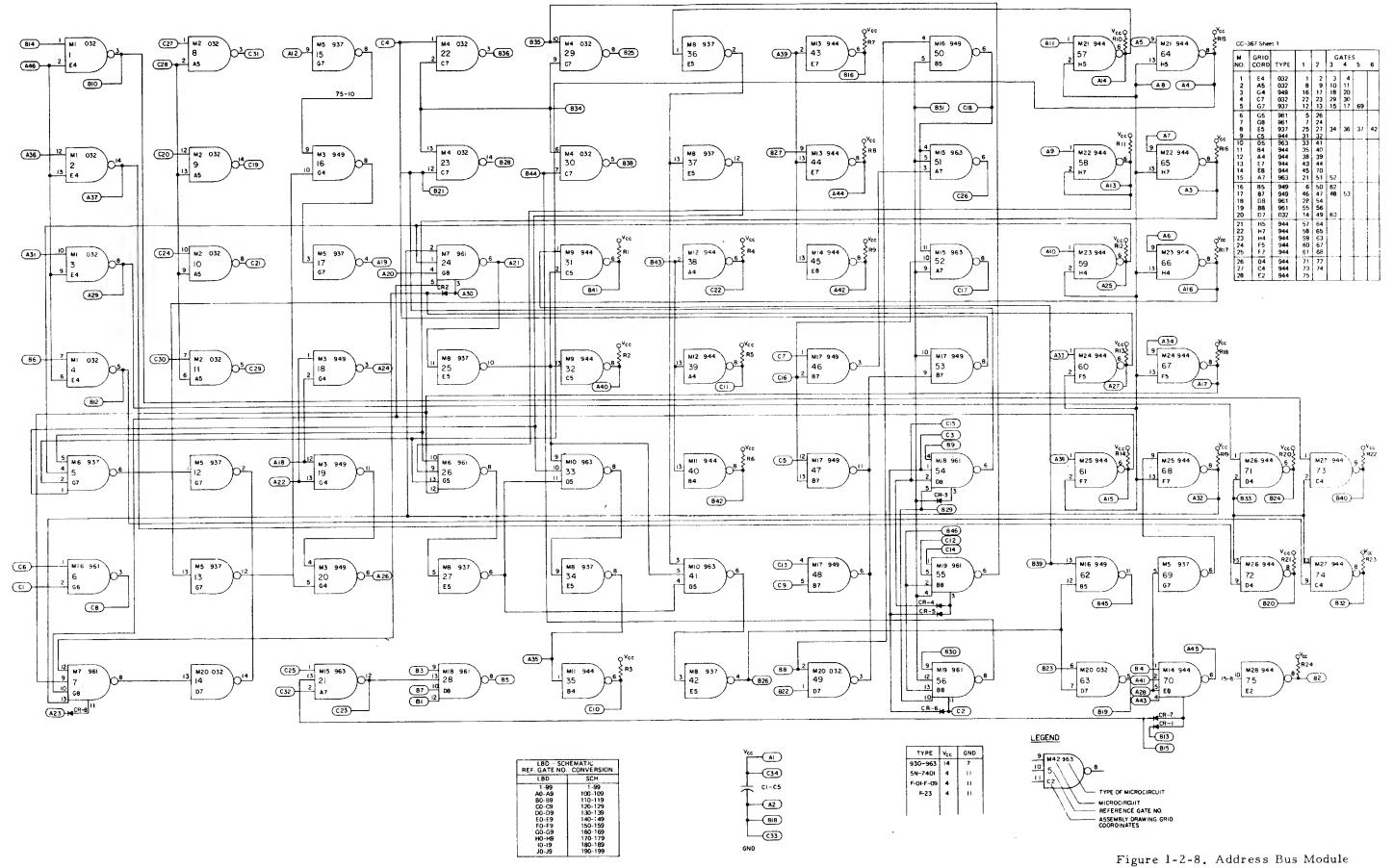
ADDRESS BUS MODULE, MODEL CC-367

Ref. Desig.	Description	Part No.
C1-C5	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 µF ±20%, 50 Vdc	70 930 313 016
CR1-CR8	DIODE: Replacement type 1N914	70 943 083 092
M1, M2, M4, M20	MICROCIRCUIT: 032, quad NAND gate integrated circuit	70 950 100 032
M3, M16, M17	MICROCIRCUIT: 949, quad NAND gate integrated circuit	70 950 105 010
M5, M8	MICROCIRCUIT: 937, fast hex inverter integrated circuit	70 950 105 011
M6, M7, M18, M19	MICROCIRCUIT: 961, dual NAND gate integrated circuit	70 950 105 009
M9, M11-M14, M21-M28	MICROCIRCUIT: 944, power amplifier integrated circuit	70 950 105 008
M10, M15	MICROCIRCUIT: 963, triple NAND gate integrated circuit	70 950 105 012
R1-R9	RESISTOR, FIXED, COMPOSITION: 2K ±5%, 1/4W	70 932 007 056
R10-R24	RESISTOR, FIXED, COMPOSITION: 1K ±5%, 1/4W	70 932 007 049
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Figure 1-2-7. Address Bus Module Parts Location



Schematic Diagram

SHIFT REGISTER MODULE, MODEL CC-368

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Ref. Desig.	Description	Part No.
C1-C8	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 µF ±20%, 50 Vdc	70 930 313 016
CRI, CR3- CR14	DIODE: Replacement type 1N914	70 943 083 002
M1, M5, M7, M8, M11, M14, M15, M18, M20, M22, M25, M28, M29, M33, M35, M37, M41, M42		70 950 i05 002
M2, M9, M16, M23, M31, M38	MICROCIRCUIT: 936, hex inverter integrated circuit	70 950 105 004
M3, M6, M10, M13, M17, M19, M24, M26, M32, M34, M39, M40	MICROCIRCUIT: 962, triple NAND gate integrated circuit	70 950 105 006
M4, M12, M21, M27, M30, M36	MICROCIRCUIT: 032, quad NAND gate integrated circuit	70 950 100 032
M43	MICROCIRCUIT: 932, power amplifier integrated circuit	70 950 105 005
M44	MICROCIRCUIT: 930, dual NAND gate integrated circuit	70 950 105 001
M45-M50	MICROCIRCUIT: F-04, flip-flop integrated circuit	70 950 100 004
M51-M54	MICROCIRCUIT: 944, power amplifier integrated circuit	70 950 105 008
R1, R2	RESISTOR, FIXED, COMPOSITION: 2K ±5%, 1/4W	70 932 007 056
R3-R10	RESISTOR, FIXED, COMPOSITION: 1K ±5%, 1/4W	70 932 007 049

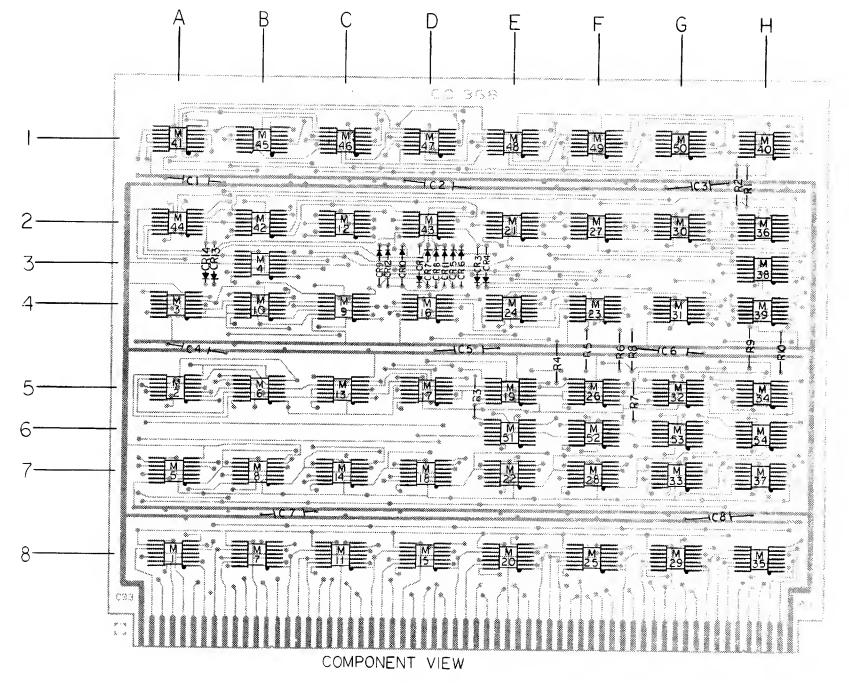
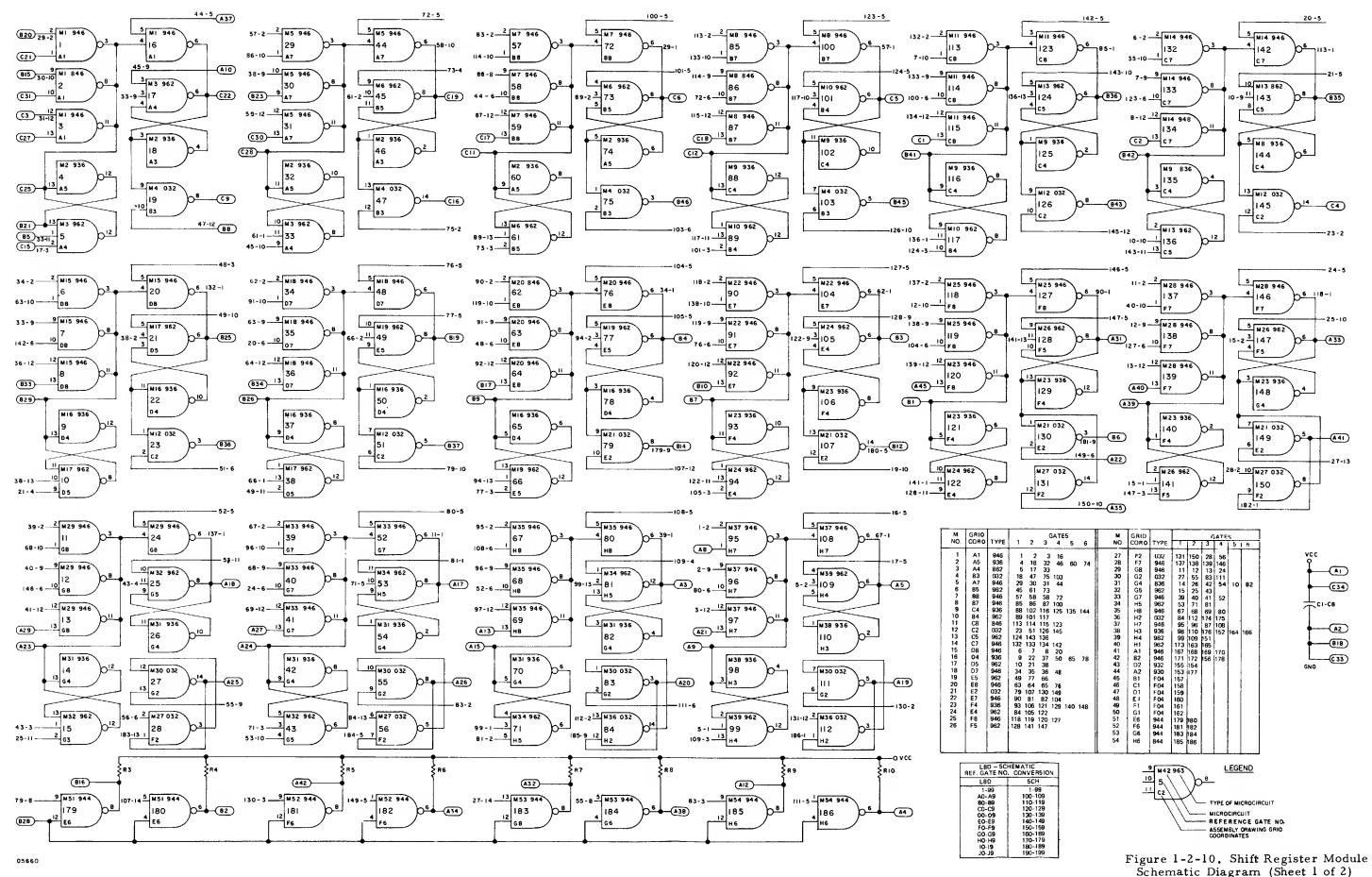


Figure 1-2-9. Shift Register Module Parts Location



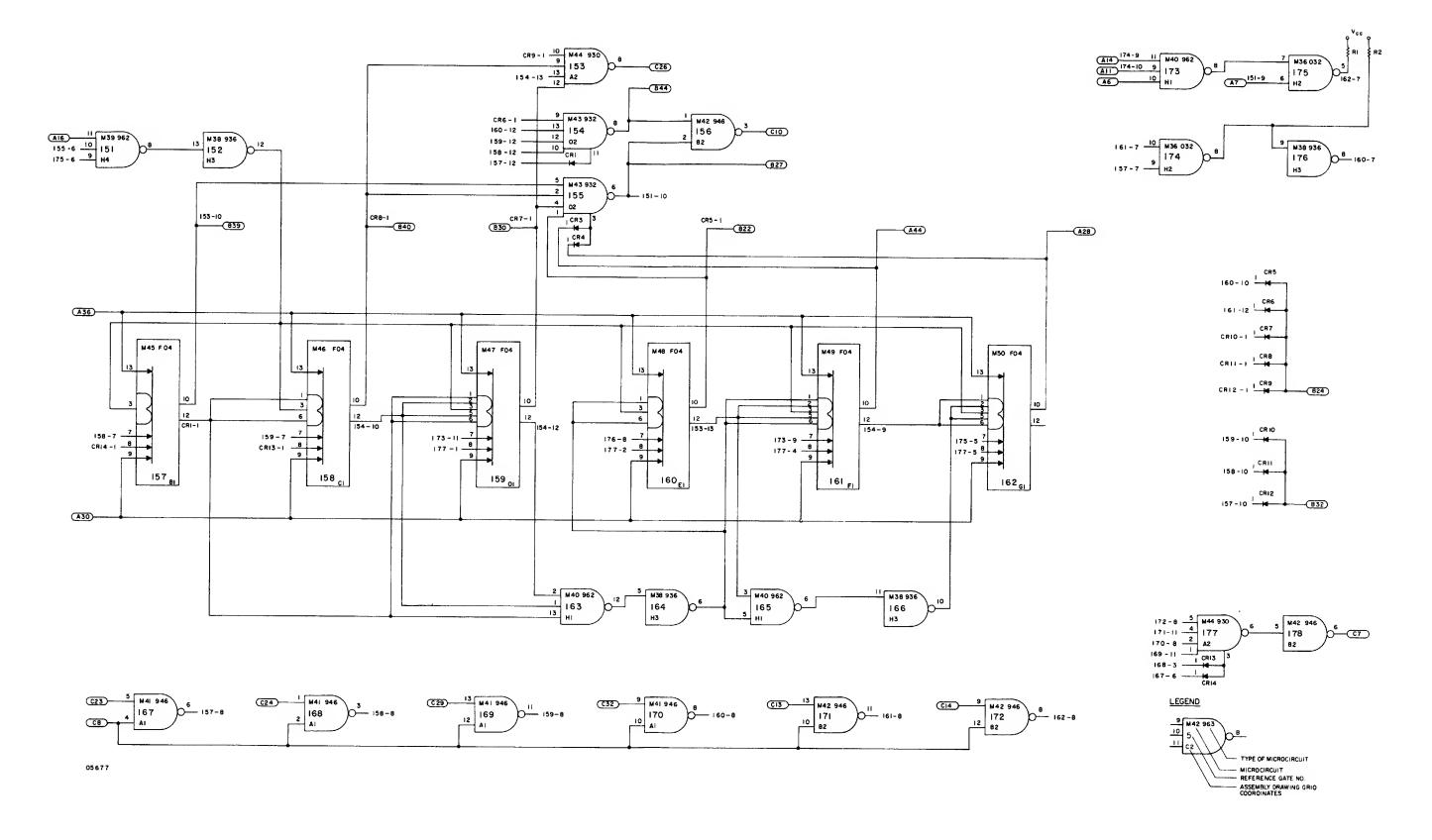


Figure 1-2-10. Shift Register Module Schematic Diagram (Sheet 2 of 2)

LAMP DRIVER MODULE, MODEL CC-369B

Ref. Desig.	Description	Part No.
C1 - C3	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 µF ±20%, 50 Vdc	70 930 313 016
CR1-CR19, CR20A-CR20S, CR21-CR23	DIODE: Replacement type 1N914	70 943 083 002
M1-M16	MICROCIRCUIT: 936, hex inverter integrated circuit	70 950 105 004
M18-M20	MICROCIRCUIT: 937, fast hex inverter integrated circuit	70 950 105 011
M21, M22, M25	MICROCIRCUIT: 032, quad NAND gate integrated circuit	70 950 100 032
M23, M17	MICROCIRCUIT: 949, quad NAND gate integrated circuit	70 950 105 010
M24	MICROCIRCUIT: 961, dual NAND gate integrated circuit	70 950 105 009
Q1A-Q1S, Q2	TRANSISTOR, SILICON, NPN:	70 943 744 003
R1A-R1P	RESISTOR, FIXED, COMPOSITION: $2K \pm 5\%$, $1/4W$	70 932 007 056
R2A-R2S, R7,	RESISTOR, FIXED, FILM: 1.1K ±1%, 1/2W	70 932 123 203
R3A-R3S, R4	RESISTOR, FIXED, COMPOSITION: 820 ohms ±5%, 1/4W	70 932 007 047
R5, R9-R12	RESISTOR, FIXED, COMPOSITION: $1 \text{K} \pm 5\%$, $1/4 \text{W}$	70 932 007 049
R6	RESISTOR, FIXED, FILM: 100 ohms ±1%, 1/2W	70 932 123 101

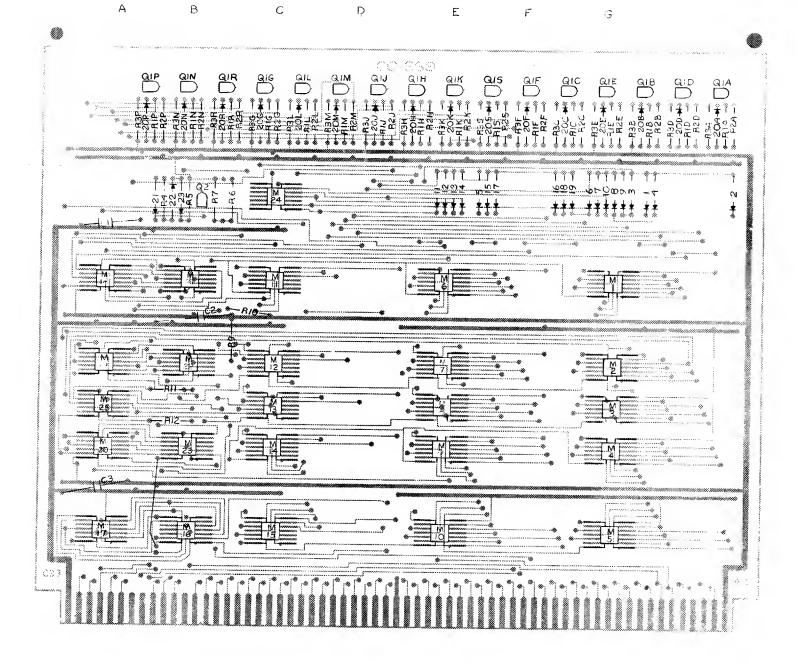
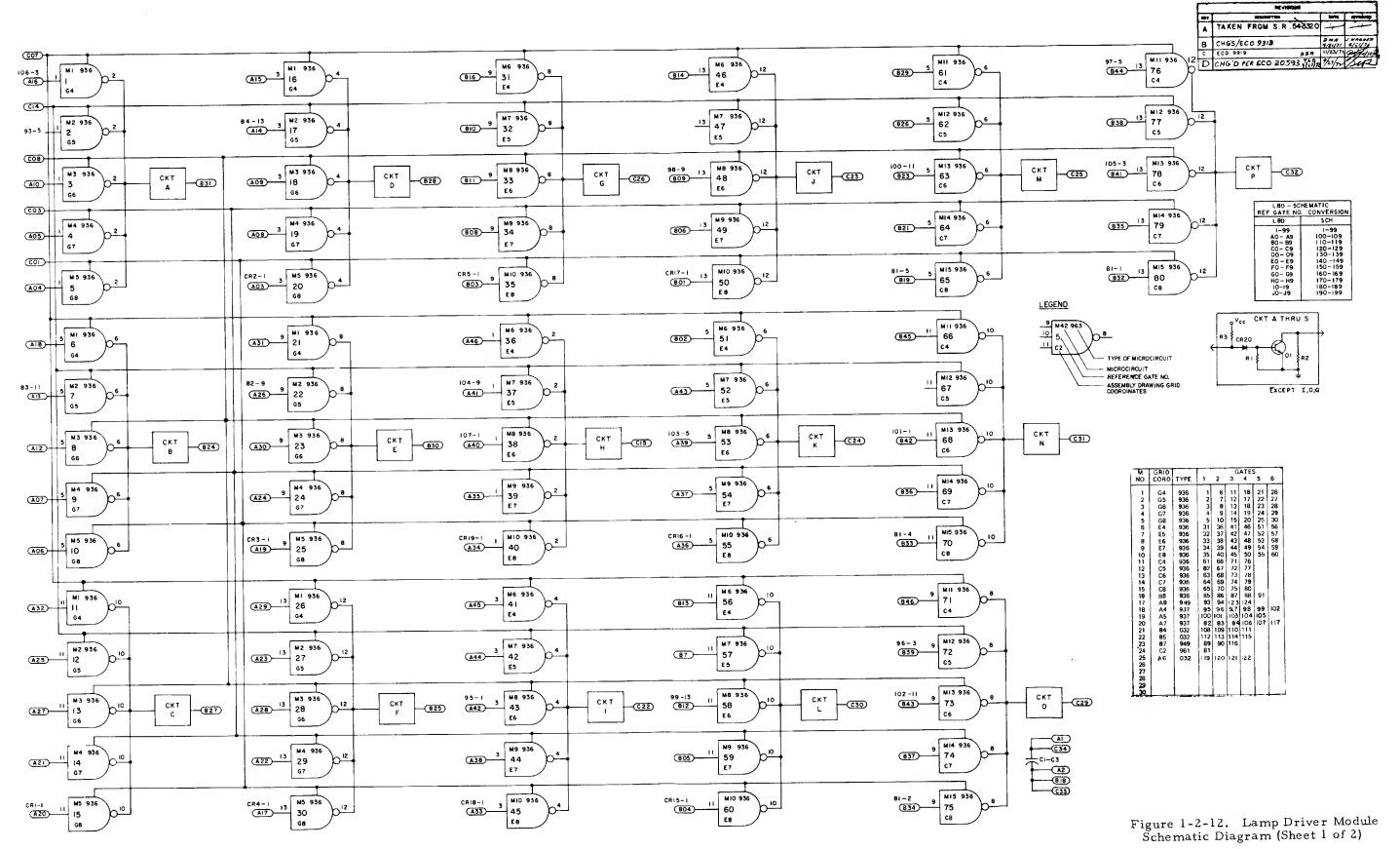


Figure 1-2-11. Lamp Driver Module Parts Location



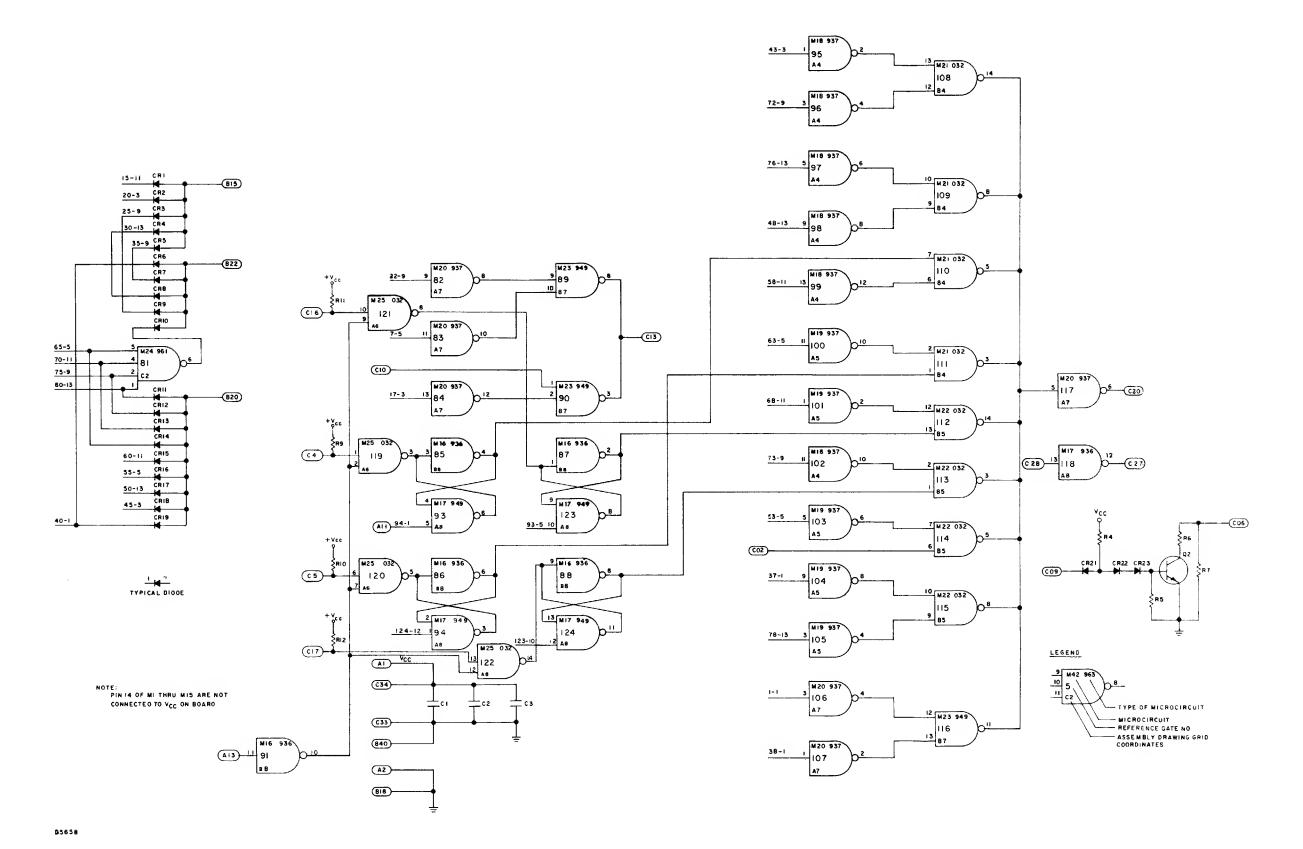
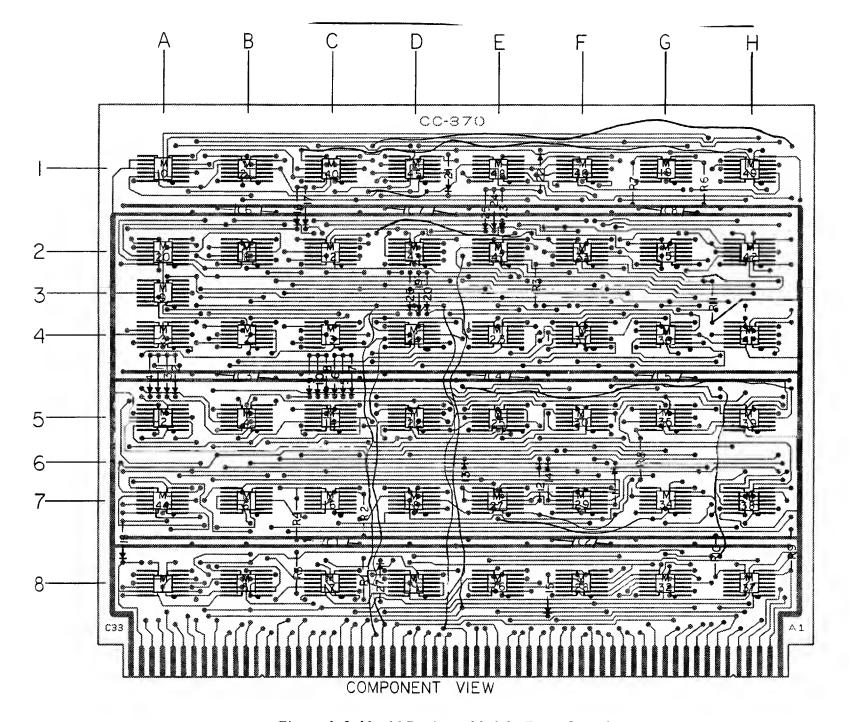


Figure 1-2-12. Lamp Driver Module Schematic Diagram (Sheet 2 of 2)

M REGISTER MODULE, MODEL CC-370

Ref. Desig.	Description	Part No.
C1 -C8	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 µF ±20%, 50 Vdc	70 930 313 016
CR1-CR27	DIODE: Replacement type 1N914	70 943 083 002
M1, M7, M10, M22, M33, M48	MICROCIRCUIT: 937, fast hex inverter integrated circuit	70 950 105 011
M2, M18	MICROCIRCUIT: 032, quad NAND gate integrated circuit	70 950 100 032
M3, M6, M9	MICROCIRCUIT: F-09, dual power amplifier integrated circuit	70 950 100 009
M4, M14, M15, M25, M31, M38, M42	MICROCIRCUIT: 949, quad NAND gate integrated circuit	70 950 105 010
M5, M8, M11, M12, M24, M26, M32, M36, M41, M46, M49	MICROCIRCUIT: 963, triple NAND gate integrated circuit	70 950 105 012
M13, M20, M21, M29, M30, M35, M39, M40, M43, M44, M45	MICROCIRCUIT: 961, dual NAND gate integrated circuit	70 950 105 009
M16, M17, M19, M23, M27, M28, M34, M37, M47	MICROCIRCUIT: 944, power amplifier integrated circuit	70 950 105 008
R1-R11	RESISTOR, FIXED, COMPOSITION: 2K ±5%, 1/4W	70 932 007 056



CC-370

Figure 1-2-13. M Register Module Parts Location

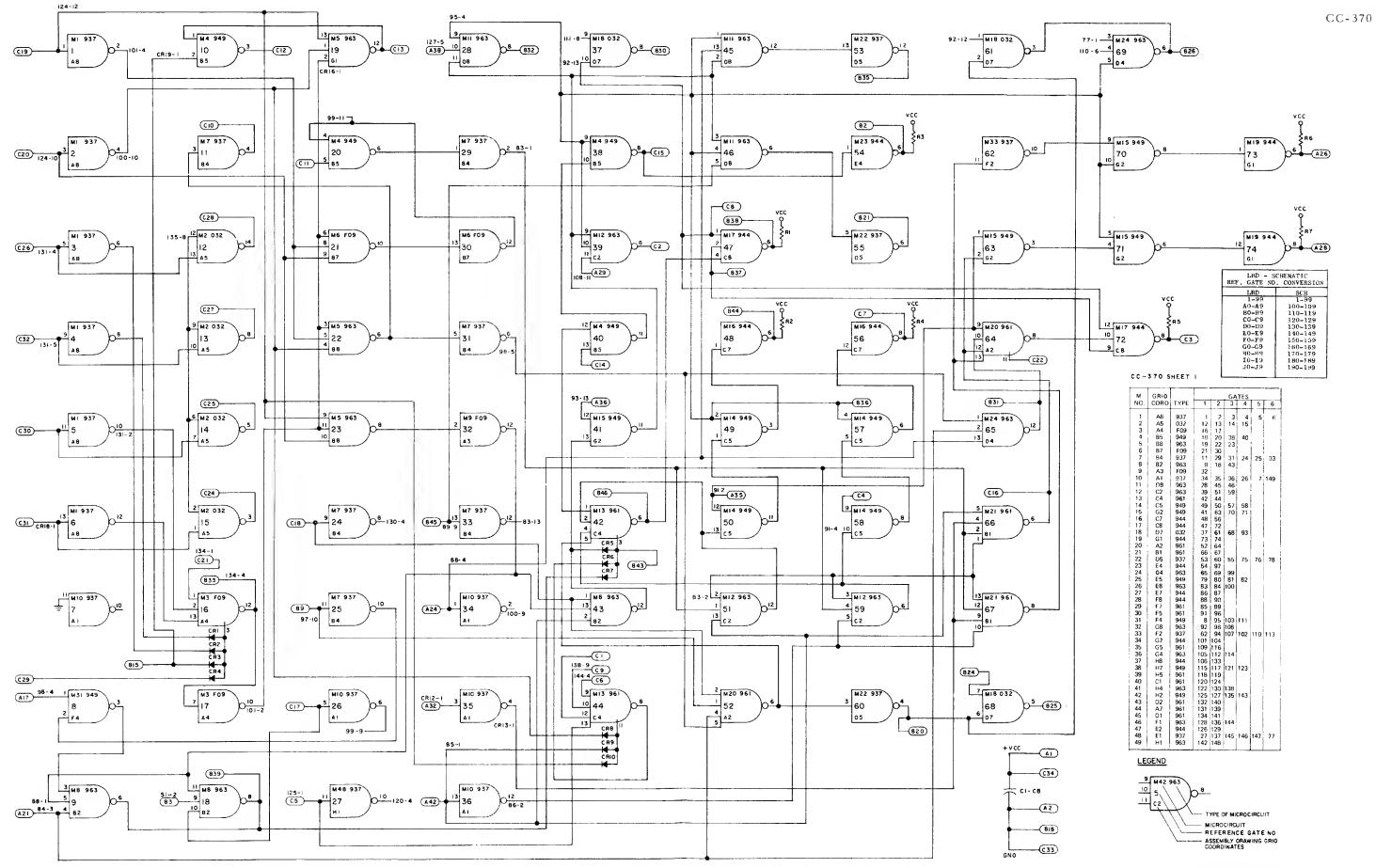


Figure 1-2-14. M Register Module Schematic Diagram (Sheet 1 of 2)

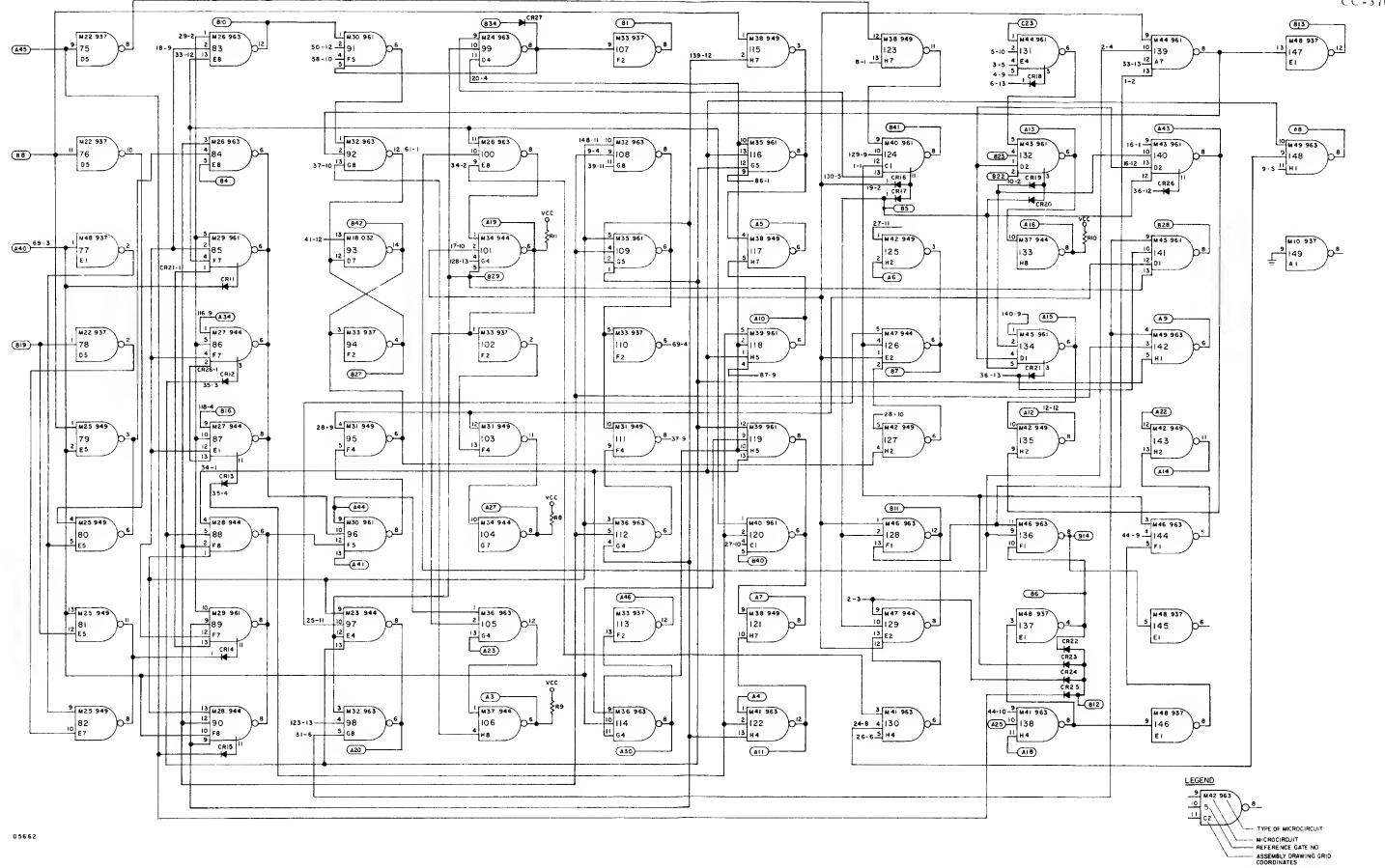
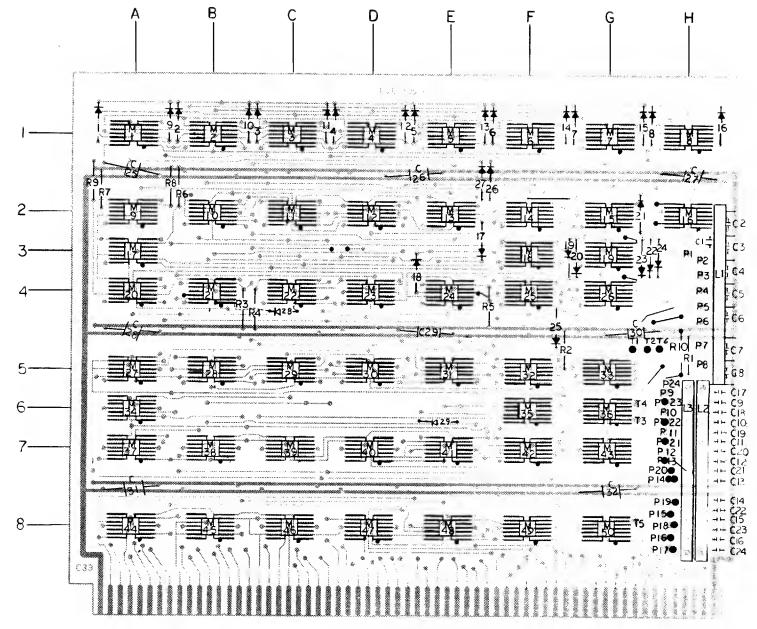


Figure 1-2-14. M Register Module Schematic Diagram (Sheet 2 of 2)

CLOCK MODULE, MODEL CC-371

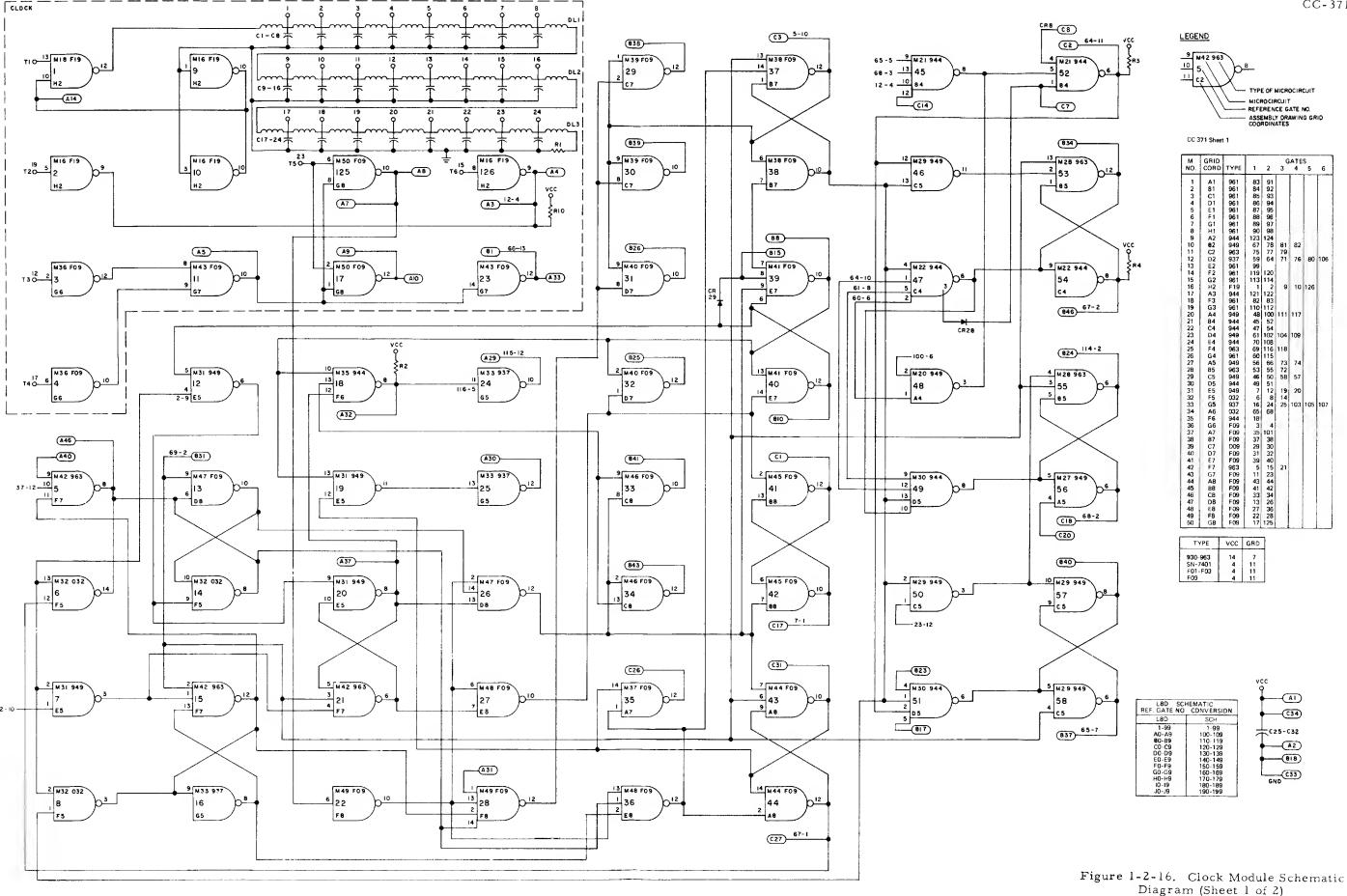
Electrical Parts List

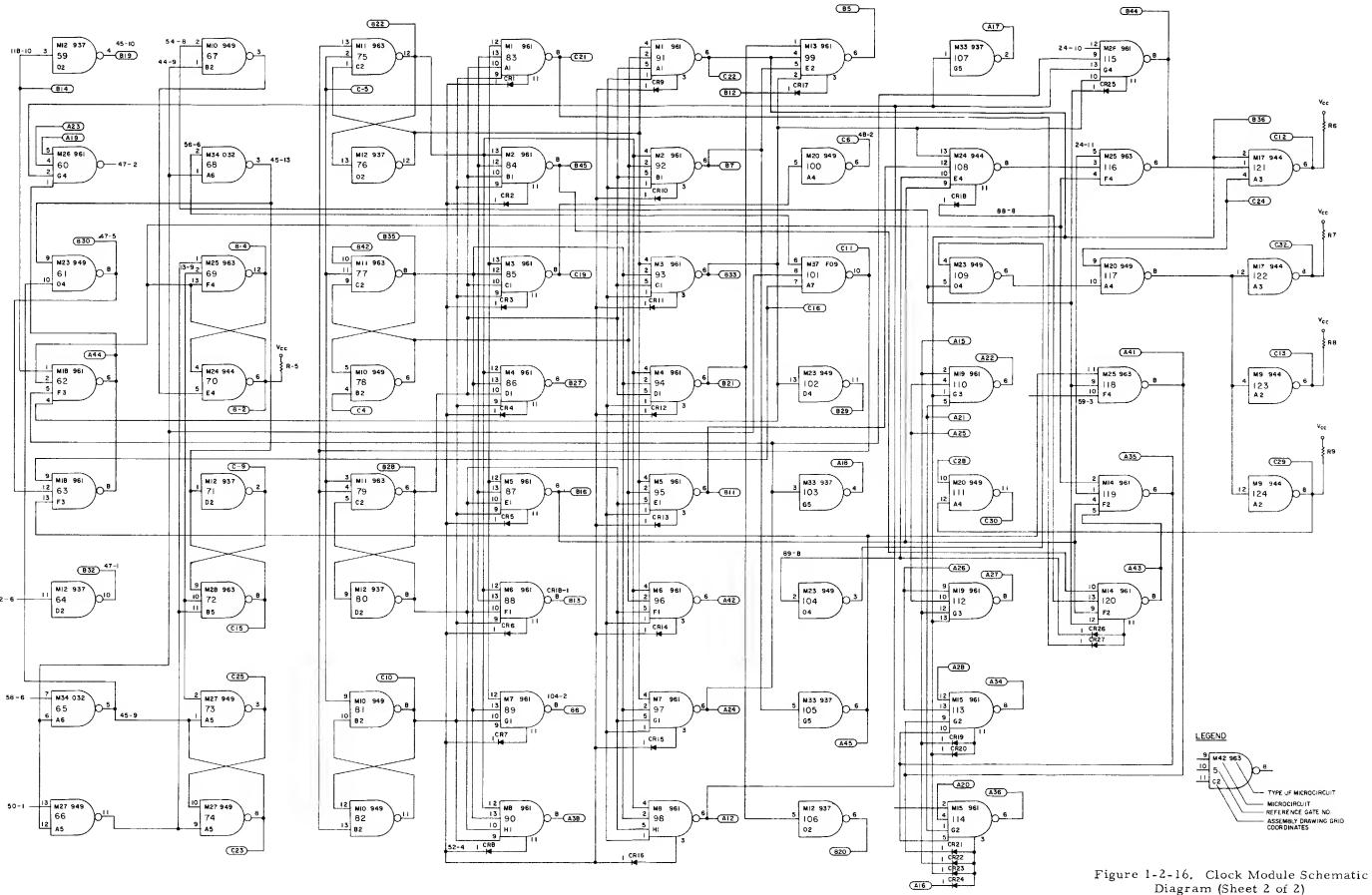
Ref. Desig.	Description	Part No.
C1-C24	CAPACITOR, FIXED, MICA DIELECTRIC: 75 pF ±2%, 100 Vdc	70 930 004 214
C25-C32	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 μF ±20%, 50 Vdc	70 930 313 016
CR1-CR29	DIODE: Replacement type 1N914	70 943 083 002
L1-L3	DELAY LINE	70 000 206 703
M1-M8, M13-M15, M18, M19, M26	MICROCIRCUIT: 961, dual NAND gate integrated circuit	70 950 105 009
M9, M17, M21, M22, M24, M30, M35	MICROCIRCUIT: 944, power amplifier integrated circuit	70 950 105 008
M10, M20, M23, M27 M29, M31	MICROCIRCUIT: 949, quad NAND gate integrated circuit	70 950 105 010
M11, M25, M28, M42	MICROCIRCUIT: 963, triple NAND gate integrated circuit	70 950 105 012
M12, M33	MICROCIRCUIT: 937, hex inverter integrated circuit	70 950 105 011
M16	MICROCIRCUIT: F-19, logic gate integrated circuit	70 950 100 019
M32, M34	MICROCIRCUIT: 032, quad NAND gate integrated circuit	70 950 100 032
M36-M41, M43-M50	MICROCIRCUIT: F-09, power amplifier integrated circuit	70 950 100 009
R1	RESISTOR, FIXED, COMPOSITION: 130 ohms ±5%, 1/4W	70 932 007 028
R2-R9	RESISTOR, FIXED, COMPOSITION: 2K ±5%, 1/4W	70 932 007 056
R10	RESISTOR, FIXED, COMPOSITION: 510 ohms ±5%, 1/4W	70 932 007 042



COMPONENT VIEW

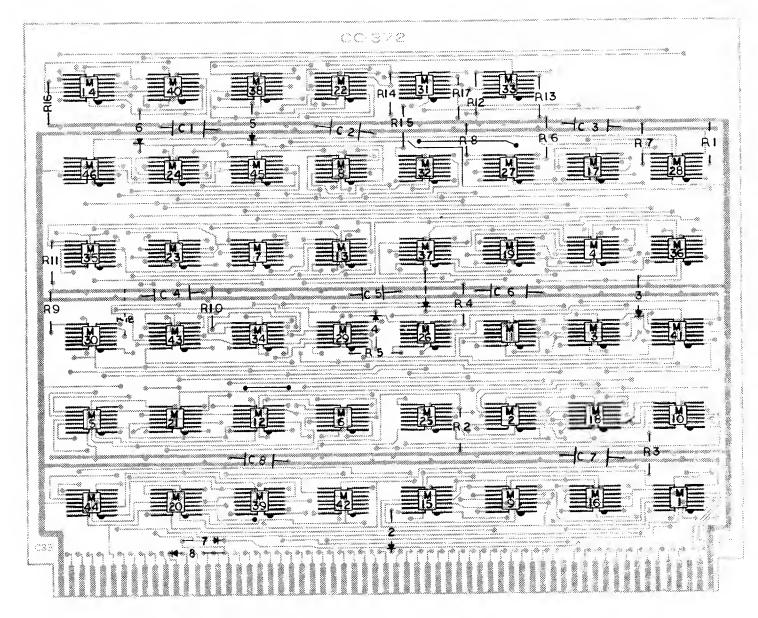
Figure 1-2-15. Clock Module Parts Location





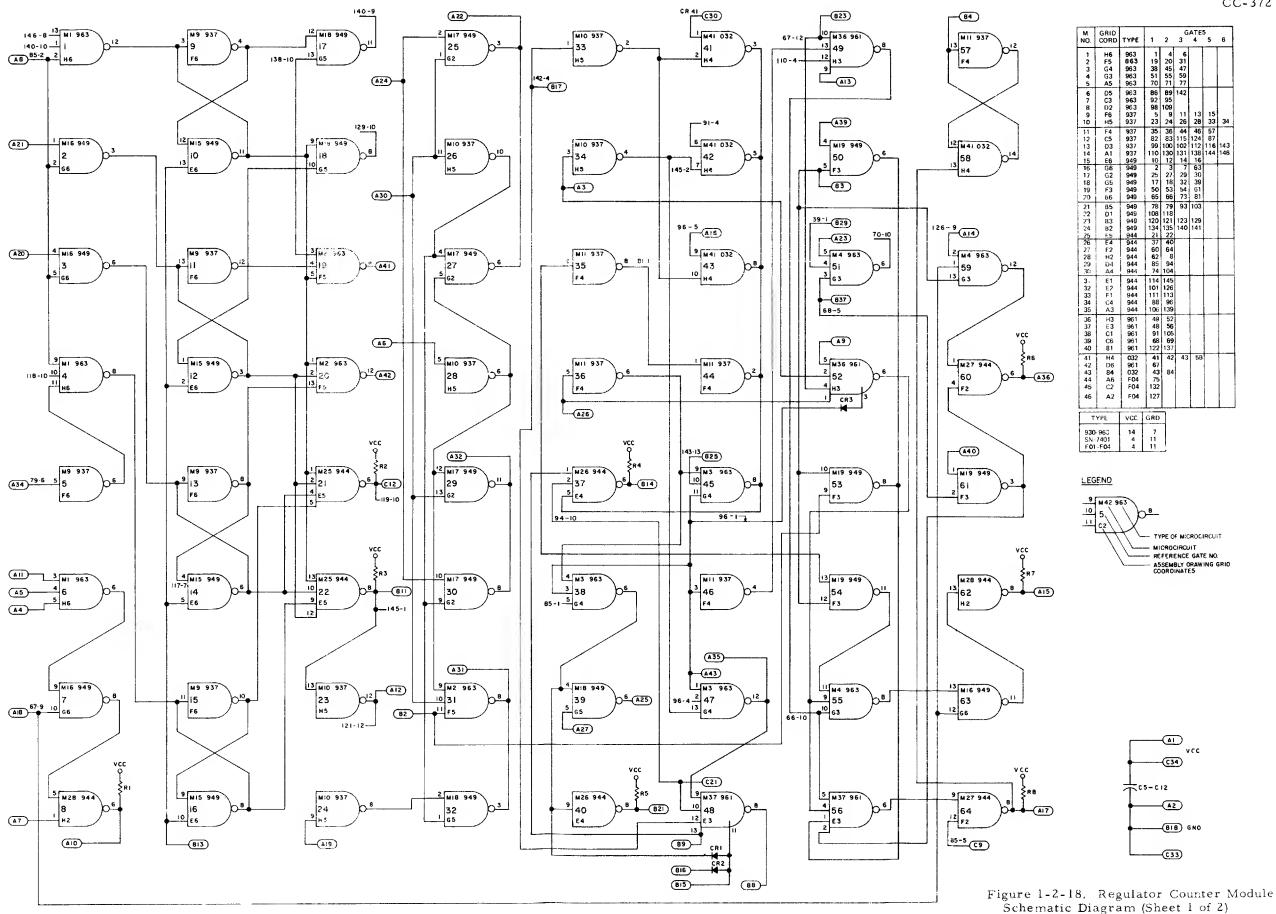
REGULATOR COUNTER MODULE, MODEL CC-372

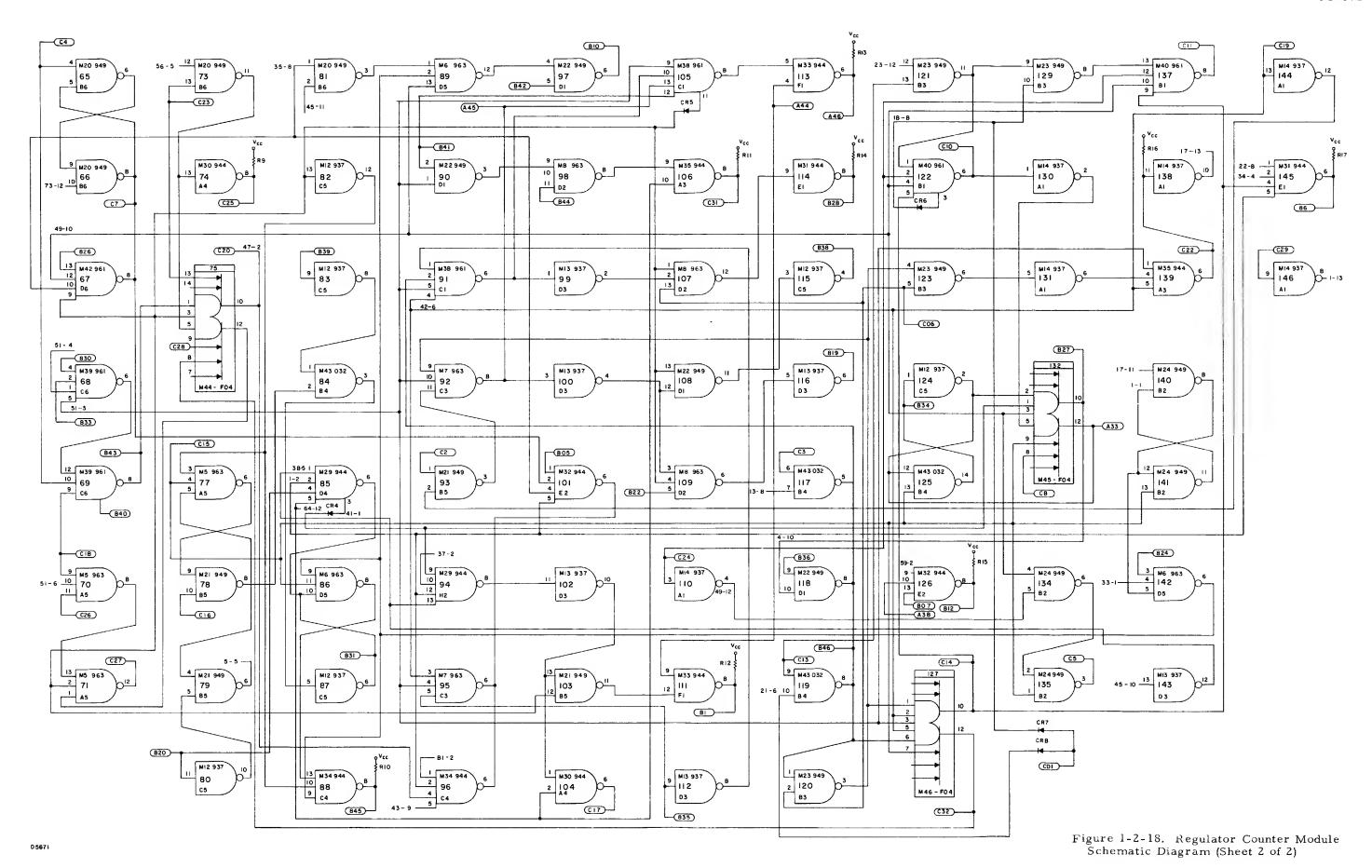
Ref. Desig.	Description	Part No.
C1-C8	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 µF ±20%, 50 Vdc	70 930 313 016
CRI-CR8	DIODE: Replacement type 1N914	70 943 083 002
M1, M3-M8	MICROCIRCUIT: 963, triple NAND gate integrated circuit	70 950 105 012
M2, M15-M24	MICROCIRCUIT: 949, quad NAND gate integrated circuit	70 950 105 010
M9-M14	MICROCIRCUIT: 937, hex inverter integrated circuit	70 950 105 011
M25-M35	MICROCIRCUIT: 944, power amplifier integrated circuit	70 950 105 008
M36-M40, M42	MICROCIRCUIT: 961, dual NAND gate integrated circuit	70 950 105 009
M41, M43	MICROCIRCUIT: 032, quad NAND gate integrated circuit	70 950 100 032
M44-M46	MICROCIRCUIT: F-04, flip-flop integrated circuit	70 950 100 004
R1, R2, R6- R14, R16-R18	RESISTOR, FIXED, FILM: 2K ±2%, 1/4W	70 932 114 056
R3, R4, R5	RESISTOR, FIXED, FILM: 510 ohms ±2%, 1/4W	70 932 114 042
R15	RESISTOR, FIXED, FILM: 1K ±2%, 1/4W	70 932 114 049



COMPONENT VIEW

Figure 1-2-17. Regulator Counter Module Parts Location





MEMORY TIMING MODULE, MODEL CC-373

Ref. Desig.	Description	Part No.
C1-C32	CAPACITOR, FIXED, MICA DIELECTRIC: 120 µF ±2%, 100 Vdc	70 930 004 219
C33-C40	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 μ F ±20%, 50 Vdc	70 930 313 016
M1, M2, M9 M10, M11	MICROCIRCUIT: 949, quad NAND gate integrated circuit	70 950 105 010
M3, M5, M8 M19, M27	MICROCIRCUIT: 963, triple NAND gate integrated circuit	70 950 105 012
M4, M7, M14 M22, M24-M26	MICROCIRCUIT: 961, dual NAND gate integrated circuit	70 950 105 009
M6, M15, M16	MICROCIRCUIT: 937, fast hex inverter integrated circuit	70 950 105 011
M12, M13, M17, M18, M20, M21 M23	MICROCIRCUIT: 944, power amplifier integrated circuit	70 950 105 008
M28-M36	MICROCIRCUIT: F-03 power amplifier integrated circuit	70 950 100 003
CR1-CR8, CR11	DIODE: Replacement type 1N914	70 943 083 002
CR9, CR10	DIODE	70 943 088 001
Q1	TRANSISTOR, SILICON, NPN: Replacement type 2N3011	70 943 722 001
Q2	TRANSISTOR, SILICON, PNP: Replacement type 2N3012	70 943 721 001
DL1-DL4	DELAY LINE	70 000 206 703
Rl-R4, Rl0, Rl8	RESISTOR, FIXED, COMPOSITION: 510 ohms ±5%, 1/4W	70 932 007 042
R5, R7, R8	RESISTOR, FIXED, COMPOSITION: 1K ohms ±5%, 1/4W	70 932 007 049
R9	RESISTOR, FIXED, COMPOSITION: 820 ohms ±5%, 1/4W	70 932 007 047
Rll	RESISTOR, FIXED, COMPOSITION: $100 \text{ ohms } \pm 5\%$, $1/4\text{W}$	70 932 007 025
R12	RESISTOR, FIXED, COMPOSITION: 750 ohms $\pm 5\%$, $1/4$ W	70 943 007 046

Electrical Parts List (Cont)

Ref. Desig.	Description	Part No.
R13	RESISTOR, FIXED, COMPOSITION: 39 ohms ±5%, 1/2W	70 932 004 015
R14-R16	RESISTOR, FIXED, COMPOSITION: 330 ohms ±5%, 1/4W	70 932 007 037
R17	RESISTOR, FIXED, COMPOSITION: 180 ohms ±5%, 1/2W	70 932 004 031

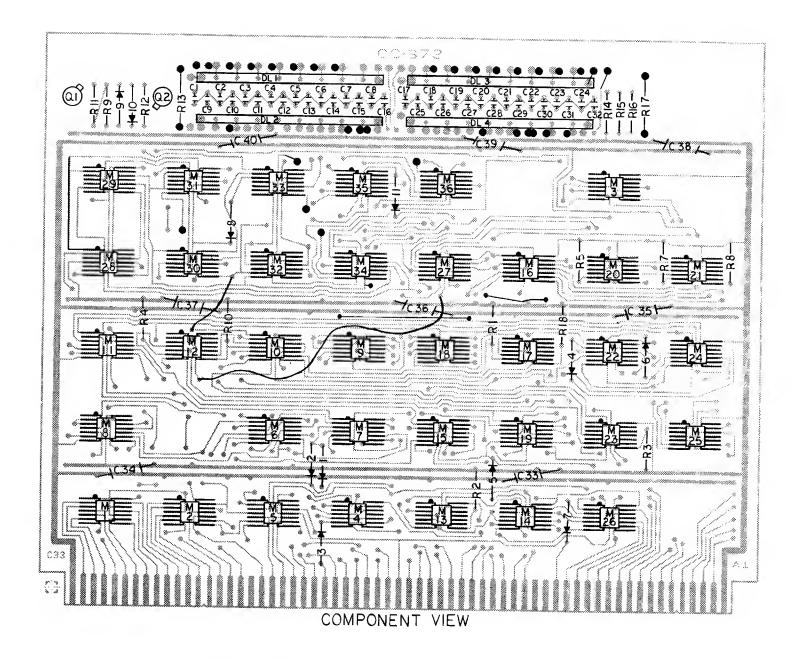


Figure 1-2-19. Memory Timing Module Parts Location

The following temporary jumpers must be inserted prior to the start of any tests.

a. CC-373

Connect P3 to T30
P5 to T40
P1 to T25
P6 to T15
P7 to T13
P8 to T33
P9 to T35
P10 to T12
P11 to T14
P12 to T12
P13 to T2
P14 to T30
P17 to T35
P5 to P15

b. CC-899

Connect P3 to T23
P5 to T40
P7 to T13
P8 to T33
P9 to T36
P10 to T14
P11 to T14
P12 to T8
P13 to T1
P14 to T30
P15 to T40
P17 to T38
P18 to T13
P6 to T14
P1 to T22

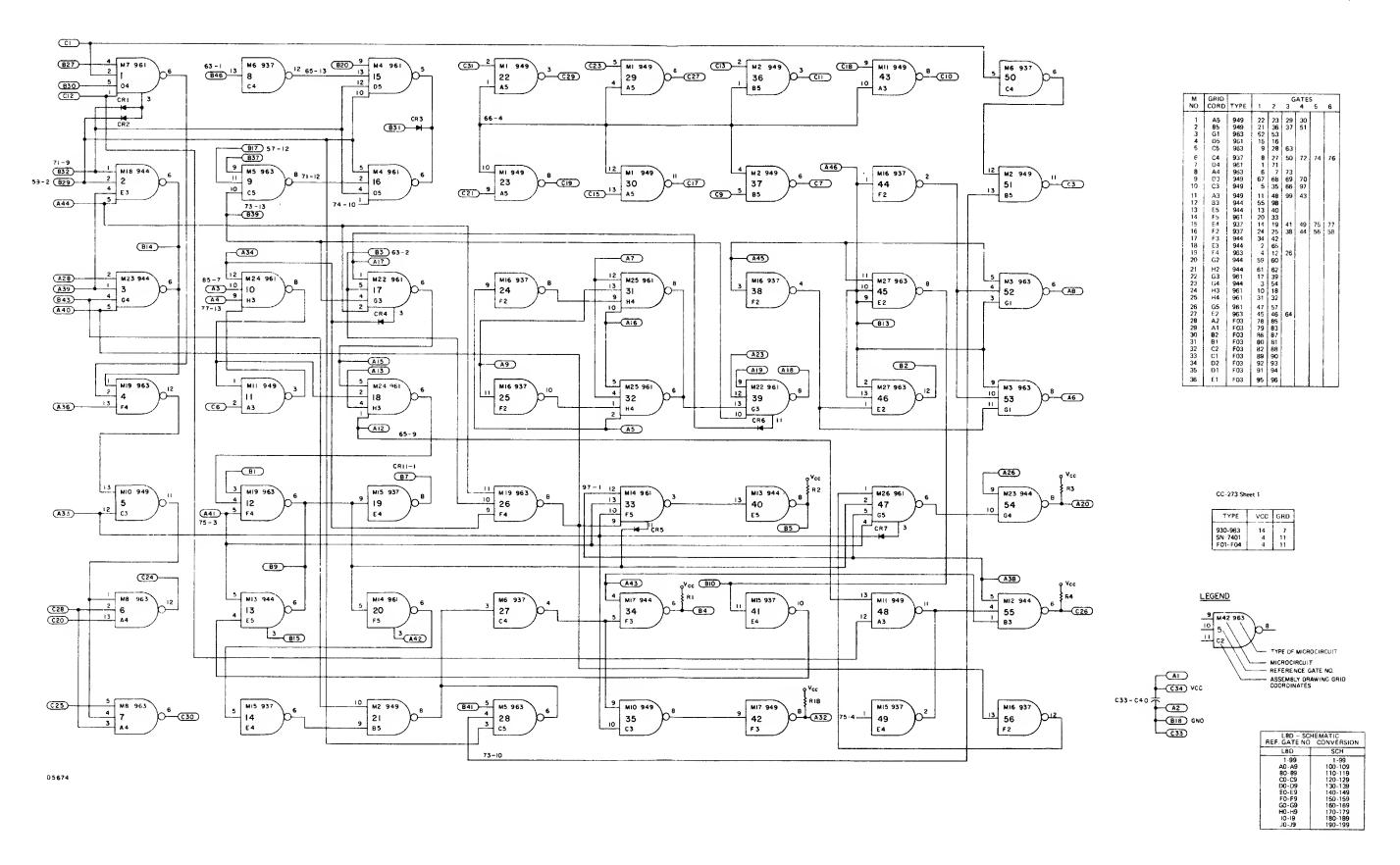


Figure 1-2-20. Memory Timing Module Schematic Diagram (Sheet 1 of 2)

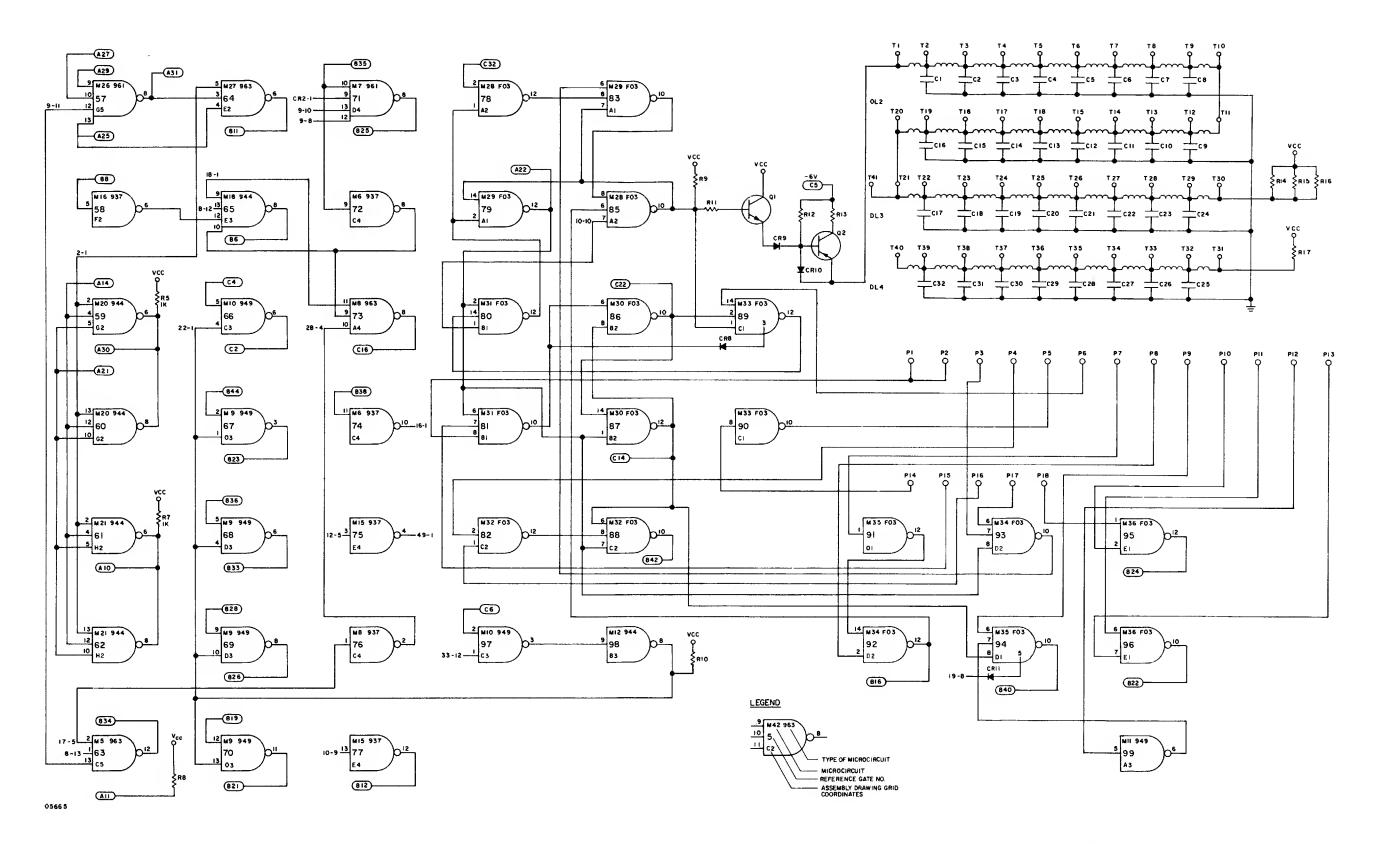


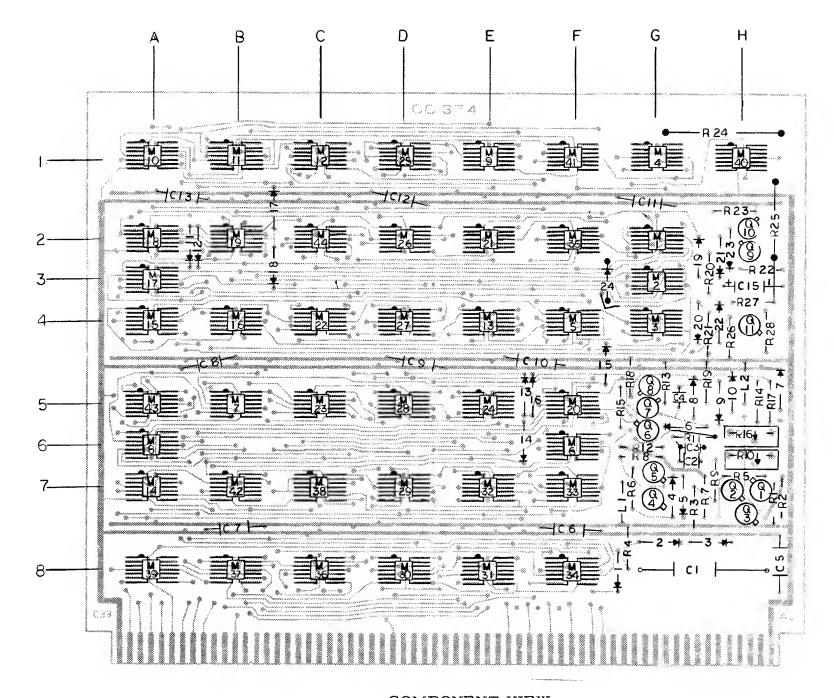
Figure 1-2-20. Memory Timing Module Schematic Diagram (Sheet 2 of 2)

ASR INTERFACE MODULE, MODEL CC-374

Ref.		
Desig.	Description	Part No.
C1	CAPACITOR, FIXED, PLASTIC DIELECTRIC: l µF ±5%, 50 Vdc	70 930 316 037
C2	CAPACITOR, FIXED, MICA DIELECTRIC: 300 pF ±5%, 100 Vdc	70 930 011 239
C3	CAPACITOR, FIXED, MICA DIELECTRIC: 10 pF ±5%, 100 Vdc	70 930 011 105
C4	CAPACITOR, FIXED, MICA DIELECTRIC: 680 pF ±5%, 100 Vdc	70 930 011 049
C5-C13	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 µF ±20%, 50 Vdc	70 930 313 016
C15	CAPACITOR, FIXED, ELECTROLYTIC-TANTALUM: 1 µF ±10%, 35 Vdc	70 930 217 054
CR1-CR6, CR8-CR24	DIODE: Replacement type 1N914	70 943 083 002
CR7	DIODE: Replacement type FD777	70 943 088 001
L1, L2	COIL, R. F: 6.8 µH ±10%	70 939 207 023
M1, M10, M11, M17, M36, M43	MICROCIRCUIT: 962, triple NAND gate integrated circuit	70 950 105 006
M2, M12, M14, M18, M44	MICROCIRCUIT: 936, hex inverter integrated circuit	70 950 105 004
M3, M4, M6, M8, M9, M15, M16, M21, M26-M35, M41	MICROCIRCUIT: F-04, flip-flop integrated circuit	70 950 100 004
M5, M13, M25, M37, M38, M42	MICROCIRCUIT: 946, quad NAND gate integrated circuit	70 950 105 002
M7, M19, M20	MICROCIRCUIT: 930, dual NAND gate integrated circuit	70 950 105 001
M22, M23	MICROCIRCUIT: 032, quad NAND gate integrated circuit	70 950 100 032
M24	MICROCIRCUIT: 944, power amplifier integrated circuit	70 950 105 008
M39, M40	MICROCIRCUIT: F-03, power amplifier integrated circuit	70 950 100 003

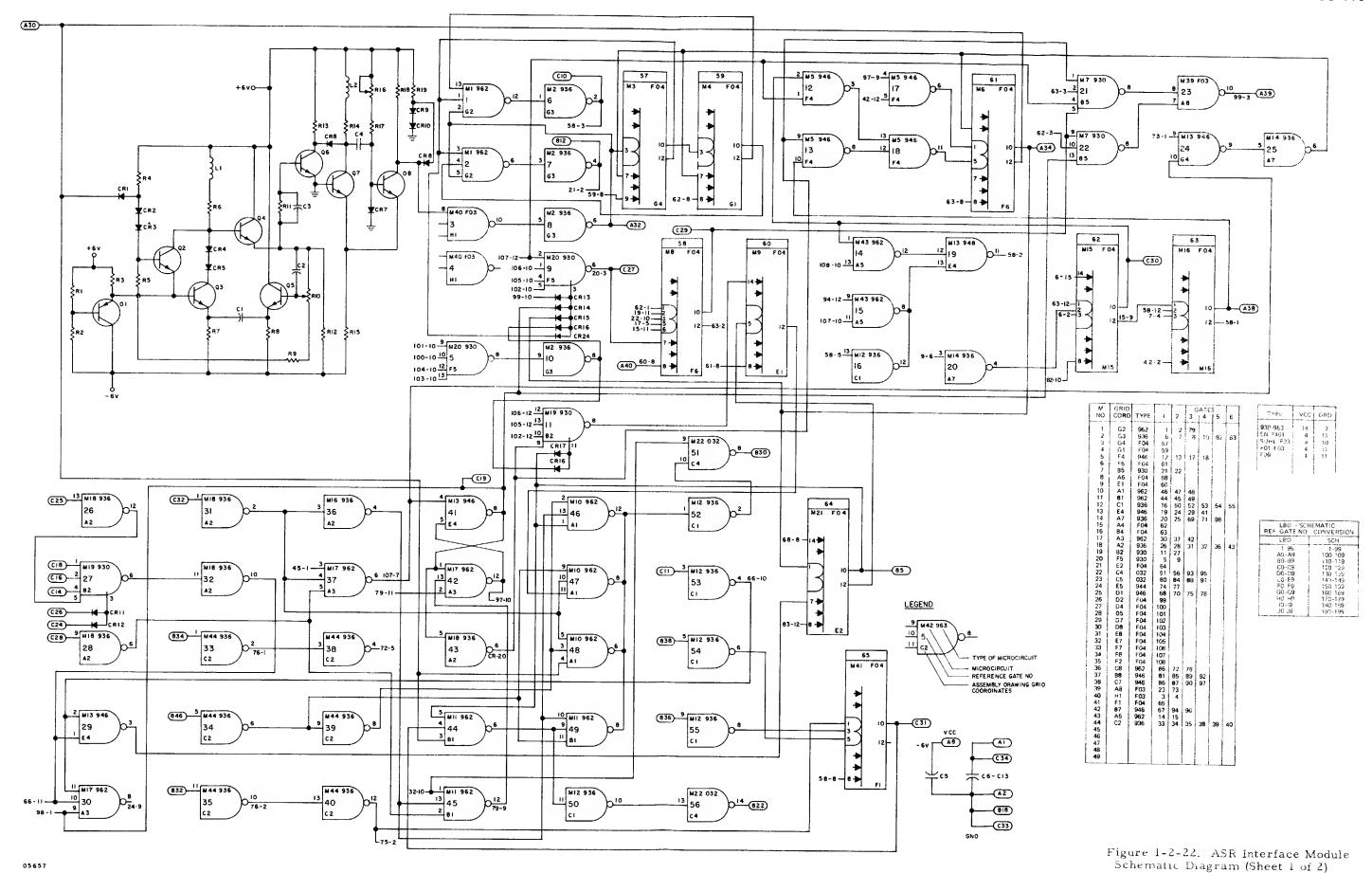
Electrical Parts List (Cont)

Ref. Desig.	Description	Part No.
Q1	TRANSISTOR, SILICON, PNP: Replacement type 2N3012	70 943 721 002
Q2-Q8, Q11	TRANSISTOR, SILICON, NPN: Replacement type 2N3011	70 943 754 002
Q9, Q10	TRANSISTOR, SILICON, NPN: Replacement type 2N2369	70 943 720 001
R1, R3, R5, R12, R13, R18, R23, R26, R28	RESISTOR, FIXED, COMPOSITION: $1K \pm 5\%$, $1/4W$	70 932 007 049
R2	RESISTOR, FIXED, COMPOSITION: 750 ohms ±5%, 1/4W	70 932 007 046
R4, R6, R11	RESISTOR, FIXED, COMPOSITION: $1.5K \pm 5\%$, $1/4W$	70 932 007 053
R7, R8	RESISTOR, FIXED, FILM: 2.2K ±2%, 1/4W	70 932 114 057
R9, R17	RESISTOR, FIXED, FILM: 1.5K ±2%, 1/4W	70 932 114 053
R10	RESISTOR, VARIABLE, FILM: 1K ±10%	70 933 302 007
R14	RESISTOR, FIXED, FILM: 1K ±2%, 1/4W	70 932 114 049
R15	RESISTOR, FIXED, FILM: 360 ohms ±2%, 1/4W	70 932 114 038
R16	RESISTOR, VARIABLE, FILM: 10K ±10%	70 933 302 010
R19	RESISTOR, FIXED, COMPOSITION: 270 ohms $\pm 5\%$, $1/4$ W	70 932 007 035
R20, R21	RESISTOR, FIXED, COMPOSITION: $2K \pm 5\%$, $1/4W$	70 932 007 056
R22	RESISTOR, FIXED, COMPOSITION: 4.7K ±5%, 1/4W	70 932 007 065
R24	RESISTOR, FIXED, FILM: 220 ohms ±2, 1 W	70 932 115 033
R25	RESISTOR, FIXED, FILM: 180 ohms ±2%, 1W	70 932 115 031
R27	RESISTOR, FIXED, COMPOSITION: 9.1K ±5%, 1/4W	70 932 007 072



COMPONENT VIEW

Figure 1-2-21. ASR Interface Module Parts Location



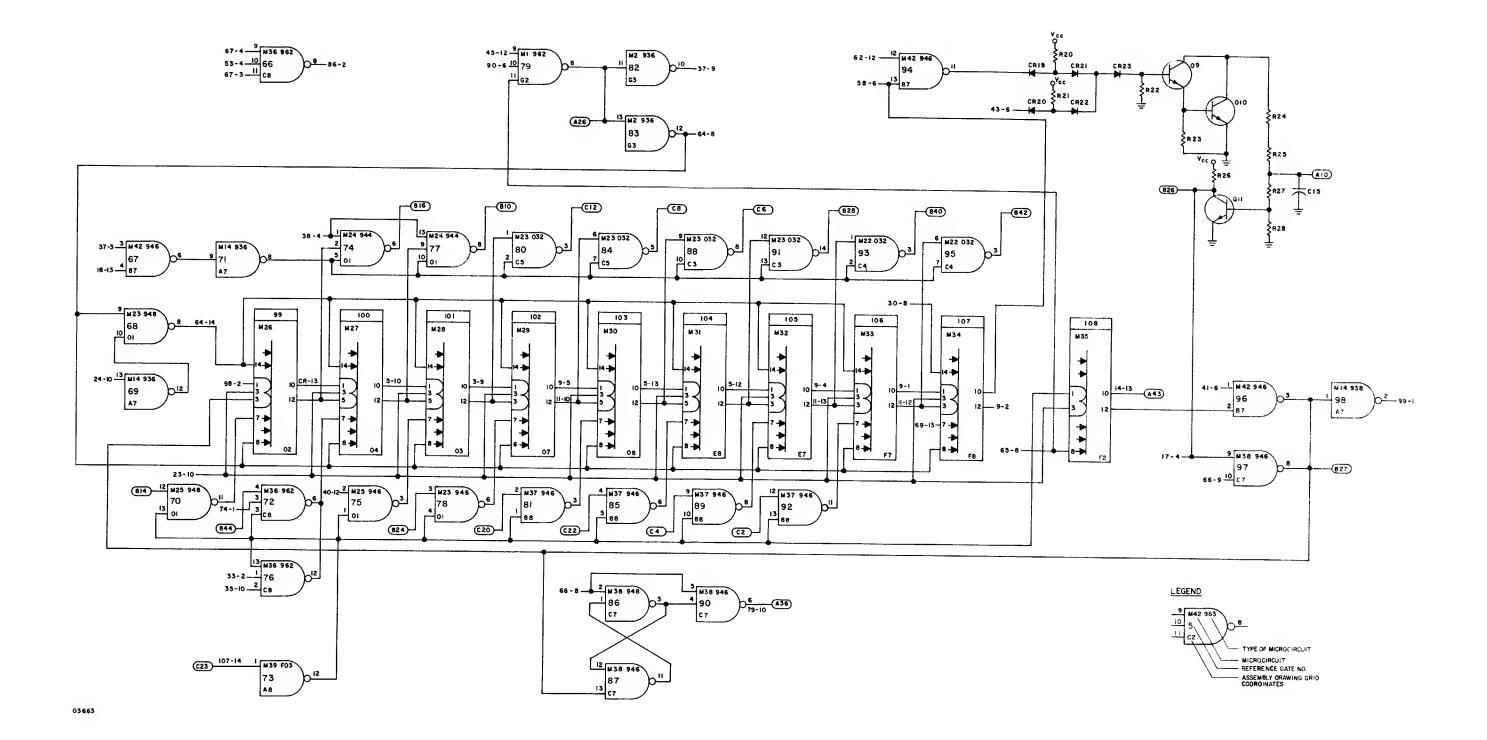


Figure 1-2-22. ASR Interface Module Schematic Diagram (Sheet 2 of 2)

HIGH SPEED A-U NO. 1 MODULE, MODEL CC-375

Ref. Desig.	Description	Part No.
C1 - C5	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 µF ±20%, 50 Vdc	70 930 313 016
CR1-CR17	DIODE: Replacement type 1N914	70 943 083 002
M1-M4, M17	MICROCIRCUIT: 032, quad NAND gate integrated circuit	70 950 100 032
M5, M10, M12, M20-M23, M25	MICROCIRCUIT: 944, power amplifier integrated circuit	70 950 105 008
M6, M9, M14, M15, M24, M26	MICROCIRCUIT: 963, triple NAND gate integrated circuit	70 950 105 012
M7, M18, M19	MICROCIRCUIT: 937, fast hex inverter integrated circuit	70 950 105 011
M8, M13, M29	MICROCIRCUIT: 961, dual NAND gate integrated circuit	70 950 105 009
M11, M16, M27, M28	MICROCIRCUIT: 949, quad NAND gate integrated circuit	70 950 105 010
R1, R2	RESISTOR, FIXED, COMPOSITION: 2K ±5%, 1/4W	70 932 007 056

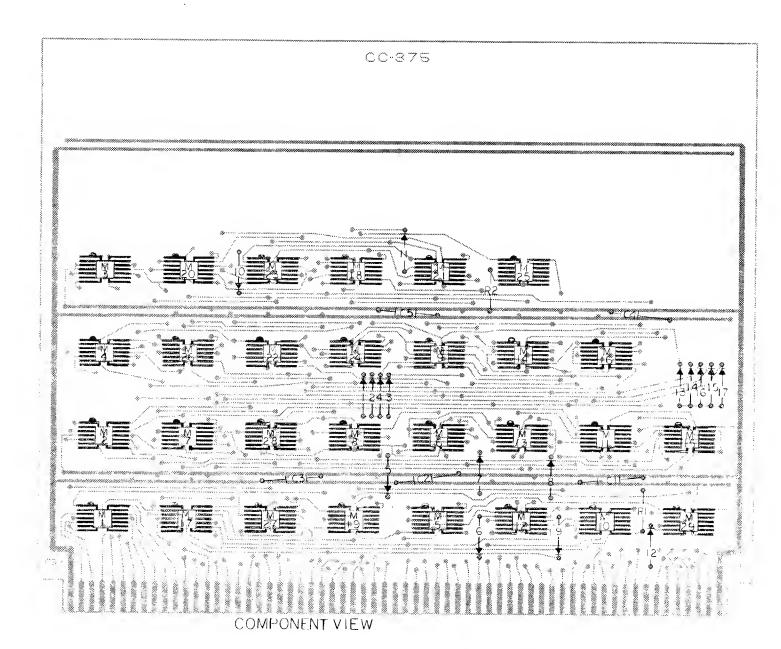


Figure 1-2-23. High Speed A-U No. 1 Module Parts Location

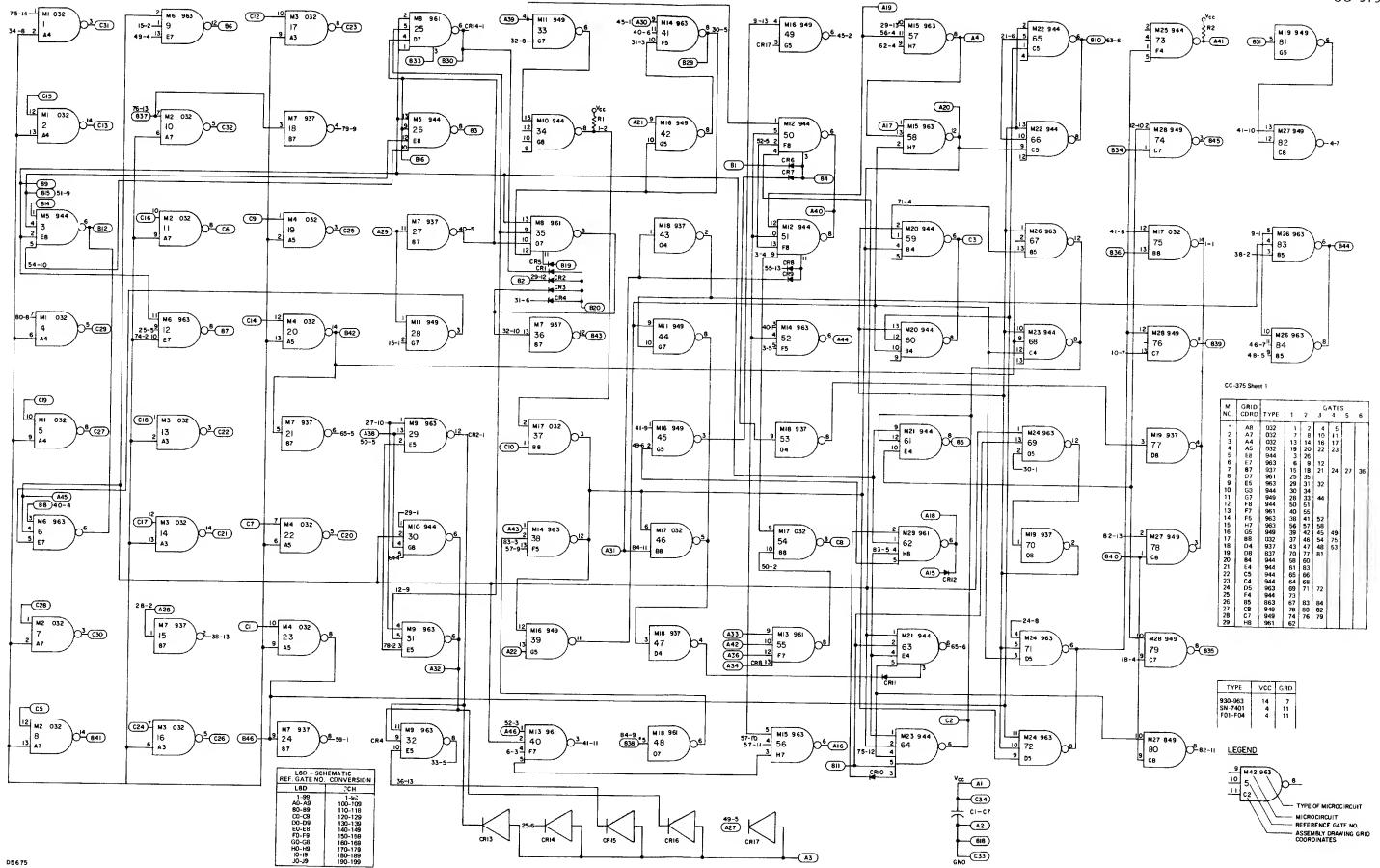


Figure 1-2-24. High Speed A-U No. 1 Module Schematic Diagram

HIGH SPEED A-U NO. 2 MODULE, MODEL CC-401

Ref. Desig.	Description	Part No.
C1-C5	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 μF ±20%, 50 Vdc	70 930 313 016
CR1-CR14	DIODE: Replacement type 1N914	70 943 083 002
M1-M6	MICROCIRCUIT: 032, quad NAND gate integrated circuit	70 950 100 032
M7, M22, M23	MICROCIRCUIT: 937, fast hex inverter integrated circuit	70 950 105 011
M8-M11, M13, M14, M18	MICROCIRCUIT: 944, power amplifier integrated circuit	70 950 105 008
M12, M21	MICROCIRCUIT: 949, quad NAND gate integrated circuit	70 950 105 010
M15-M17	MICROCIRCUIT: 961, dual NAND gate integrated circuit	70 950 105 009
M19, M20	MICROCIRCUIT: 963, triple NAND gate integrated circuit	70 950 105 012
R1, R2	RESISTOR, FIXED, COMPOSITION: 2K ±5%, 1/4W	70 932 007 056

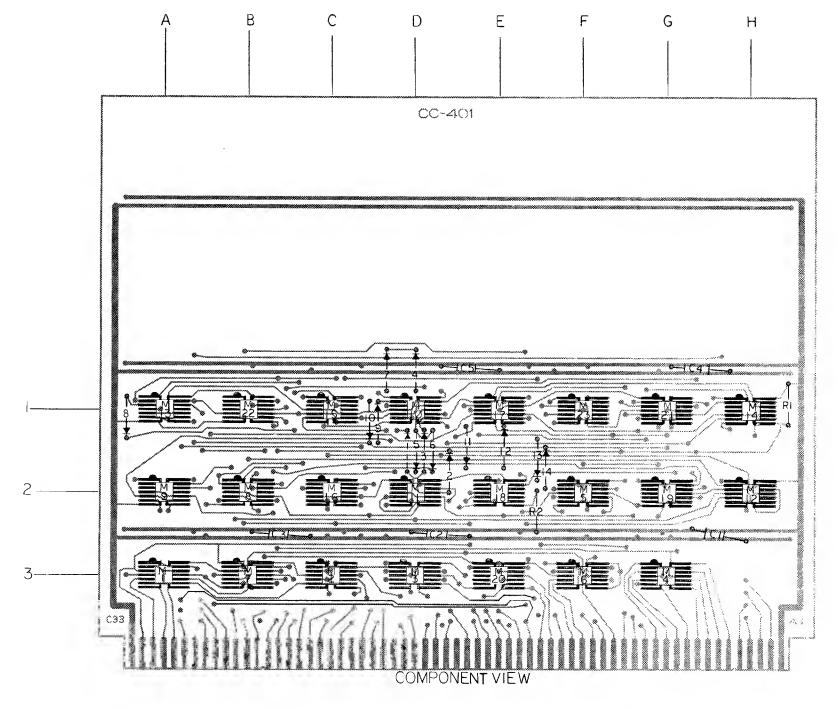
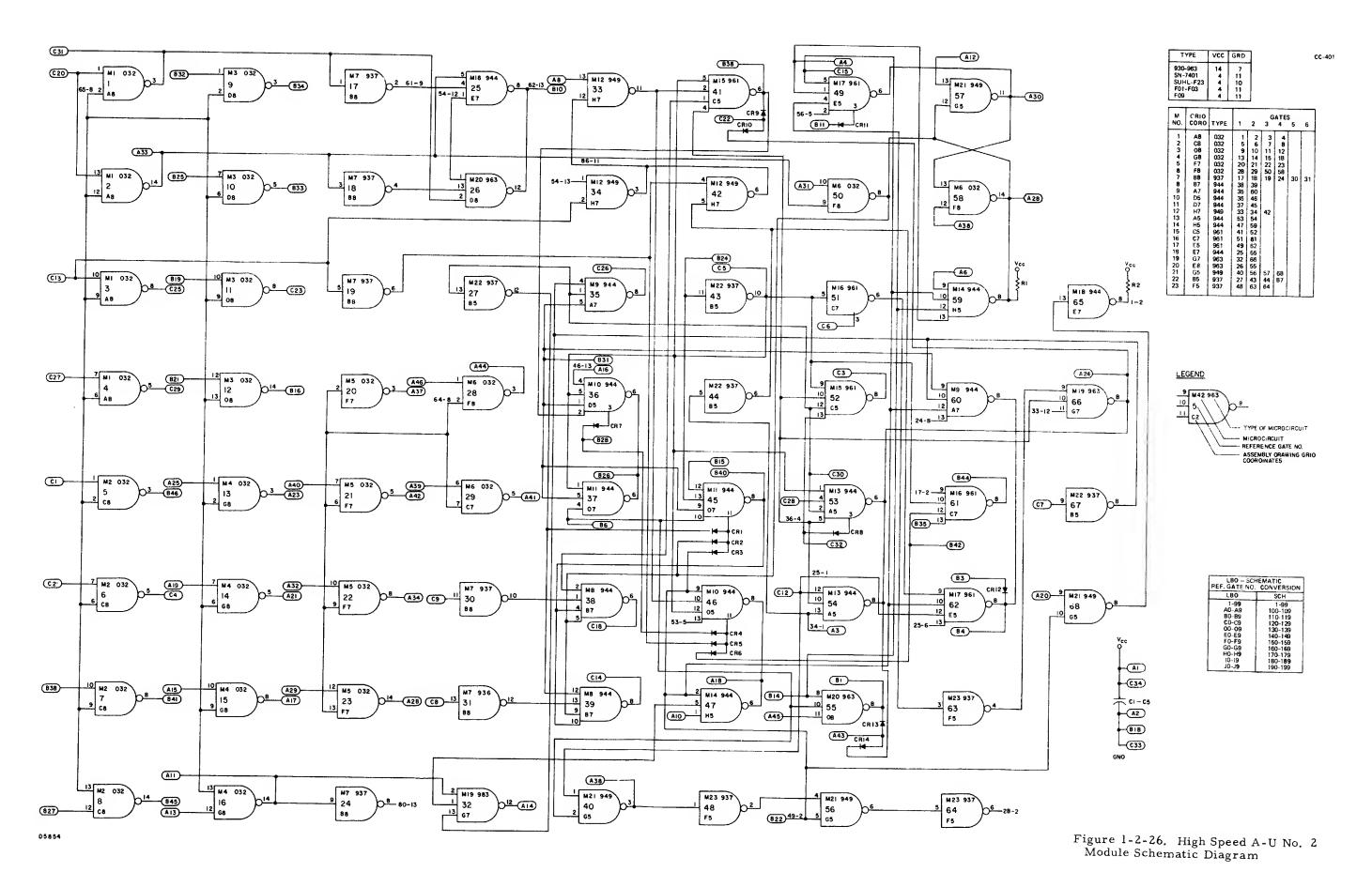


Figure 1-2-25. High Speed A-U No. 2 Module Parts Location



EXTENDED ADDRESS MODULE, MODELS CC-510A AND CC-869

Electrical Parts List

Ref. Desig.	Description	Part No.
C1 - C6	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 µF ±20%, 50 Vdc	70930313016
CRI - CR4	DIODE, SILICON	70943083002
M1, M7	MICROCIRCUIT: 937, hex inverter integrated circuit	70950105011
M2, M38	MICROCIRCUIT: 949, quad NAND gate integrated circuit	70950105010
M3, M8, M41	MICROCIRCUIT: 963, triple NAND gate integrated circuit	70950105012
M4, M10	MICROCIRCUIT: 032, NAND gate integrated circuit, Type SN 7401	70950100032
M5, M6, M37*	MICROCIRCUIT: 944, dual NAND gate integrated circuit	70950105008
М9	MICROCIRCUIT: 961, dual NAND gate integrated circuit	70950105009
M11 - M13	MICROCIRCUIT: F-04, flip-flop integrated circuit	70950100004
M14 - M21*	MICROCIRCUIT: F-01, NAND gate integrated circuit	70950100001
M22 - M36, M39*	MICROCIRCUIT: F-03, power amplifier integrated circuit	70950100003
M40	MICROCIRCUIT: F-02, quad NAND gate integrated circuit	70950100002
R1 - R23, R25 - R31, R34, R35*	RESISTOR, FIXED, COMPOSITION: 62 ohms ±5%, 1/4W	70932007020
R24, R32, R33, R36*	RESISTOR, FIXED, COMPOSITION: 1K ±5%, 1/4W	70932007049

^{*}Model CC-869 does not use M14 - M37, M39, and R1 - R36.

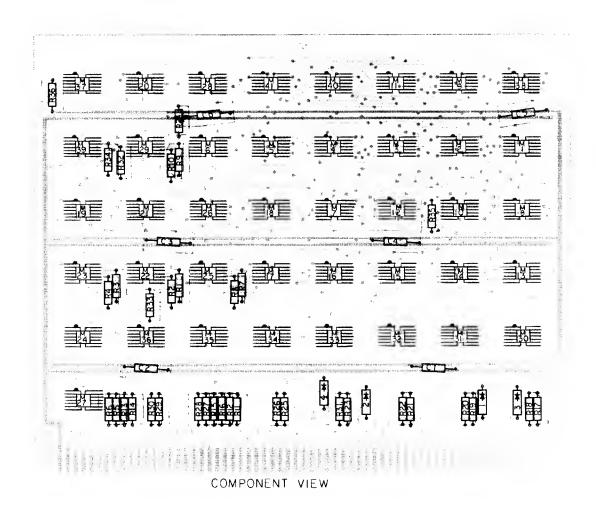


Figure 1-2-27. Extended Address Module, Model CC-510A (Drawing No. C70025464702, Rev C)

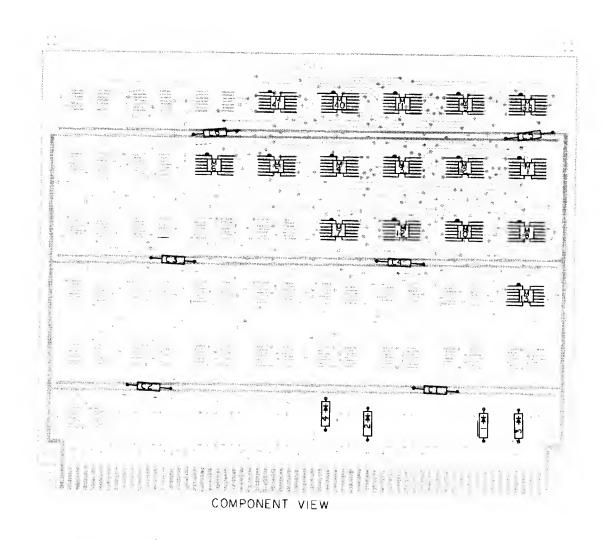


Figure 1-2-28. Extended Address Module, Model CC-869 (Drawing No. C 70025464703, Rev C)

MEMORY PARITY BOARD, MODELS CC-558 AND CC-621

Ref. Desig.	Description	Part No.
C1 - C8*	CAPACITOR, FIXED, PLASTIC: 0.033 μ F $\pm 20\%$, 50 Vdc	70930313016
CR1 - CR7*	DIODE, SILICON	70943083002
M1 - M4*	MICROCIRCUIT: 949, quad NAND gate integrated circuit	70950105010
M5 - M7*	MICROCIRCUIT: 963, triple NAND gate integrated circuit	70950105012
M8 - M12*	MICROCIRCUIT: 961, dual NAND gate integrated circuit	70950105009
M13 - M18*	MICROCIRCUIT: 032, NAND gate integrated circuit, Type SN 7401	70950100032
M19 - M22*	MICROCIRCUIT: 937, hex inverter integrated circuit	70950105011
M23, M24	MICROCIRCUIT: F-03, power amplifier integrated circuit	70950100003
M25 - M34*	MICROCIRCUIT: F-04, flip-flop integrated circuit	70950100004
M35	MICROCIRCUIT: F-02, NAND gate integrated circuit	70950100002
R1, R2*	RESISTOR, FIXED, COMPOSITION: $1K \pm 5\%$, $1/4W$	70932007049

^{*}Model CC-621 does not use C1, C4, C7, CR1 - CR7, M3, M4, M7, M9 - M17, M19 - M22, M25 - M34, R1, R2.

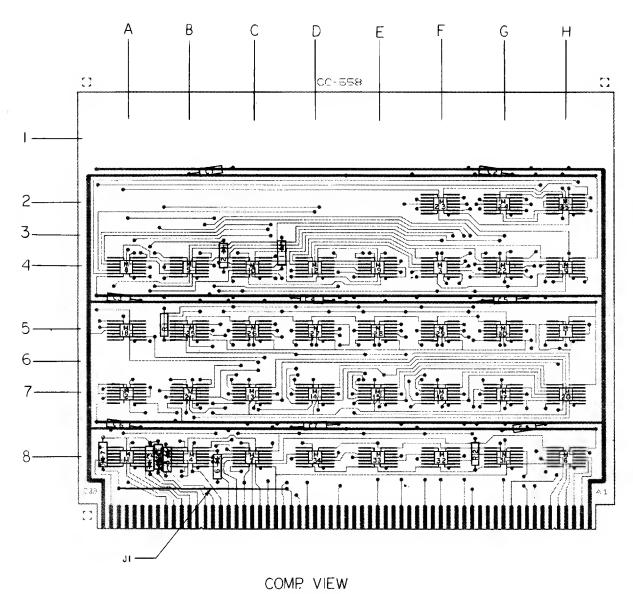
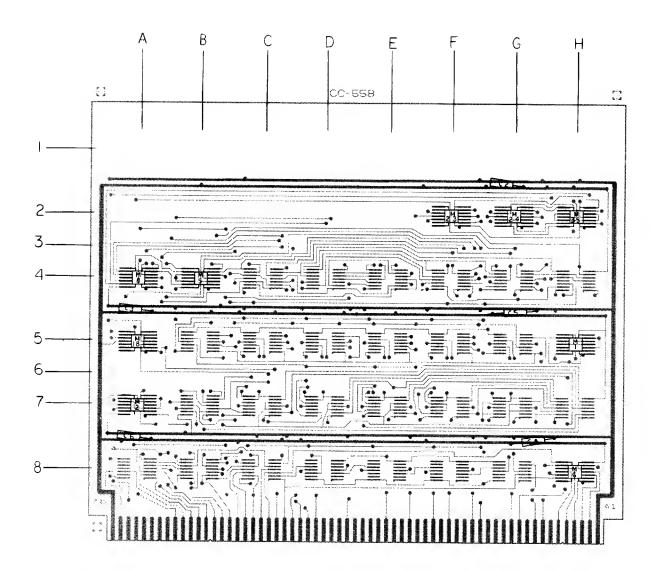


Figure 1-2-29. Memory Parity Board, Model CC-558 (Drawing No. C 70025966701, Rev B)



COMP. VIEW

Figure 1-2-30. Memory Parity Board, Model CC-621 (Drawing No. C 70025966702, Rev B)

CABLE PAC, MODEL CC-672

The Cable PAC, Model CC-672 (Figures 1-2-31 and 1-2-32), contains 16 1K resistors and one 2.2 µF capacitor. One side of each component is connected to +6V. The other side of each component is connected to individual plated-through holes and connector pins. In addition, 16 plated-through holes (numbers 18-31) are connected directly to 16 connector pins (numbers 51-66). All plated-through holes can accept No. 24 AWG wire.

Model CC-672 Electrical Parts List

Ref. Desig.	Description	Part No.
C1	CAPACITOR, FIXED, ELECTROLYTIC: 2.2 µF ±20%, 35 Vdc	70930217017
J1, J2	WIRE, TINNED: No. 24 AWG	70940001020
R1-R16	RESISTOR, FIXED, COMPOSITION: $1K \pm 5\%$, $1/4W$	70932007049
	SLEEVING, ELECTRICAL	70981003814

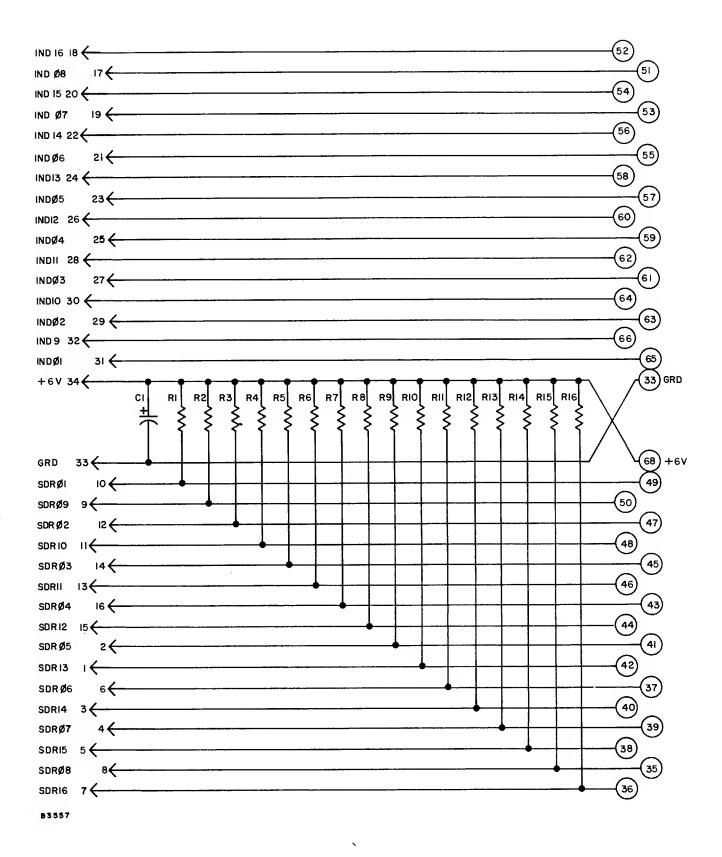


Figure 1-2-31. Cable PAC, Model CC-672, Schematic Diagram

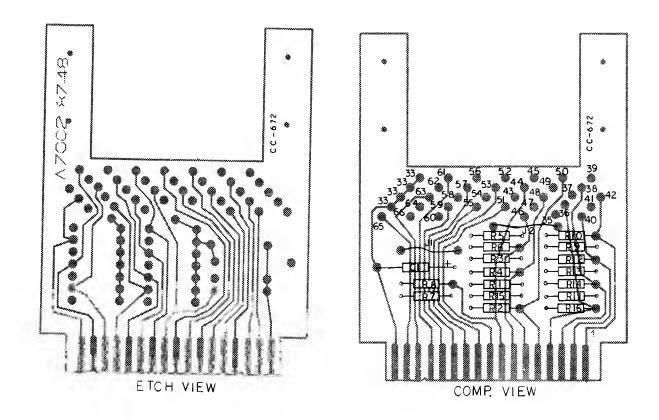


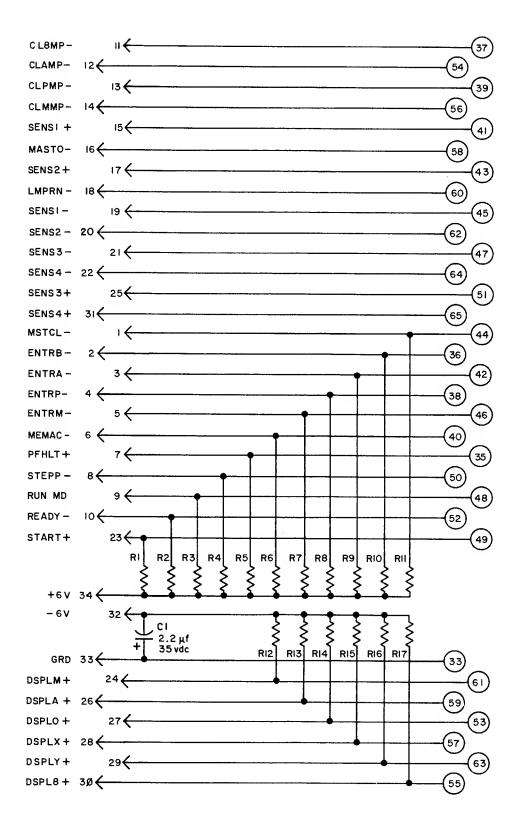
Figure 1-2-32. Model CC-672 Parts Location

CABLE PAC, MODEL CC-681

The Cable PAC, Model CC-681 (Figures 1-2-33 and 1-2-34), contains 17 1K resistors and one 2.2 µF capacitor. One side of 11 resistors (R1-R11) is connected to +6V, and six resistors and one capacitor are connected to -6V. The other side of each component is connected to individual plated-through holes and connector pins. In addition, 14 plated-through holes (numbers 11-22, 25, 31) are connected directly to 14 connector pins. All plated-through holes can accept No. 24 AWG wires. This PAC is used with the bottom harness and can be used in the Model 316 ruggedized computer.

Model CC-681 Electrical Parts List

Ref. Desig.	Description	Part No.
Cl	CAPACITOR, FIXED, ELECTROLYTIC: 2.2 μ F ± 20%, 35 Vdc	70930217017
J1-J3 R1-R17 	WIRE, TINNED: No. 24 AWG RESISTOR, FIXED, COMPOSITION: 1K ± 2%, 1/4 W SLEEVING, ELECTRICAL	70940001020 70932114049 70981003804



A3560

Figure 1-2-33. Cable PAC, Model CC-681, Schematic Diagram

CC-681

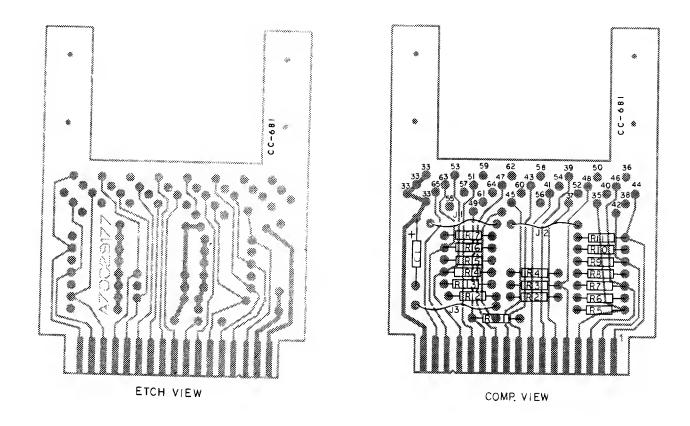


Figure 1-2-34. Model CC-681 Parts Locations

CHAPTER II CSM-160 CORE MEMORY MODULE

SECTION 1 DESCRIPTION

The CSM-160 Core Memory Module is a high-speed, digital storage device capable of storing a maximum of 16 bits of information in 4096 locations, expandable to 16,384 locations in increments of 4096. Data is stored in an array of 30 mil ferrite cores. Selection of address is accomplished by use of conventional four-wire coincident-current techniques. The switching time of the cores and the frequency characteristics of the driving and logic circuitry permit a full-cycle time of 1.6 µs. The memory does not contain a data register or a timing generator. Memory address signals are received from the address bus at the beginning of any memory operation. The appropriate timing signals are also received and the selection of a location is accomplished in the memory core array. During a memory load (clear-write) cycle, data are supplied to the memory from the computer and stored at the selected address. During a memory-unload (read-regenerate) cycle, the data word at the selected location is first transferred to the computer and then regenerated (rewritten) into the core array.

SYSTEM LAYOUT

The system consists of modular connector BLOC assemblies holding groups of μ -PACs. The solderless-wrap connector assembly is a single piece of molded, glass-filled phenolic capable of holding eight μ -PACs. The memory module is contained in three connector assemblies arranged in a 1 x 3 connector plane.

The core stack is a plug-in unit requiring six μ -PAC connectors, three on each side (Figure 2-1-1). The stack assembly is made up of four glass epoxy boards, each containing four core mats of 4096 cores interconnected to make a stack of 16 bit words.

LOGIC SIGNAL LIST

Logic signals used in the memory are identified and defined in Table 2-1-1. Positive signals (+6V) are labeled "+", and ground signals (0V) are labeled "-". Amplified signals have a letter following the polarity indicator (e.g., XXXX+A).

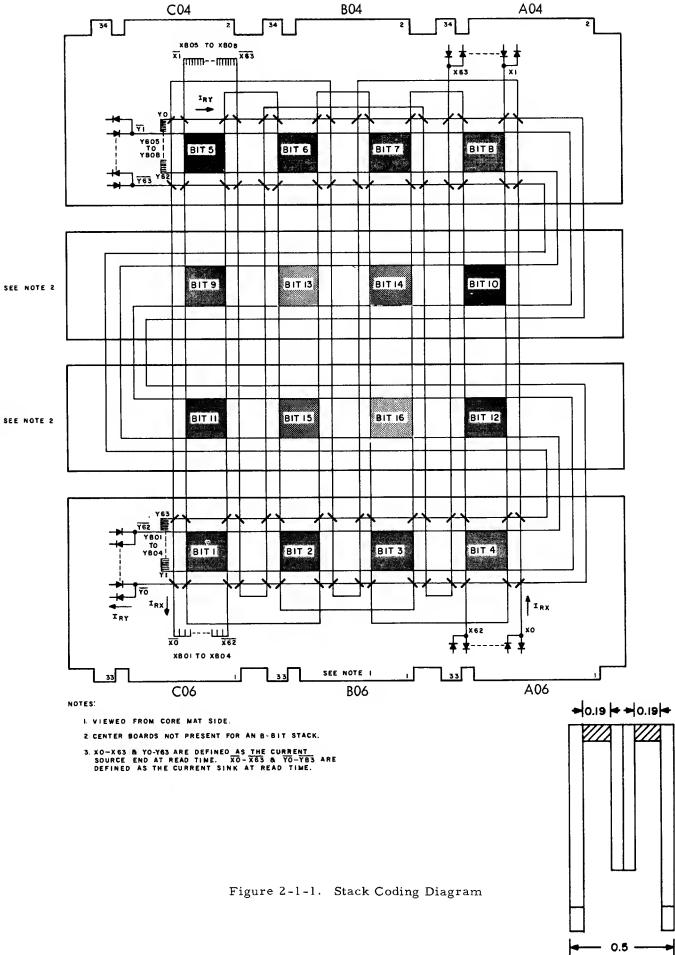


Table 2-1-1 Logic Signal List

Mnemonic

Memory Bank Select

BANK- A through D INHBX+

Inhibit Command

M01FF+ to M16FF+

Memory Module Data Inputs

Name

MAD05- to MAD16-

Memory Address Inputs

MADCL-

Memory Address Clear Command

MBSYX+ MEMCI+

Memory Busy Signal

MM01F - to MM16F

Memory Cycle Initiate

Sense Amplifier Output Pulses

MSTCL-

Master Clear Pulse

RMBSX-RTDL-

Reset Memory Busy Pulse

Reset Timing Delay Line Pulse

RZ01+ to RZ16+

Inhibit Winding Termination Resistors

STROB-

Sense Amplifier Strobe

SW01+ tp SW16+

Sense Windings

SWCYX-

Start Write Cycle Pulse

UNSL-

Unit Select Command

UNSL+A through C WRITE-

Unit Select Signal

XB01+ to XB08+

Write Enable Signal

X-Bus Selection Outputs

XD01+ to XD16+

X-Current Source Resistor X-Drive Selection Outputs

XRSW-

X-Read Switch Signal

XTIMG+

XCSR+

X-Read/Write Timing

XWSW-

X-Write Switch Signal

XYRE-

X & Y Read Enable Signal

XYWE-

Y-Read Switch Signal X & Y Write Enable Signal

YB01+ to YB08+

Y-Bus Selection Outputs

YCSR+

Y-Current Source Resistor

YD01+ to YD16+

Y-Drive Selection Outputs

YTIMG+

Y-Read/Write Timing

Inhibit Windings

 $ZW01\pm$ to $ZW16\pm$

SPECIFICATIONS

Capacity

4K randomly addressable 16-bit words, expandable to 16K in 4K increments.

Storage Mode

Coincident-current magnetic core array (3D, 4-wire) X0 through X63 X Drive Line Y0 through Y63 Y Drive Line

Cycle Time

 $1.6 \mu s$

Input Levels

Positive (Passive): +2.4V to +6.3V Ground (Active): 0V to 0.5V at 2.0 mA (max)

Output Levels

Positive (Passive): +6.3V max at 0 mA; +3.0V to +5.0V at 0.3 mA Ground (Active): +0.5V max at 13.6 mA

Memory Cycle Timing

For each cycle, the computer must provide the memory with an address and a read or write indication, and provide the timing circuits (located outside the memory) with a start signal. Once the cycle has been initiated, another cycle cannot be started until 1.6 µs has elapsed. During a read cycle, information will be available no more than the time presented in Figure 2-1-2. If the memory is performing a write cycle, information must be made available to the memory within the time specificied in Figure 2-1-2. Interface connections are shown in Section 4 (LBD 80.06).

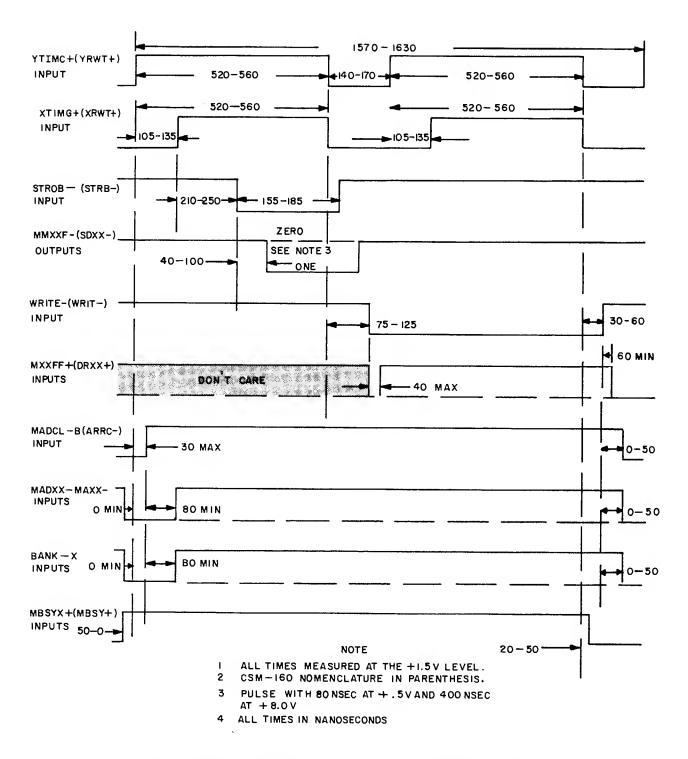


Figure 2-1-2. Interface Timing Requirements for all Units Except A70023577705 (70942507002 Stack) (A70110011397, Rev G)

SECTION 2 PRINCIPLES OF OPERATION

PRINCIPLES OF MAGNETIC CORE MEMORIES

Magnetic Core Storage

The memory core stack, housed in the magnetic core unit, is a matrix configuration of individual (30 mils O.D., 18 mils I.D.) ferrite cores. Basically, the ferrite core is a 1-bit storage element in the form of a ferrite ceramic ring that can be magnetically saturated to either positive of negative flux density. The ferrite material retains a large part of the magnetic flux developed at the time the core is saturated which is an important characteristic of the core. The time required to switch a core from one polarity or state to another is primarily dependent on the core material and size. Consequently, cores measuring only tenths of an inch in diameter are used in the memory core array to permit fast switching speeds.

A similarity exists between the magetic core and the flip-flop in that both provide storage for one bit of data. The two extremes of saturation in a magnetic core represents ZERO and ONE, as do the two stable states of a flip-flop. A core can be set to a ONE state by the application of a current pulse of similar magnitude applied in the opposite direction. Similarly, a flip-flop is set or reset by applying pulses to the appropriate inputs. Both the magnetic core and the flip-flop provide memory of the last pulse applied, but the core does so without requiring power to hold its state.

The ferrite core has a nearly rectangular hysteresis loop. The hysteresis loop is a graphical representation of the flux density produced in a magnetic material, plotted against the magnetizing force that produces it. Figure 2-2-1 is a simplified drawing showing the generation of a typical ferrite core hysteresis loop. Starting with an unmagnetized core, an increase in magnetizing current (H) increases the flux density (B) along the S-shaped curve (A). The flux density levels off when the core is saturated, and any additional current applied does not appreciably increase the flux density because the core material is supporting as much flux as it can. As the current is decreased, then made to flow in the opposite direction, the flux does not collapse along the same line (B); and most of the flux remains even after the current has fallen to zero. The amount of flux actually remaining is a function of the retentivity of the magnetic material. As a magnetizing current is applied in the opposite direction, it has little effect on the flux level until the current reaches the knee of the hysteresis loop.

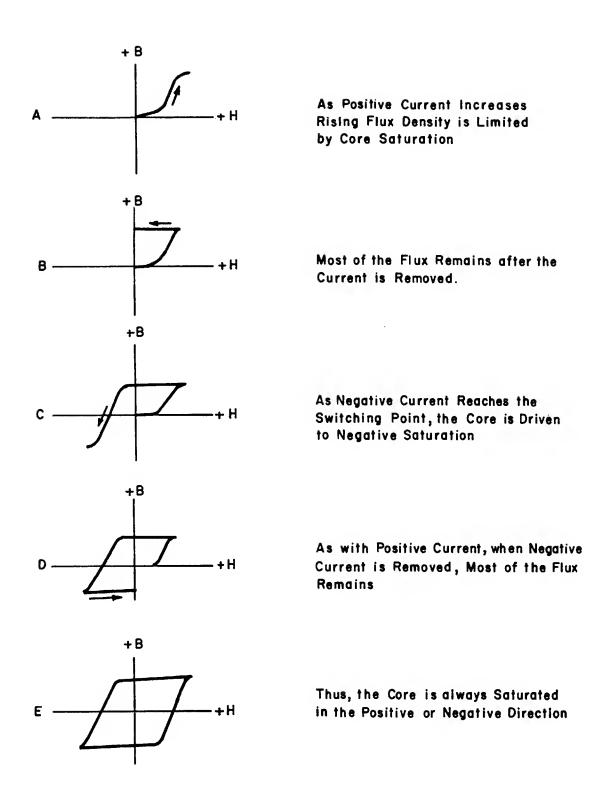


Figure 2-2-1. Ferrite Core Hysteresis Loop

A slight increase in current beyond the knee of the curve switches the core rapidly to negative saturation (C). The point on the curve representing the amount of current required to change the state of the core is termed the coercive current. When the negative magnetizing current is removed, most of the flux is retained as before (D). Note that the original sweep from a magnetically neutral condition is never repeated (E). A memory core in coincident-current use is never in a neutral condition, but is switched from one saturated state to the other. The core is thus an extremely useful binary component because it can exist in either of two stable states and can switch rapidly from one to the other.

For any given toroidal magnetic core, the necessary magnetomotive force required to effect switching is a function of the product of the number of turns of wire and the current driven through those turns. It is not economically feasible to wind multiple turns of wire around the small toroidal cores used in core memories; rather the number of turns is reduced to two, one in each of the perpendicular driving coordinates, and the current in these coordinate wires is of such a magnitude as to cause switching (rapid flux change) to occur.

In addition to the perpendicular (X and Y) coordinate selection lines, each core is also threaded by two other wires, each of which passes through every core in a plane. One is the sense winding, which detects flux-change due to switching of a core and thus provides a readout signal from the plane. The other winding is the inhibit winding which is used, as its name suggests, to inhibit or prevent the writing of a ONE into the core, thereby causing ZERO to be stored. A single memory core, with its associated control windings is illustrated in Figure 2-2-3.

A disadvantage of the memory core is that it does not provide a static indication of its state, as does a flip-flop. To obtain an indication of the condition of the flux in a memory core, the state of the core must be switched.

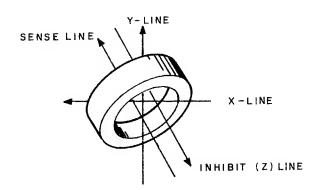


Figure 2-2-2. Core Control Windings

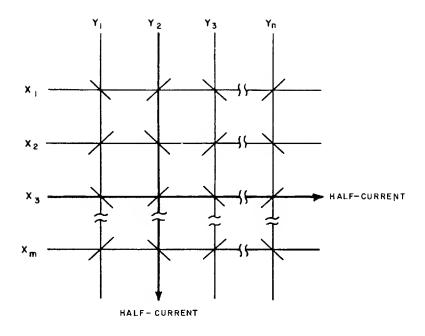


Figure 2-2-3. Coincident-Current Selection

Information Sensing

Sense lines allow the reading of information stored in the cores. One sense line (Figure 2-2-2) is threaded through all memory cores of each mat.

To read any of the words stored in memory, half-currents in the proper direction are generated in the selected X- and Y-lines (Figure 2-2-3). The read half-currents combine at the coincident junction of the X- and Y-lines to change the state of the affected core in each memory mat. If the affected core is storing a ONE at that instant, the effect of the read half-currents will change the state of the core to ZERO. If the core was previously in the ZERO state, the read half-currents will have no effect on the core. When the core is switched from the ONE to the ZERO state, the rapid change in flux from positive saturation to negative saturation induces a voltage pulse in the corresponding sense line. Therefore, the presence of a voltage pulse in the sense line during the read operation indicates that a ONE has been stored in the indicated core. If no voltage pulse occurs in a sense line during read operation, a ZERO is indicated. The sense lines designated SW01 through SW16 in the memory core stack are connected to sense amplifiers. A ONE input to any of the sense amplifiers is amplified and applied to the information register. Thus, output data is transferred from its storage location in the core stack to the information register.

Addressing

The complete core stack for a magnetic core unit consists of a number of individual matrices or mats. Each mat contains memory cores assembled in a rectangular configuration. The memory cores are threaded by X- and Y-lines in each mat so that one memory core is physically located at each junction of an X-line and Y-line.

As previously stated, pulses of current applied along the X- and Y-lines switch a memory core from one state to another. If one-half of the current required to switch a core is applied along the X-line, and one-half of the necessary current is applied along the Y-line, the core situated at the junction of the energized X- and Y-lines will receive the full switching current. This type of operation is termed coincident-current operation.

A coincident-current magnetic core memory depends upon the coincidence of two half-currents to read data from or to write data into the cores. Two additive half-current pulses will set the core to the ONE state, while two half-current pulses applied in the opposite direction will reset the core to the ZERO state. A core with two half-current inputs is essentially an AND circuit requiring that half-current be applied to both X- and Y-lines in the same direction to change the state of the flux at the core. A half-current applied to one line without a similar half-current applied to the other line has no effect on the core.

Only one X-line and one Y-line of a mat are energized during a single cycle, and only that core situated at the junction of the activated X- and Y-lines will respond to the coincident half-current pulses. Therefore, only one core in each mat will be affected during a single cycle. A simplified diagram of coincident-current selection of a memory core is illustrated in Figure 2-2-3. In effect, the X-line selects one row (X-row), and the Y-line selects one column (Y-column).

In coincident-current memories, the X- and Y-lines are wired in series through all mats of the memory core array. Thus each X-line and each Y-line threads corresponding rows or columns of cores in all memory mats. Energizing one of the X-lines (designated X_1 through X_m in Figure 2-2-3 supplies a half-current pulse to the appropriate row of cores in every mat. Similarly, energizing one of the Y-lines (designated Y_1 through Y_n), supplies a half-current pulse to the appropriate column of cores in every plane. When pulses occur simultaneously on two lines (X and Y), they select the same core position in each of the planes. Therefore, the X- and Y-lines select a word in the memory core array and enable read or write operations.

Writing

Inhibit lines are used to enable a computer word or instruction to be written into memory at a selected address location. A single inhibit line is threaded through each memory core in a mat (Figure 2-2-2) and each mat of the magnetic core stack requires an individual inhibit line.

To write information into memory, half-current pulses in the direction opposite to those generated for read operation are applied to the selected X- and Y-coincident junction to switch the affected core in each memory plane.

Since all the cores at the selected address have been cleared to the ZERO state prior to the application of the write half-currents, the write half-currents operate to switch all cores to the ONE state. If the incoming data dictates that a ZERO is to be written into a specific core, some means must be used to prevent the core from switching to the ONE state when the write half-currents are generated. This is accomplished by the inhibit (Z) lines designated ZW01 through ZW16. An inhibit pulse, when transmitted through the inhibit line of the memory plane at the same time that the write half-currents are applied through the X- and Y-lines, prevents the writing of a ONE because the inhibit current subtracts from X- and Y-write current.

The inhibit pulse is of the same magnitude but of the opposite polarity to the write half-current pulses. Therefore, the inhibit pulse directly cancels the effect of one write half-current pulse. The net effect of the two write half-current pulses and an inhibit pulse, is equivalent to a single write half-current pulse on the addressed core. This prevents the core from switching from the ZERO to the ONE state.

Information to be written into memory is stored in the information register prior to being transferred to the memory core stack. During the transfer operation, a passive signal from the register flip-flop will prevent the generation of an inhibit pulse whereas an active signal from the register flip-flop allows an inhibit pulse to be generated. In this way information is rewritten (or new information is written) into the selected memory location exactly as it appears in the information register.

CORE STACK CONFIGURATION

The storage array is organized about a conventional four-wire "3D" configuration where 4096 addressed cores are made available by the intersection of 64 X lines and 64 Y lines in each bit area.

ADDRESSING AND SELECTION

Addressing-Random Access

The memory address register consists of cross-coupled flip-flops located on the CM-306 Selector PAC. Data received by the 12 single-ended, address input lines (MAD05 through MAD16) will set the flip-flops and a reset pulse (MADCL-) will commonly reset all the flip-flops at the end of the cycle. The address flip-flop outputs control the drive line selection circuits. Section 5 contains a detailed description of this PAC.

Decoding and Selection

Figure 2-2-4 is a simplified diagram of the address decoding and selection for a typical bit of a 4K memory. Three address bits are transferred to the X switches and three others to the X sinks. The X switches uniquely enable one of eight read/write line pairs going to the diode matrix; the X sinks select one of eight read/write busses. The selected buss enables one end of eight drive lines, each of which has its other end connected to an enabled diode matrix. Thus, only one of 64 X lines has been selected. The Y-line selection is accomplished in a similar manner.

Figure 2-2-5 is a simplified schematic diagram of the X decoding and selection matrix. Two diodes per line isolate a single line when selected. Consider a read-regenerate cycle involving drive line X60. During the read portion of the cycle, X read switch (Q1) and X read sink (Q4) are selected by related address register outputs. These selection outputs are turned on when read timing pulses XRSW-for the switch and XYRE-for the sink go to 0V. Read current then flows in line X60 from +15V through R1, Q1, CR1, CR2, X60, and Q4 to ground. Read current ceases to flow when signals XRSW- and XYRE- return to +6V. During the write portion of the cycle the addresses do not change. Write timing pulses XYWE- for the sinks and XWSW- for the switches are generated. When these signals go to 0V, sink Q2 and switch Q3 are turned on. Write current then flows from +15V through R1, Q3, CR3, line X60, CR4 and Q2 to ground. Write current ceases when signals XYWE- and XWSW- return to +6V. At the end of the cycle, the addresses will change and, by similar manner, the remainder of the X lines will be selected.

The Y-selection matrix is similar to the one described with the exception of being decoded by different addresses and command signals. For a detailed description of the CM-306 Selector PAC, refer to Section 5.

TIMING AND CONTROL

Section 4 contains the timing and control logic diagrams to illustrate the logical functions associated with the control and distribution of memory timing pulses. Interface timing is presented in Figure 2-1-2.

OPERATING MODES

Read-Regenerate Mode

Memory interface signals are provided by the CPU or the memory expansion option. When the Selector PAC control pulses XRSW- and XYRE- are generated, the sinks and switches are turn on. Stored data present in the address register will be read out (Figure 2-2-6). The sense amplifier strobe input (STROB-) will sample the data. If a ONE was stored at that address, the sense amplifier associated with that bit will produce an output, setting the data registers external to the memory module. The set side of the data registers (MXXFF+) will be presented to the input of the inhibit drivers and disable it. If a ZERO was stored at that address, no output will occur. The data register will remain reset and enable the inhibit drivers. During the write portion of the cycle, the selector PAC

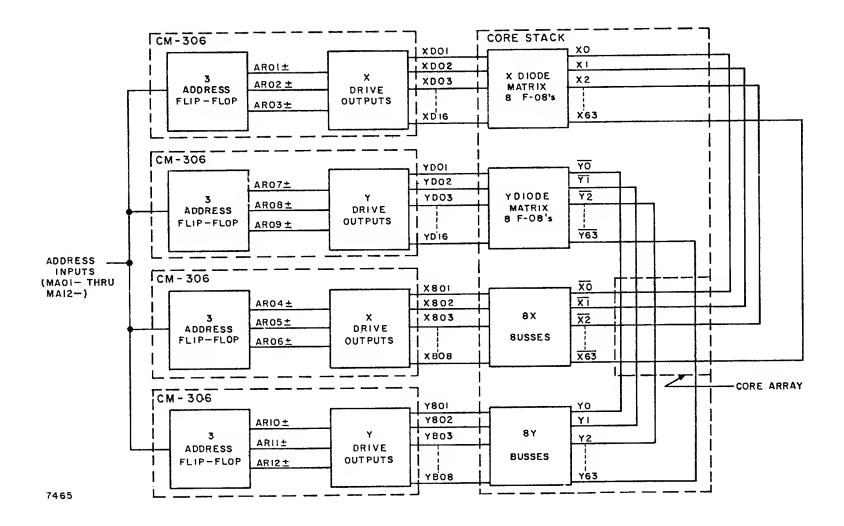


Figure 2-2-4. Address Decoding and Selection, Simplified Block Diagram

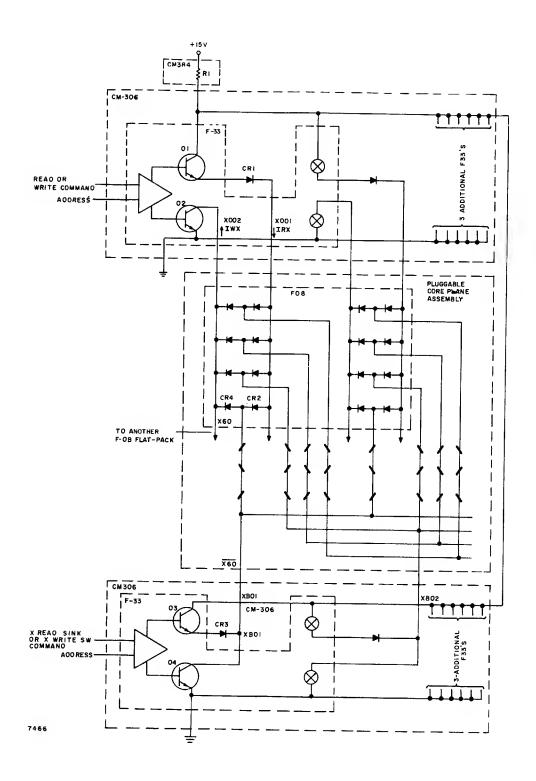


Figure 2-2-5. Decoding and Selection Matrix, Simplified Schematic

control pulses (XRSW- and XYWE-) are generated, and X- and Y-line currents are once again established. When the inhibit pulse (INHBX+) is generated, a ONE will be inserted into the stack if the inhibit drivers were disabled. A ZERO will be reinserted if the drivers were enabled.

Clear-Write Mode

The clear-write mode operation is identical to the read-regenerate mode except the sense amplifier strobe signal is not generated. Without the sense amplifier strobe, data stored in a selected address are destroyed. During the write portion of the cycle, new information stored in the data register is inserted in the core stack in the same manner that information is regenerated.

INTERFACE TIMING

The interface timing for the read-regenerate and clear-write modes is shown in Figure 2-1-2. The timing distributor does not form an integral part of the memory system, therefore, with the exception of signals XYRE-, XYWE-, XRSW-, and XWSW-, all signals, whether used internally or as commands, are classified as interface timing.

The address inputs (MAD05 through MAD16-) must be present for all cycles for the duration shown on the interface timing diagram. The data lines (M01FF+ through M16FF+) must be stable for the duration of the INHBX+ pulse as defined on the timing diagram for a read-regenerate or clear-write cycle.

MEMORY RETENTION

The magnetic core array does not require power to provide a static memory capability. A pulse of power is required to switch cores from one state to the other, but the pulse is not necessary to hold cores in their respective states. All cores remain in the state to which they have been switched because of material retentivity in the core. If power is removed or lost, the magnetic core array retains stored information indefinitely.

The turn-on sequencing of the main power supply is designed to allow the +15 voltage to remain off until the +6V and -6V logic supplies are stabilized. Similarly, the +15V supply is turned off before the logic supplies go out of regulation. This feature ensures that no current can flow during the power supply turn-on and turn-off transients providing memory input commands are quiescent which might change data previously stored in the core array.

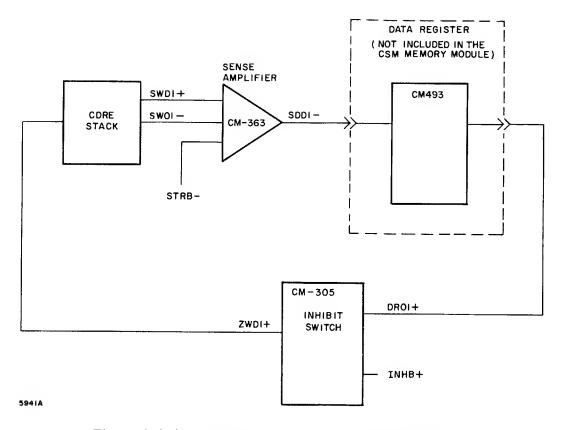


Figure 2-2-6. Regeneration Loop, Simplified Diagram

INTERFERENCE FROM MAGNETIC FIELD

Fan motors or power supplies having large magnetic fields should not be mounted close to the core stacks (some fan motors have fields that exceed 10 gauss). Reliable memory operation is guaranteed only if the peak magnetic field is held below 3 gauss in the region of the core mats.

SECTION 3 MAINTENANCE

This section contains data on preventive and corrective maintenance, service and repair for the H316 Magnetic Core Memory Module. Detailed PAC descriptions are included in Section 5 of this chapter.

TOOLS AND TEST EQUIPMENT

Table 2-3-1 lists the tools and test equipment required to service the memory. Detailed information on wire-wrapping tools and procedures is contained in the Instruction Manual for Solderless Wrapping of μ -PAC Digital Modules, Doc. No. 70130071371.

RECOMMENDED SPARE PARTS

One spare PAC of each type specified in Section 4 (LBD 80.08) is recommended as a spare part. Two F-08 microcircuits (70950100008) are recommended as spare parts if a spare correstack is not purchased. Section 5 contains parts lists for all PACs in the memory.

PAC HANDLING AND REPAIR PROCEDURES

Inserting and Removing System PACs

The μ -PAC connector is polarized to protect against incorrect PAC insertion. μ -PAC removal from the memory is accomplished by engaging the two holes in the handle of the PAC with the μ -PAC extractor tool. Do not remove or insert printed circuit cards without turning off the dc power to the unit.

PAC Troubleshooting

The Extender PAC, Model XP-330, can be used to gain access to points on the μ -PACs. Signals on the pins of the μ -PACs may be ascertained from the PAC descriptions contained in Section 5.

Component Checking

Many μ -PACs have identical channels. Components can be checked by resistance comparison with parts on other channels or other μ -PACs.

Component Replacement

When replacing defective components, use a low-wattage soldering iron and rosin core 60/40 solder. Remove excess solder from the printed circuit board. Care should be taken to avoid lifting the etch.

Table 2-3-1
Tools and Test Equipment

Quantity	Description	Type (or Equivalent)
1	Oscilloscope	Tektronix 585
1	Dual-Trace Preamplifier	Tektronix 82
1	Multimeter	Simpson 260
1	Card Extender PAC	XP-330
1	μ-PAC Extractor Tool	B008428
1	AC Current Probe	Tektronix P6016 probe and passive termination (or type 131 amplifier)
1	Hand Wire-Unwrapping Tool	70 917 202 001 (Gardner-Denver 505084-LH)
1	Hand Wire-Wrapping Tool, Battery Operated	70 917 200 001 (Gardner-Denver No. 14R2)
1	Wire Stripper	70 917 250 001 (Ideal 45-179)
25 ft	No. 30 AWG Solid Wire	70 940 061 010
1	Quick Disconnect Terminal Crimper	T and B WT 145
25 ft	No. 30 AWG Twisted-Pair Solid Wire	70 940 402 002
1	Precision DC Voltmeter	Weston Model 931-1905003 30/7 5/3 volts, ±1/2%, 1000 ohms/volt

Insert the leads of the new component through the drilled hole or eyelet, clip off excess wire, and solder to the printed circuit etch. A flat pack should be placed squarely on the etched area, using an insulator between it and the μ -PAC (except F-33 use Insulgrease instead of insulator). The leads should then be cut to the proper length and soldered. Examine the PAC carefully for excess solder. Remove rosin deposits with a commercial cleaning solvent and wipe the PAC clean with a dry lint-free cloth.

MAINTENANCE INSPECTION

Conduct a visual inspection periodically. Watch for accumulation of dust, dirt, improperly seated PACs, and damaged or improperly dressed cable and signal leads. Check to see that all connectors are securely mated and that the cooling fans are operating properly. Clean fan filters periodically. Do not clean core stack with air hose.

PREVENTIVE MAINTENANCE PROCEDURE

The memory is thoroughly tested at Honeywell Inc., Framingham, Mass., prior to shipment. All planes are tested simultaneously under all ZEROs, all ONEs, and worst-pattern conditions. The drive currents and strobe timing are set so that optimum operating margins result. The memory should be tested periodically, as a preventive maintenance procedure, by using a memory test program.

Memory Drive and Inhibit Voltage Calibration

The memory drive and inhibit currents are determined by the setting of the ± 15 Vdc supply and the CM-384A precision resistors. The ± 15 V supply setting should be periodically checked by using a voltmeter capable of reading the voltage within $\pm 1\%$. Measurements should be made at the memory terminals while a program is running in the memory.

The +15 Vdc supply should be within the following ranges as a function of stack inlet ambient temperature.

Temperature	+15 Vdc Range
0°C	$+16.0 \pm 0.6V$
25°C	$+15.0 \pm 0.8V$
50°C	$+13.8 \pm 0.6V$

The memory may be operated at marginal +15 Vdc supply for corrective or preventative maintenance purposes. The diagnostic program should contain at least the worst pattern (exclusive-OR of MA01-, MA03-, MA04-, MA07-, MA09-, and MA10-), all ONEs and all ZEROs. Failure points at high +15V setting (do not exceed +17.5V) and low +15V setting should be noted; their differences should be at least 1.6V at 0°C and 25°C and 1.1V at 50°C. The +15V supply may be set at the center of the failure point margins or at the values shown above.

Strobe Timing Calibration

The timing of the sense amplifier strobe pulse is set for each unit to give optimum operating margins. It should not be necessary to adjust the strobe timing. If a change in timing is required to obtain proper memory operation, the associated PACs should be checked (e.g., CM-306, CM-305) before a timing change is made. The CC-373 description in the Appendix should be referred to if a timing change is required. The STROB- pulse should be between 150 ns and 200 ns wide at the 1.5V points.

CORRECTIVE MAINTENANCE PROCEDURES

Memory system troubleshooting consists of determining the type of problem, predicting the μ -PAC at fault, and locating the faulty circuit. Test procedures to aid in troubleshooting are as follows.

CAUTION

Use oscilloscope probes carefully to avoid shorting of connector terminals resulting in damage to the PAC.

- a. In some cases, spare PACs may be used to isolate faulty circuits by interchanging identical PACs and noting any shift in the faulty bits or addresses. All memory PACs with the same designation are interchangeable.
- b. Refer to PAC schematic and assembly drawings in Section 5 to isolate the defective components on the printed circuit card. Replace defective components.
 - c. Memory failures are generally of the following types:
 - (1) Operation failures, which are caused by faulty timing and control circuits.
 - (2) Partial data word failures caused by a faulty sense amplifier, data register flip-flop, or data regeneration circuits.
 - (3) Address failures caused by faulty address register or selection circuits.
 - d. Memory failures may be localized by the following procedures:
 - (1) Load the test pattern into the memory.
 - (2) Initiate a read operation at each address sequentially and check each readout data word for the following failures:
 - (a) Operation failures: No apparent response to commands applied to the memory, or faulty operation at all addresses (Table 2-3-3).
 - (b) Partial data word failures: Failures of one bit or series of two or more bits at all addresses (Table 2-3-4).
 - (c) Address failures: Faulty memory operation at particular addresses only (Table 2-3-5).

MAGNETIC CORE STACK MAINTENANCE

Under normal operating conditions, it is unlikely that troubles will occur within the magnetic core stack. However, continuity measurements of the sense inhibit and drive windings will enable maintenance personnel to check core stack wiring. Exercise caution in taking these measurements to avoid damaging the matrix windings.

CAUTION

Multimeter current and voltage should be kept below 300 mA and 30V, respectively, to avoid damage to matrix windings and components.

Sense Windings

- a. Turn off memory power. Remove the Sense Amplifier PAC, CM-363A associated with the sense windings to be checked.
- b. Place the ohmmeter leads across the sense winding inputs (SWXX+ and SWXX-) to the Sense Amplifier PAC as determined from the logic diagrams of Section 4 and check for continuity. One sense winding links 4096 cores (Table 2-3-5).

Table 2-3-2 Operational Failures

Symptoms	Probable Fault		
No apparent response to commands	1. DC voltage		
	2. CC-373 PAC		
	3. MBSYX-, MEMCI+, RTDL- signals		
Unable to read from any address	1. CC-373 PAC		
	2. 15.5 volt supply		
	3. STROB- Signal		

Table 2-3-3
Partial Word Failures

Symptoms	Probable Fault
Failure of one bit (ZERO or ONE)	1. Sense Amplifier PAC (CM-363A)
at all addresses	2. Data register
	3. Inhibit PAC
	4. Sense winding
	5. Inhibit winding
	6. Resistor PAC
Failure of one bit at particular	l. Sense Amplifier PAC
addresses	2. X or Y-switch or sink PAC
	3. Sense winding
	4. X or Y-drive line
	5. X or Y-selection diode (F-08)
Failure of one bit at one address	1. Marginal Sense Amplifier PAC
	2. Marginal core

Table 2-3-4
Address, Decoding, and Selection Failures

Symptom	Probable Fault
All bits fail as a function of particular address bits	1. X or Y-switch or sink PAC
	2. CC-363A PAC
	3. X- or Y-drive line
	4. X- or Y-selection diode

c. Resistance readings should be approximately 28 ohms for all sense windings. The resistance readings for all bits should agree within $\pm 10\%$.

Drive Windings

- a. Turn off memory power. Remove the Selector PAC, CM-306 associated with the X- and Y-drive line to be checked. This can be determined from the logic diagrams by relating the bad address to a sink and switch output for both the X- and Y-coordinates. The drive winding connections to the core stack are shown in Figure 2-1-1.
- b. The actual drive line connections are located on the core stack printed circuit board. The selection switch outputs are isolated by a diode from each drive line so that the resistance reading between any dual bus (XDXX) and line bus (XBXX) will include a diode forward drop.
- c. Measure continuity by referring to the simplified selection diagram, Figure 2-2-5. For example, to check the continuity of drive line X60, put one ohmmeter probe on the corresponding sink output (collector output of transistor Q4) and the other ohmmeter probe on the proper switch output (collector of transistor Q2). A low resistance (one forward diode drop plus a drive line resistance of approximately 6 ohms) indicates continuity for both diodes and the drive line. It may be necessary to reverse the probes to obtain the correct polarity to forward-bias the selection diodes. The continuity of the current path for the opposite drive polarity should be similarly checked by moving the probe from the collector of Q2 to the emitter of Q1 and reversing the polarity. In this mode of measuring, two diodes will be in the circuit. A high resistance reading in both drive current polarity paths indicates an open drive winding or drive bus. If a drive bus is open, the other drive lines connected to the same bus will also have a high resistance reading. A high resistance reading in only one of the read or write current paths indicates an open F-08 flat pack diode.

Inhibit Windings

- a. Turn off memory power. Remove the Inhibit PAC CM-305 associated with the inhibit line to be checked.
- b. Place the ohmmeter leads across the inhibit winding inputs (ZWXX+ and ZWXX-) to the Inhibit PAC as determined from the logic diagram of Section V and Table 2-3-6.
- c. Resistance readings should be approximately 11 ohms for all inhibit windings. The resistance windings for all bits should agree within $\pm 10\%$.

Table 2-3-5 Sense Winding Check List

Sense Winding	Location	Sense Winding	Location
SW01+	A1BX0323	SW09+	AlBX0114
SW01-	A1BX0321	SW09-	A1BX0116
SW02+	A1BX0319	SW10+	A1BX0110
SW02-	A1BX0317	SW10-	A1BX0112
SW03+	A1BX0315	SWll+	A1BX0124
SW03-	A1BX0313	SW11-	A1BX0122
SW04+	A1BX0311	SW12+	A1BX0118
SW04-	A1BX0309	SW12-	A1BX0120
SW05+	A1BX0324	SW13+	A1BX0123
SW05-	A1BX0322	SW13-	A1BX0121
SW06+	A1BX0318	SW14+	A1BX0119
sw06-	A1BX0320	SW14-	A1BX0117
SW07+	A1BX0314	SW15+	A1BX0115
SW07-	A1BX0316	SW15-	A1BX0113
SW08+	A1BX0310	SW16+	A1BX0111
SW08-	A1BX0312	SW16-	A1BX0109

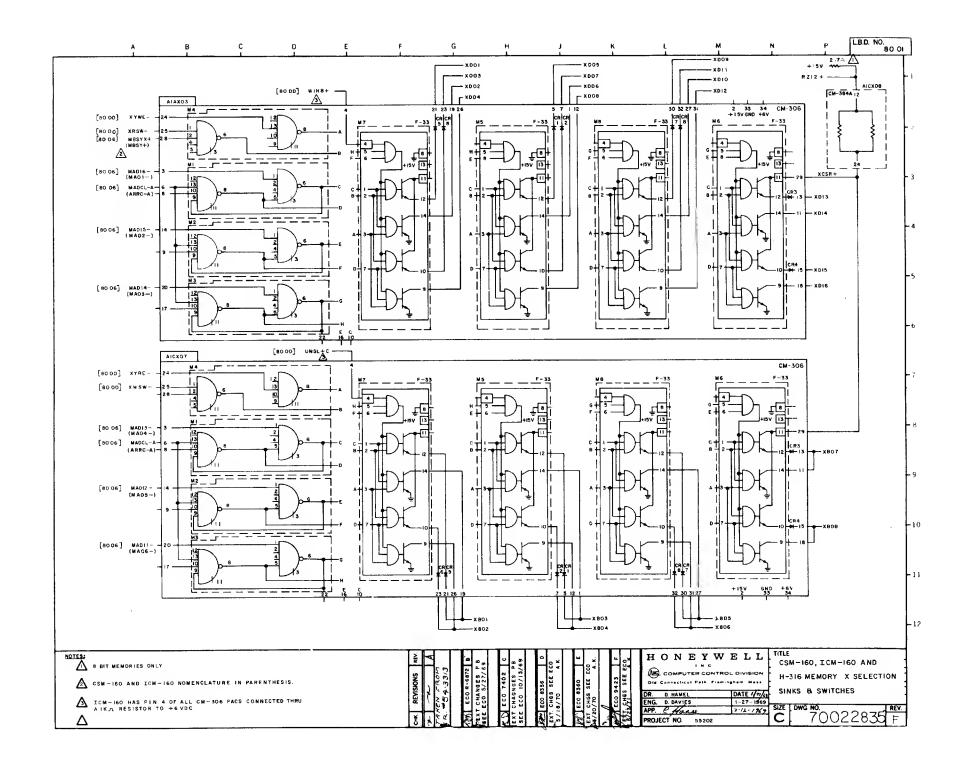
Table 2-3-6 Inhibit Winding Check List

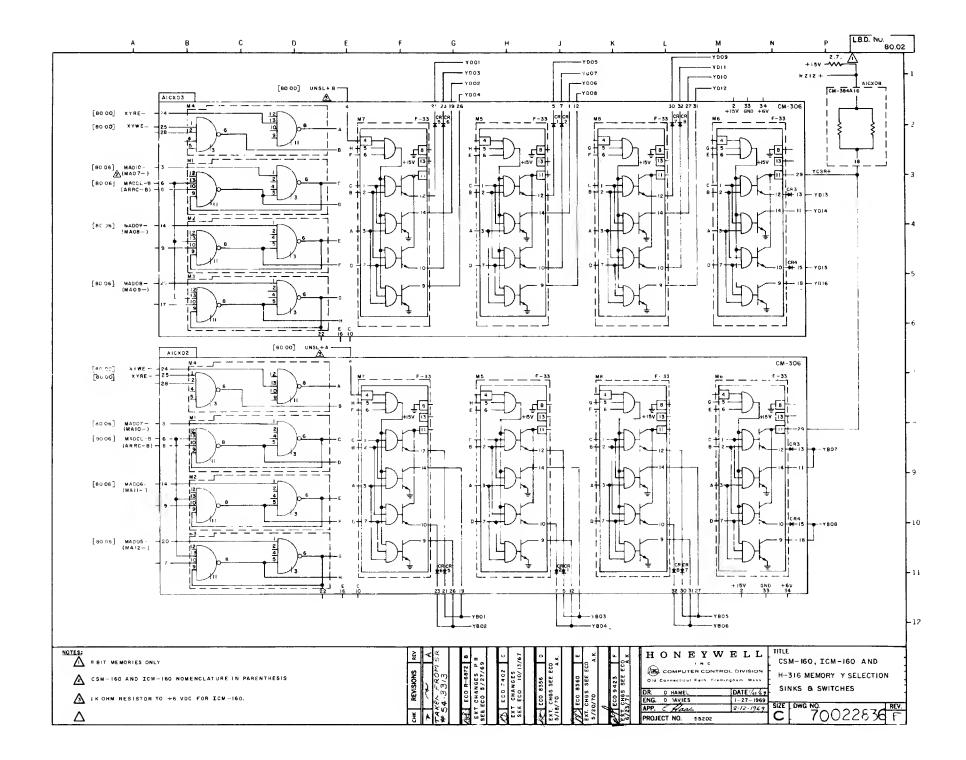
Sense Winding	Location	Sense Winding	Location
ZW01+	A1CX0603	ZW09+	A1CX0406
ZW01-	A1CX0601	ZW09-	A1C X0408
ZW02+	A1BX0632	ZW10+	A1AX0426
ZW02-	A1BX0631	ZW10-	A1AX0428
ZW03+	A1BX0601	ZW11+	A1CX0607
ZW03-	A1BX0602	ZW11-	A1CX0605
ZW04+	A1AX0631	ZW12+	A1AX0627
ZW04-	A1AX0629	ZW12-	A1AX0625
ZW05+	A1CX0402	Z W13+	A1BX04-30
ZW05-	A1C X0404	ZW13-	A1BX04-29
ZW06+	A1BX0432	ZW14+	A1BX04-03
ZW06-	A1BX0431	ZW14-	A1BX04-04
ZW07+	A1BX0401	Z W15+	A1BX06-30
Z W07-	A1BX0402	ZW15-	A1BX06-29
ZW08+	A1AX0430	ZW16+	A1BX06-03
ZW08-	A1AX0432	ZW16-	A1BX06-04

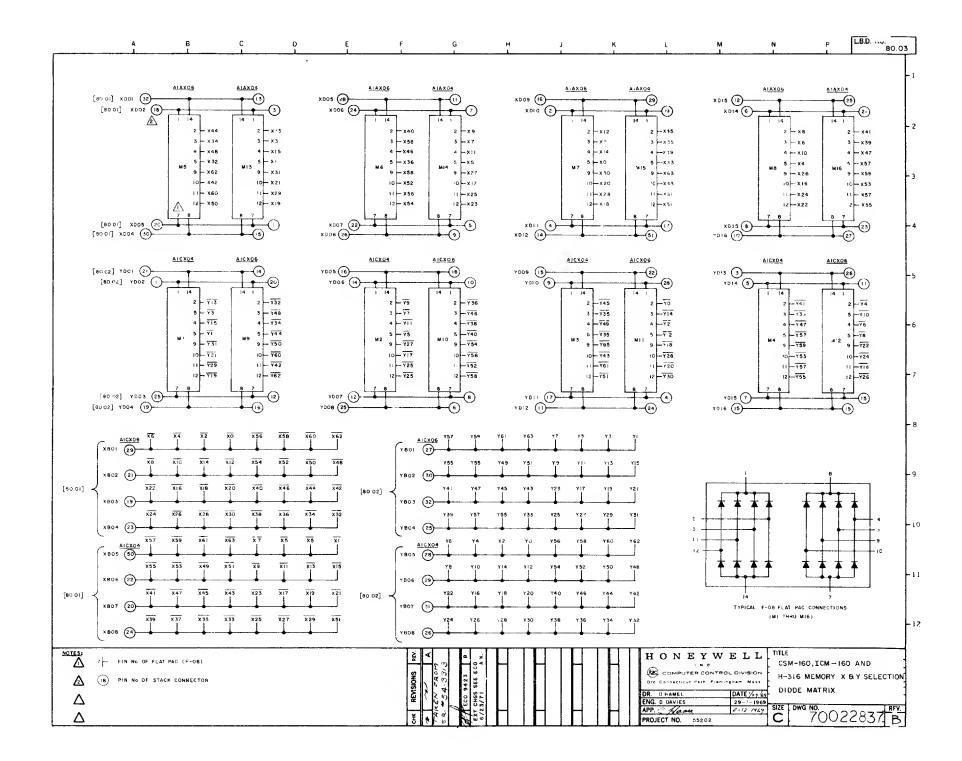
SECTION 4 LOGIC BLOCK DIAGRAMS

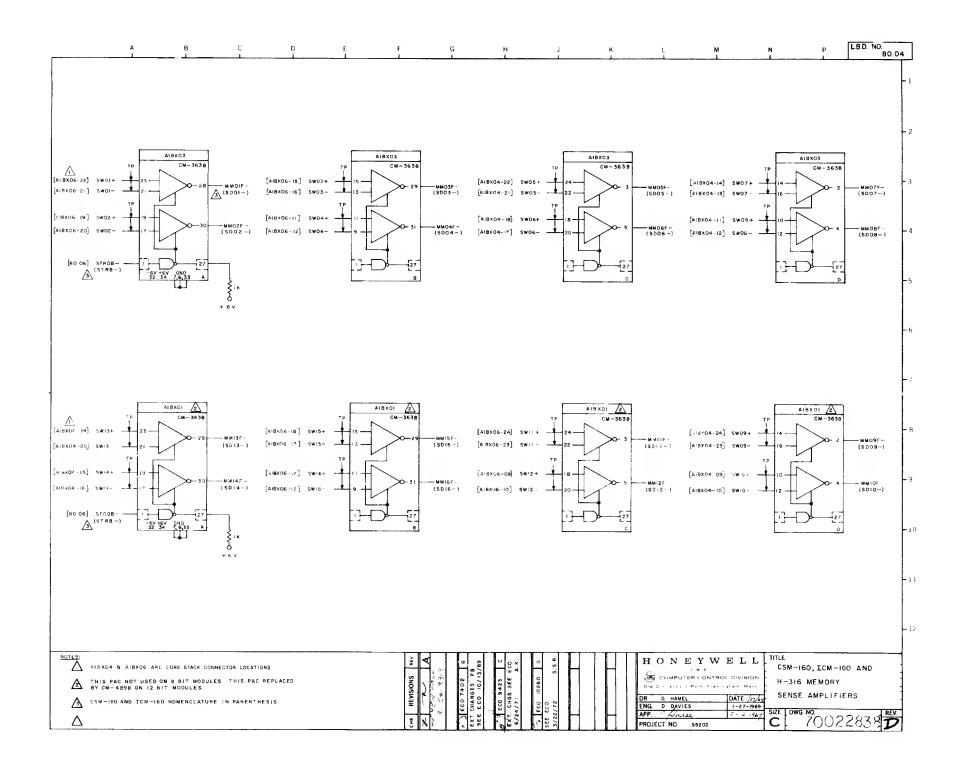
This section contains the following logic block diagrams. The logic block diagram (LBD) number is shown in the upper righthand corner of each drawing.

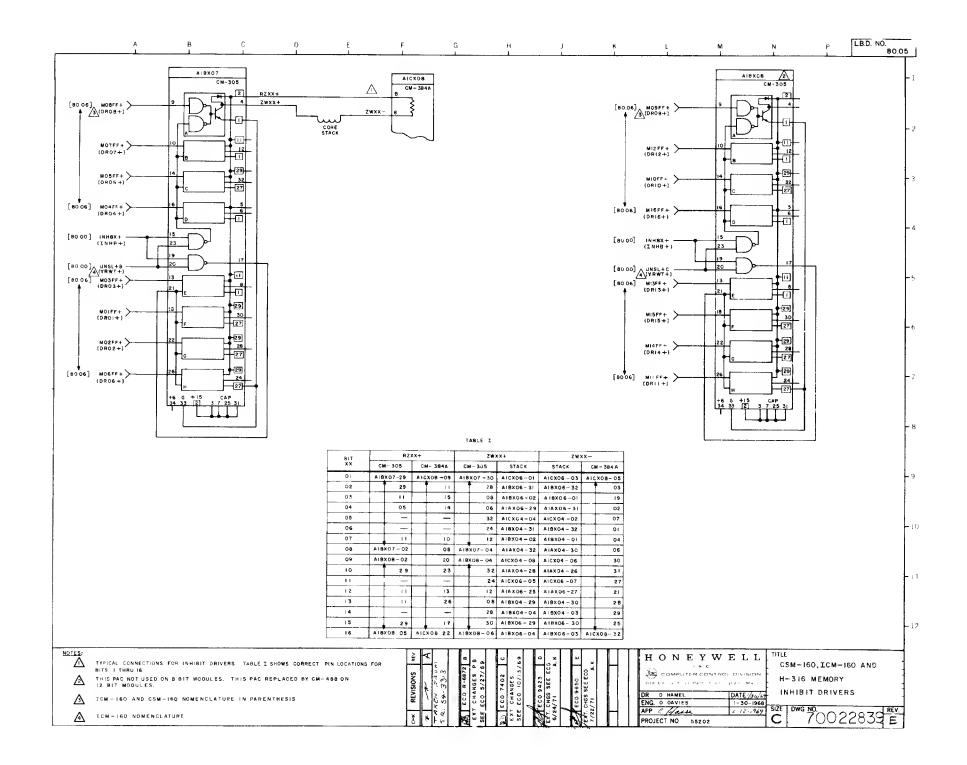
LBD No.	Dwg. No.	Description
80.00	C70022843	Timing and Control
80.01	C70022835	X-Selection Sinks and Switches
80.02	C70022836	Y-Selection Sinks and Switches
80.03	C70022837	X - and Y -Selection Diode Matrix
80.04	C70022838	Sense Amplifiers
80.05	C70022839	Inhibit Drivers
80.06	C70022840	1 x 3 Connector Wiring
80.08	C70022841	PAC Complement and Allocation
	P70022841	Parts List

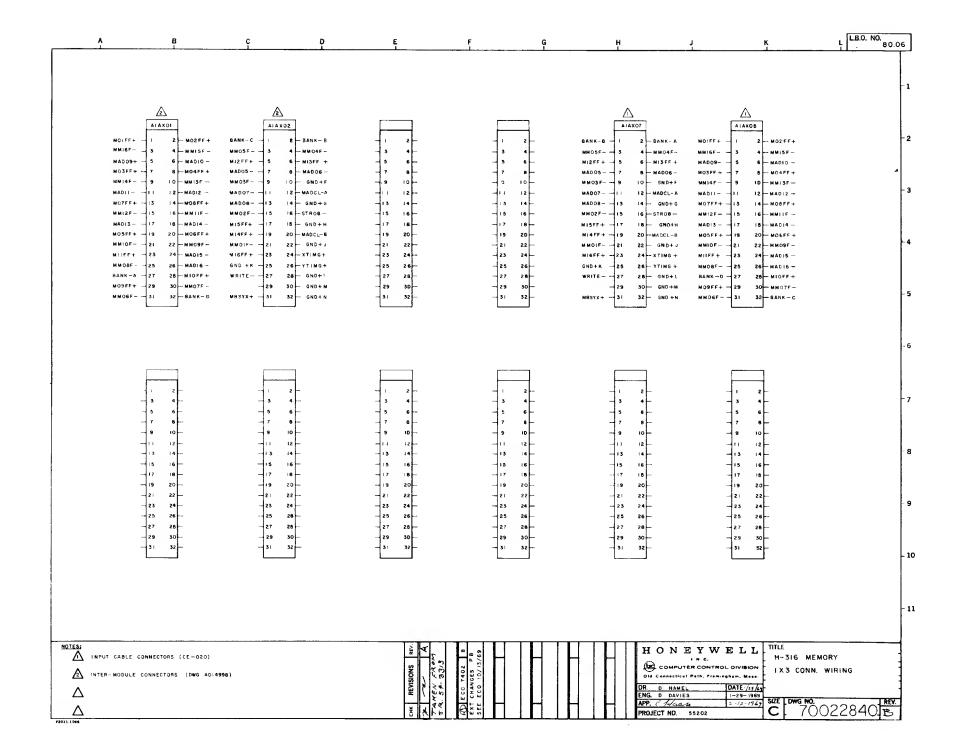


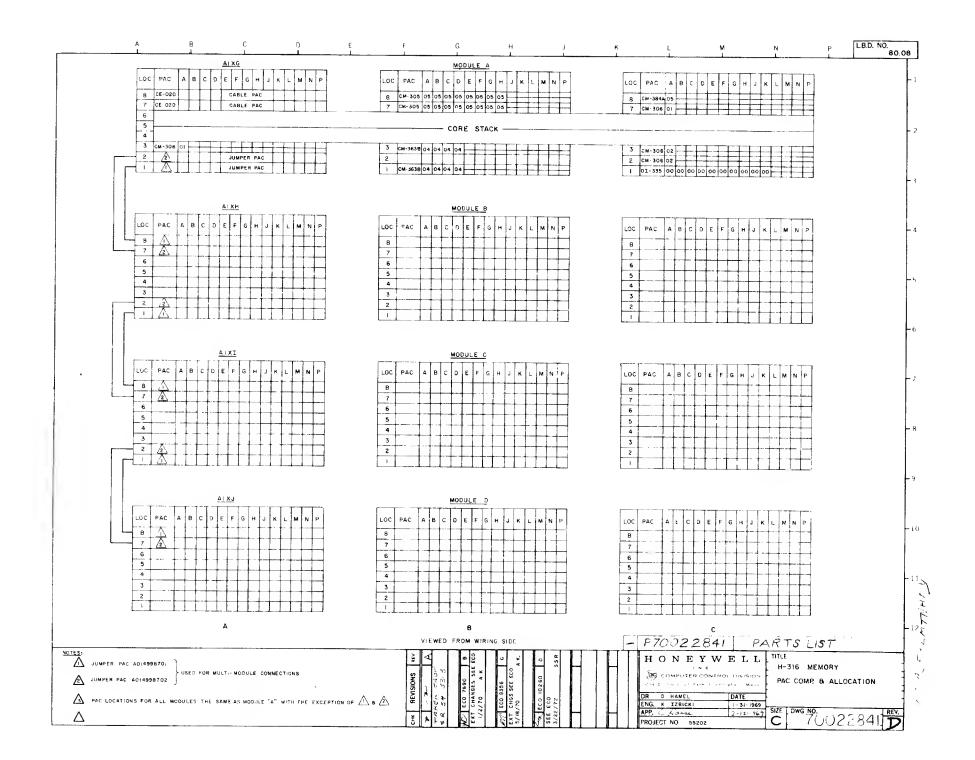












H316 Memory PAC Complement

Part Number Description		Quantity
70 006 707 701	NAND Type 1 PAC, Model DI-335	1
70 021 896 701	Selector µ-PAC, Model CM-306	4
70 022 970 702	Resistor µ-PAC, Model CM-384A	1
70 022 955 707	Sense Amplifier µ-PAC, Model CM-363B	2
70 021 402 701	Inhibit μ-PAC, Model CM-305	2
70 942 507 002	Core Memory Unit, Plugable	1

SECTION 5 MEMORY PAC DESCRIPTIONS

This section contains the following circuit descriptions and parts lists for the special $\mu\text{-PACs}$ used in the H316 Magnetic Core Memory Modules.

CM-305/CM-488 Inhibit PAC CM-306/CM-640 Selector PAC CM-363A/CM-489A/ Sense Amplifier PAC CM-734/CM-735 CM-363B/CM-489B/ Sense Amplifier PAC CM-734/CN-735 CM-384A Resistor PAC DI-335 NAND Type 1 PAC XP-330 Extender PAC

INHIBIT µ-PAC, MODELS CM-305/CM-488

The Inhibit μ -PAC, Model CM-305 (Figure 1 and 2), contains two groups of four 425 mA transistor switches and one NAND gate. Each switch is controlled by a data input and strobed by a common line within each circuit.

An output switch is turned on (active state) when the corresponding data input is at an active state, the timing input for circuits A, B, C and D is at a passive state, and the timing input for circuits E, F, G, and H is at an active state.

The emitters of the output transistors are brought out to external pins 1 and 27. Optional capacitors C1, C2, and C3 are provided for filtering the +15V supply. Clamp diodes at each collector are used with inductive loads.

The CM-488 contains one group of four transistor switches. Circuits D, E, F, and G of Figure 1 and 2 are omitted.

Specifications

Frequency of Operation

DC to 2 MHz

Input Loading

l unit load each (1.6 mA)

Output Characteristics

Current: 425 mA (max) Voltage: 17.5V (max) Power: 200 mW (max)

Current Requirements

+6V: 70 mA (max)

Circuit Delay (420 mA Resistive Load)

Turn-on Delay (1.5V of input 190 ns (max)

to 10% of current)

Turn-off Delay (1.5V of input 190 ns (max)

to 90% of current)

Power Dissipation

2.2W (max)

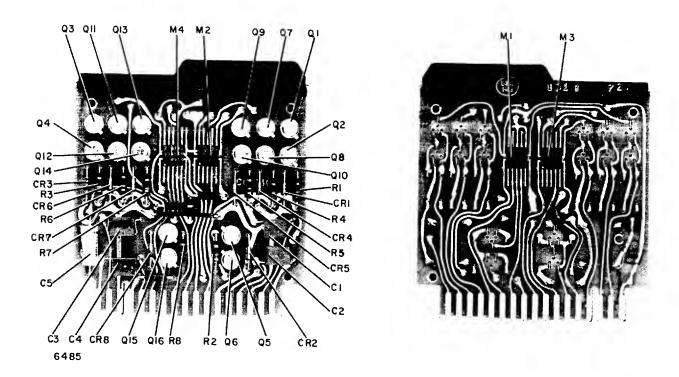


Figure 1. Inhibit $\mu\text{-PAC}$, Models CM-305/CM-488, Parts Location (Dwg B70021402, Rev. D)

Electrical Parts List (No. P70021402, Rev. E)

Ref. Desig.	Description	Part No.
C1-C4	CAPACITOR, FIXED, SOLID TANTALUM: 6.8 μF ±20%, 20 Vdc	70 930 235 211
C5	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 μF ±20%, 20 Vdc	70 930 313 016
CR1-CR8 CR1-CR3, CR8*	DIODE, SILICON	70 943 083 003
Ml	MICROCIRCUIT: Type 936, hex single-input inverter integrated circuit	70 950 105 004
M2-M4 M4*	MICROCRICUIT: Type 946, quad two-input NAND gate integrated circuit	70 950 105 002
Q1, Q3, Q5, Q7, Q7, Q9, Q11, Q13, Q15 Q1, Q3, Q5, Q15*	TRANSISTOR: Silicon NPN	70 943 722 002
Q2, Q4, Q6, Q8, Q10, Q12, Q14, Q16 Q2, Q4, Q6, Q16*	TRANSISTOR: Silicon NPN Type 778-2	70 943 778 002
R1-R8 R1-R3, R8*	RESISTOR, FIXED, COMPOSITION: 100 ohms ±5%, 1/4W	70 932 007 025

^{*}CM-488 only

Figure 2. Inhibit μ-PAC, Models CM-305/CM-488, Schematic Diagram and Logic Symbol (Dwg B70021402, Rev. D)

936 TYPE OF MICROCIRCUIT

SELECTOR µ-PAC, MODELS CM-306/CM-640

The Selector μ -PAC, Model CM-306 (Figures 1 and 2), contains three registers, as well as decoding and drive circuitry for half of an 8 x 8 selection matrix. The outputs can sink or switch inductive loads of up to 450 mA with voltages up to +17V.

The CM-640 is identical to the CM-306 except the address gates are connected as buffers rather than register stages.

Address Circuits

Three Type 961 power amplifier gates constitute the three register stages of the CM-306. Pin 6 is a common reset input to all three register stages. Pins 3, 14, and 20 are set inputs; pins 8, 9, and 17 are reset inputs; pins 10, 16, and 22 are set outputs. One type 961 gate serves as an address buffer. Five type 961 gates serve as address buffers for the CM-640.

Decoding and Drive Circuitry

Four F-33 flat packs decode the address circuit inputs and sink or switch up to 450 mA of current into inductive loads. Input pin 24 at logic ONE enables the switch outputs. Pins 25 and 28 are inputs to a NAND gate whose output, at logic ONE, activates the sink outputs. Only one output (sink or switch) of an F-33 can be activated during a given cycle.

The expansion input, pin 4, must be at logic ONE to enable the CM-306 μ -PAC.

Input and Output Signals

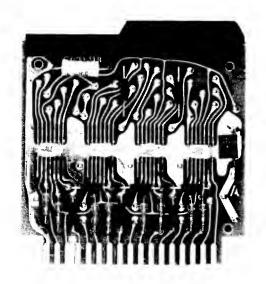
Table 1 lists logic levels on various pins and the resulting active outputs.

Table 1
Input/Output Logic Signals

Pin 20 (A3+)	Pin 14 (A2+)	Pin 3 (Al+)	Pin 24 (Timing Switch)	Pins 25 and 28 (Timing Sink)	Active Output Pin No.
0	0	0	0	1	11
0	0	0	1	0	13
0	0	1	0	ì	18
0	0	1	1	0	15
0	1	0	0	1	27
0	1	0	1	0	30
0	1	1	0	1	31
0	1	1	1	0	32
1	0	0	0	i i	1
1	0	0	1	0	5
1	0	1	0	1	12
1	0	1	1	0	7
1	1	0	0	1	19
1	1	0	1	0	21
1	1	1	0	1	26
1	1	1	1	0	23

Specifications

Input Loading		Circuit Delay (430 mA Re	esistive Load)	
	l unit load	Turn-on Delay (1.5V of timing input to 90% of	Sink 120 ns (max Switch 140 ns (max	
Reset Input	3 unit loads	current)	BWITCH 110 MB (Man-	-,
Expansion Input	6 unit loads	Turn-off Delay (1.5V of	Sink 200 ns (max	
Timing Inputs	l unit load	timing input to 10% of current)	Switch 120 ns (max	(۲
Output Characteristics		Current Requirements		
Current (sink or switch) 450 mA (max)		100 mA at 15V		
Voltage (sink or switch)) 17V (max)	45 mA at +6V		
Power (sink or switch)	560 mW (max)	Power Dissipation		
Collector-Emitter Saturation Voltage (sink or switch)	0.9V (max)	2.5W (max)		
Register Set Output	4 unit loads			



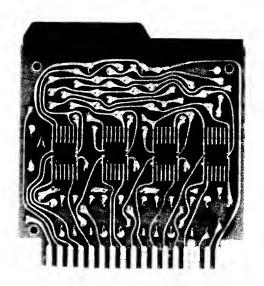


Figure 1. Selector $\mu\text{-PAC}$, Model CM-306/CM-640, Parts Location (Dwg B70021896, Rev. D)

Electrical Parts List (No. P70021896, Rev. D)

Ref. Desig.	Description	Part No.
C1	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 µF ±20%, 50 Vdc	70 930 313 016
C2	CAPACITOR, FIXED, SOLID TANTALUM: 6.8 µF ±20%, 20 Vdc	70 930 235 211
CR1-CR8	DIODE, SILICON	70 943 083 003
M1-M4	MICROCIRCUIT: Type 961, dual four-input NAND integrated circuit	70 950 105 009
M5-M8	MICROCIRCUIT: F-33, selection switch integrated circuit	70 950 100 033

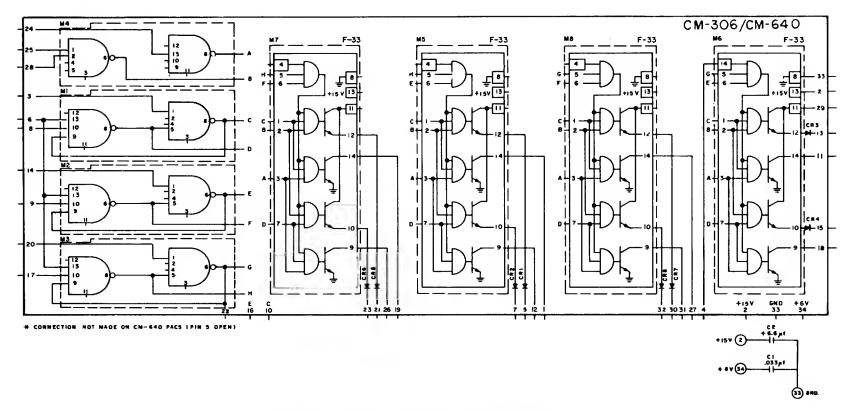


Figure 2. Selector μ-PAC, Model CM-306, Schematic Diagram and Logic Symbol (Dwg B70021896, Rev. D)

SENSE AMPLIFIER µ-PAC, MODELS CM-363A/CM-489A/CM-734/CM-735

The Sense Amplifier μ -PAC, Models CM-363A and CM-734, contains four dual-in-line integrated circuit sense amplifiers, each of which contains two complete amplifier circuits capable of detecting and amplifying core signals. Each circuit has its own strobe input, all inputs being driven by the same buffer amplifier. A resistor divider network determines the threshold voltage for the eight circuits. Each amplifier output is connected to an inverter gate. The μ -PAC also contains the sense line termination resistors for each circuit.

The CM-489A and CM-735 contain only two dual-in-line integrated circuit sense amplifiers. Circuits A and B are omitted.

Circuit Function

A differential signal which is greater than the threshold voltage will produce a positive sense amplifier output if the strobe circuit is enabled. A negative strobe signal applied to the strobe buffer amplifier will enable the strobe gate and a positive signal will disable it. The sense amplifier output will be inverted, making a negative signal available to perform a logical OR function.

Specifications

Strobe Input

Input loading: 1.6 mA

DC Threshold

14 mV to 28 mV

Current Requirements

+6V: 332 mA (max) -6V: 110 mA (max)

Output

2.7W (max)

Power Dissipation

Delay from strobe input to PAC output

Leading edge: 155 ns (max) Trailing edge: 155 ns (max)

Pulse width with 100 ns sense input pulse width: 80 ns (min) Drive capability: 12.8 mA

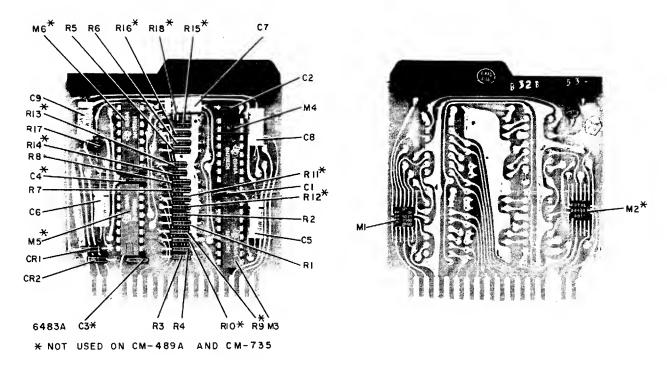


Figure 1. Sense Amplifier μ-PAC, Models CM-363A/CM-489A, CM-734/CM-735, Parts Locations (Dwg No. A70022955, Rev. E)

Electrical Parts List

Ref. Desig.	Description	Part No.
C1-C4	CAPACITOR, FIXED, MICA DIELECTRIC: 120 pF ±10%, 100 Vdc	70 930 016 030
C5-C9	CAPACITOR, FIXED, PLASTIC DIELECTRIC: $0.033\mu F$ $\pm 20\%$, 50 Vdc	70 930 313 021
CR1, CR2	DIODE, SILICON	70 943 083 002
Ml	MICROCIRCUIT: Type 936, hex inverter integrated circuit	70 950 105 004
M2	MICROCIRCUIT: Type 946, quad two-input NAND gate integrated circuit	70 950 105 002
M3-M6 ¹ M3, M4 ²	MICROCIRCUIT: Dual sense amplifier integrated circuit (See note 5)	70 950 100 XXX
M3-M6 ³ M3, M4	MICROCIRCUIT: Dual sense amplifier integrated circuit	70 950 100 042
R1-R16	RESISTOR, FIXED, FILM: 150 ohms ±2%, 1/4W	70 932 114 029
R17	RESISTOR, FIXED, FILM: 270 ohms ±2%, 1/4W	70 932 114 035
R18	RESISTOR, FIXED, FILM: 1 ohm ±2%, 1/4W	70 932 114 145
	lCM-363/CM-363A 2CM-489/CM-489A 3CM-734 4CM-735 Part No. 70 950 100 034 (plastic) may be used interchangeably with 70 950 100 042 (ceramic)	

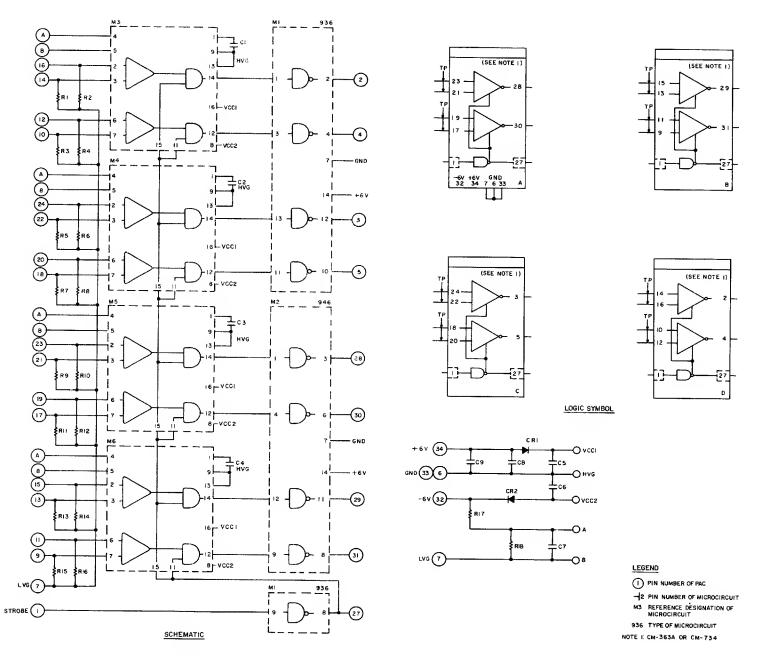


Figure 2. Sense Amplifier μ -PAC, Models CM-363A/CM-734, Schematic Diagram and Logic Symbol (Dwg A70022955, Rev. E)

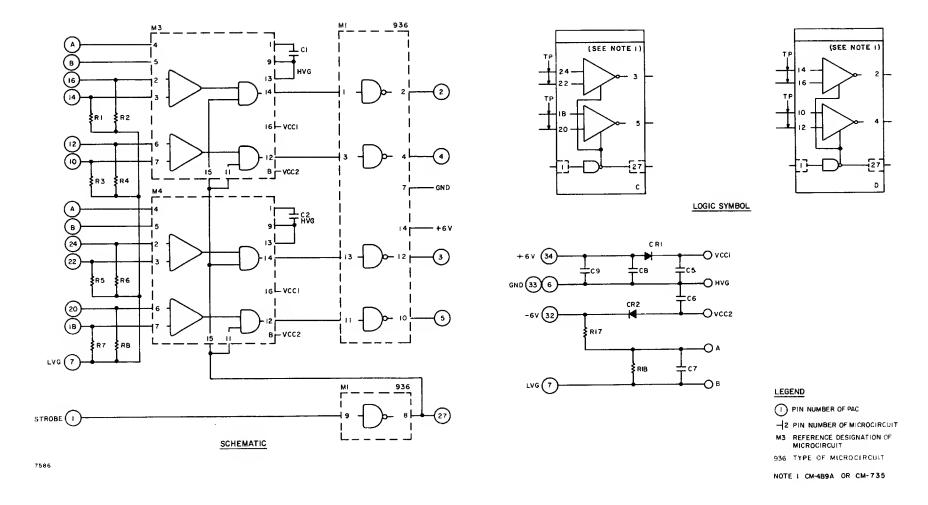


Figure 3. Sense Amplifier μ -PAC, Models CM-489A/CM-735, Schematic Diagram and Logic Symbol (Dwg A70022955, Rev E)

SENSE AMPLIFIER µ-PAC, MODELS CM-363B/489B/734/735

The Sense Amplifier μ -PAC, Models CM-363B and CM-734, contains four dual-in-line integrated circuit sense amplifiers, each of which contains two complete amplifier circuits capable of detecting and amplifying core signals. Each circuit has its own strobe input, all inputs being driven by the same buffer amplifier. A resistor divider network determines the threshold voltage for the eight circuits. Each amplifier output is connected to an inverter gate. The μ -PAC also contains the sense line termination resistors for each circuit.

The CM-489B and CM-735 contain only two dual-in-line integrated circuit sense amplifiers. Circuits A and B are omitted.

Circuit Function

A differential signal which is greater than the threshold voltage will produce a positive sense amplifier output if the strobe circuit is enabled. A negative strobe signal applied to the strobe buffer amplifier will enable the strobe gate and a positive signal will disable it. The sense amplifier output will be inverted, making a negative signal available to perform a logical OR function.

Specifications

Strobe Input

Input loading: 1.6 mA

DC Threshold

14 mV to 28 mV

Current Requirements

+6V: 332 mA (max)

-6V: 110 mA (max) Power Dissipation

2.7W (max)

Output

Delay from strobe input to PAC output

Leading edge: 155 ns (max) Trailing edge: 155 ns (max)

Pulse width with 100 ns sense input pulse width: 80 ns (min) Drive capability: 12.8 mA

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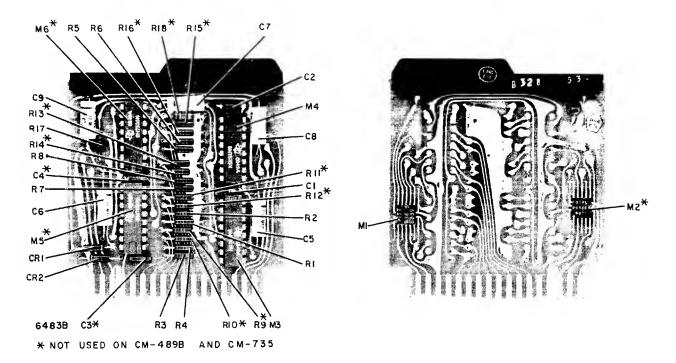


Figure 1. Sense Amplifier μ -PAC, Models CM-363B/489B/734/735, Parts Locations (Dwg No. A70022955, Rev. F)

Electrical Parts List

Ref. Desig.	Description	Part No.
C1-C4	CAPACITOR, FIXED, MICA DIELECTRIC: 120 pF ±10%, 100 Vdc	70 930 016 030
C5-C9	CAPACITOR, FIXED, PLASTIC DIELECTRIC: $0.033\mu\text{F}$ $\pm 20\%$, 50 Vdc	70 930 313 021
CR1, CR2	DIODE, SILICON	70 943 083 002
Ml	MICROCIRCUIT: Type 936, hex inverter integrated circuit	70 950 105 004
M2	MICROCIRCUIT: Type 946, quad two-input NAND gate integrated circuit	70 950 105 002
M3-M6 ¹ M3, M4	MICROCIRCUIT: Dual sense amplifier integrated circuit (See note 5)	70 950 100 XXX
M3-M6 ³ M3, M4	MICROCIRCUIT: Dual sense amplifier integrated circuit	70 950 100 042
R1-R16	RESISTOR, FIXED, FILM: 150 ohms ±2%, 1/4W	70 932 114 029
R17	RESISTOR, FIXED, FILM: 270 ohms ±2%, 1/4W	70 932 114 035
R18	RESISTOR, FIXED, FILM: 1 ohm ±2%, 1/4W	70 932 114 145
	¹ CM-363B ² CM-489B ³ CM-734 ⁴ CM-735 ⁵ Part No. 70 950 100 034 (plastic) may be used interchangeably with 70 950 100 042 (ceramic)	

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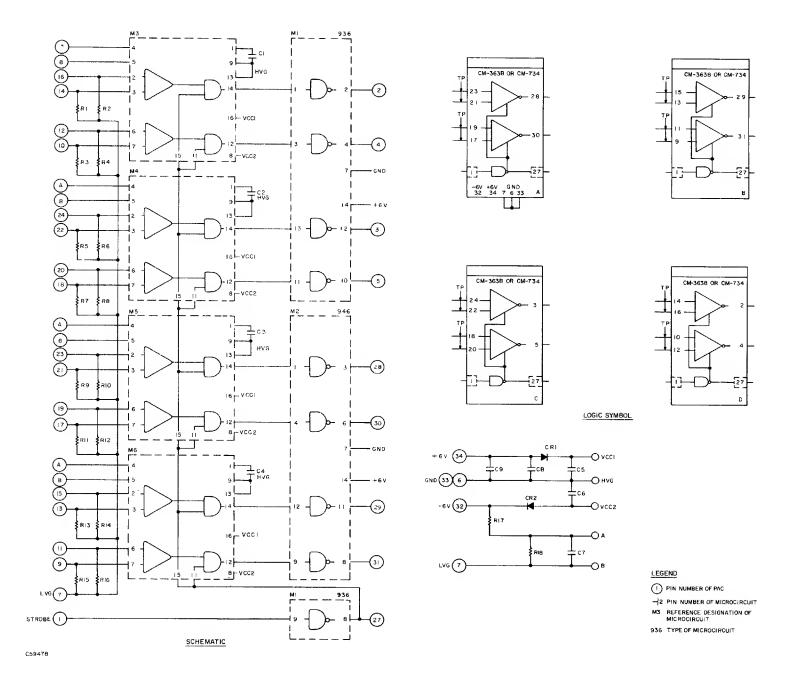


Figure 2. Sense Amplifier μ -PAC, Models CM-363B/734, Schematic Diagram and Logic Symbol (Dwg No. A70022955, Rev. F)

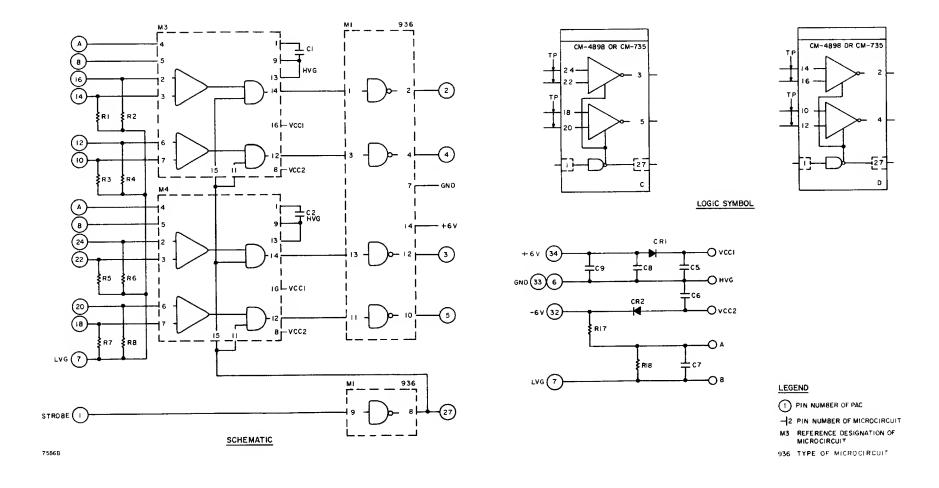


Figure 3. Sense Amplifier $\mu\text{-PAC}$, Models CM-489B/735, Schematic Diagram and Logic Symbol (Dwg No. A70022955, Rev. F)

RESISTOR μ -PAC, MODEL CM-384A

The Resistor μ -PAC, Model CM-384A (Figures 1 and 2), contains 20 3W wirewound resistors. Sixteen of these (R1 through R16) are used as current limiting resistors for the inhibit drive lines. The four noninductive resistors form two groups of parallel pairs used as current-limiting resistors for the X- and Y- drive lines.

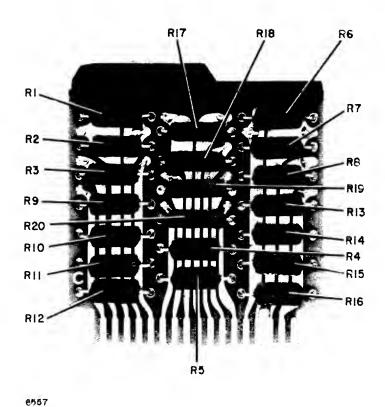
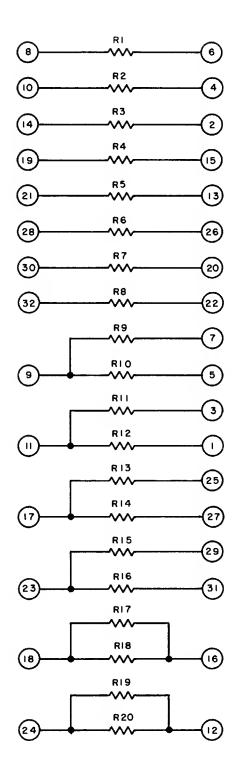


Figure 1. Resistor µ-PAC, Model CM-384A, Parts Locations (A70022970, Rev D)

Electrical Parts List (No. P70022970, Rev D)

Ref. Desig.	Description	Part No.
R1-R16 R17 R18-R20	RESISTOR, FIXED, WIREWOUND: 30 ohms ±1%, 3W RESISTOR, FIXED, WIREWOUND: 60 ohms ±1%, 3W RESISTOR, FIXED, WIREWOUND: 50 ohms ±1%, 3W	70 932 206 409 70 932 223 123 70 932 223 122



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Figure 2. Resistor µ-PAC, Model CM-384A, Schematic Diagram

NAND TYPE 1 PAC, MODEL DI-335

The NAND Type 1 PAC, Model DI-335 (Figures DI-335-1 and DI-335-2), contains 10 independent 2-input NAND gates. Each gate performs the NAND function for positive logic (+6V = ONE, 0V = ZERO). For negative logic, it becomes a NOR gate.

Two of the 10 gates have separate load connections available at the PAC terminals. Outputs of these gates can be tied together, using a single load resistor, without loss of output drive capability. A detailed description of the basic NAND circuit appears in Section 1.

INPUT AND OUTPUT SIGNALS

Inputs

When both inputs to a gate are +6V or not connected, the output is at ground. When any input is at ground, the output is +6V.

Load

This point is internally connected through a collector load resistor to +6V.

Collector Output

The collector output must be connected to at least one load resistor, either internal or external to the module.

Output

Each output terminal is internally connected to a collector load resistor. If an output is connected to load points or other outputs, the output drive capability of the structure is reduced.

SPECIFICATIONS

Frequency of Operation (System) Circuit Delay

DC to 5 MHz (Measured at +1.5V, averaged over two

0.67W (max)

Input Loading stages)
30 ns (max)

l unit load each Current Requirements

<u>Fan-In</u> +6V: 112 mA (max)

Refer to Section 1 Power Dissipation

Output Drive Capability

8 unit loads each

Outputs in Parallel

Red Refer to Section 1

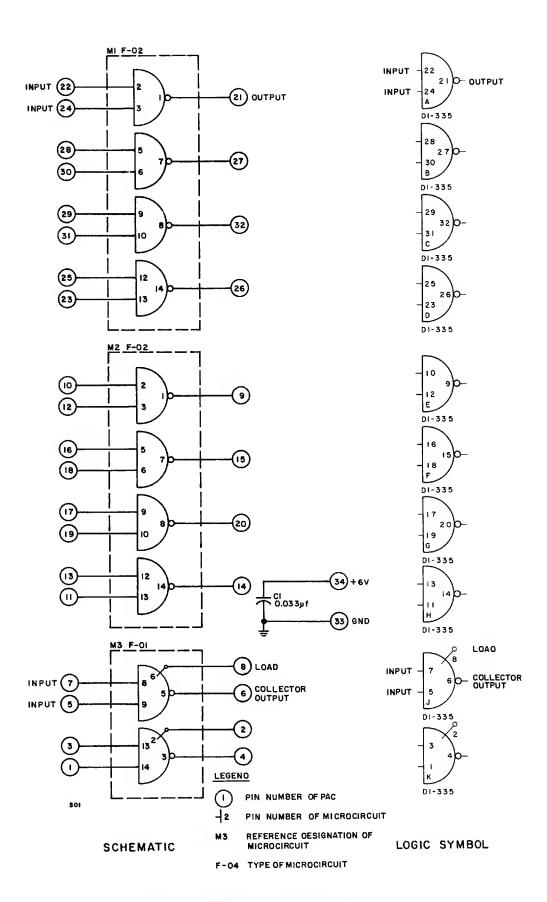
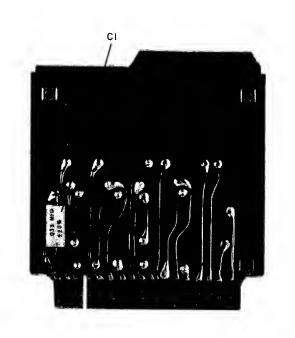
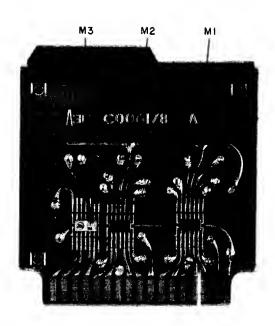


Figure DI-335-1. NAND Type 1 PAC, Schematic Diagram and Logic Symbol





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Figure DI-335-2. NAND Type 1 PAC, Parts Locations

Electrical Parts List

Ref. De s ig.	Description	3C Part No.
M1, M2	MICROCIRCUIT: F-02, quad NAND gate integrated circuit	950 100 002
М3	MICROCIRCUIT: F-01, dual NAND gate integrated circuit	950 100 001
Cl	CAPACITOR, FIXED, PLASTIC DIELECTRIC: 0.033 µF ±20%, 50 Vdc	930 313 016

APPLICATIONS

The NAND gates operate on levels, pulses, or combinations of both. Two gates can be wired back-to-back to form a dc set-reset flip-flop.

The two gates with separate load outputs form standard NAND gates when the load and collector output terminals are connected. When the collector outputs of gates are connected in parallel as in Figure DI-335-3, the AND-OR-INVERT function is performed. At the point where the outputs are tied together, an AND operation with logic ONEs (OR operation with logic ZEROs) takes place.

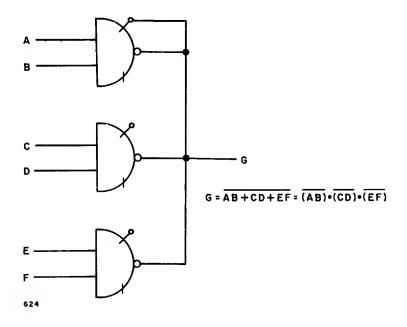


Figure DI-335-3. NAND Type I PAC, Gates Used in Parallel

EXTENDER PAC, MODEL XP-330

The Extender PAC, Model XP-330 (Figure XP-330-1), provides unobstructed access to any μ -PAC while it is electrically mounted in its appropriate μ -BLOC connector. The connector terminals at the front end of the XP-330 mount into any μ -BLOC connector and the connector at the rear accepts the μ -PAC it is displacing. Front and rear terminals are directly tied together electrically.

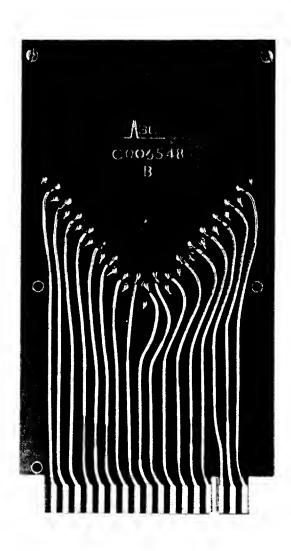


Figure XP-330-1. Extender PAC

CHAPTER III CSM-150 CORE MEMORY MODULE

SECTION 1 INTRODUCTION

GENERAL DESCRIPTION

The 8192-word CSM-150 Core Memory Module, used for the Type 316 processor main memory, has a word length of 17 bits. The 17th bit is not used if the mainframe does not have the parity option. The nominal memory cycle time is 1600 ns. The module occupies one 1-by-3 location in the processor drawer and can be paralleled with up to three modules on a single memory bus. A 4096-word, 17-bit memory module is also available for mainframes requiring only 4096 words of memory. Expansion above 4096 or 8192 words is allowable in 8192-word increments only.

Physical Description

The core memory module is packaged on a backplane with 7 rows of 3-connector-high assemblies. The connectors are mounted on 0.375-inch centers. Each connector is 2.3 inches long and has a double row of 34 solderless-wrap pins. The backplane assembly, when mounted in the H316 drawer, takes the same area as the CSM-160 Core Memory Module but requires extra height, which is available in the drawer. The printed circuit board used in the design is the MACRO-PAC with three connector tongues. The MACRO-PAC measures 8.45 by 4.5 inches. The core plane unit is a two-board folded design that plugs into two rows of six connectors. The X and Y drive electronics is packaged on one printed circuit board, and the sense-digit electronics is packaged on two printed circuit boards, thus requiring three rows of connectors for circuit boards. The I/O and module-to-module interconnections are accomplished by using cable PACs that plug into two connectors in each outside row of the backplane assembly.

Electrical Design

The CSM-150 Core Memory Module is built around a magnetic core array wired in a 3D, 3-wire organization, where each core is threaded by three wires; two of these wires are used for addressing a word, and the third is used for both reading and writing data in the bits of a word. Integrated circuits are used for addressing and read sensing, and a transformer-coupled discrete transistor driver is used for writing. The remaining circuits

are of the common or high-speed TTL type, with open-collector drivers on all outputs. The required memory voltages are +6, -6, and +15 Vdc, with the last one requiring temperature compensation for operation over the specified temperature range. The data outputs from the module are the outputs of open collector hex buffers.

SPECIFICATIONS

General

Organization 3-wire, 3-D coincident current

Capacity 4096 or 8192 words, expandable in 8192-word

increments only

Word Size 17 bits

Addressing Random access

Modes of Operation Clear-Write

Read-Write

Cycle Time 1600 ns (maximum rate at which memory may

be cycled for all modes)

Access Time 350 ns max from MXYTM+ input

Physical (Nominal)

Width 2-3/4 in. (7.00 cm)

Length 9-7/16 in. (24.00 cm)

Thickness 5-3/4 in. (14.60 cm)

Weight 2.3 lb (1.05 kgm)

Environment

Operating Temperature 0 to +60°C

Storage Temperature -55 to +85°C

Relative Humidity 95% without condensation

Cooling 220 linear ft per min.

Altitude 15,000 ft max.

Magnetic Fields 3.0 gauss max. magnetic field strength at

the core plane

Power

Current requirements are listed in Table 3-1-1. The +6 Vdc and -6 Vdc inputs must be held within ± 5 percent at the backplane of the core memory module. The +15 Vdc must be within the range shown in Table 3-1-2 at the backplane pins. Current drain on the

+15 Vdc supply and power dissipation in the core memory module are strongly dependent on the number of data zeros being written into the memory.

Table 3-1-1. Current Requirements

Voltage,	Current, Amperes	
Vdc	Active	Standby
+6	1.27	1.01
-6	0.25	0.25
+15	3.50	0.32

Table 3-1-2.
Operating Limits of TemperatureCompensated 15 VDC Supply

Temperature,	Limit, <u>Vdc</u>
0	15.6 ± 0.6
25	15.0 ± 0.8
60	14.0 ± 0.6

Interface

Input, Standard	One standard TTL load -2.0 mA max. at +0.4V +50 µA max. at +2.4V +1.0 mA max. at +5.5V Input uncertainty range, +0.8 to +2.0V
Input, Exceptions MXYTM+ WRITE-, MADCL-A, Address and Bank Select	Three standard loads Two standard loads
Output, Standard	One open-collector drive +0.4V max. at +20 mA +250 µA max. at +5.5V All outputs are 7407 except EPARB+ (74H04) and PAMEO- (7405)

Data Retention

Data stored in the memory will not be altered during power on/off sequencing if the following conditions are met.

- a. Sequencing Up -- No commands to the memory module should be initiated until all the supply voltages have attained their nominal values (within the limits of the specified tolerances). The +6 and -6 voltages should attain 90 percent of their nominal values prior to sequencing up the +15V supply.
- b. Sequencing Down -- Memory cycle should not be in progress (all commands to the memory are halted) prior to or during the power down sequencing. The +15V should reach +3V prior to sequencing down the -6V and +6V supplies.

Parity

All core memory modules contain storage for the parity (17th) bit, the data register, and the parity generation electronics. These circuits are not used if the CPU does not have the parity option.

SECTION 2 OPERATING PROCEDURES

OPERATING MODES

The core memory, when commanded by the processor, performs read or write cycles at 1600 ns or slower. The address, mode, and exact timing of these cycles are controlled by the processor. All operating modes, each requiring one memory cycle, are listed in Table 3-2-1.

Table 3-2-1. Operating Modes

Mode	Description	
Read-Write	One word read from storage onto memory data output bus. Storage location cleared by fetch but written into storage from data input bus.	
Clear-Write	One word in storage cleared and written with new data from memory data input bus.	

ADJUSTMENTS AND LIMITATIONS

Adjustments

No operating adjustments are required for the core memory module. The power supply voltages and strobe calibration should be checked, as specified in Section 6.

Limitations

Cooling. -- Systems containing core memory must not be operated unless the cooling system is functioning properly. Fan failures longer than 30 seconds cause overheating and may damage components. Blockage of cooling by cables or dust must be avoided to ensure cool air at a uniform temperature (± 5 °C) to all core memory modules operated from a single temperature-compensated power supply.

<u>Looping.</u> -- Higher memory reliability and lower power drain are achieved if a single cycle loop is avoided. Preferred loops occupy two or three cycles and contain mostly ONEs in instruction and operand words.

SIGNALS

The following signal descriptions assume the reader has some familiarity with the organization and operation of the core memory module. Persons unfamiliar with the module should read Section 3, Functional Theory of Operation.

Address Interface Signals

Address Inputs (MADD04+ through MADD16+). -- Input signals to the address registers are single ended and are stored in registers under the control of MADCL-A.

Bank Select Input (BANKX-). -- The memory bank-select input, a single-ended signal, is stored in a register under the control of MADCL-A. A ground level on BANKX- signifies module selection. BANKA-, BANKB-, BANKC- and BANKD- control memory modules A, B, C and D, respectively.

Data Interface Signals

Data Inputs (M01FF+ through M16FF+). -- Data inputs to the inhibit drivers are single ended and buffered through a 74H04. A high data input during the write cycle results in no inhibit current, and a ONE will be stored in the memory.

Data Outputs (MM01F- through MM16F-). -- Data outputs are single ended and supplied in open collector 7407 gates for wire-OR'ing with other modules. A negative data output pulse signifies a ONE output from the memory.

Timing and Control Interface Signals

Memory Read/Write Timing (MXYTM+). -- MXYTM+ is a single rail, positive-going double pulse that starts the read and write cycle timing in the core memory module.

Memory Strobe Enable (MSTEN-). -- MSTEN- is a single rail input to the core memory module that, when low, enables the memory sense strobe generation circuit.

Memory Address Register Clear Command (MADCL-A). -- Address register clear command is a single rail negative pulse whose trailing edge latches the address and bank register flip-flops. It is also used as parity data register clear pulse.

Write Enable (WRITE-). -- Write enable, a single rail negative pulse, gates the MXYTM+ command to generate the write timing for the core memory module.

Parity Bit Data Output (PAMEO-). -- The sense data output of the parity bit is stored in the parity data register, and the buffered output of the register (PAMEO-) is transmitted to the processor for parity error checking.

<u>Parity Generator Output (PAGEO-).</u> -- This is the output of the parity tree transmitted on a single rail to the processor.

Parity Error Strobe (EPARB+). -- This is a parity strobe pulse generated in the core memory module and transmitted single rail to the processor for parity error strobing.

SECTION 3 FUNCTIONAL THEORY OF OPERATION

BASIC OPERATION

The core memory module consists of an array of 139, 264 ferrite cores including those for the parity bits, surrounded by interface and control electronics. The core plane serves as a storage device due to the magnetic properties of the ferrite cores. Each ferrite core has two possible stable magnetic states, arbitrarily called ONE and ZERO. The act of writing a ONE consists of altering or switching a ferrite core from its ZERO state. To write a ZERO, the ferrite core is prevented or inhibited from altering its state. To read a ONE, the ferrite core is switched from its ONE to its ZERO state. The change of flux thus produced develops a voltage that is detected by the sense amplifier connected to the sense-inhibit line. To read a ZERO, the core remains in its ZERO state; therefore, no change of flux is detected. The purpose of the electronics surrounding the core array is to detect a particular word-set of cores in the array and either clear them and write in new data, or sense them and then, since the word has been set to ZERO in order to sense it, save and rewrite the sensed data back into the word. The time taken by either of these two operations, clear-write or read-regenerate, is one memory cycle.

FUNCTIONAL ELEMENTS

LBD 8114, Drawing No. 70032889, in Section 9 best illustrates the CSM-150 Core Memory Module. For additional details of each functional element and circuit, see Section 4, Detailed Theory of Operation, and the logic block diagrams in Section 9.

Storage Array

The storage array, which is the core plane, consists of 139,264 ferrite cores, including the parity bit, wired into an array to permit access of one of 8192 words (17 bits per word) per memory cycle. Addressing the array requires selecting one of the 128 X-lines and one of the 64 Y-lines and pulsing these lines with two address selection currents (nominally 400 mA in amplitude and 300 ns wide) twice per cycle. The core plane is also threaded with 17 sense-inhibit lines, each passing through one ferrite core at each of the 8192 different X- and Y-line intersections. In every cycle each sense-inhibit line requires a nominal 750 mA, 350 ns wide inhibit current, if, in that bit, a ZERO is to be written. A data output from the array on the sense-inhibit winding is a differentially sensed voltage, approximately 38 mV for a ONE and less than 12 mV for a ZERO. Included on the core plane are 8-by-8 and 8-by-16 bipolar diode matrices which, coupled with the inherent 64-by-128 decoding in the array, simplify the addressing of 8192 separate words. These diodes are packaged in a 14-pin dual in-line package with 16 diodes per package. In the

two-diodes-per-line selection scheme used in this design, 16 DIPs (256 diodes) for the X-line selection (128 lines) and 8 DIPs (128 diodes) for the Y-line selection (64 lines) are required, thus making a total of 24 diode DIPs to complete the X-line and Y-line selection for the 8192-word core plane.

Selection Interface Circuits

Address selection currents are driven through the storage array from selection interface circuits, via the X- and Y-diode matrices. The address bits (13 for an 8192-word memory and 12 for a 4096-word memory) and Bank-Select signal supplied to the memory are latched in registers within the core memory module. These registers are set up before a memory cycle and remain stable for the duration of that cycle. The MA04 address register output is disabled for 4096-word memories, as shown in LBD 8101, Drawing No. C70032890, in Section 9. Selection circuits decode the address bits to select and drive a unique word in the memory. All currents are disabled if the core memory module is not selected by the BANKX- signal.

Write or Regenerate Interface Circuits

The core memory module contains 17 write circuits, one per bit in the data word. The information present on the data input bus lines is used to write data into the memory. During the second, or write, portion of a memory cycle, a write-inhibit current will be supplied to the core array if that data bit is to be stored as a ZERO. No inhibit current occurs if a ONE is to be written. Write circuits are required to write data in a word being read (Read-Write cycle) as well as to alter the stored data (Clear-Write cycle).

Read Interface Circuits

The core memory module contains 17 read circuits, one per bit in the data word. During the first, or read, portion of a memory cycle, the sense amplifiers, at strobe time, discriminate between the core ONE and ZERO signals on the sense-inhibit lines. If a ONE is detected, the Memory Data output bus is pulled to ground for the time shown in Section 9, LBD 8110, Drawing No. C70032895. If a ONE is not detected in a bit, no action occurs, and the data output bus remains high.

Timing and Control Circuits

Input signals MXYTM+ and WRITE- control the majority of timing in the core memory module. These signals are gated and buffered to control the inhibit-current pulse widths and delayed to provide the proper read- and write-drive current timings.

The sense amplifier strobe pulse is generated by a one-shot during the read portion of a read-write cycle. The MSTEN- input gates the sense amplifier strobe during a read-write cycle.

Parity Logic

Electronics to generate odd parity during every memory cycle are included in every core memory module. Also included is a parity data register to store the parity bit data output from the read portion of a read-write cycle for use later in the cycle for parity error check and parity rewrite.

The output of the parity generator is buffered through two separate buffers to drive two individual memory interface lines, PAGEO- and PAMEO-. The signal PAGEO- indicates to the processor the output state of the parity generator for comparison with PAMEO-.

The buffered outputs of the parity register and parity generator output (gated with LPREG+) are collector-OR'ed to drive the memory interface line PAMEO- and also tied internally to the memory write interface circuits to close the parity regeneration loop.

The use of parity by the processor is an optional feature at the CPU.

SECTION 4 DETAILED THEORY OF OPERATION

STORAGE ELEMENT

Information in a core memory is stored in an array of ferrite toroidal cores. Each core may be individually set to one of two magnetic states, thereby representing one bit of binary information. A discussion of ferrite core storage is best conducted in terms of the core B-H relationship, shown in Figure 3-4-1. Magnetizing force, H, is proportional to the total current on wires passing through the core. Magnetic flux density. B. is proportional to the resulting magnetization of the core. Figure 3-4-1 illustrates two useful properties of the core. First, the core is a threshold element. A core in state Bo remains in that state if a magnetizing force of magnitude \boldsymbol{H}_{l} or less is applied and removed. Second, the core is a memory element. If a larger magnetizing force, H2, is applied, the core switches from the state of negative magnetic flux density, B₀, to the state of positive magnetic flux density, B1, and remains there even after H is reduced to zero. The core remains in state \boldsymbol{B}_1 until an equally strong magnetizing force in the opposite direction switches it back to B_{n} . Figure 3-4-1 also illustrates one difficulty of core storage. In order to sense the state of a core it is necessary to measure the change in B resulting from the application of a force H, and the change in B is almost undetectable until that force exceeds H1. Therefore, a core must be switched to be sensed.

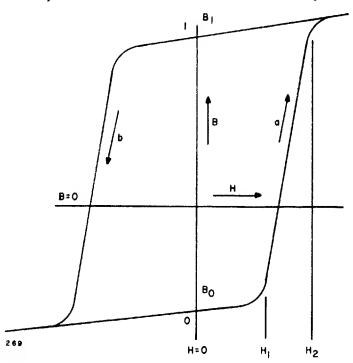
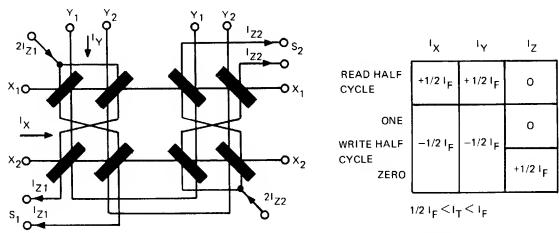


Figure 3-4-1. Ferrite Core B-H Characteristics

Read-Write Cycle and Coincident Current Selection

The storage array is formed by arranging cores and wiring so that there are as many sets of cores as there are bits in the storage word. In each set of cores a common sense-inhibit wire threads every core, and running through all sets are X- and Y-address selection lines that intersect each other only once in each bit-set of cores. A two-bit, four-word array is shown in Figure 3-4-2.



WHERE IT IS THE MINIMUM CURRENT REQUIRED TO SWITCH A CORE.

Figure 3-4-2. Two-Bit, 4-Word, 3D, 3-Wire Core Array

Figure 3-4-2 shows that if a current, slightly weaker than required to switch a core, is applied to one X-line and one Y-line, then only one core per bit mat will see a current $I_{\rm x}$ + $I_{\rm y}$ strong enough to cause switching. If that core switches, a voltage is induced in the sense winding for that bit and shows up at the sense terminals, S1 or S2. A core that switches as a result of such read-select currents is defined as having been in the ONE state. All cores in the selected word are then in the ZERO state after the read-select currents have ended, either because they were already ZERO, or because the read currents switched them to ZERO. After the read half cycle currents have read and cleared the word, write half cycle currents are applied to the same X- and Y-lines. These currents are equal to, but of opposite polarity from, the read-select currents. Again, only one core per bit set may see a total current strong enough to cause switching. The write half cycle currents drive all the bits in the selected word back to the ONE state. If a ZERO is to be written into a particular bit instead of a ONE, the sense-inhibit winding for that bit is driven with an inhibit current $^{
m 2I}_{
m Z1}$, which cancels one write-select current in the selected core. The inhibit current prevents that core from switching out of the ZERO state. As many inhibit currents are required as there are ZEROs in the word to be written. Study of Figure 3-4-2 will prove that the inhibit current does not add to any write select currents, so no other core in that bit-set will be switched during a write half cycle.

Figure 3-4-3 shows the means of connecting two diodes to one end of each X- or Y-selection line and bussing the other ends of the selection lines to form a 2-by-2 bipolar diode matrix. The matrix permits driving a particular selection line, without driving any other line, by selection of one bus line and one pair of drive lines (one drive line for each current polarity). The simplified matrix shown is not efficient, but the actual matrix is efficient, since one of the two matrices, namely the Y-matrix on the core plane, addresses 64 drive lines with only eight bus lines and eight drive line pairs. The X-matrix addresses 128 lines with 16 bus lines and 8 drive line pairs. A 4096 word memory module has an 8192 word core plane, but half the X address lines are disabled by the MA04 address register wiring change shown in Section 9, LBD 8101, Drawing No. C70032890.

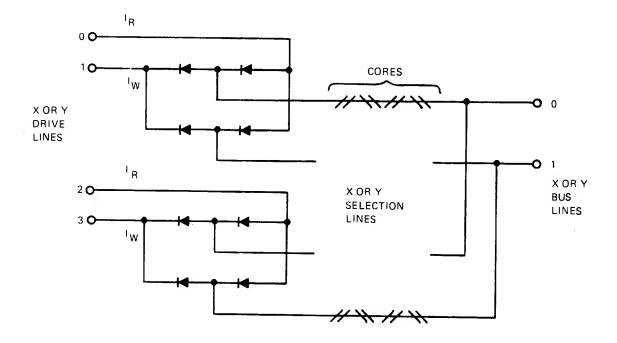


Figure 3-4-3. Two-by-Two Bipolar Diode Matrix

SELECTION CIRCUITS

Selection Switches

Figure 3-4-4 illustrates how bipolar selection currents are driven through the storage array. Each switch circuit acts as a single-pole, double-throw switch. If all six address bits are true, a pair of read-timing or write-timing commands cause a current path to be completed through the selection line, from the drive current node to ground. The current flows through the selection line in either of two opposite directions, depending whether read or write timing is commanded. The core memory module contains 8 drive line switches and 8 bus line switches for the Y-axis and 8 drive line switches and 16 bus line switches for the X-axis.

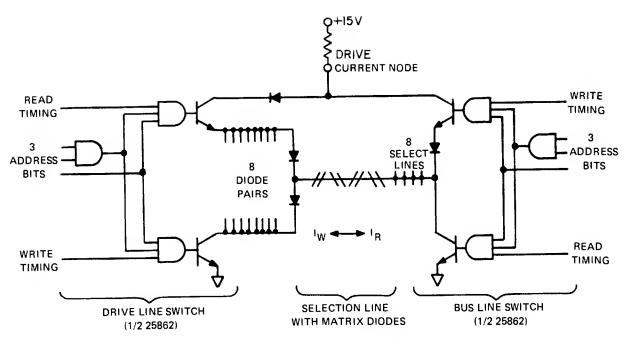


Figure 3-4-4. Selection Switches

DATA LOOP

Read Data Path

The read data path is illustrated in Figure 3-4-5. The ONE signal from the core plane is a differential signal of typically 38 mV peak amplitude, of either polarity (hence the sense amplifier exclusive-OR symbol). The ZERO signal is ideally zero, but various effects bring it up to about 10 mV at strobe time. The sense amplifier is biased with external resistors to discriminate between ONEs and ZEROs at a nominal threshold of 18 mV. The sense amplifier is strobed early in a memory cycle when the address selection noise on the sense-inhibit lines has decayed below the threshold level. If a ONE is detected, a negative going pulse appears on the data output bus. If a ZERO is present, the data output remains high. A pulse stretcher circuit on each data output circuit guarantees the minimum pulse width needed to set the memory information register in the CPU. All data output lines are from open collector 7407 buffers.

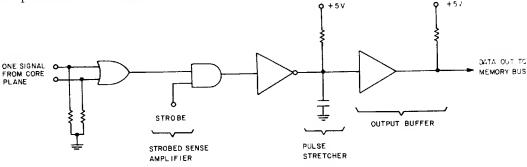


Figure 3-4-5. Read Data Circuits

There are 17 read circuits in a core memory module, including the parity bit. The 17th bit is not used if the CPU does not have the parity option.

Write Data Path

The write data path is shown in Figure 3-4-6. Inhibit current is driven into a sense-inhibit winding only when a ZERO is to be written in that bit of the word. The two-input gate turns on (ground output) at inhibit time if the memory data input is low. Current in the gate output is coupled through a 1 to 1 transformer to turn on the inhibit driver transistor. The saturated transistor completes the inhibit current path, from +15 Vdc through the sense-inhibit winding to ground. The value of inhibit current is set by the +15 Vdc supply and the inhibit resistor. A balun-connected transformer forces equal current sharing in the two legs of the winding.

When inhibit time ends and the transistor is turned off, inductance of the inhibit winding tends to continue the current flow in the same direction as before, and the inhibit driver end of that winding swings sharply to a negative voltage. The turnoff diode clamps this swing and provides a path for the current to decay exponentially to zero. There are 17 inhibit circuits in a core memory module.

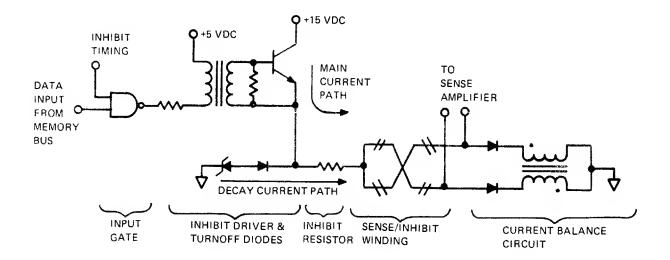


Figure 3-4-6. Inhibit Circuit

TIMING AND CONTROL

Refer to Section 9 for detailed diagrams of the timing circuits. Signal names used below follow the same conventions used in the LBDs in Section 9; that is, when several similar signals (e.g., data inputs) are described together, their differentiating characters (e.g., MO1FF+) are replaced with double letters (MXXFF+). Also, signals that differ only by a suffix (INHEN+A and INHEN+B) have identical timing except for differences in gate delays.

Address and Current Timing

Prior to a memory cycle, address and bank-select are gated into registers by MADCL-A. Register outputs follow the inputs as long as MADCL-A is low.

The cycle begins with the leading edge of the first positive pulse of MXYTM+. The leading and trailing edges of this first pulse are shifted in an RLC network and combined in gates to form read current timing commands (XRSW+, XRSK+A, XRSK+B, YRSW+ and YRSK+). The second positive pulse of MXYTM+ is similarly shaped to produce the write-timing (XWSW+A, XWSW+B, XWSK+, YWSW+, YWSK+) and inhibit-timing (INHEN+A and INHEN+B) signals.

Data Loop Timing

Sense amplifier strobe (STROB-) timing is generated by ANDing three signals: XRSW+ (read current timing signal), MSTRB- (reset output of a one-shot triggered from YRSK+), and MSTEN+ (buffered memory strobe enable input from the CPU).

The XRSW+ input removes a race condition due to triggering delay in the one-shot and also defines the trailing edge of strobe. The MSTRB- input defines a critical timing edge, the leading edge of strobe. The MSTEN+ input disables the strobe pulse during clear-write cycles. The strobe pulse enables the sense amplifier data to the data output bus through the pulse stretcher and buffer.

Parity Logic

The electronics and logic associated with the parity bit consist of the following:

- a. The 17th bit (parity bit) read data path,
- b. The 17th bit (parity bit) write data path,
- c. The parity generator,
- d. The parity data register.

The 17th bit, read-data and write-data paths have previously been explained. The parity generator consists of two 8-bit parity generator checker circuits (PG1 and PG2) connected in series to generate odd parity. The system data input lines are broken into two 8-bit groups. The buffered outputs of M01FF+ through M08FF+ drive PG1, and the output of PG1 and buffered outputs of M09FF+ through M16FF+ drive PG2 (see Figure 3-4-7). The output of the parity generator is buffered through the 7404 and 7407 gates to drive the memory interface line designated PAGEO-. The output of PG2 is also gated with a timing pulse called LPREG+. The output of this gate is collector-OR'ed with the parity register's buffered output to control the interface signal line called PAMEO-. The PAMEO- has two functions depending upon the memory cycle in progress. During a read-write cycle the 17th bit is stored in the parity register and PAMEO- is used to compare with PAGEO- at the processor end. It is also tied internally to the write interface to complete the regeneration or write portion of the cycle. During clear-write cycles PAMEO- is controlled by the gated output of PG2 to write the parity information into the memory.

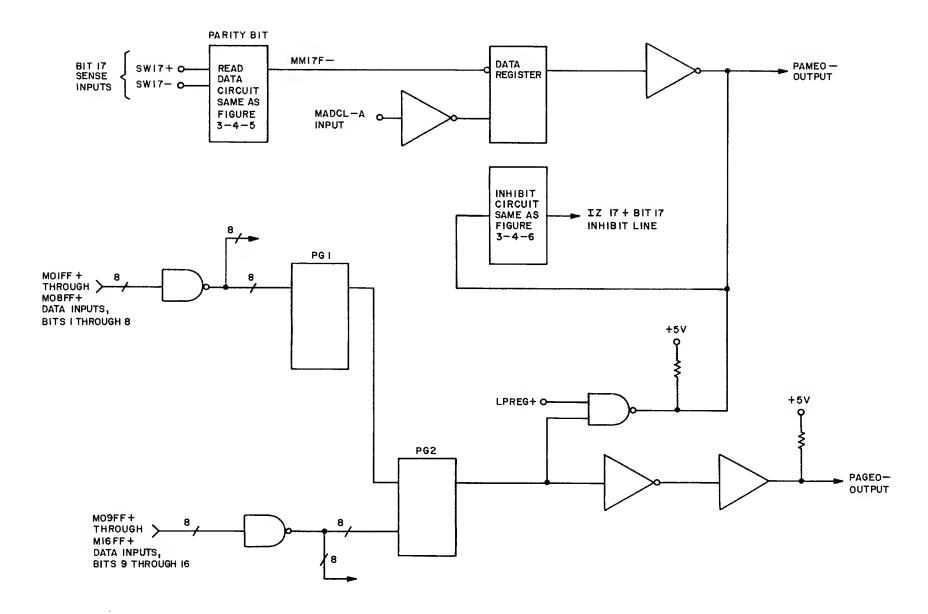


Figure 3-4-7. Parity Generation and Register Logic

TIMING DIAGRAMS

Refer to Section 9, LBDs 8110 and 8111, Drawing No. C70032895 and C70032897, for interface and internal timing, respectively.

SECTION 5 INSTALLATION

Service personnel should be familiar with the complete installation procedure and the interface requirements before attempting to install the core memory module.

TOOLS AND TEST EQUIPMENT

Table 3-5-1 lists the tools and equipment required to install the core memory module.

Table 3-5-1.
Installation Tools and Test Equipment

Quantity	Description	Type or Equivalent
1	Digital voltmeter	Honeywell Model 623 (±0.05% F.S., l Megohm Input Resistance)
1	Trimpot adjustment tool or screwdriver	
1	Screwdriver	Phillips
2	Screw, pan head	70904113021
2	Lockwasher, split	70902006078
2	Washer, flat	70902054003
2	Bushing, insulated	70916300007
2	Spacer	A700322753701

SPACE AND ENVIRONMENT

The core memory module occupies the same space as a 1-by-3 omni-BLOC. Environmental specifications are listed in Section 1.

INTERFACE CONSIDERATIONS

The interface requirements are met by inserting the two I/O cable PACs into the appropriate connector slots provided in the memory connector block. Interface pin connections and cable PAC locations are shown in LBD 8112, Drawing No. C70032896, in Section 9.

INSTALLATION PROCEDURES

Unpacking, Repacking and Reshipping

Upon receipt of the core memory module, care must be exercised in unpacking. A thorough visual inspection should be made for damage and loose hardware. Check for

foreign objects between the core plane boards. Extreme caution must be observed to prevent any object from penetrating into the core plane area.

Should reshipping become necessary, wrap the module in plastic, seal with tape, and place in a sturdy cardboard box with more than one inch of resilient packaging on all sides.

Mechanical Procedures

Insert the core memory module with the circuit boards side up in the upper level of the chassis. Use the spacer, tools, and mounting hardware outlined in Table 3-5-1.

Electrical Checkout Procedure

To perform the electrical checkout procedure,

- a. Load the Core Memory Test Program, CMT5, Document No. 70181454000.
- b. Run the diagnostic test in the installed module.
- c. Halt the program, fetch any location in the module, turn power off and on, and fetch the location again to see that it is unchanged.
- d. Perform the voltage and strobe margin checks described in Section 6.

SECTION 6 MAINTENANCE

EQUIPMENT CONFIGURATION

Mechanical Assemblies

The mechanical components of the core memory module are shown in Section 10. There are five major subassemblies: three circuit boards, one core plane, and one solderless-wrap connector backplane.

Module Location

The core memory module occupies the same area as a 1-by-3 omni-BLOC. Since the CSM-150 Core Memory Module is higher than a CSM-160 Core Memory Module, it requires slightly different mounting methods, as described in Section 5.

OPERATOR MAINTENANCE

No operator maintenance is necessary on the core memory module. The operator should periodically check the cooling fans and air filters.

STANDARD MAINTENANCE

Tools and Test Equipment

The tools and equipment listed in Table 3-6-1 are needed for maintenance and troubleshooting in addition to those listed in Table 3-5-1.

Table 3-6-1.
Troubleshooting and Maintenance Tools and Test Equipment

Quantity	<u>Description</u>	Type or Equivalent
1	Oscilloscope	Tektronix 454
1	Multimeter	Simpson 260
3	Card Extender PACs	Honeywell XP-330
1	MACRO-PAC Extractor Tool	Honeywell B70026032701
1	AC Current Probe	Tektronix P6020
1	Hand Wire-Unwrapping Tool	Gardner-Denver 505244
1	Hand Wire-Wrapping Tool, Battery-Operated	Honeywell 70917200001 (Gardner-Denver No. 14R2)
1	Wire Stripper	Honeywell 70917250001 (Ideal 45-179)

Table 3-6-1. (Cont)

Quantity	Description	Type or Equivalent
5 Ft	No. 30 AWG Solid Wire	Honeywell 70940061010
1	Quick Disconnect Terminal Crimper	T & B WT 145

Preventive Maintenance

<u>Cleanness.</u> -- The core memory module must be kept free of dust, dirt, and any foreign objects. The air filter of the cooling system must be kept clean to ensure sufficient air flow. Should it be necessary to clean the core plane, only use de-ionized water. However, cleaning the core plane is not recommended as a field procedure.

CAUTION

Never use an air hose to clean the core plane.

Margin Checks. -- The power-supply margin checks can detect performance degradation before operational failures occur. The memory drive and inhibit currents are determined by the setting of the +15 Vdc supply and the resistors on the CM-866 and CM-867 boards. The +15V supply setting should be periodically checked by using a voltmeter capable of reading the voltage within ±1 percent. Measurements should be made at the memory terminals while a program is running in the memory. The CMT5 diagnostic program contains several test patterns, including the worst pattern (exclusive-OR of MAD13- and MAD08-), all ONEs and all ZEROs. Failure points at the high +15V setting (do not exceed +17.5V) and low +15V setting should be noted; their differences should be at least 1.6V at 25°C and 1.2V at 0 and 60°C. The +15V supply should be set at the center of the failure point margins. Temperature tracking specifications are listed in Section 1.

Adjustment

The core memory module has no adjustable components. The timing of the sense amplifier strobe pulse is set at Honeywell Inc. for each unit to give optimum operating margins. It is not necessary to adjust the strobe timing. If a change in timing is required to obtain proper memory operation, the associated boards and core plane should be checked before a change is made.

Table 3-6-2 presents the strobe jumpers that can be added for test purposes to uncover marginal operation. The jumper locations are shown in Figure 3-10-1 in Section 10 and on LBD 8101, Drawing No. C70032890, in Section 9.

Table 3-6-2. Memory Strobe Test Modes

Mode	Mean	Function
Early Strobe	Jumper J_2 (between SST5 and SST2)	Increase tendency for memory to pick ONEs (detect margi- nal ZERO bits)
Late Strobe	Jumper J ₃ (between SST1 and SST4)	Increase tendency for memory to drop ONEs (detect margi- nal ONEs)
Normal	No Jumpers	Normal

Removal and Replacement

The board connectors are polarized to protect against incorrect board insertion. Board removal from the memory is accomplished by engaging the cut-out in the handle of the board with the board extractor tool. Do not remove or insert printed circuit cards without turning off the dc power. Additional care should be taken when removing the CM-867 data board adjacent to the I/O cable slot in the first memory module as the cable sleeving can be ruptured due to scratching by the DIP leads on the etch side of this board.

CAUTION

Remove the boards on both sides of the core plane. This allows more room for gripping the handle when removing the core plane. Do not use the MACRO-PAC Extractor Tool or any other tool; otherwise, damage to the core plane will result.

When replacing defective components, use a low-wattage soldering iron and rosin 60/40 solder. Remove excess solder from the printed circuit board. Care should be taken to avoid lifting the etch.

SECTION 7 TROUBLESHOOTING

GENERAL PROCEDURES

The following steps should be performed before repairing the module.

- a. Uncover symptoms.
- b. Determine type of problems.
- c. Determine section at fault.
- d. Locate faulty circuit.

If the module is to be forwarded for repair, troubleshooting should nonetheless be carried at least through Step b and specifics of the problem forwarded along with the module. Include the module serial number with all documentation. If the module is to be replaced, use the checkout procedure in Section 5 on the new module. The reader should be familiar with the material in previous sections of the manual before attempting repairs other than module replacement. Refer to Section 6 for maintenance tools and procedures, Section 8 for signal mnemonics, Section 10 for mechanical assemblies, parts locations, and parts lists, and Section 9 for logic diagrams and detailed timing diagrams.

SPECIFIC PROCEDURES

Module Interchangeability

Module interchangeability involves no wiring changes. Unless the problem is a marginal condition in the processor or power supply, module swapping will isolate a faulty module. Because of the above uncertainty, diagnosis should be carried beyond module swapping. All memory boards with the same designation are interchangeable. For example, a CM-867B will replace a CM-867B, CM-867A or CM-867. A CM-867 will not be interchangeable with a CM-867A or CM-867B.*

Core Memory Test Program

The core memory test (CMT) program exercises the memory in various troublesome and diagnostic patterns and prints out errors. It is useful for uncovering and determining the type of problem.

Control Panel Debugging

Control panel debugging is invaluable if the processor cannot load and run CMT, but is almost useless for intermittent or pattern-sensitive errors. A general path to try is as

^{*}This is an example only. CM-867A and CM-867B do not exist at this time.

follows. Store ONEs throughout the module, and examine suspect locations. Repeat with ZEROs. To check if address bit circuits are operating, go to the lowest address in the module, and store ZERO in it. Set each address bit (4 through 16) to ONE, one at a time, and store the address in itself. Fetch the lowest location again, check that it is still ZERO. Store ZERO in it again. Fetch each of the other locations stored; they should be unchanged. Any errors in the words being read will point to the address bit at fault. This test is most stringent with +6 Vdc supply to the module set 5 percent low. In all above tests, fetching two or three times at the same address will check regeneration.

Waveform Checks

Waveform checks isolate a problem to a specific circuit. The majority of signals can be observed on the backplane connector pins or the board test point terminals (labelled TP on the LBDs and assembly drawings). If additional signals must be viewed, three XP-330 $\mu\text{-PAC}$ extenders can be used.

The drawings in Sections 9 and 10 can be used to determine the proper waveforms. Common circuits (e.g., data bits) can be compared to determine signal differences. Check the CM-866 drive and timing signals if failures are common to all data bits. Observe the CM-867 sense and inhibit waveforms if failures are at all locations and at some or all data bits. Probing sense amplifier inputs requires a differential oscilloscope preamplifier and should be done carefully to avoid component damage and introduction of spurious signals.

CORE PLANE TROUBLESHOOTING

Under normal operating conditions it is unlikely that troubles will occur within the core plane. However, continuity measurements of the sense-inhibit and drive windings enable maintenance personnel to check core-plane wiring. Exercise caution in taking these measurements to avoid damaging the matrix windings.

Repair should not be attempted on the core plane since it may affect vendor warranties. A defective core plane should be returned to Honeywell Inc. for repair or replacement. A report describing failure symptoms or diagnosis should be returned with it.

CAUTION

Multimeter current and voltage should be kept below 300 mA and 30V, respectively, to avoid damage to matrix windings and components.

Sense-Inhibit Windings

- a. Turn off memory power. Remove the CM-867 data board associated with the sense-inhibit windings to be checked.
- b. Place the ohmmeter leads across the sense winding inputs (SWXX+ and SWXX-) to the CM-867 data board, as determined from LBD 8104, Drawing No. C70032893, in Section 9 (bits 1 to 16) or from LBD 8105, Drawing No. C70032894, (parity bit 17), and check for continuity. One sense-winding links 8192 cores.

- c. Resistance readings should be typically 13 ohms (across SWXX+ and SWXX-) for all sense-inhibit windings. The resistance readings for all windings should agree within ±7 percent.
- d. Measure between signals IZXX+ and SWXX+ to check inhibit wiring continuity. Results should be 6.4 ohms ±7 percent. Repeat for IZXX+ to SWXX-.

Drive Windings

- a. Turn off memory power. Remove the CM-866 address board. The drive winding connections to the core plane are shown in LBDs 8102 and 8103, Drawing No. C70032891 and C70032892, respectively, in Section 9 and Figures 3-10-3 and 3-10-4 in Section 10.
- b. The actual drive line connections are located on the core plane printed circuit board. The selection switch outputs are isolated by a diode from each drive line so that the resistance reading between any drive bus (e.g., XDXX) and line bus (e.g., XBXX) includes a diode forward drop.
- c. Measure continuity by putting one ohmmeter probe on the XDXX (or YDXX) pin and the other probe on the XBXX (or YBXX) bus. A low resistance of one forward diode drop plus a drive line resistance of approximately 8.5 ohms indicates continuity for the diode and the drive line. It may be necessary to reverse the probes to obtain the correct polarity to forward bias the selection diodes. A high impedance measurement in both directions indicates an open line or diode.

Troubleshooting Table

Memory failures are localized by loading the test pattern into the memory and by initiating a read operation at each address sequentially and then checking each readout data word for the type of failures. Generally, memory failures are operational failures, partial data word failures, or address, decoding and selection failures. An operational failure, caused by faulty timing and control circuits, occurs when commands applied to the memory have no apparent response or when there is a faulty operation at all addresses.

Partial data word failures are caused by a faulty sense amplifier, data register flipflop (in the processor), or by data-write circuits.

Address, decoding and selection failures are caused by a faulty address register or selection circuits. The memory operation is faulty at only particular addresses.

Table 3-7-1 lists the general type of memory failure along with symptoms and probable causes.

Table 3-7-1.
Troubleshooting Memory Failures

Failure	Symptom		Probable Cause
Operational	No apparent response to commands	1. 2. 3.	Dc voltage No timing inputs (CPU failure) MXYTM+, WRITE-, MADCL-A, BANK X- signals and associated logic.
	Unable to read from any address	1. 2. 3.	+15 Vdc supply MSTEN-, STROB- CPU

Table 3-7-1. (Cont)

<u>Failure</u>	Symptom		Probable Cause	
Partial Data Word	Failure of one bit (ZERO or ONE) at all addresses		CM-867 data board	
			CPU data register	
			Sense-inhibit winding	
	Failure of one bit at	1.	CM-867 data board	
	particular addresses	2.	CM-866 address board	
		3.	Sense-inhibit winding	
		4.	X- or Y-drive line	
			X- or Y-selection diode	
	Failure of one bit at one	1.	Marginal data board (CM-867)	
	address		Marginal core	
Address, Decoding, and Selection	All bits fail as a function of particular address bits	1.	CM-866 address board	
		2.	X- or Y-drive line	
		3.	X- or Y-selection diode	
	All bits fail at lower or upper 4096 addresses		Configuration jumper (LBD 8101) incorrect	

Cable Information

LBD 8113, Drawing No. 70032899, in Section 9 shows the locations of two μ -PAC jumper cables required for each CSM-150 Core Memory Module. LBD 8112, Drawing No. 70032895, in Section 9 shows the backplane pins for all interface signals. Power (+15 Vdc, +6 Vdc, -6 Vdc and ground) is connected to the Heyco connectors on the solderless-wrap backplane.

SECTION 8 REFERENCE DATA

The signal mnemonics for the CSM-150 Core Memory Module are listed below.

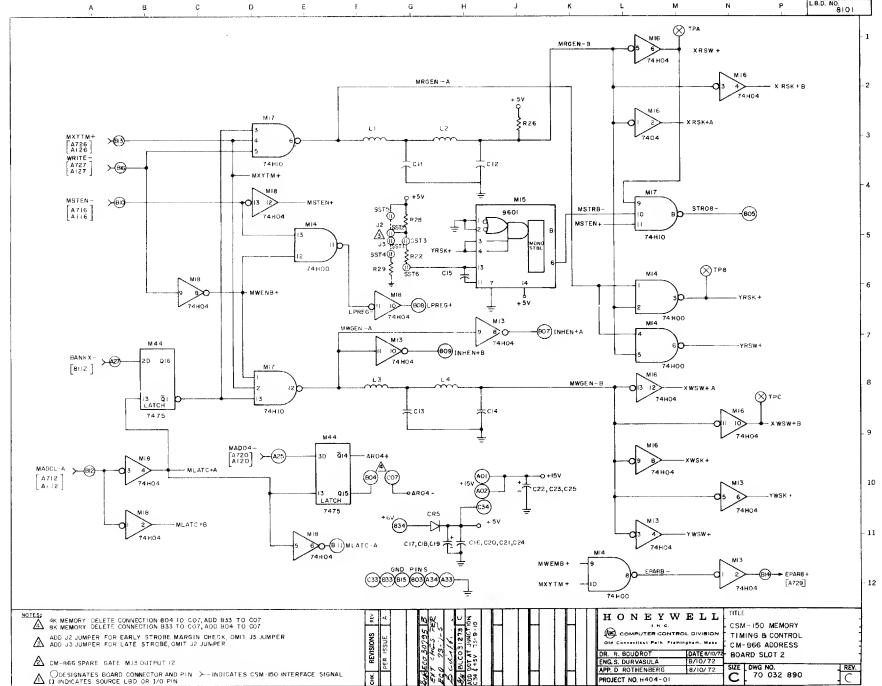
Signal	Description	LBD
BANKA- through BANKD-	Memory Bank Select Inputs	8101, 8112
INHEN+ A, B	Inhibit Timing Command	8101, 8104, 8105
M01FF+ througn M16FF+	Memory Module Data Inputs	8104, 8105, 8112
MAD04- through MAD16-	Memory Address Inputs	8101, 8102, 8103, 8112
MADCL-A	Memory Address Clear Command	8101, 8112
MM01F- through MM16F-	Memory Data Outputs (sense amplifier outputs)	8104, 8105, 8112
PAMEO-	Parity Bit Data Output	8105, 8112
PAGEO-	Parity Generator Output	8105, 8112
EPARB+	Parity Error Strobe Output	8105, 8112
APGNO+	8-Bit Parity Generator Output	8105, 8112
IZ01+ through IZ17+	Inhibit Windings	8104, 8105
STROB±	Sense Amplifier Strobe Command	8101, 8104, 8105
SW01± through SW17±	Sense Windings	8104, 8105
MXYTM+	Memory Read and Write Timing Commands	8101, 8112
WRITE-	Write-Enable Timing Command	8101, 8112
MSTEN±	Memory Strobe-Enable Command	8101, 8112
MWENB+	Memory Write-Enable Command	8101
LPREG±	Load Parity Register Command	8101, 8105
MLATC+ A, B, and -A	Memory Address Latch Command	8101, 8102, 8103
AR04± through AR16±	Memory Address Latch Output Commands	8101, 8102, 8103
MSTRB-	Memory Strobe Leading Edge Timing Command	8101
MRGEN-A and MRGEN-B	Memory Read-Enable Command	8101
MWGEN-A and MWGEN-B	Memory Write-Enable Command	8101
Test Points A, B, C, and X	Test Points	8101
XRSW+	X-Read Switch Timing Command	8101, 8103
XRSK+A and XRSK+B	X-Read Sink Timing Command	8101, 8103
XWSW+A and XWSW+B	X-Write Switch Timing Command	8101, 8103
XWSK+	X-Write Sink Timing Command	8101, 8103
YRSW+	Y-Read Switch Timing Command	8101, 8102

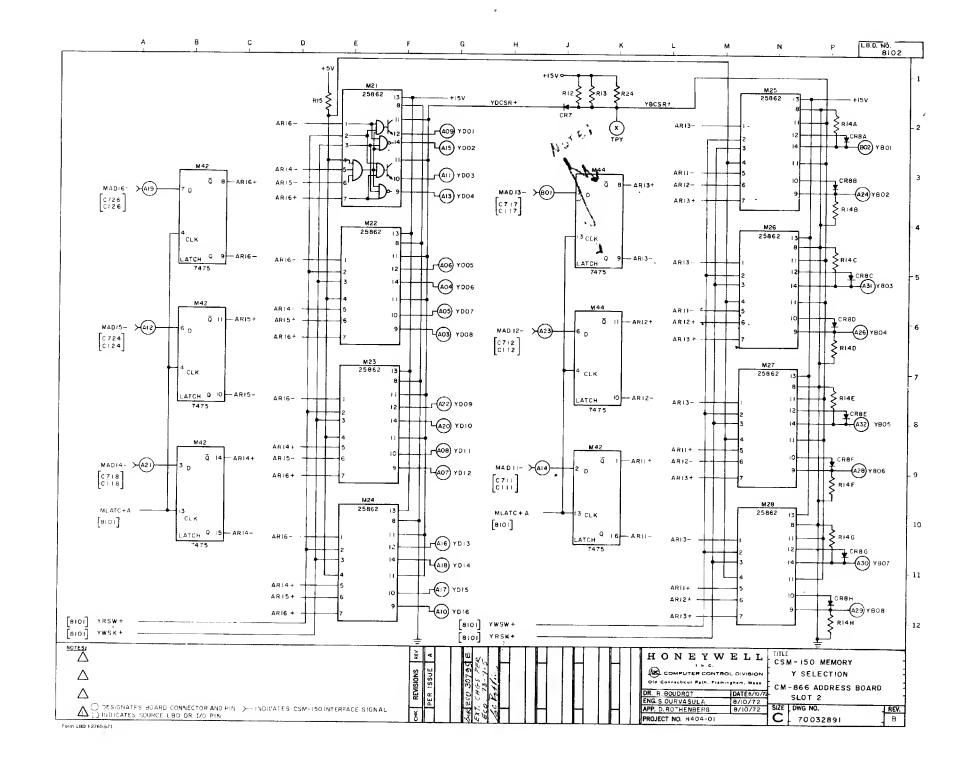
Signal	Description		LBD
YRSK+	Y-Read Sink Timing Command	8101,	8102
YWSW+	Y-Write Switch Timing Command	8101,	
YWSK+	Y-Write Sink Timing Command	8101,	8102
XDCSR+	X-Diode Drive Current Source	8103	
XBCSR+	X-Bus Drive Current Source	8103	
YDCSR+	Y-Diode Drive Current Source	8102	
YBCSR+	Y-Bus Drive Current Source	8102	
SAVTH-	Sense Amplifier Threshold Voltage	8104,	8105
MIT01- through MIT17-	Memory Inhibit Bit 01 through 17	8104,	8105
M01FF-A through M17FF-A	Buffered Data Inputs	8104,	

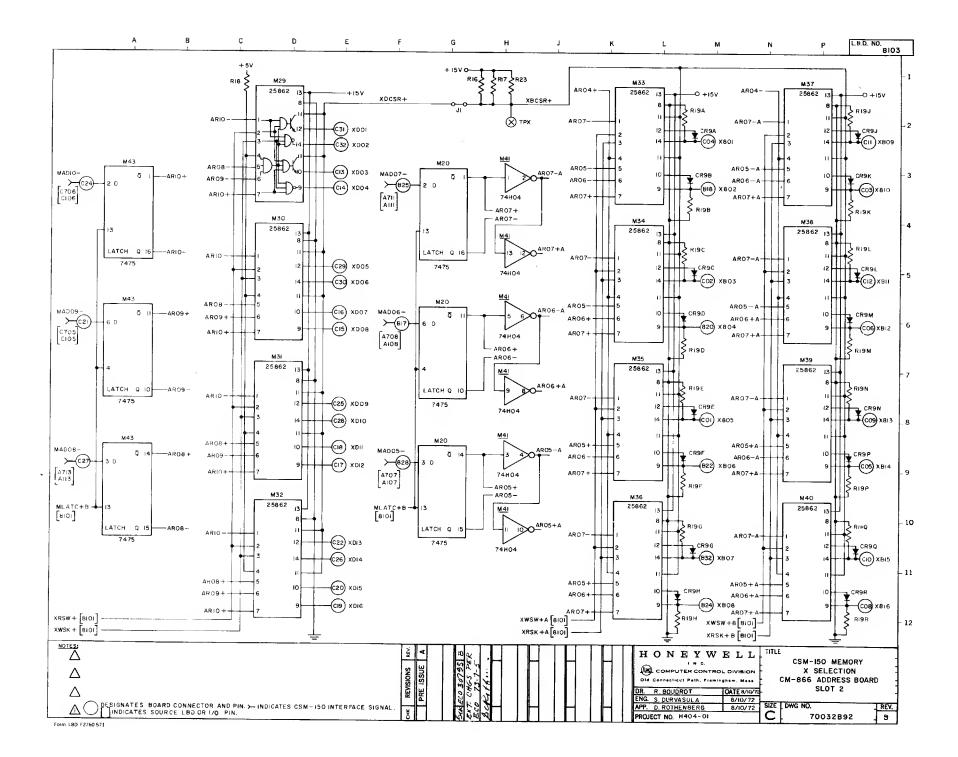
SECTION 9 LOGIC BLOCK DIAGRAMS

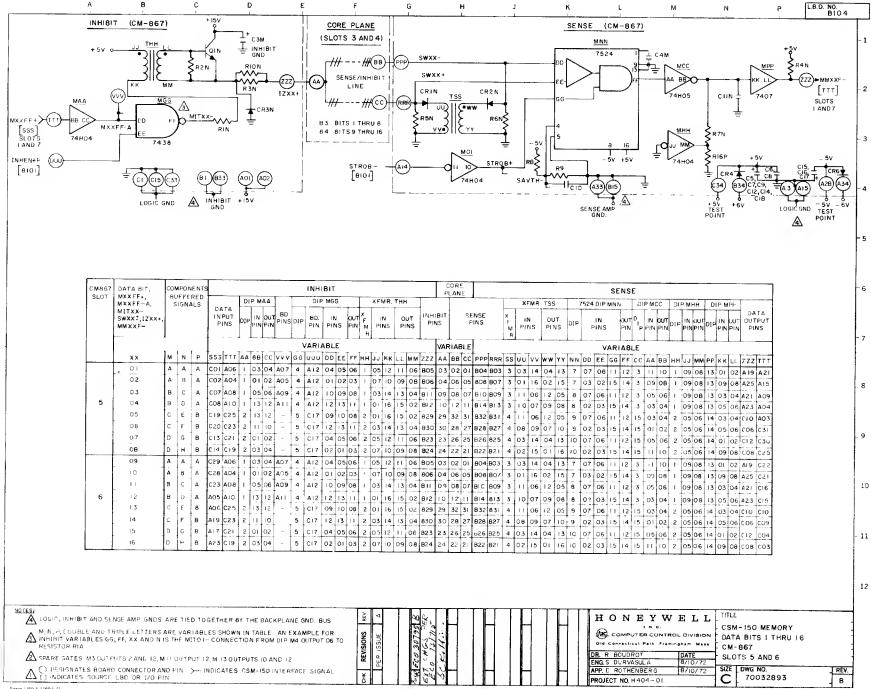
This section includes the logic block diagrams (LBD) referenced throughout Chapter 3. The LBD number of each drawing is shown in the upper right-hand corner.

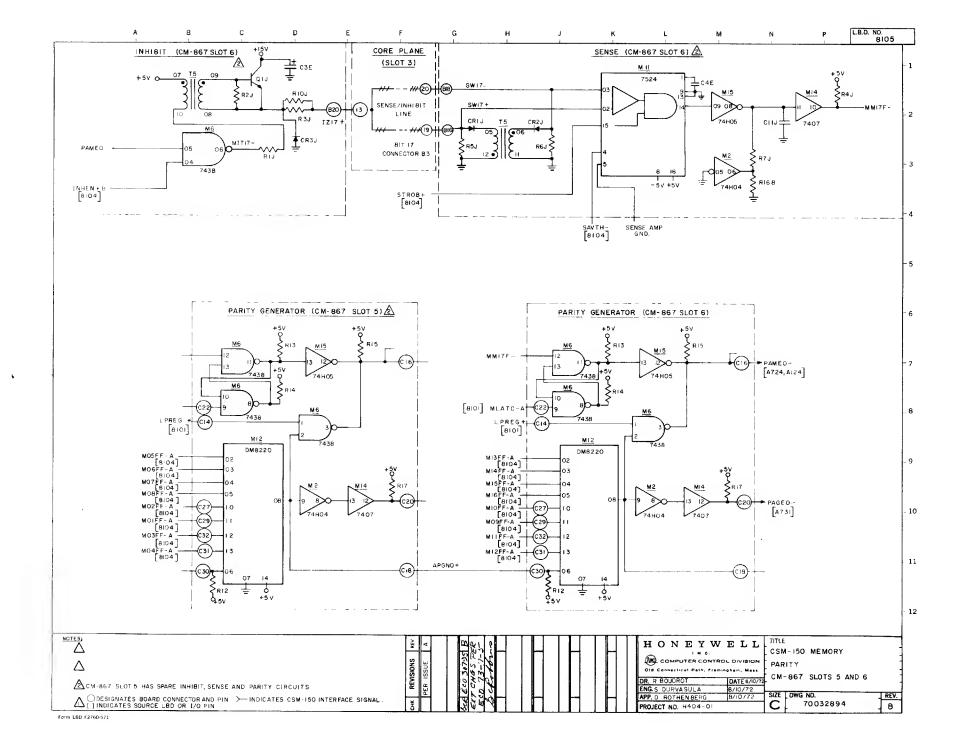
LBD No.	Drawing No.	Description
8101	C70032890	CSM-150 Memory Timing and Control, CM-866 Address Board, Slot 2
8102	C70032891	CSM-150 Memory Y-Selection, CM-866 Address Board, Slot 2
8103	C70032892	CSM-150 Memory X-Selection, CM-866 Address Board, Slot 2
8104	C70032893	CSM-150 Memory Data Bits 1 through 16, CM-867, Slots 5 and 6
8105	C70032894	CSM-150 Memory Parity, CM-867, Slots 5 and 6
8110	C70032895	CSM-150 Memory Interface Timing
8111	C70032897 ·	CSM-150 Memory Internal Timing Diagram
8112	C70032896	CSM-150 1-by-3 Connector Wiring
8113	C70032899	CSM-150 Memory PAC Complement/ Allocation
8114	C70032889	CSM-150 Memory Block Diagram

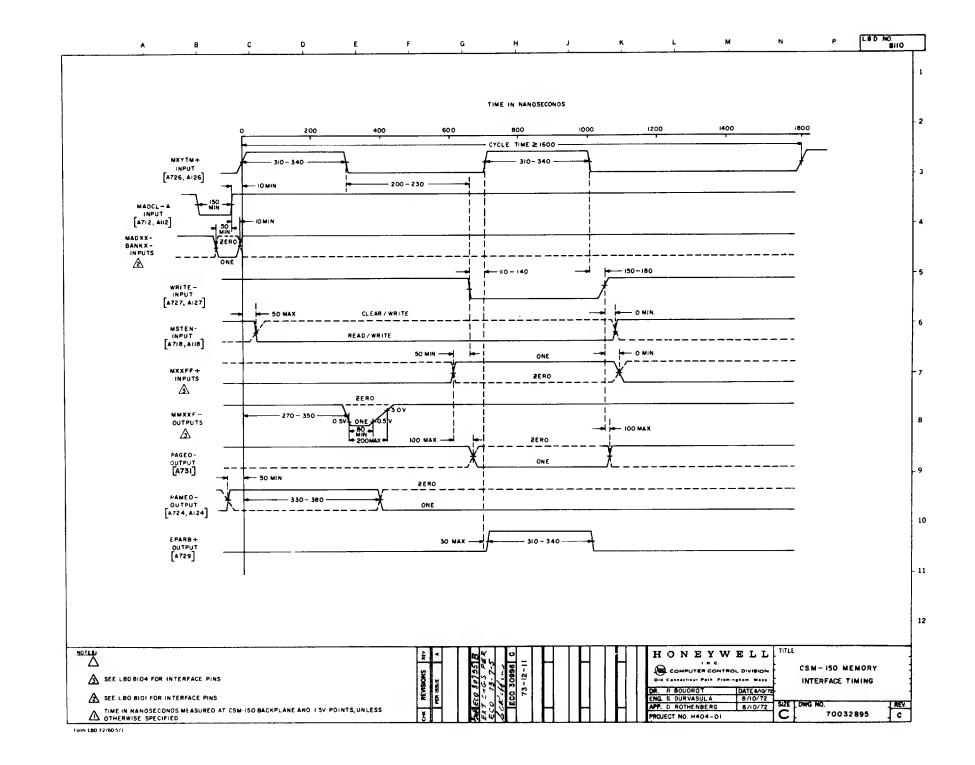


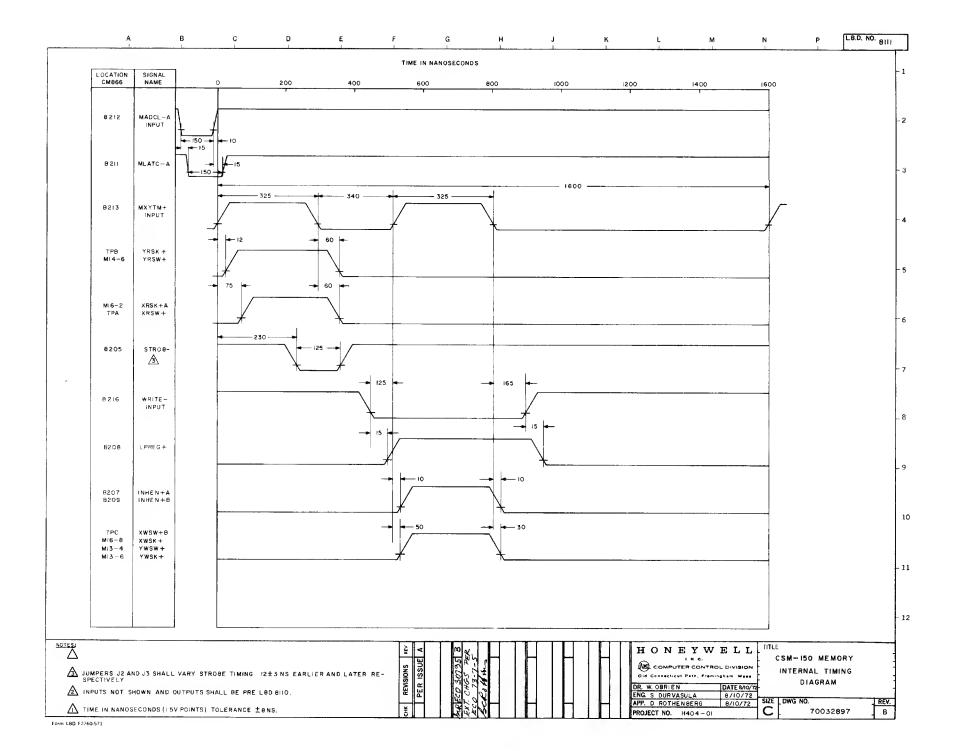


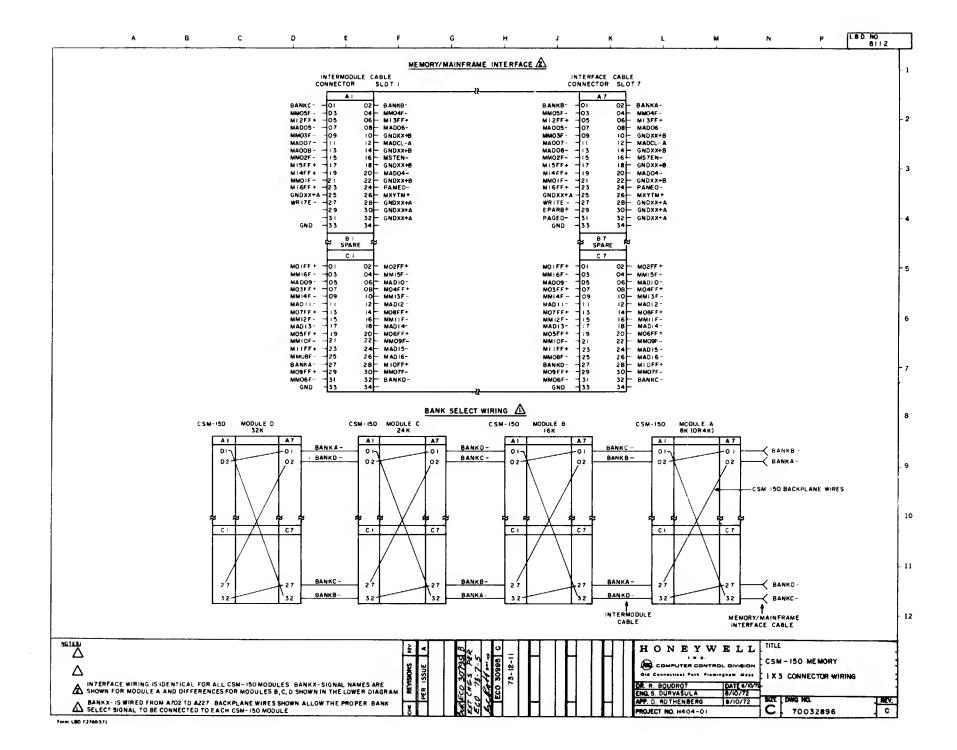


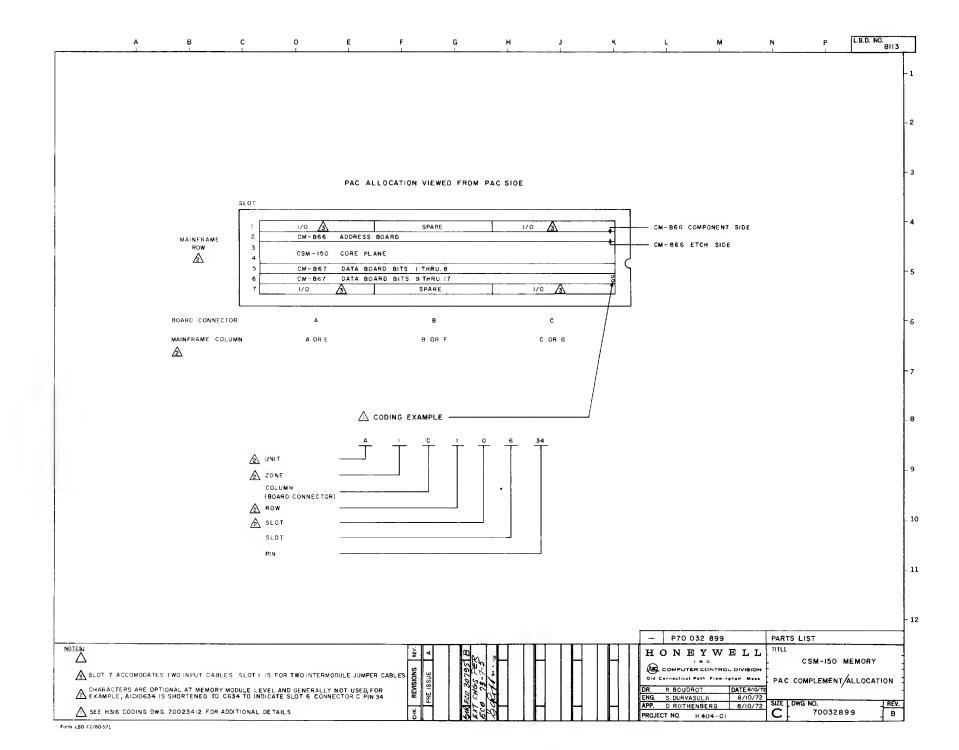












SECTION 10 MEMORY PAC DESCRIPTIONS

This section contains the following circuit descriptions and parts lists for the special Address Board, Model CM-866, and Data Board, Model CM-867, used in the CSM-150 Core Memory Module. For board locations, refer to the PAC complement, shown in LBD 8113, Drawing No. 70032899, in Section 9.

INTEGRATED CIRCUIT DESCRIPTIONS

The majority of integrated circuits are standard devices listed in vendor catalogs. Reference information is also contained in System 700, Type 716, Integrated Circuits Manual, Doc. No. 70130072667, which may be ordered from Honeywell Inc.

RECOMMENDED SPARE PARTS

One CM-866 address board, one CM-867 data board, and one CSM-150 core plane are recommended as spares.

ADDRESS BOARD, MODEL CM-866

The Address Board, CM-866, contains circuitry to perform the following functions.

- a. Store bank enable and address inputs received from the processor. This is implemented with four 7475-quad latches. The latch circuit outputs in turn drive the 25862 selection drivers.
- b. Provide selection and drive currents for an 8K matrix. This is implemented with twenty 25862-dual in-line packages, each of which includes two sink-switch pairs with decoding.
- c. Provide logic and timing circuitry to control matrix read-write timing, inhibit timing, register latch timing, sense amplifier strobe generation (pulse width control and leading edge adjustment), load parity register timing, and parity error strobe pulse. LBDs 8101, 8102, and 8103, Drawing No. C70032890, C70032891, and C70032892, respectively, in Section 9 illustrate the schematics for the CM-866 address board. Figure 3-10-1 is the assembly drawing for the CM-866 and Table 3-10-1 contains a listing of parts.

Specifications are as follows:

- a. Input Loading -- One standard TTL unit load except for MXYTM+, WRITE- and MADCL-A, which are two unit loads each.
- b. Selection Output Characteristics -- Current: 480 mA, max.; voltage: 17.5V, max.
- c. <u>Timing</u> -- Refer to LBDs 8110 and 8111, Drawing No. C70032895 and C70032897, respectively, in Section 9.

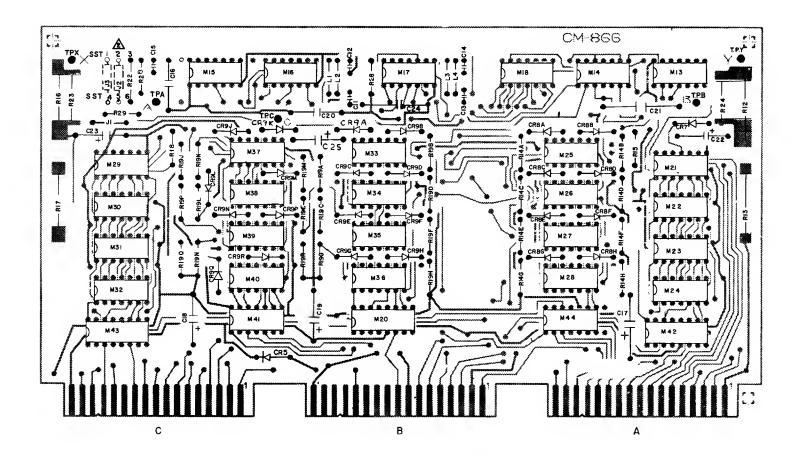


Figure 3-10-1. Address Board, Model CM-866, Assembly (Drawing No. C70050523, Rev A)

^{2.} INSTALL J2 OR J3 TEMPORARILY AT SYSTEM TEST IF REQUIRED FOR STROBE MARGIN CHECK PER LBD 8101.

I. POWER RESISTORS RI2,13,16,17,23,24. WILL BE MOUNTED OFF P.C. BD. NOT TO EXCEED THE COMPONENT HEIGHT SPEC. OF .230 MAX.

Table 3-10-1. Address Board, Model CM-866, Parts List (P70050523, Rev C)

ITEM	DOCUMENT	DESCRIPTION	QTY
NO.	NO.		701
06 A	70950118 01	NTEGRATED DEVICE	001
07 A	70950118 01:	M14 3 INTEGRATED DEVICE 74H10 M17	001
08 A	70950104 009	INTEGRATED DEVICE 9601	001
09 A	70950118 011	M15 INTEGRATED DEVICE 74H04	004
10 A	70950118 006	M13.M41.M18.M16 INTEGRATED DEVICE	
		7475	004
11 A	P04040854-002	M44.M20.M42.M43 2 INTEGRATED DEVICE 25862 M21 THRU M40	020
12 A	70943083 003	DIODE SILICON	025
		CR7.CR8A THRU CR8H CR9A THRU CR9R	025
13 C		ELE SCHMATIC REF DWG	REF
14 C		ELE SCHMATIC REP DWG	REF
16 A	70032892 000	ELE SCHMATIC REF DWG	REF
*0 7	70930004 134	CAPACITOR 10 PF 6/-5%	002
NOTES			
	NOTE 1 ASSE	MBLE PER C70050523	
	NOTE 2 VALUE	E MAY CHANGE AT FINAL	TFST
	RANGE 4.7K	70932114065 TO 12.0K	70932114075

Table 3-10-1. (Cont)

ITEM	DOCUMENT	DESCRIPTION	OTY
NO.	NO.		701
17 A.	70932226 259	C13.C14 RESISTOR FIXED W/W 40.2 OHMS 6/-1% 3WNI R12.R13.R16.R17	004
18 A	70932004-029	RESISTOR 150 OHMS 1/2W 6/-5% R24	001
19 A	70932114 049		027
		RIAA THRU RIAH	
#20 P	04420034 001	RIGA THRU RIGR DIODE SI RECT CR5	001
21 A	70939207 025		004
22 A	70930100 208	L1.L2.L3.L4. CAPACITOR .01MFD 6/-20%	004
23 A	70930004 112	C21,C24,C20,C16 CAPACITOR 62PF 6/~5%	002
24 A	70930230 023	6.8MFD 6/-2% 25V	006
25 A	70932114-070	C22,C23,C17,C18,C19 C25 RESISTOR	001
		7.5K OHMS 1/4W 6/-2% R22 NOTE 2	
26 A	70930004 106	35 PF 6/-5%	001
27 A	70932114 047	C15 RESISTOR 820 OHMS 1/4W 6/-2%	001
28 A	70932114 075	R28	001
29 A	70937077 004	T.P.X.T.P.Y.	005
		T.P.A.	
30 A	70937010 00	T.P.B.T.P.C 1 TERMINAL STUD SST1 THRU SST6	006
31 A	04910040 00	4 JUMPER	001
32 A	70932004 02	J1 6 RESISTOR 110 OHMS 1/2W 6/=5%	001
33 B	70008913 86	R23 6 PLATE IDENT.	001

DATA BOARD, MODEL CM-867

The CM-867 data board contains circuitry to implement the following functions:

- a. Amplify sense winding signals for 9 bits and adapt them for presentation to the central processor.
- b. Generate inhibit currents for 9 bits, depending upon the state of the data input lines to the board.
- c. Provide parity generation. Store the sense output of the parity bit in the parity data register.
- d. Reduce the +6V and -6V power supply levels to +5V and -5V, respectively, for use with TTL circuits.

The schematics for the CM-867 data board are shown in LBDs 8104 and 8105, Drawing No. 70032893 and 70032894, respectively, in Section 9. The assembly drawing for the CM-867 data board is shown in Figure 3-10-2, and the associated parts list is presented in Table 3-10-2.

Specifications are as follows:

- a. <u>Sense Input</u> -- ONE: 25 mV minimum for 30 ns; ZERO: 12 mV max. for the duration of strobe.
- b. Inhibit Output -- Max. current: 850 mA; max. voltage: 17V
- c. Timing -- See LBDs 8110 and 8111, Drawing No. 70032895 and C70032897, respectively, in Section 9.

CSM-150 CORE PLANE

The CSM-150 plug-in core plane is a conventional 3-wire, 3D, coincident current configuration. Cores are switched by controlling currents in two orthogonal wires threaded through the cores, called X- and Y-lines. The sense and inhibit functions are shared by the third line that is parallel to the Y-line. A current through the sense-inhibit line during the write portion of a cycle prevents the core plane from switching and thus controls whether a ONE or ZERO is written into the core plane. The flux change during the read time is also sensed on the sense-inhibit wire during read-write cycles. There are 17 mats, each containing 8192 cores, for a total of 8192 words, each 17 bits long (parity is included).

The core plane assemblies vary according to the manufacturer, but all have the same interface characteristics. Figures 3-10-3 and 3-10-4 illustrate the assembly. Figure 3-10-3 is a simplified schematic diagram of the CSM-150 core plane, and Figure 3-10-4 illustrates the interface connections of the CSM-150 core plane.

Specifications are as follows:

Core O.D. = 18 mils

Core signals at nominal drive (400 mA) and inhibit (375 mA) currents:

Min. ONE: 25 mV for 30 ns

Max. ZERO: 12 mV

Temperature Compensation: 0.25 percent per °C

Peaking Time: 180 ns typical Switching Time: 290 ns max.

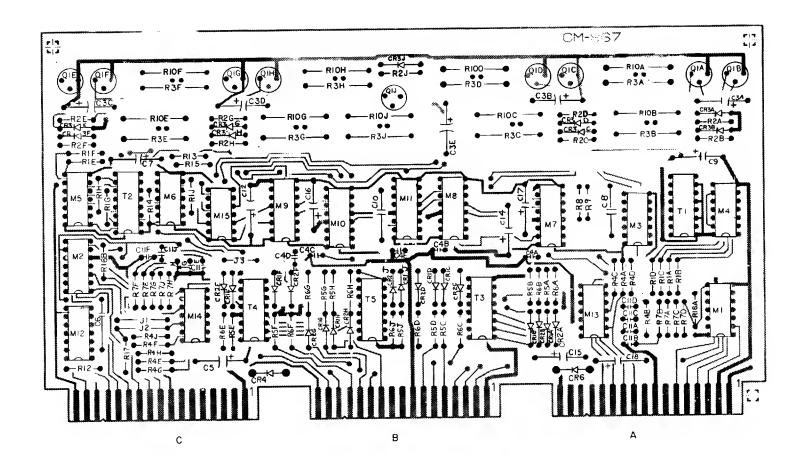


Figure 3-10-2. Data Board, Model CM-867, Assembly (Drawing No. C70050524, Rev B)

Table 3-10-2.
Data Board, Model CM-867, Parts List (P70050524, Rev C)

ITEM	DOCUMENT	DESCRIPTION	QTY	
NO.	NO.		701	702
06 A	70950118 011	74H04	002	002
07 A	70950118 019	7438	003	003
OS A	70950100 344	M4.M5.M6 INTEGRATED DEVICE 7524	005	005
09 A	70938024 001	M7 THRU M11 THANSFORMER DIP T1 THRU T5	005	005
10 A	70943778 001	TRANSISTOR NPN	009	009
11 A	70943083 003	QIA THRU QIJ DIODE SILICON CRIA THRU CRIJ	027	027
12 C	70033903 000	CRZA THRU CRZJ CR3A THRU CR3J ELE SCHMATIC REF DWG	net	
13 C	70032894 000		REF	REF
15 A	70916400 002		009	REF
16 A	70932114 029		027	009 027
		150 OHMS 1/4W 6/-2% R2A THRU R2J R5A THRU R5J	-	32,
17 A	70932226 245	RESISTOR FIXED W/W	018	018
NOTES				
- 0	ASSEMBLE PER 701 - CM-867			

702 = CM - 867A

Table 3-10-2. (Cont)

28.7 OHMS 6/-1% 3WNI R3A THRU R3J, R10A THRU R10J 18 A 70932114 001 RESISTOR 001 00 19 A 70932114 060 RESISTOR 001 00 20 A 70930230 023 CAPACITOR 014 (6.8 MFD 6/-20% 25V C3A THRU C3E.C5.C7. C9.C12.C14.C15. C16.C17.C18 003 00. 21 A 70930100 208 CAPACITOR 005 005 C6.C10.C8 C6.C10.C8 C7.C10.C8 C8 THRU C4E CAPACITOR 009 009 22 A 70930004 019 CAPACITOR 009 009 24 A 04040405 001 INTEGRATED DEVICE 001 001 0M8220N M12 C4 A 70950118 032 INTEGRATED DEVICE 002 002 7407 M13.M14 THRU C4E 7405 M3.M15 M27 P 04420034 001 DIODE SI RECT 002 002 CR4.CR6 CR4.CR6 CO09 009 009 47 OHM 1/4W 6/-2% R1A THRU R1J	ITEM	OCCUMENT	DESCRIPTION	01Y	
R3A THRU R3J, R10A THRU R10J 18 A 70932114 001 RESISTOR 001 00 19 A 70932114 060 RESISTOR 3K 0MM 6/-2% 1/4W R8 20 A 70930230 023 CAPACITOR 014 (20 A 70930230 023 CAPACITOR 014 (21 A 70930100 208 APACITOR 003 00. 22 A 70930004 019 CAPACITOR 005 005 120PFD 6/-10% C4A THRU C4E 23 70930004 012 CAPACITOR 009 009 24 A 04040405 001 INTEGRATED DEVICE 001 001 25 A 70950118 092 INTEGRATED DEVICE 002 002 26 A 70950118 050 INTEGRATED DEVICE 002 002 27 P 04420034 001 DIODE SI RECT 002 002 28 A 70932114 017 RESISTOR 009 009 29 A 70932114 056 RESISTOR 009 009 20 A 70932114 017 RESISTOR 009 009 21 A 70932114 017 RESISTOR 009 009 22 A 70932114 017 RESISTOR 009 009 23 A 70932114 017 RESISTOR 009 009 24 A 0404004 004 UMMPER 003 003 25 A 70932114 056 RESISTOR 009 009 26 A 70932114 056 RESISTOR 009 009 27 P 0442004 001 DIODE SI RECT 002 002 28 A 70932114 017 RESISTOR 009 009 29 A 70932114 056 RESISTOR 009 009 20 A 70932114 056 RESISTOR 009 009 21 A 70932114 056 RESISTOR 009 009 22 A 70932114 056 RESISTOR 009 009 23 A 70932114 056 RESISTOR 009 009 24 A 70932114 056 RESISTOR 009 009 25 A 70932114 056 RESISTOR 009 009 26 A 70932114 056 RESISTOR 009 009 27 P 04420040 004 JUMPER 003 003 28 A 70932114 056 RESISTOR 009 009 29 A 70932114 056 RESISTOR 009 009 20 D D D D D D D D D D D D D D D D D D D		NO's		701	,
18 A 70932114 001 RESISTOR 001 00 10 OHM 6/-2% 1/4W R9 19 A 70932114 060 RESISTOR 001 06 3K OHM 6/-2% 1/4W R8 20 A 70930230 023 CAPACITOR 014 6.8 MFD 6/-20% 25V C3A THRU C3E.C5.C7. C9.C12.C14.C15. C16.C17.C18 21 A 70930100 208 APACITOR 003 00. APACITOR 005 005 C6.C10.C8 22 A 70930004 019 CAPACITOR 005 005 120PFD 6/-10% C4A THRU C4E 23 70930004 012 CAPACITOR 009 009 62 PF 6/-10% C11A THRU C11J 24 A 04040405 001 INTEGRATED DEVICE 001 001 07407 M13.M14 25 A 70950118 092 INTEGRATED DEVICE 002 002 7407 M13.M14 26 A 70950118 050 INTEGRATED DEVICE 002 002 7407 M13.M15 #27 P 04420034 001 DIODE SI RECT 002 002 CR4.CR6 28 A 70932114 017 RESISTOR 009 009 47 OHM 1/4W 6/-2% R1A THRU R1J R1A O4910040 004 JUMPER 003 003 32 B 70008913 86, PLATE IDENT 001			R3A THRU R3J. R10A		
19 A 70932114 060 RESISTOR	18 A	70932114 001	RESISTOR	001	00
20 A 70930230 023 CAPACITOR 014 (6.8 MFD 6/-20% 25V C3A THRU C3E.C5.C7. C9.C12.C14.C15. C16.C17.C18	19 A.	70932114 060	R9 RESISTOR 3K OHM 6/-2% 1/4W	001	00
6.8 MFD 8/-20% 25V C3A THRU C3E.C5.C7. C9.C12.C14.C15. C16.C17.C18 21 A 70930100 208 APAC4TOR 003 00. 01MFD 6/-20% C6.C10.C8 22 A 70930004 019 CAPACITOR 005 005 120PFD 6/-10% C4A THRU C4E 23 70930004 012 CAPACITOR 009 009 62 PF 6/-10% C11A THRU C11J C11A THRU	20 A	70030230 023	R8 CAPACITOR	014	(
### ### ### ### ######################			6.8 MPD 6/-20% 25V C3A THRU C3E.C5.C7. C9.C12.C14.C15. C16.C17.C18	003	00.
22 A 7093Q004 019 CAPACITOR 120PFD 6/-10% C4A THRU C4E 23 7093Q004 012 CAPACITOR 009 009 62 PF 6/-10% C11A THRU C11J C11A THRU C11A C11A C11A C11A C11A C11A C11A C11	21 *	70930100 200	.01MFD 6/-20%		
THRU C4E CAPACITOR 62 PF 6/-10% C11A THRU C11J CM8220N M12 C5 A 70950118 092 INTEGRATED DEVICE C6 A 70950118 050 INTEGRATED DEVICE C7407 26 A 70950118 050 INTEGRATED DEVICE C7407 27 P 04420034 001 DIO0E SI RECT C7408 C74	22 A	70930004 019	C6.C10.C8 CAPACITOR	005	005
C11A THRU C11J OM8220N M12 25 A 70950118 032 INTEGRATED DEVICE O02 O02 7407 M13,M14 26 A 70950118 050 INTEGRATED DEVICE 7405 M3,M15 M27 P 04420034 001 DIODE SI RECT CR4,CR6 CR4,CR6 28 A 70932114 017 RESISTOR 47 0HM 1/4W 6/-2% R1A THRU R1J 29 A 70932114 056 RESISTOR 2K 0HM 1/4W 6/-2% R1A THRU R1J R13 THRU R1J R13 THRU R1J R13 THRU R1J R13 THRU R1J R14 THRU R1J R15 R7A THRU R7J R16A=B R17, R12 31 A 04910040 004 JUMPER J1,J2,J3 32 B 70008913 86, PLATE IDENT O01 O01	23	70930004 01	THRU C4E 2 CAPACITOR	009	009
#12	24 A	04040405 00	CITA THRU CITY 1 INTEGRATED DEVICE	001	001
26 A 70950118 050 INTEGRATED DEVICE 74H05 M3,M15 M27 P 04420034 001 DIO0E SI RECT 002 002 CR4,CR6 28 A 70932114 017 RESISTOR 009 009 47 0HM 1/4W 6/-2% R1A THRU R1J 29 A 70932114 056 RESISTOR 025 025 2K 0HM 1/4W 6/-2% R4A THRU R4J R13 THRU R4J R13 THRU R15 R7A THRU R7J R16A=B R17 R12 31 A 04910040 004 JUMPER 003 003 32 B 70008913 8b, PLATE IDENT 001	25 Å	70950118 03	M12 2 INTEGRATED DEVICE	002	002
#27 P 04420034 001 DĪOOE SI RECT CR4.CR6 28 A 70932114 017 RESISTOR 009 009 47 0HM 1/4W 6/-2% RIA THRU RIJ 29 A 70932114 056 RESISTOR 025 025 2K 0HM 1/4W 6/-2% R4A THRU R4J R13 THRU R4J R13 THRU R7J R16A=B R17. R12 31 A 04910040 004 JUMPER 003 003 J1.J2.J3 32 B 70008913 86, PLATE IDENT 001	26 A	70950118 05	M13+M14 O INTEGRATED DEVICE 74H05	002	002
28 A 70932114 017 RESISTOR 47 0HM 1/4W 6/-2% R1A THRU R1J 29 A 70932114 056 RESISTOR 2K 0HM 1/4W 6/-2% R4A THRU R4J R13 THRU R15 R7A THRU R7J R16A=8 R17 • R12 31 A 04910040 004 JUMPER 31 B 70008913 8b, PLATE IDENT 001 001	#27 P	04420034 00	1 DIOOE SI RECT	002	002
RIA THRU RIJ RIA THRU RIJ RESISTOR 2K OHM 1/4W 6/-2% R4A THRU R4J RI3 THRU RIS R7A THRU R7J R16A=B R17 R12 31 A 04910040 004 JUMPER J1.J2.J3 32 B 70008913 8b, PLATE IDENT 001 001	28 A	70932114 01	7 RESISTOR	009	009
R13 THRU R15 R7A THRU R7J R16A=B R17 • R12 31 A 04910040 004 JUMPER 003 003 J1.J2.J3 32 B 70008913 86, PLATE IDENT 001 33 B 70025642867 PLATE IDENT 001	29 A	70932114 05	RIA THRU RIJ 6 RESISTOR 2K OHM 1/4W 6/-2%	025	025
R16A-B R17 • R12 31 A 04910040 004 JUMPER 003 003 32 B 70008913 86, PLATE IDENT 001 33 B 70025642867 PLATE IDENT 001		and the second section is a second section of	R13 THRU R15		-
32 B 70008913 86, PLATE IDENT 001 33 B 70025642867 PLATE IDENT 001	31 A	04910040 00	R16A-B R17 • R12)4 JUMPER	003	003
33 B 70025642867 PLATE IDENT 001	32 B	70008013 84		001	_
33 D 10023012001 ====-					001
				4AWG	A/R

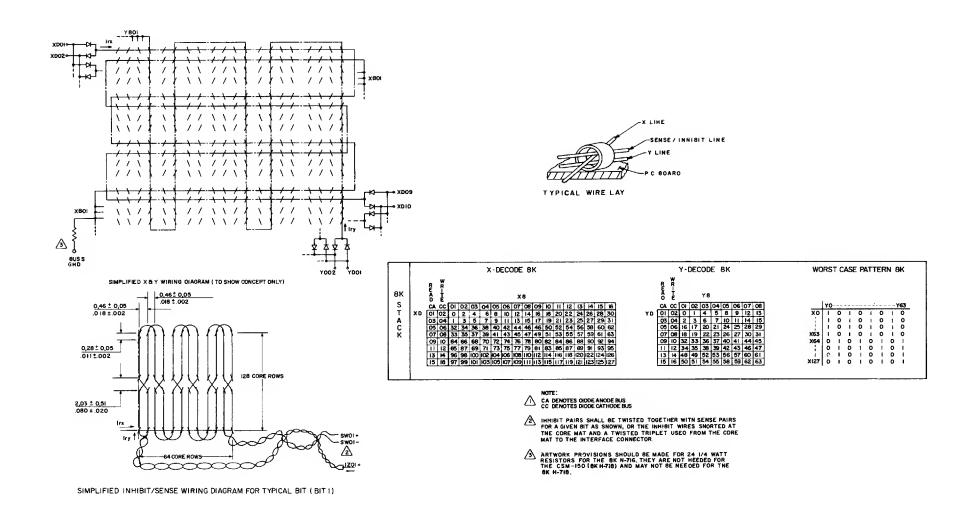


Figure 3-10-3. Simplified Schematic Diagram of the CSM-150 Core Plane (Drawing No. D70033040, Rev C)

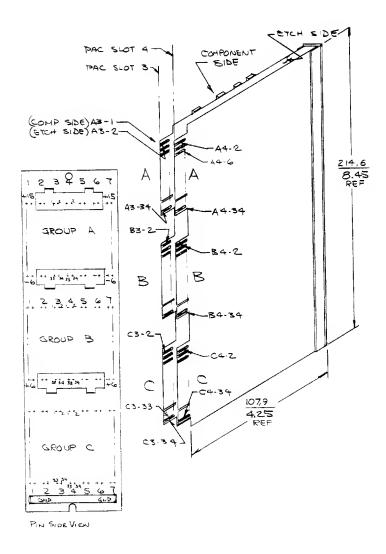
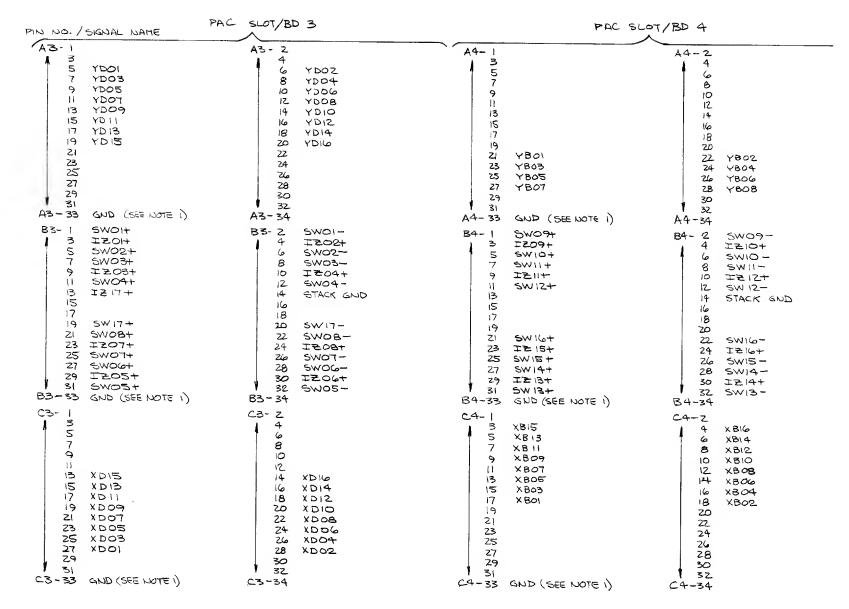


Figure 3-10-4. Interface Connections of the CSM-150 Core Plan (Drawing No. C70032758, Rev A) (Sheet 1 of 2)



NOTES

Figure 3-10-4. Interface Connections of the CSM-150 Core Plane (Drawing No. C70032758, Rev A) (Sheet 2 of 2)

I- BACKPLANE GROUND SHOWN FOR REFERENCE. "STACK GND" SHOULD NOT BE TIED TO THESE PINS BY VENDOR.

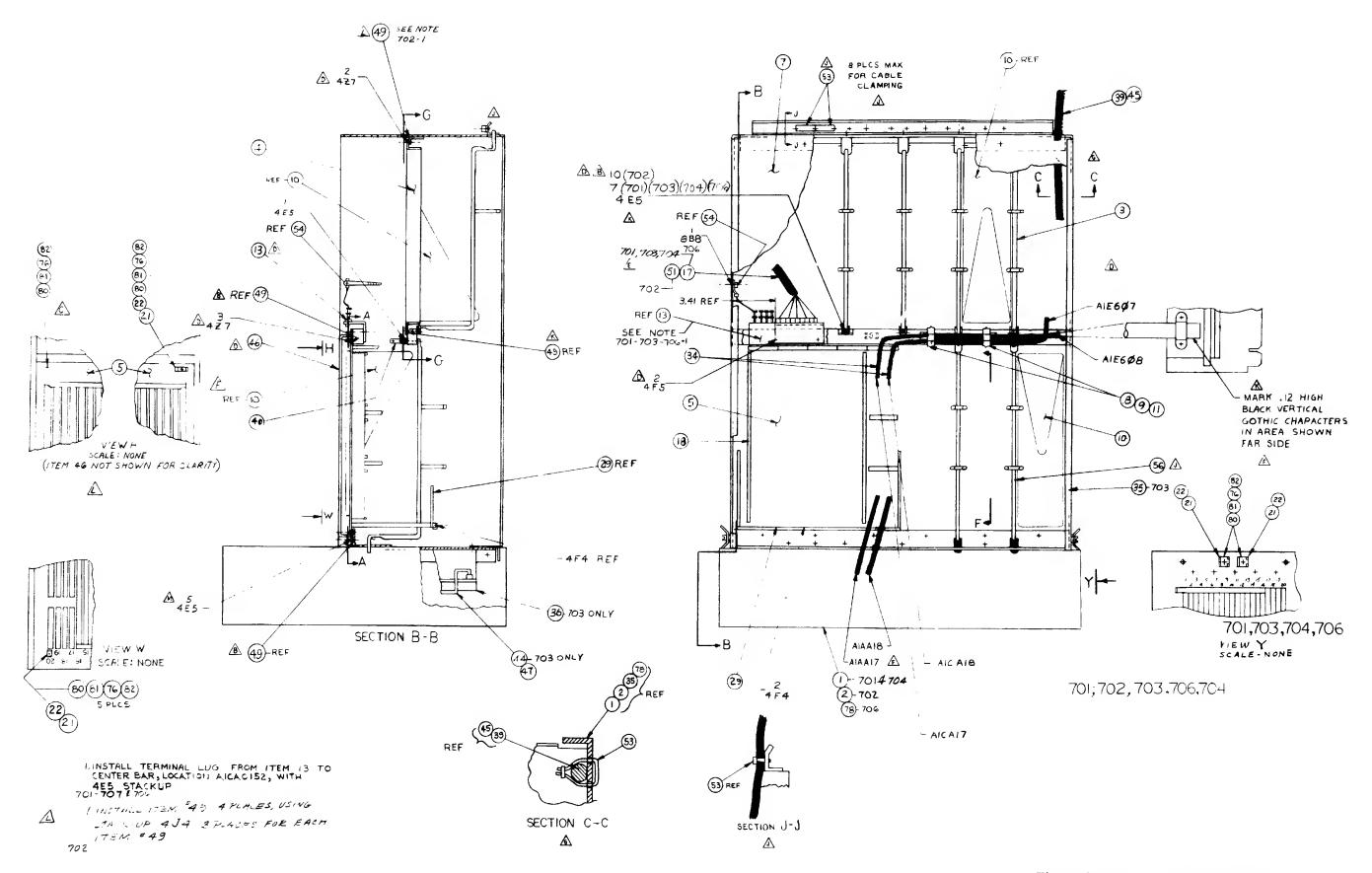
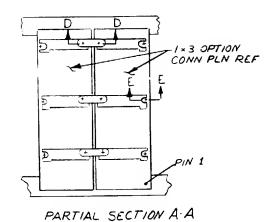
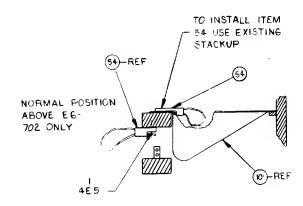


Figure 3-10-5. Logic and Option Drawer Assembly (D70030064, Rev Z, Sheet 1 of 4)



NORMAL POSITION A4 - 701, 703, 704, 706 A1 - 702

SCALE : NONE



NOTE: ITEM 54 ONLY TO BE INSTALLED TO SECURE UNTERMINATED POWER WIRING IF NO OPTION (AI/A4) OR MEMORY/OPTION (E6) IS INSTALLED

BUS - 6V REF +15.5 V REF SECTION D-D SHOWING INTERCOMMETTICS OF +6V REF +6V & GND BUS BE THEEN ADJACENT OPTIONS 21 PLACES MAX 701 4 704 \$ 706 30 PLACES MAX 702 SCALE : NONE GND REF 0 REF 425 A BUS -GRD BUS -INSULATOR r-**24**) --- + 6V BUS -6V FROM P.S. REF ITEM 14,31 < conn PARTIAL SECTION GG SHOWING MEMORY MTG & 1X3 OPTION SCALE: NONE SECTION E-E SHOWING TERMINATION OF +6V & GND BUS WHEN NO FILLER PNLS OR OPTION CONN PNLS ARE ADJACENT 6 PLACES
MAX 701,7024704[NOPTIONS LOCATIONS AIX6 & XIX6 ONLY SCALE NONE SECTION F.F GRD BUS LOCATION XIEG TOZ ONLY LOCATION -INSULATOR (NO MEMORY) XIAI +6V BUS -702 ONLY -GRD SECTION F-F SHOWING INSTALLATION OF VOLTAGE & GND WIRES & 4E4 1×3 CONN ASS'Y OF VERTICAL GY BUS WITH INSULATOR PLANE REF LOCATION AIA4-701,703-706, XIA1-702 SCALE: NONE GRD SECTION F-F SHOWING INSTALLATION OF VOLTAGE & GND. WIRES & ASSY OF VERTICAL GV BUS WITH INSULATOR 2 PLCES

Figure 3-10-5. Logic and Option Drawer Assembly (D70030064, Rev Z, Sheet 2 of 4)

MAX 701 \$ 702 \$ 704 \$ 706 LOCATION AIEX ONLY-701 \$ 702 \$ 706 \$ 704

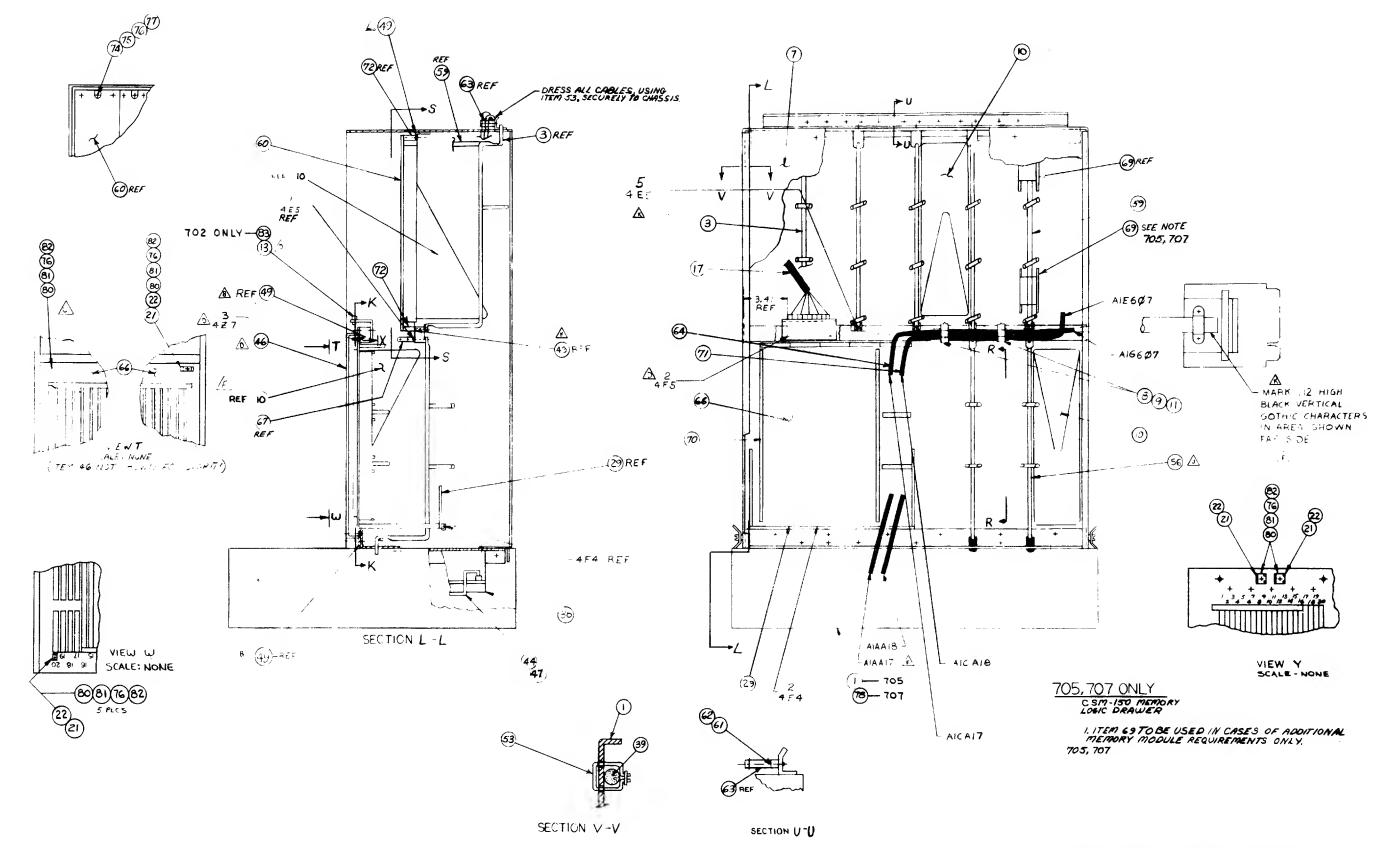
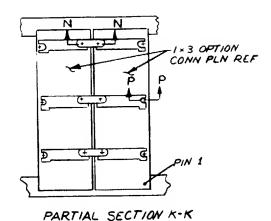
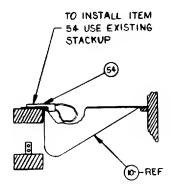


Figure 3-10-5. Logic and Option Drawer Assembly (D70030064, Rev Z, Sheet 3 of 4)



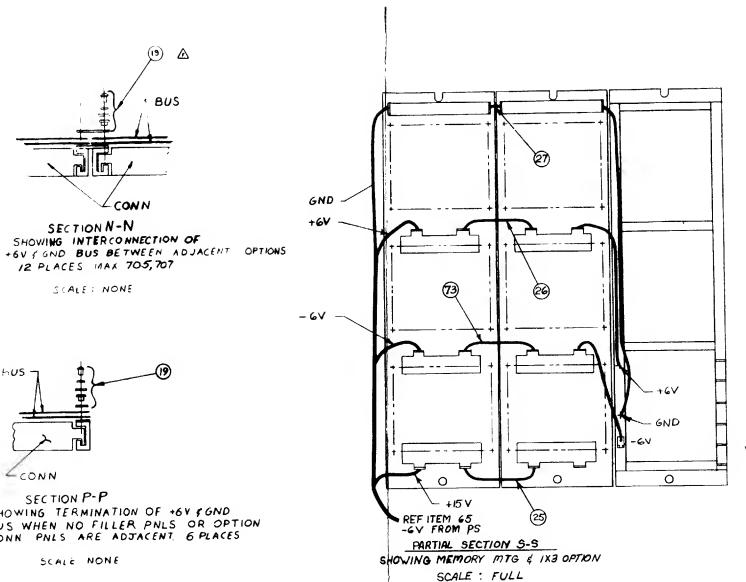
NORMAL POSITION A4 - 705, 707

SCALE : NONE



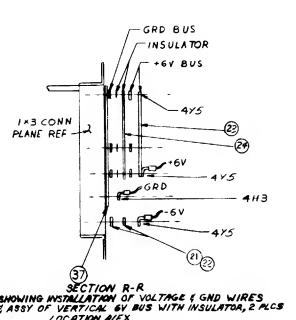
NOTE: ITEM 54 ONLY TO BE INSTALLED TO SECURE UNTERMINATED POWER WIRING IF NO OPTION (AI/A4) OR MEMORY/OPTION (E6) IS INSTALLED

◮

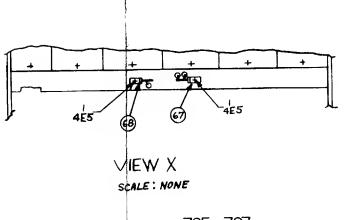


SHOWING TERMINATION OF +6V & GND BUS WHEN NO FILLER PNLS OR OPTION CONN PNLS ARE ADJACENT, 6 PLACES

HUS



SECTION R-R
SHOWING INSTALLATION OF VOLTAGE & GND WIRES
& ASSY OF VERTICAL 64 BUS WITH INSULATOR, 2 PLCS
LOCATION A/EX
SCALE: NONE



705, 707 ONLY CSM-150 MEMORY LOGIC DRAWER

SECTION R-R SHOWING INSTALLATION OF VOLTAGE & GRD WIRES & ASSY OF VERICAL GY BUS WITH INSULATOR LOCATION AIA4 SCALE : NONE

(37)

-GRD BUS -INSULATOR

-+6V BUS

Figure 3-10-5. Logic and Option Drawer Assembly (D70030064, Rev Z, Sheet 4 of 4)

CHAPTER IV MAINFRAME ILLUSTRATED PARTS BREAKDOWN

This chapter contains the illustrated parts breakdown (IPB) for the three configurations of the H316 General Purpose Computer: table top, rack-mountable, and rack-mounted, Types 316-01, 316-0100, and 316-0110, including control panel, chassis assembly, and memory. Options are documented in separate manuals.

GENERAL

The mainframe IPB is designed to aid logistical personnel in identification and procurement of replaceable parts including assemblies and components.

EQUIPMENT CODING

Coding drawings have been provided for use as an aid to further identify equipment.

METHODS OF USE

Locating a part in this chapter can be done in several ways. The method used depends upon the availability of information initially. Once having knowledge of the name of the assembly on which the part is located, find the assembly name listed in Table 4-1. Having obtained the location of the part, refer to Figures 4-1 and 4-2 in the Group Assembly Parts List and proceed as follows:

- a. Identify on the illustration the equipment rack and locate the unit within the rack, indicated by a block leader line containing a number (Index).
- b. Refer to the parts lists immediately following the illustration.
- c. Read the information as it applies.
- d. Refer to another illustration (figure) that presents a detailed breakdown of that assembly.
- e. Immediately following the breakdown illustration, the parts list will contain the following information:
 - 1. Figure and Index Number: Each illustration is identified by a figure number. Each illustration contains leader lines and index numbers that key the order in which the parts are identified in the parts list. The only exceptions are the PACs, which are keyed in a different manner.

- 2. <u>Designation</u>: Honeywell coding designation (refer to coding explanation and coding drawings).
- 3. <u>Honeywell Part Number</u>: Honeywell part numbers are given unless otherwise indicated by an asterisk.
- 4. Indenture: The relationship of an item to its next higher assembly (NHA) is indicated in this column. The "B" level is an inherent part of the first preceding "A" level. The "C" level is an inherent part of the first preceding "B" level, etc.
- 5. Description: This column may contain the following:
 - (a) Data sufficient to identify parts for ordering purposes.
 - (b) Instructions for locating a more detailed illustration for breakdown, i. e., "(See Figure 4-6 for breakdown)."
 - (c) Re-establishing how that particular figure was arrived at, i.e., "(Refer to Figure 4-5-1 for NHA)."
 - (d) Reference to the coding drawing for a better understanding of the coding technique used, i.e., "See Drawing Number 70023412, sheet 3 for coding drawing."
- 6. Quantity per Assembly: Each new figure is considered an assembly and the quantity indicated in the column is the unit quantity representing the total used common to that assembly. The appearance of "REF" indicates that the quantity was stated at its first appearance (NHA).

PARTS PROCUREMENT GUIDE

- 1. When ordering from this manual, always reference the model and serial number of the computer.
- 2. Give the location of the assembly where the part is used.
- 3. State the part number with the description given in this manual.
- 4. Direct all inquiries to the following address:

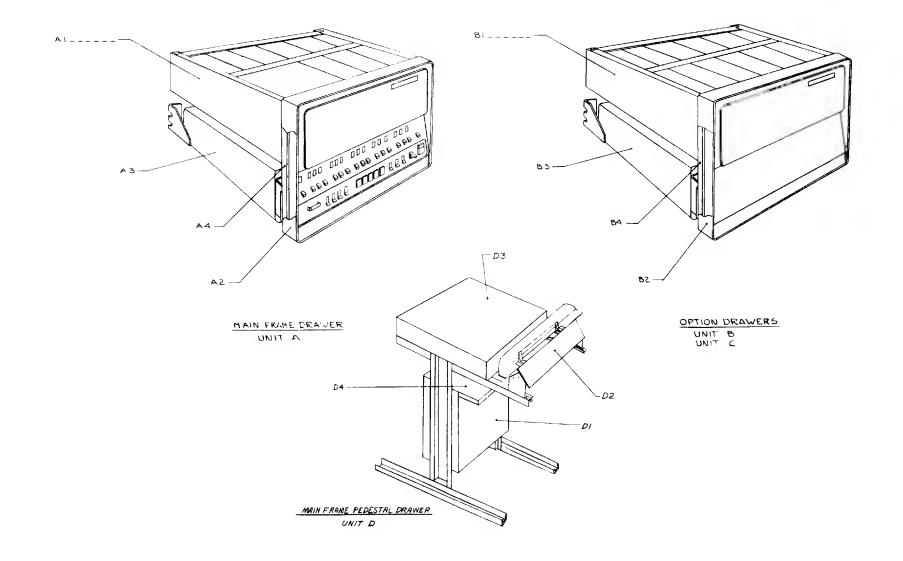
Honeywell Inc. Old Connecticut Path Framingham, Massachusetts 01701

Telephone: 617-879-2600 TWX: 710-380-6706

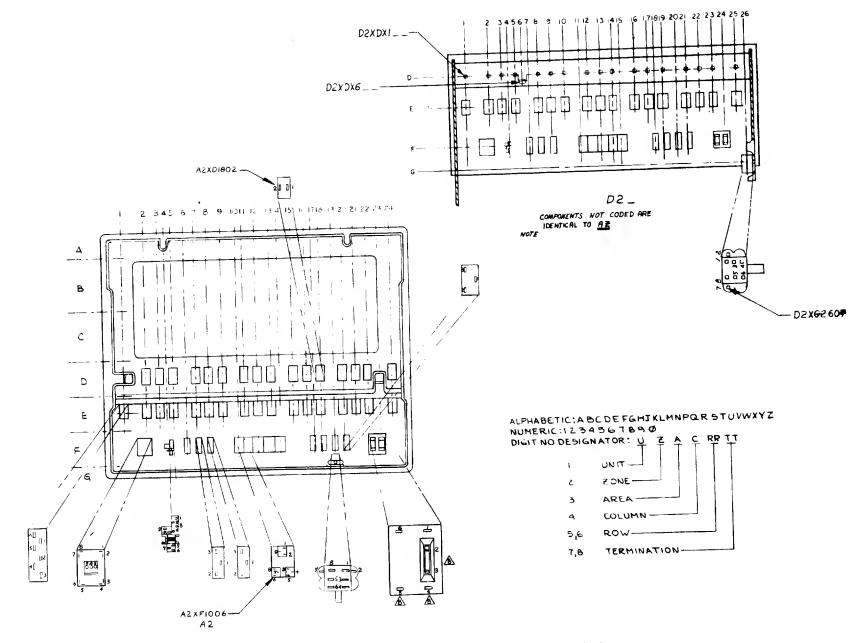
Important:

The illustrations shown are representative of all Honeywell Inc. H316 computers; therefore, the illustrations used may not show minor differences between industrial machines. If the differences are major, changes will be added to the illustration.

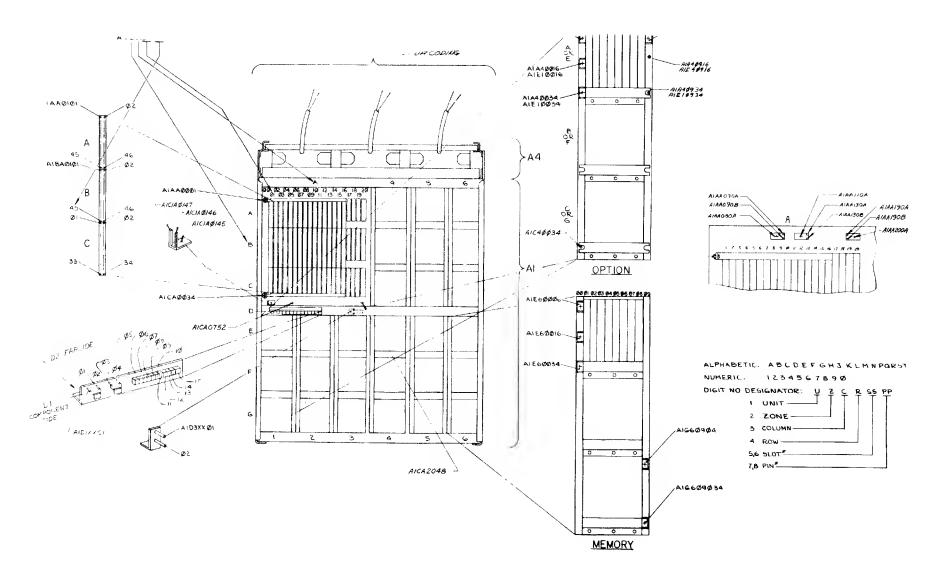
As changes are made to the equipment, this publication will be updated.



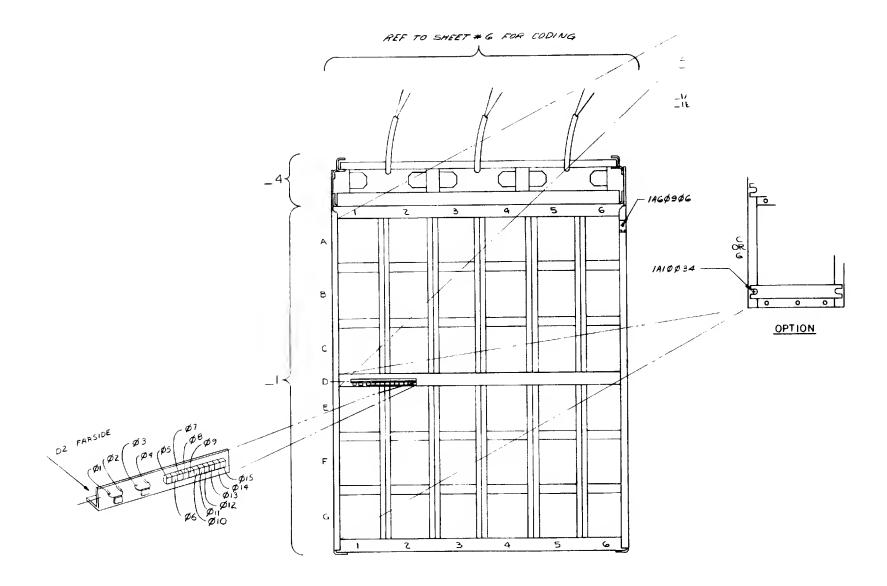
Coding Drawing No. 70023412, Rev P (Sheet 1 of 9)



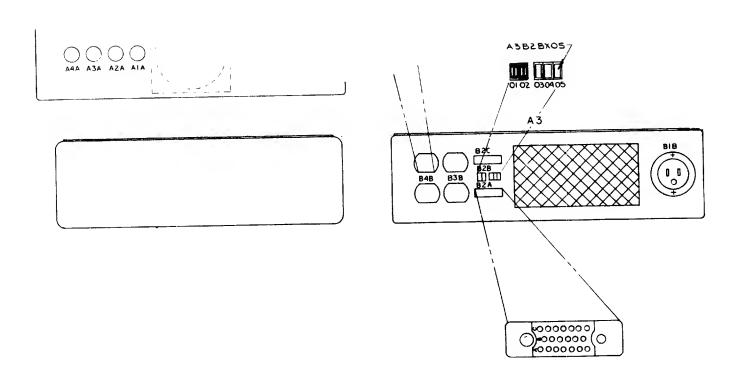
Coding Drawing No. 70023412, Rev P (Sheet 2 of 9)



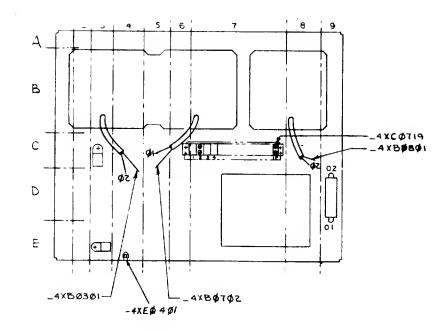
Coding Drawing No. 70023412, Rev P (Sheet 3 of 9)



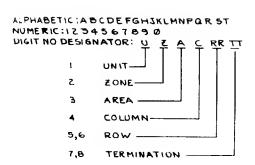
Coding Drawing No. 70023412, Rev P (Sheet 4 of 9)

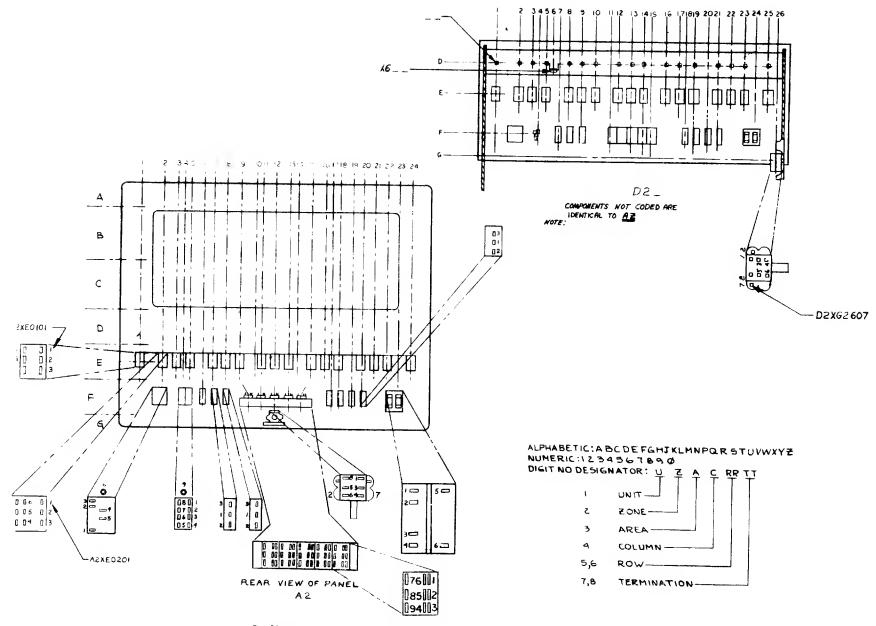


Coding Drawing No. 70023412, Rev P (Sheet 5 of 9)

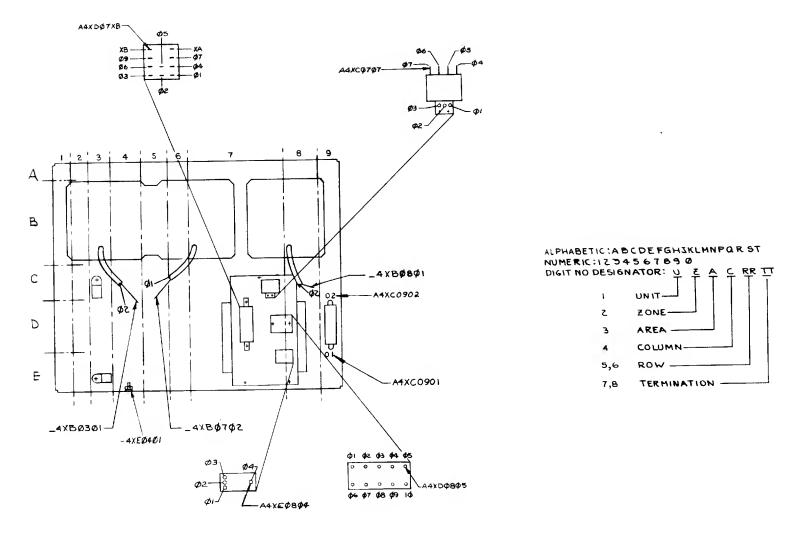


Coding Drawing No. 700224

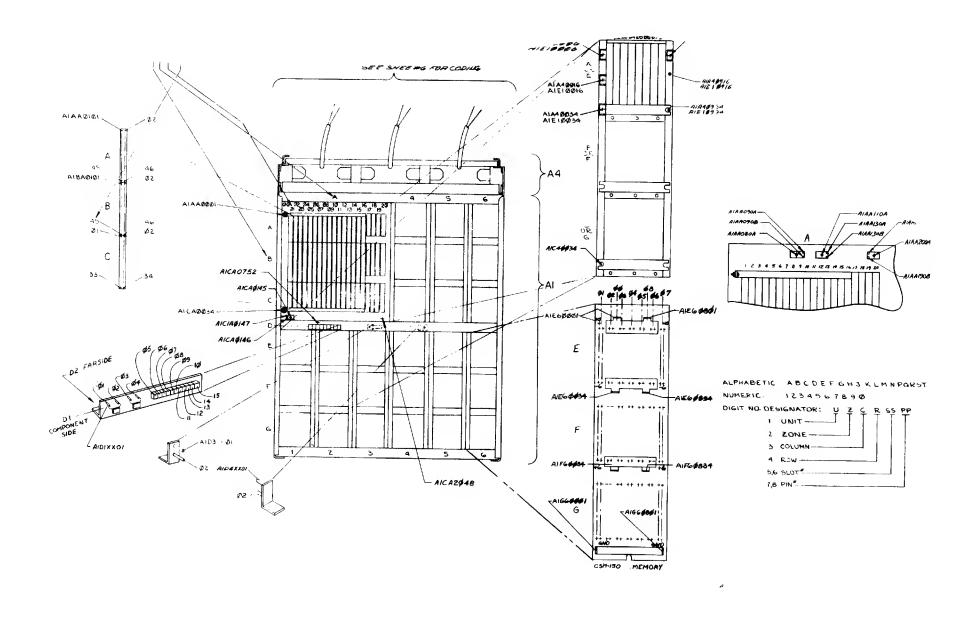




Coding Drawing No. 70023412, Rev P (Sheet 7 of 9)



Coding Drawing No. 70023412, Rev P (Sheet 8 of 9)



4-11

GROUP ASSEMBLY PARTS LIST

Table 4-1 lists the figure number used to locate the Group Assembly Parts List for a particular subassembly

Table 4-1 Figure Number Cross Reference

Fig. No.	Description	Part No.
4-1	H316 General Purpose Computer, Rack-Mounted Model, Type 316-01	70023278501
4-2	H316 General Purpose Computer, Rack-Mounted Model, Types 316-0100 and 316-0110	70030063701
4-3	H316 General Purpose Computer, Table Top Model, Type 316-01	70023278703
4-4	H316 General Purpose Computer, Table Top Model, Types 316-0100 and 316-0110	70030071703
4-5	Control Panel, Type 316-01	70023065
4-6	Control Panel, Types 316-0100 and 316-0110	70030065
4-7	Chassis Assembly, Type 316-01	70023235
4-8	Chassis Assembly, Types 316-0100 and 316-0110	70030054701
4-9	Mainframe Logic and Option Drawer Assembly, Type 316-01	70023232
4-10	Mainframe Logic and Option Drawer Assembly, Types 316-0100 and 316-0110	70030064701
4-11	CSM-160 Core Memory Unit, Types 316-01, 316-0100, and 316-0110	70023577
4-12	CSM-150 Core Memory Unit, Types 316-01, 316-0100, and 316-0110	70032935
4-13	Logic Module Layout, Types 316-01, 316-0100, and 316-0110	No number
4-14	Cable Block Diagram	No number
4-15	Cable Assembly, Power, Electrical, Type 316-01	70023838701
4-16	Cable Assembly, Power, Electrical, Types 316-0100 and 316-0110	70030072701
4-17	Cable Assembly, Power, Electrical, Types 316-01, 316-0100, and 316-0110	70023837701
4-18	Cable Assembly, Special Purpose, Type 316-01	70024016701
4-19	Cable Assembly, Special Purpose, Types 316-0100 and 316-0110	70029942701
4-20	Cable Assembly, Special Purpose, Type 316-01	70024010701
4-21	Cable Assembly, Special Purpose, Types 316-0100 and 316-0110	70029943701
4-22	Cable Assembly, Special Purpose, μ -PAC to μ -PAC, Types 316-01, 316-0100, and 316-0110	70013826701



Figure 4-1. H316 General Purpose Computer, Rack-Mounted Model, Type 316-01

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-1-	Α	70023278701	A	H316 GENERAL PURPOSE COMPUTER, RACK-MOUNTED MODEL, TYPE 316-01.	
-1	A2	70023065	В	CONTROL PANEL ASSEMBLY (see Figure 4-5 for breakdown and Coding Drawing No. 70023412, Sheet 2).	1
-2	A4	70023235	В	CHASSIS ASSEMBLY (see Figure 4-7 for breakdown and Coding Drawing No. 70023412, Sheet 6).	1
-3	Al	70023232	В	MAINFRAME LOGIC AND MEMORY DRAWER (see Figure 4-9 for breakdown and Coding Drawing No. 70023412, Sheet 3).	1
-4	A3	70960061001	В	POWER SUPPLY (see Coding Drawing No. 70023412, Sheet 5).	



Figure 4-2. H316 General Purpose Computer, Rack-Mounted Model, Types 316-0100 and 316-0110

Fig. & Index	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-2-	A	70030063701	А	H316 GENERAL PURPOSE COMPUTER, RACK-MOUNTED MODEL, TYPES 316-0100 and 316-0110.	
-1	A2	70030065	В	CONTROL PANEL ASSEMBLY (see Figure 4-6 for breakdown and Coding Drawing No. 70023412, Sheet 7).	1
-2	A4	70030054	В	CHASSIS ASSEMBLY (see Figure 4-8 for breakdown and Coding Drawing No. 70023412, Sheet 8).	1
-3	Al	70030064701	В	MAINFRAME LOGIC AND MEMORY DRAWER (see Figure 4-10 for breakdown and Coding Drawing No. 70023412, Sheet 3).	1
-4	A3	70023699	В	POWER SUPPLY (see Coding Drawing No. 70023412, Sheet 5).	1

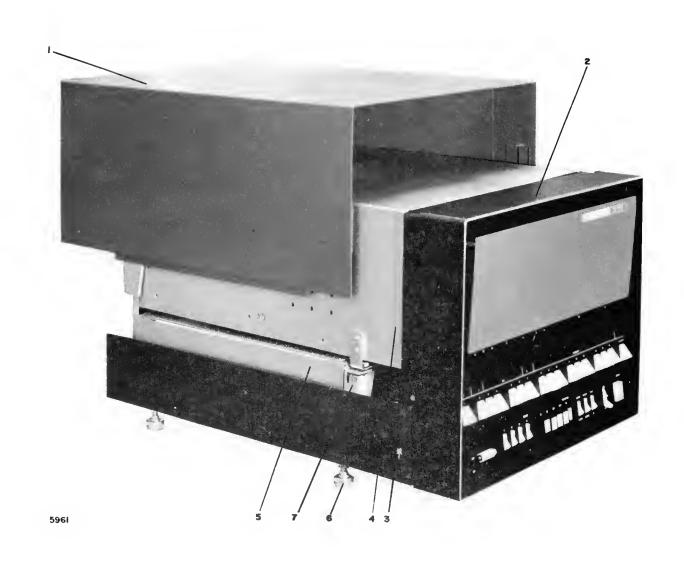


Figure 4-3. H316 General Purpose Computer, Table Top Model, Type 316-01

Fig. & Index	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-3-	Α	70023278703	Α	H316 GENERAL PURPOSE COMPUTER, TABLE TOP MODEL, TYPE 316-01.	
-1	1	70023697701	В	COVER TOP.	1
-2	A2	70023065	В	CONTROL PANEL ASSEMBLY (same as Rack-Mounted Model, see Figure 4-5 for breakdown).	1
-3	A4	70023235701	В	CHASSIS ASSEMBLY (same as Rack- Mounted Model, see Figure 4-7 for breakdown).	1
-4	Al	70023232701	В	MAINFRAME LOGIC AND MEMORY DRAWER (same as Rack-Mounted Model; see Figure 4-9 for breakdown).	1
- 5	A3	70023699701	В	POWER SUPPLY, MODIFIED (same as Rack Mounted Model except for mounting hardware).	1
- 6		912251001	С	LEVELING FOOT.	4
-7		906320002	С	SNAPSLIDE FASTENER.	2

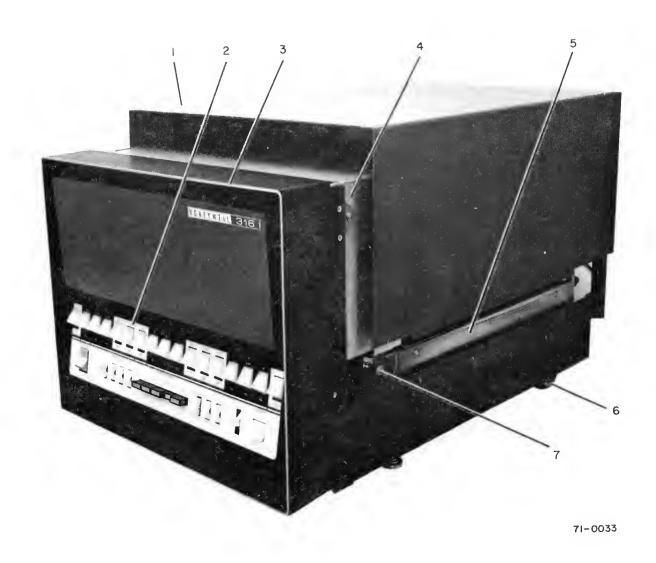


Figure 4-4 H316 General Purpose Computer, Table Top Model, Types 316-0100 and 316-0110

Fig. & Index	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-4-	A	70030071703	A	H316 GENERAL PURPOSE COMPUTER, TABLE TOP MODEL, TYPES 316-0100 and 316-0110.	
-1		70023697701	В	COVER TOP.	1
-2	A2	70030065	В	CONTROL PANEL ASSEMBLY (same as Rack-Mounted Model, see Figure 4-6 for breakdown).	1
-3	A4	70030054701	В	CHASSIS ASSEMBLY (same as Rack- Mounted Model, see Figure 4-8 for breakdown).	1
-4	Al	70030064	В	MAINFRAME LOGIC AND MEMORY DRAWER (same as Rack-Mounted Model, see Figure 4-10 for breakdown).	1
-5	A3	70023699701	В	POWER SUPPLY, MODIFIED (same as Rack-Mounted Model except for mounting hardware).	1
-6		912251001	С	LEVELING FOOT.	4
-7		906320002	С	SNAPSLIDE FASTENER.	2

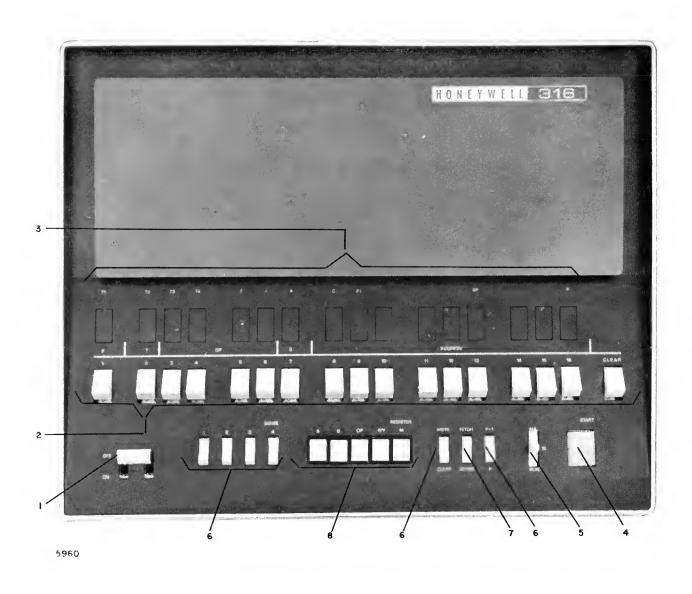


Figure 4-5. Control Panel, Type 316-01

Fig. & Index No.	Designation	Part No.	Inden- ture	Description	Qty per Ass'y
4-5-	A2	70023065	В	CONTROL PANEL ASSEMBLY (Refer to Figure 4-1-1 and 4-3-1, Type 316-01 for NHA)	Ref.
- 1	A2E23	70960056001	С	CIRCUIT BREAKER, DOUBLE POLE: 1st pole series trip at 30A, 250 Vac 50/60 Hz, curve 3; 2nd pole relay trip 6 Vdc, 50 mA curve p.	1
-2	A2E24, 22, 21, 20, 18, 16, 15, 13, 12, 11, 09, 08, 07, 05, 03, 02, 01	70934278001	C	SWITCH PUSH-ROCKER DPDT: 60A ac; 0.5A dc.	17
		70023068701	С	BUTTON, CAP-MOLDED LIGHT: grey plastic; 0.527 by 0.912 inch.	17
-3	A2D24, 22, 21, 20, 18, 16, 15, 13, 12, 11, 09, 08, 07, 05, 03, 02,	70908281001	С	HOUSING, LIGHT INDICATOR.	16
		70935081203	С	LIGHT, INDICATOR: 28V at 0.04A; yellow lens.	16
-4	A2F2		С	PUSHBUTTON LIGHT INDICATOR ASSEMBLY CONSISTING OF:	1
		70935031002	D	LAMPHOLDER ASSEMBLY: short flange type	1
		70910353001	D	LENS SWITCH ACTUATOR.	1
		70934263001	D	SWITCH, PUSH - SPDT: 5A at 250V.	1
		70945002002	D	LAMP, INCANDESCENT: 0.04 A at 28V 7-1 3/4 bulb, midget flange base.	2
- 5	A2F4	70934020003	С	SWITCH, LEVER LOCKING: 3 position, 3A, 200 W.	1
-6	A2F06,08, 17,18,19,20	70934276001	С	SWITCH, PUSH, ROCKER - SPDT: 6A at 125 Vac, 3A at 250 Vac; 1.0 A dc.	6
-7	A2F07	70934272001	С	SWITCH, PUSH, ROCKER - SPDT: 6A at 125 Vac; 3A at 250 Vac, 1.0 A dc.	1
-8	A2F10,11,12 13,14		С	PUSHBUTTON ASSEMBLY CONSISTING OF:	1
		70934275001	D	SWITCH, PUSH, INTERLOCK: 5 station interlock; 3A, 300W max; ac noninductive load.	1
		70910303001	D	PUSHBUTTON: molded plastic, black/white face.	5
		70943083002	D	SEMICONDUCTOR DEVICE, DIODE: silicon type.	1

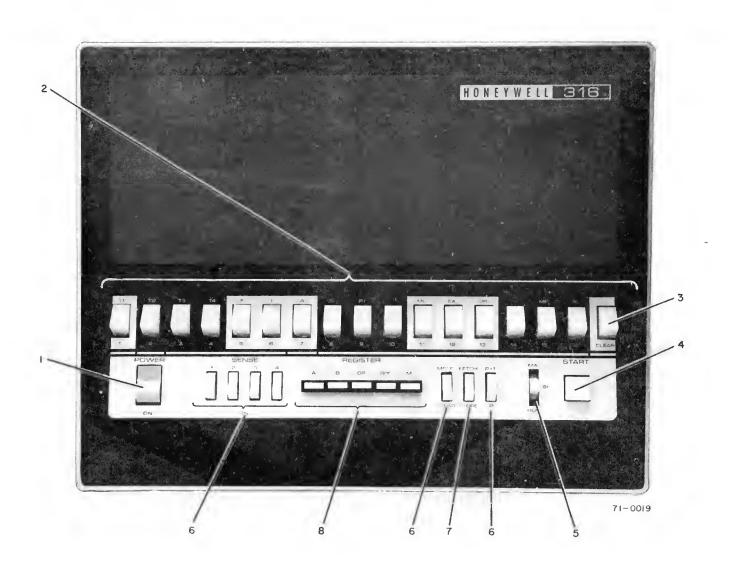


Figure 4-6. Control Panel, Types 316-0100 and 316-0110

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-6-	A2	70030065	В	CONTROL PANEL ASSEMBLY (Refer to Figures 4-2-1 and 4-4-1, Types 316-0100 and 316-0110 for NHA).	Ref.
-1	A2E23	70960058001		CIRCUIT BREAKER, DOUBLE POLE: lst pole series trip at 30A, 250 Vac 50/60 Hz, curve 3; 2nd pole relay trip 6 Vdc, 50 mA curve p.	1
-2	A2E24, 22, 21, 20, 18, 16, 15, 13,	70934284001		SWITCH PUSH-ROCKER DPDT: 60A ac; 0.5A dc.	16
-3	12, 11, 09, 08, 07, 05, 03, 02, 01	70934283001		SWITCH PUSH SPDT.	1
-4	A2F2	70934287001		PUSHBUTTON LIGHT INDICATOR ASSEMBLY:	1
- 5	A2F4	7093428801		SWITCH, LEVER LOCKING: 3 position, 3A, 200W	1
-6	A2F06,08, 17,18,19, 20	70934285001		SWITCH, PUSH, ROCKER - SPDT; 6A at 125 Vac, 3A at 250 Vac; 1.0A dc.	6
-7	A2F07	70934285002		SWITCH, PUSH, ROCKER - SPDT: 6A at 125 Vac; 3A at 250 Vac; 1.0A dc.	1
-8	A2F10,11, 12,13,14	70934286001		PUSHBUTTON ASSEMBLY.	1

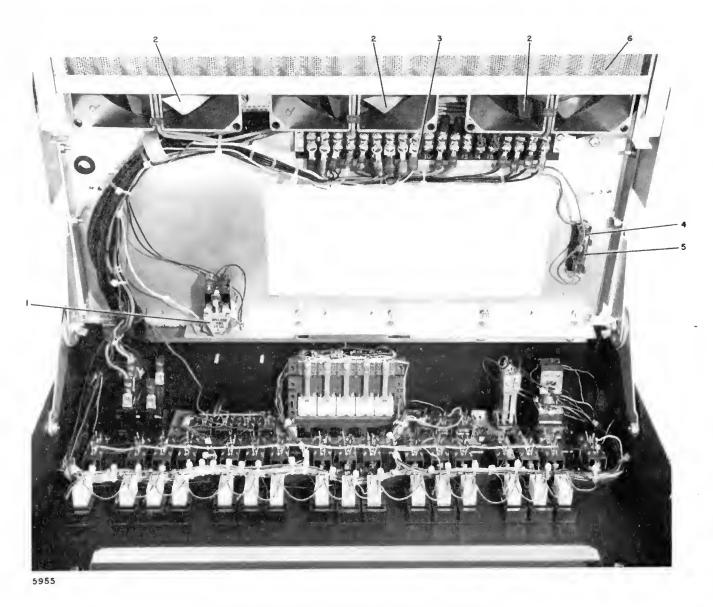


Figure 4-7. Chassis Assembly, Type 316-01

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-7-	A4	70023235701	В	CHASSIS ASSEMBLY, TYPE 316-01 (Refer to Figures 4-1-2 and 4-2-2 for NHA).	Ref
-1	A4E03	70963015007	С	RELAY ARMATURE - DPDT: l sec delay contacts rated 5A, 125/250Vac; coils 24 Vdc, 2W continuous duty.	1
-2	A4B03, 06, 08	70964007001	С	FAN AXIAL: 4.13 in. square by 1.970 in. thick.	3
-3	A4C07	70937502019	С	TERMINAL BOARD: barrier type; 19 terminals; 20A rated, black molded bakelite.	1
-4	A4D09	7096002005	С	FUSE, CARTRIDGE: 0.5A; 250V; 1/4 in. diameter by 1-1/4 in. long instantaneous - Littelfuse 312.500.	1
- 5	A4D09	70935008001	С	FUSEHOLDER: indicating types accom. 1/4 in. by 1-1/4 diameter fuse, rated 30A at 90 to 250V.	1
-6		70911003701	С	FILTER, AIR CONDITIONING.	1

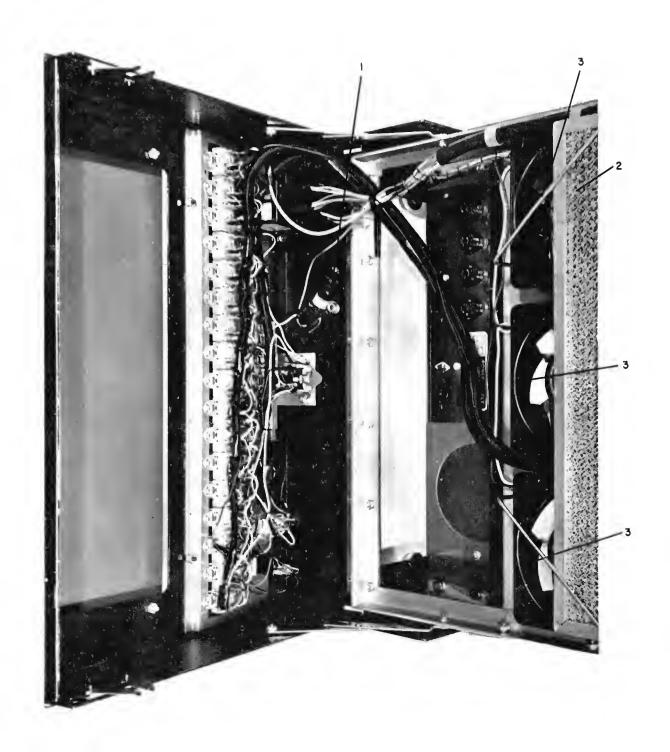


Figure 4-8. Chassis Assembly, Types 316-0100 and 316-0110

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-8-	A4	70030054701	В	CHASSIS ASSEMBLY, TYPES 316-0100 and 316-0110 (Refer to Figures 4-2-2 and 4-4-2 for NHA).	Ref.
-1		70960002005	С	FUSE, CARTRIDGE: 0.5A; 250V; 1/4 in diameter by 1-1/4 in. long instantaneous. Littelfuse 312.500.	. 1
		70935011002	С	FUSEHOLDER, IN-LINE: indicating types accom. 1/4 in. by 1-1/4 in. diameter fuse, rated 30A at 90 to 250V.	1
-2		70911003009	С	FILTER, AIR CONDITIONING.	1
-3	A4B03, 06,08	70964008006	С	FAN, AXIAL: 4.13 in square by 1.970 in. thick.	

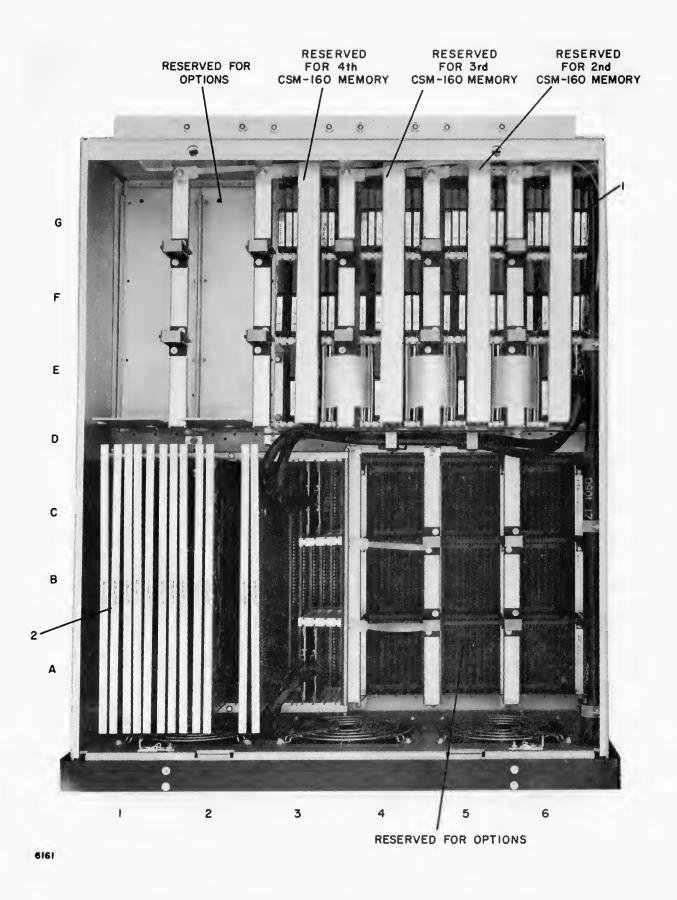
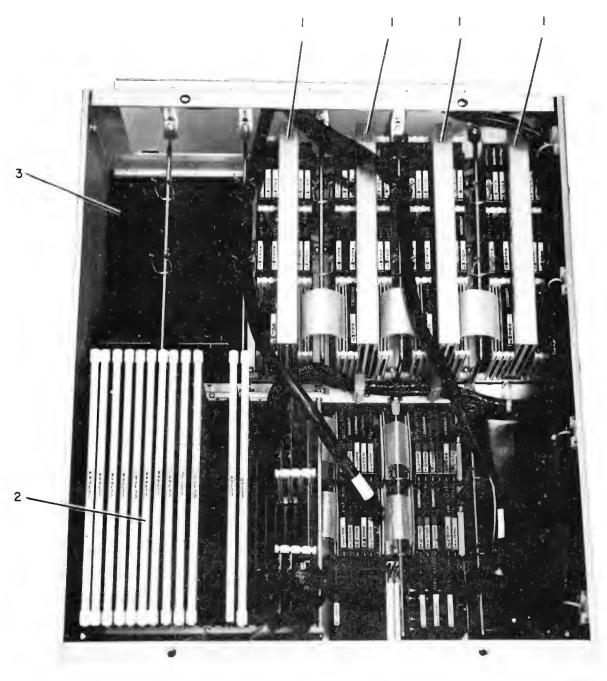


Figure 4-9. Mainframe Logic and Option Drawer Assembly, Type 316-01

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-9-	Al	70023232701	В	LOGIC AND OPTION DRAWER ASSEMBLY, TYPE 316-01 (Refer to Figures 4-1-3 and 4-4-4 for NHA).	Ref
-1		70023577704	С	CORE MEMORY UNIT (see Figures 4-11 and 4-12 for breakdown).	1
-2		No number	С	LOGIC PAC LAYOUT (see Figure 4-13 for breakdown).	1



71-0021

Figure 4-10. Mainframe Logic and Option Drawer Assembly, Types 316-0100 and 316-0110

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-10-	Al	70030064701	В	LOGIC AND OPTION DRAWER ASSEMBLY, TYPES 316-0100 and 316-0110 (Refer to Figures 4-2-3 and 4-4-4 for NHA).	Ref
-1		70023577704	С	CORE MEMORY UNIT (see Figures 4-11 and 4-12 for breakdown).	1
-2		No number	С	LOGIC PAC LAYOUT (see Figure 4-13 for breakdown).	1
-3		70030069001		PLATE FILLER.	Ref

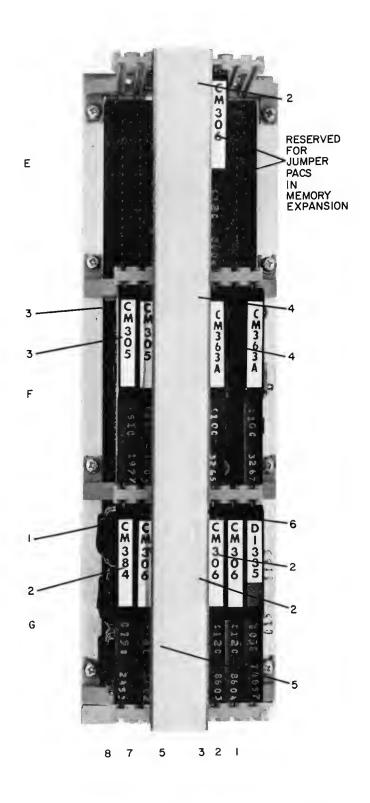


Figure 4-11. CSM-160 Core Memory Unit, Types 316-01, 316-0100, and 316-0110

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-11-	AIE-G	70023577	С	CSM-160 CORE MEMORY UNIT (Refer to Figure 4-10-1 for NHA).	Ref
-l	A1G608	CM-384	D	RESISTOR PAC (see Chapter II, Section 5 for breakdown).	1
-2	A1G607, A1E603, A1G602, A1G603	CM-306	D	SELECTOR PAC (see Chapter II, Section 5 for breakdown).	4
-3	A1F607, 08	CM-305	D	INHIBIT PAC (see Chapter II, Section 5 for breakdown)	2
-4	A1F601, 03	CM-363A	D	SENSE AMPLIFIER PAC (see Chapter II, Section 5 for breakdown).	2
- 5	A1G04 A1G05	70	D	CORE STACK: 4096 words, 16 bits per word.	1
-6	A1G601	DI-375	D	NAND PAC (See Chapter II, Section 5, for breakdown).	1

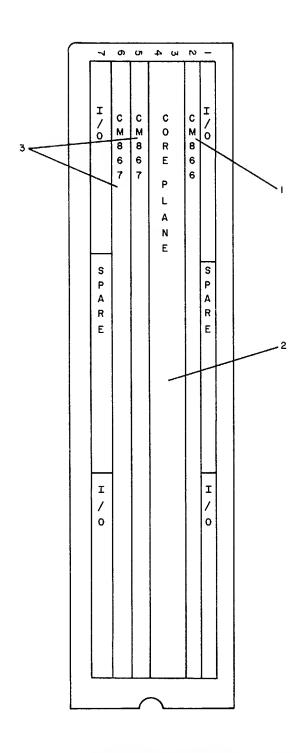


Figure 4-12. CSM-150 Core Memory Unit, Types 316-01, 316-0100, and 316-0110

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-12-	AIE -G	70032935	С	CSM-150 CORE MEMORY UNIT (Refer to Figure 4-10-1 for NHA).	Ref
-1	A1E602	CM-866	D	ADDRESS BOARD (see Chapter III, Section 10 for breakdown).	1
-2	A1E603 A1E604	70	D	CORE STACK: 8192 words, 17 bits per word.	1
-3	A1E605 A1E606	CM-867	D	DATA BOARD (See Chapter III, Section 10 for breakdown).	2

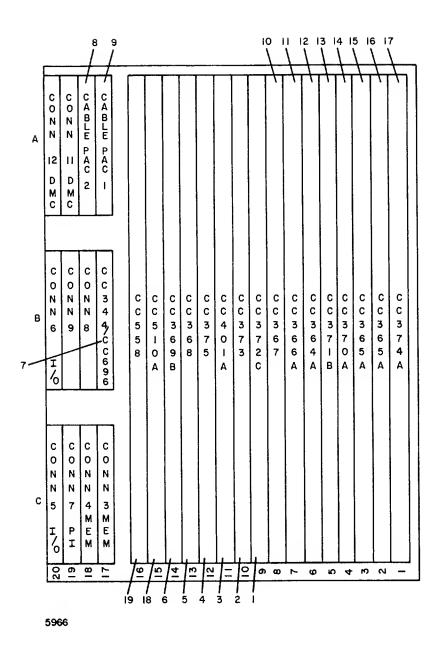


Figure 4-13. Logic Module Layout

Fig. & Index No.	Designation	Part No.	Inden- ture	Description	Qty per Ass'y
4-13-	AlBA	No Number	С	LOGIC PAC LAYOUT - PAC SIDE VIEW (Refer to Figure 4-9-2 and 4-10-2 for NHA).	Ref
- 1	AlAA09	CC-372C	D	REGULATOR COUNTER MODULE (See Chapter I, Section 2 for breakdown).	1
-2	A1AA10	CC-373	D	MEMORY MODULE (See Chapter I, Section 2 for breakdown).	1
-3	AlAAll	CC-401	D	HIGH SPEED A-U No. 2 MODULE (See Chapter I, Section 2 for breakdown).	1
-4	A1AA12	CC-375	D	HIGH SPEED A-U No. 1 MODULE (See Chapter I, Section 2 for breakdown).	1
- 5	A1AA13	CC-368	D	SHIFT REGISTOR MODULE (See Chapter I, Section 2 for breakdown).	1
-6	AlAAl4	CC-369B	D	LAMP DRIVER MODULE (See Chapter I, Section 2 for breakdown).	1
-7	A1BA17	CC-344/ CC-696	D	REAL TIME CLOCK PAC (See Real Time Clock Option Instruction Manual Doc. No. 70130072179A for breakdown).	1
-8	A1AA18	CC-080 CC-681*	D	CABLE PAC (See Chapter I, Section 2 for breakdown).	1
-9	AlAAl7	CC-079 CC-672*	D	CABLE PAC (See Chapter I, Section 2 for breakdown).	1
-10	AlAA08	CC-367	D	ADDRESS BUS MODULE (See Chapter I, Section 2 for breakdown).	1
-11	AlAA07	CC-366 A	D	COLUMNS 9-12 MODULE (See Chapter I, Section 2 for breakdown).	1
-12	A1AA06	CC-364A	D	COLUMNS 1-4 MODULE (See Chapter I, Section 2 for breakdown).	1
-13	AlAA05	CC-371B	D	CLOCK MODULE (See Chapter I, Section 2 for breakdown).	1
-14	AlAA04	CC-370A	D	M REGISTOR MODULE (See Chapter I, Section 2 for breakdown)	1
-15, -16	AlAA02,03	CC-365A	D	COLUMNS A-D MODULE (See Chapter I, Section 2 for breakdown).	2
-17	AlAA01	CC-374A	D	ASR INTERFACE MODULE (See Chapter I, Section 2 for breakdown)	1
-18	AlAA15	CC-510A	D		1
-19	Alaal6	CC-558	D		1

^{*}Used in Type 316-0100 only

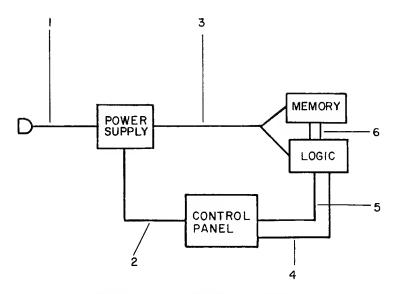


Figure 4-14. Cable Block Diagram

Fig. & Index No.	Type	Part No.	Inden- ture	Description	Qty per Ass'y
4-14-			A	CABLING BLOCK DIAGRAM.	Ref
- 1	316-01	940252003	В	CABLE ASSEMBLY, POWER: Electrical, 12 ft overall length.	1
	316-0100	940252002	В	CABLE ASSEMBLY, POWER: Electrical, 9 ft overall length.	1
-2	316-01	70023838701	В	CABLE ASSEMBLY, POWER: Electrical Power Supply to Control Panel, 9 ft overall length (see Figure 4-15 for breakdown).	l
	316-0100	70030072703	В	CABLE ASSEMBLY, POWER: Electrical Power Supply to Control Panel; 9 ft overall length (see Figure 4-16 for breakdown).	1
-3	Both types	70023837705	В	CABLE ASSEMBLY, POWER: Electrical Power Supply to Logic Drawer, 10 ft. overall length (see Figure 4-17 for breakdown).	1
-4	316-01	7024016701	В	CABLE ASSEMBLY, SPECIAL PURPOSE: Control Panel Cable No. 1 (see Figure 4-18 for breakdown).	1
	316-0100	70029942701	В	CABLE ASSEMBLY, SPECIAL PURPOSE: Control Panel Cable No. 1 (see Figure 4-19 for breakdown).	1
-5	316-01	7024010701	В	CABLE ASSEMBLY, SPECIAL PURPOSE: Control Panel Cable No. 2 (see Figure 4-20 for breakdown).	1
	316-0100	70029943701	В	CABLE ASSEMBLY, SPECIAL PURPOSE: Control Panel Cable No. 2 (see Figure 4-21 for breakdown).	1
-6	Both types	70032670703	В	CABLE ASSEMBLY, SPECIAL PURPOSE: μ -PAC to μ -PAC, 2 ft overall length (see Figure 4-22 for breakdown).	2

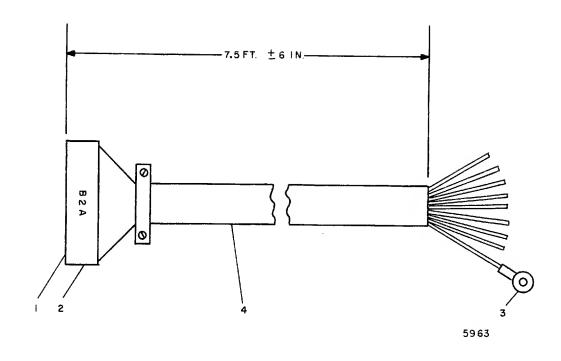


Figure 4-15. Cable Assembly, Power, Electrical, Type 316-01

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-15-		7023838701	В	CABLE ASSEMBLY, POWER: Electrical (Refer to Figure 4-14-2 for NHA).	Ref
-1	B2A	70941371001	С	CONNECTOR, PLUG, ELECTRICAL.	1
-2		70941571001	С	PLUG TIP, MALE.	15
-3	AXC	70937058003	С	TERMINAL LUG.	15
-4		70981002024	С	SLEEVING, ELECTRICAL.	8 ft

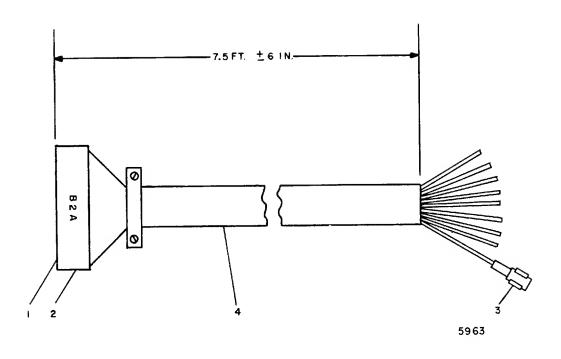


Figure 4-16. Cable Assembly, Power, Electrical, Types 316-0100 and 316-0110

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-16-		70030072703	В	CABLE ASSEMBLY, POWER: Electrical (Refer to Figure 4-14-2 for NHA).	Ref
-1	B2A	70941341003	С	CONNECTOR, PLUG, ELECTRICAL.	1
-2	•	70941571001	С	PLUG TIP, MALE.	15
-3	AXC	70937200001	С	TERMINAL.	6
-4		70981002021	С	SLEEVING, ELECTRICAL.	9 Ft

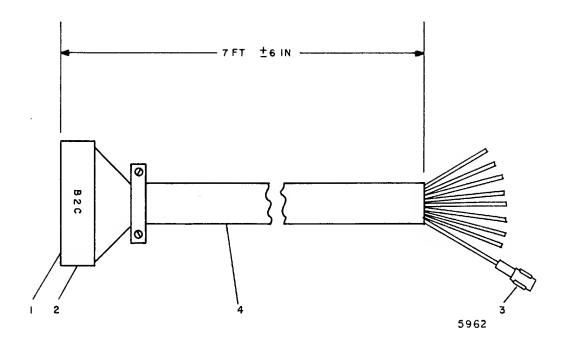


Figure 4-17. Cable Assembly, Power, Electrical, Types 316-01, 316-0100 and 316-0110

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-17-		7023837705	В	CABLE ASSEMBLY, POWER: Electrical (Refer to Figure 4-14-3 for NHA).	Ref
-1	B2C	70941341001	С	CONNECTOR, PLUG, ELECTRICAL.	1
-2		70941571001	С	PLUG TIP, MALE.	13
-3	AlD	70937200001	С	TERMINAL, QUICK DISCONNECT.	11
-4		70981002023	С	SLEEVING, ELECTRICAL.	8 Ft

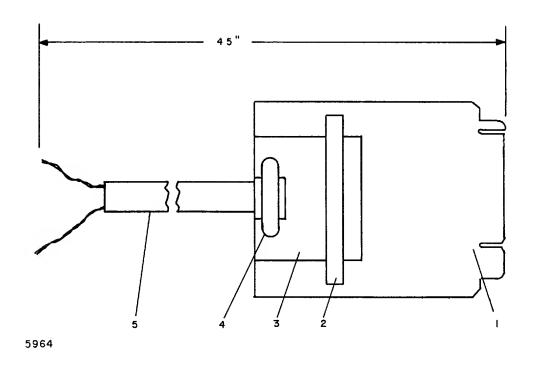


Figure 4-18. Cable Assembly, Special Purpose, Control Panel Cable No. 1, Type 316-01

Fig. & Index	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-18-		70024016701	В	CABLE ASSEMBLY, SPECIAL PURPOSE, CONTROL PANEL CABLE NO. 1, TYPE 316-01 (Refer to Figure 4-14-4 for NHA).	Ref
-1	A1AA17	CC-079	C.	CABLE PAC (See Figure 4-13-9 for PAC location and Chapter I, Section 2 for breakdown).	Ref
-2		70013624001	С	BRACKET, CLAMPING.	l
-3		70013626001	С	PLATE.	l
-4		70013623001	С	CLAMP.	l
-5		70940359001	С	CABLE, SPECIAL, ELECTRICAL.	4 Ft

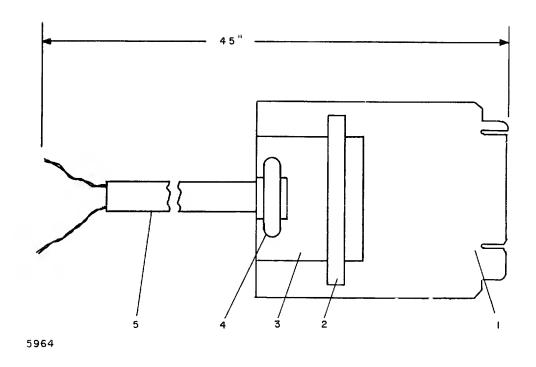


Figure 4-19. Cable Assembly, Special Purpose, Control Panel Cable No. 1, Types 316-0100 and 316-0110

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-19-		70029942701	В	CABLE ASSEMBLY SPECIAL PURPOSE, CONTROL PANEL CABLE NO. 1, TYPES 316-0100 and 316-0110 (Refer to Figure 4-14-4 for NHA).	Ref
-1	AlAA17	CC-672	С	CABLE PAC (See Figure 4-13-9 for PAC location and Chapter 1, Section 2 for breakdown).	Ref
-2		70013624001	С	BRACKET, CLAMPING.	1
-3		70029335001	С	PLATE.	1
-4		70029261001	С	CLAMP.	1
-5		70940161001	С	CABLE, SPECIAL, ELECTRICAL.	4 Ft

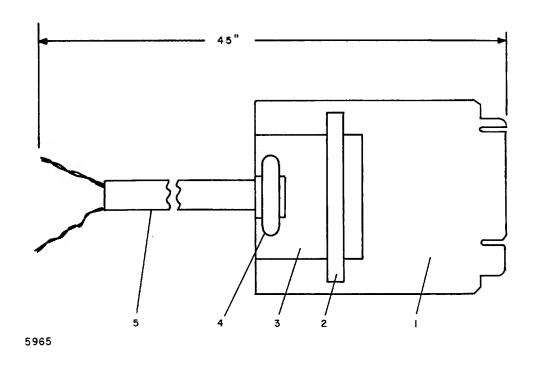


Figure 4-20. Cable Assembly, Special Purpose, Control Panel Cable No. 2, Type 316-01

Fig. & Index	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-20-		70024010201	В	CABLE ASSEMBLY, SPECIAL PURPOSE, CONTROL PANEL CABLE NO. 2, TYPE 316-01 (Refer to Figure 4-14-5 for NHA).	
-1	AlAA18	CC -080	С	CABLE PAC (See Figure 4-13-8 for PAC location and Chapter I, Section 2 for breakdown).	Ref
-2		70013624001	С	BRACKET, CLAMPING.	1
-3		70013626001	С	PLATE.	1
-4		70013623001	С	CLAMP.	1
-5		70940359001	С	CABLE, SPECIAL, ELECTRICAL.	4 Ft

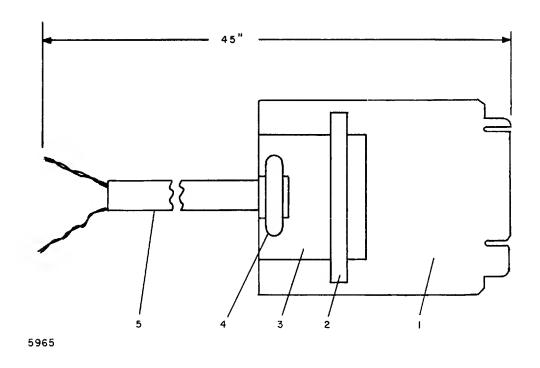


Figure 4-21 Cable Assembly, Special Purpose, Control Panel Cable No. 2, Types 316-0100 and 316-0110

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-21-		70029943701	В	CABLE ASSEMBLY, SPECIAL PURPOSE, CONTROL PANEL CABLE NO. 2, TYPES 316-0100 and 316-0110 (Refer to Figure 4-14-5 for NHA).	Ref
-1	AlAAl8	CC-681	С	CABLE PAC (See Figure 4-13-8 for PAC location and Chapter I, Section 2 for breakdown).	Ref
-2		70013624001	C.	BRACKET, CLAMPING.	l
-3		70029335001	С	PLATE.	1
-4		70029261001	С	CLAMP.	1
-5		70940159001	С	CABLE, SPECIAL, ELECTRICAL.	4 Ft.

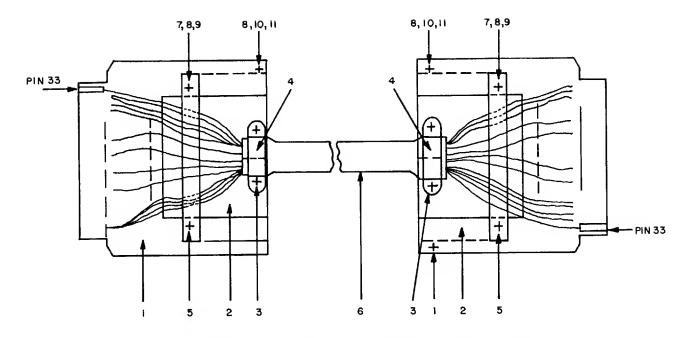


Figure 4-22. Cable Assembly, Special Purpose, μ -PAC to μ -PAC, for Types 316-01, 316-0100, and 316-0110 (Drawing No. A70032670 Rev C)

Fig. & Index No.	Designation	Part No.	Inden- ture	Description	Qty per Ass'y
4-22-		70032670703	В	CABLE ASSEMBLY, μ-PAC to μ-PAC (Refer to Figure 4-14-6 for NHA).	Ref
-1	·	70013767701	В	PC CBL PAC.	2
-2		70013626001	В	Plate.	2
-3		70904109001	С	Screw, No. 2-56 x 1/8 in.	4
-4		70032671001	С	Clamp.	2
-5		70013624001	С	Bar, Clamping.	2
-6		70940377001	С	Cable, 32 Twisted Pair.	A/R
-7		70902050001	С	Washer, Flat, No. 2.	4
-8		70902006039	С	Washer, Lock, Split, No. 2.	12
-9		70982152003	С	Cable Marker .	2
-10		70904109002	С	Screw, No. 2-56 x 3/16 in.	8
-11		70902050002		Washer, Flat, No. 2.	4

SECTION 2 ILLUSTRATED PARTS BREAKDOWN

This section contains the illustrated parts breakdown (IPB) of the power supply for both rack-mounted and table top models of the Ault Power Supply Model PR-130, used in the H316 General Purpose Computer.

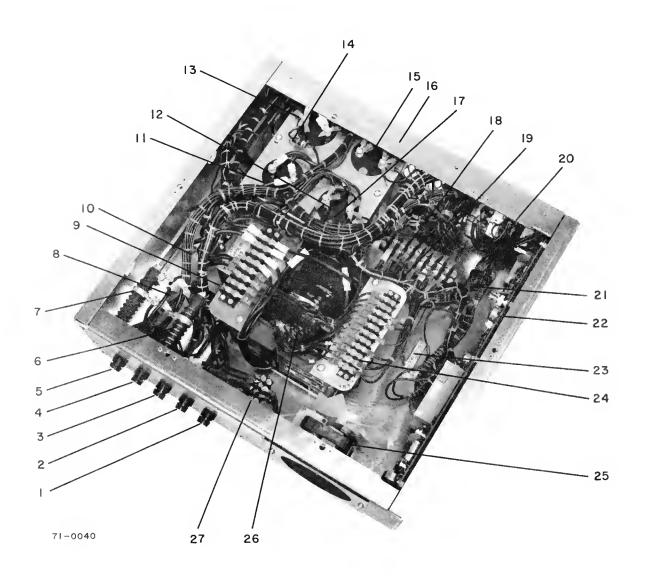


Figure 4-23. Power Supply, Rack-Mounted Configuration

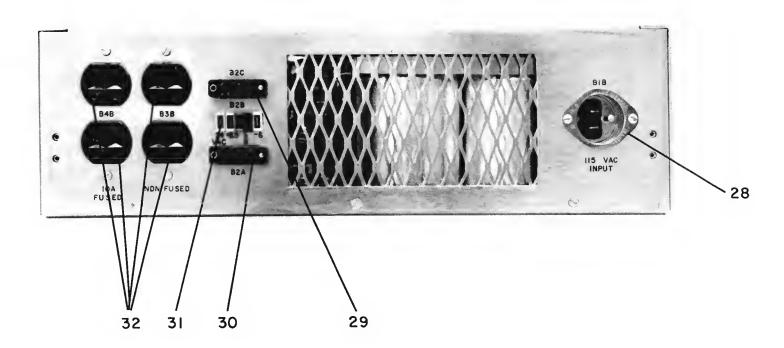


Figure 4-24. Power Supply, Table Top Configuration

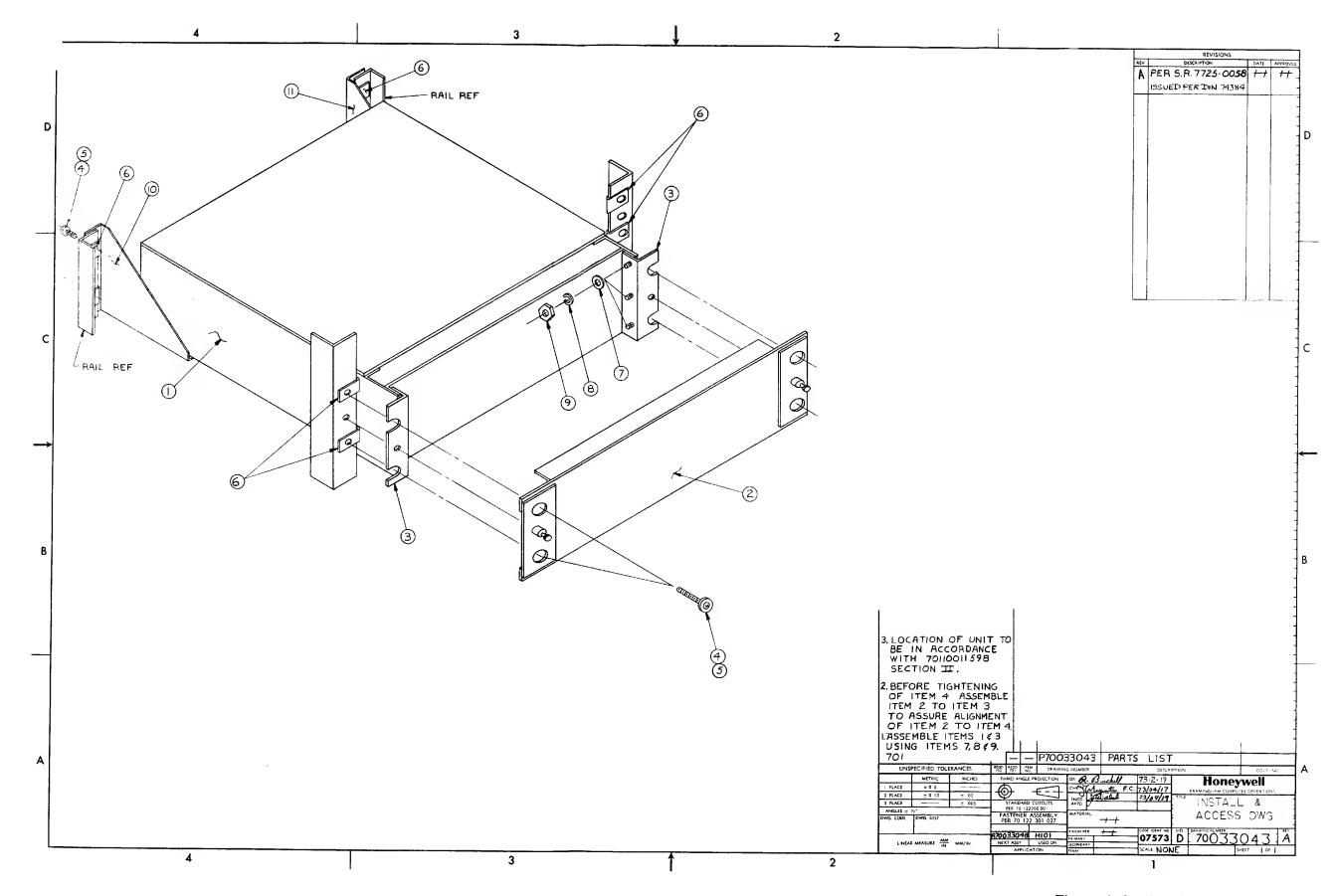


Figure A-2. Installation and Accessories (Ref. Drawing 70033043, Rev. A)

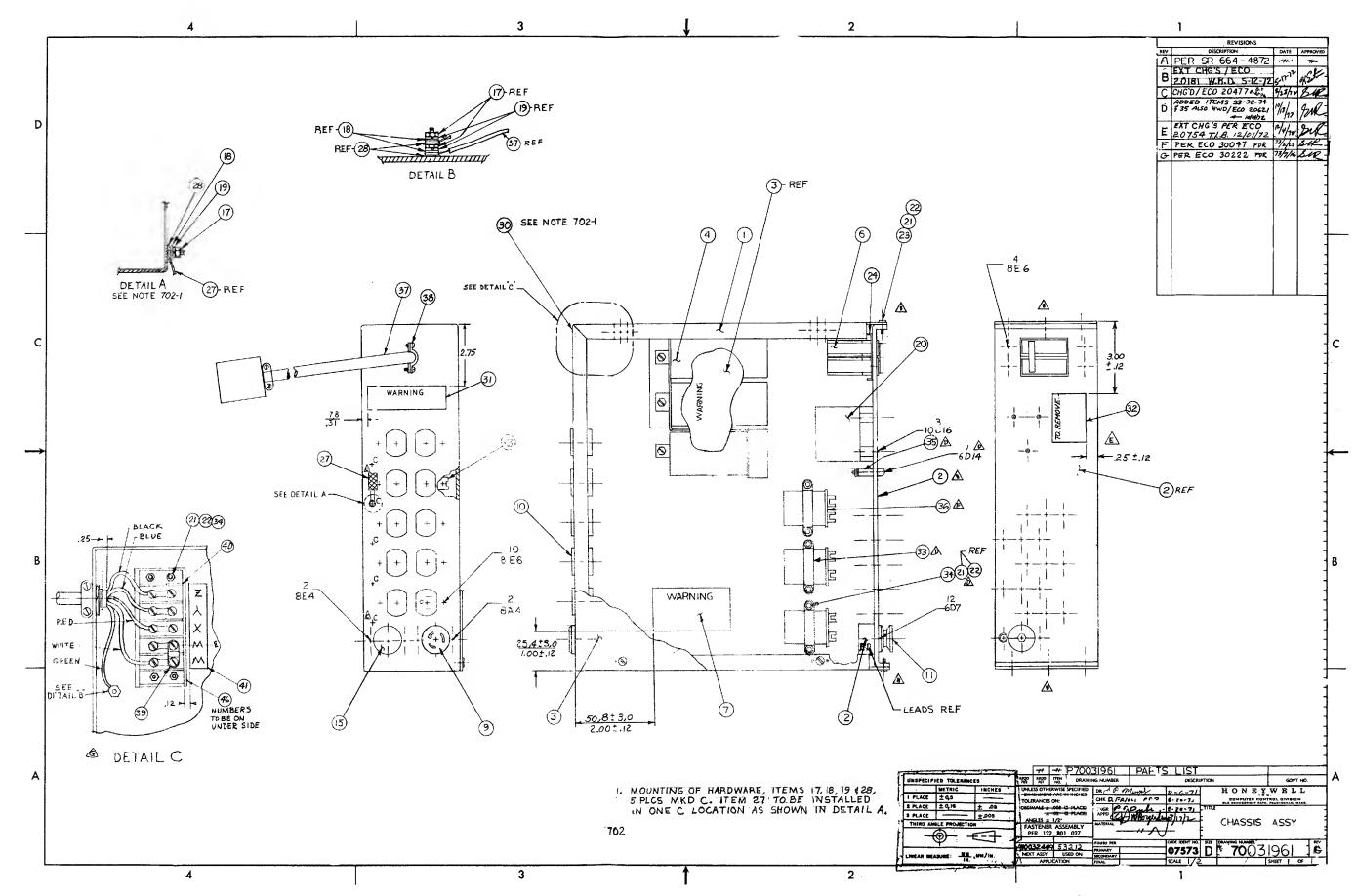


Figure A-4. Chassis Assembly (Ref. Drawing 70031961, Rev. G)

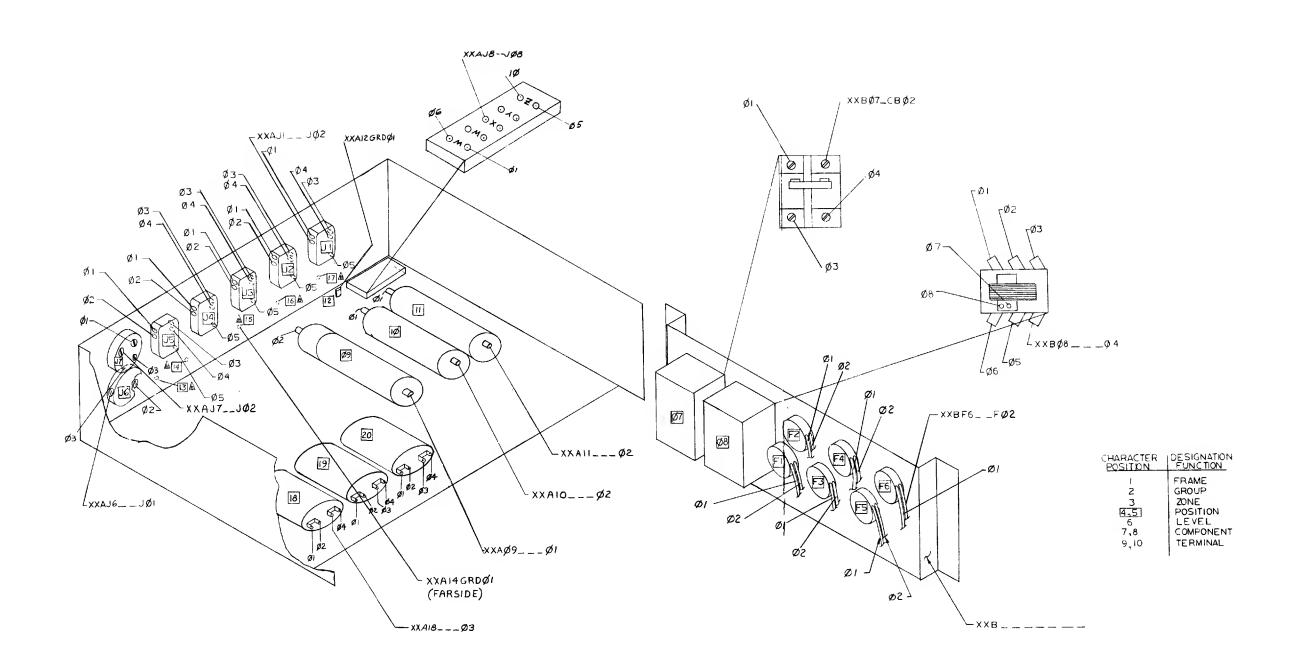


Figure A-5. Coding Diagram (Ref. Drawing 70031976, Rev.D)

APPENDIX A AULT POWER SUPPLIES

CHAPTER IV AULT POWER SUPPLIES

This chapter is divided into three parts. Each part contains illustrated parts break-down (IPB) for power supplies manufactured by Ault Inc. and used in the H316 General Purpose Computer.

Part I contains operation instruction and for IPB Ault Model PR-100 manufactured per Honeywell specification control drawing (SCD) No. 950061001; Part II presents the operating instructions and IPB for Ault Model PR-130, manufactured per Honeywell SCD No. 950061002; and Part III contains the IPB for Ault Model PR-136 and PR-143, manufactured per SCDs 950 061 003 and 950 061 004, respectively.

PART I AULT POWER SUPPLY, MODEL PR-100

Part I contains two sections presenting the assembly description and illustrated parts breakdown for Ault Model PR-100.

SECTION I ASSEMBLY DESCRIPTION

This section presents the theory of operation, maintenance, troubleshooting procedure and adjustments for Ault Model PR-100.

The H316 Power Supply is designed to provide operating voltages for the H316 Computer as follows:

24 Vac 1 ampere +6 Vdc 8-20 amperes -6 Vdc 1 ampere (max) +15.5 Vdc 0.2 - 5 amperes +24 Vdc 2 amperes (max)

A multiple secondary constant voltage transformer is used to provide these required operating potentials using an input line of 95 to 130 Vac at either 50 or 60 Hz. Logic circuitry is included in the power supply to control the turn on procedure. Circuit protection devices include fuses, a low line voltage sensing circuit, and a thermostat switch.

PHYSICAL LAYOUT

The Power Supply measures approximately 17 inches wide by 17 1/2 inches deep by 5 inches high, and it is available for mounting with either the rack-mounted or table top computer configuration. The table top configuration uses the power supply as the computer

base, with the mainframe hinged to the top of the power supply. The rack-mounted configuration places the power supply below the mainframe and separately attached to the mounting rack. Cooling is provided by a built in fan and four connectors are used for input and output voltages.

THEORY OF OPERATION

The Power Supply converts ac input power into four regulated dc outputs and one nonregulated 24 Vac output. A block diagram of the power supply is shown in Figure 4-1. Input ac power is supplied to a constant voltage transformer in the input power converter. Three secondaries of the constant voltage transformer provide the +6V, -6V and +24V output voltages. The +24V winding also provides bulk ac power to a series regulator which regulates the +15.5V output voltage. A fourth secondary provides the 24 Vac output. The logic circuitry provides the required sequencing, line sensing and overvoltage protection. Reverse diodes are included across each output to prevent accidental reversal of polarity.

Input Power Converter

Input ac power is supplied to the primary of constant voltage transformer T1. (Refer to Figure 4-2). Thermostat switch S1 interrupts ac power if the ambient temperature reaches an unsafe operating level. A3A is the input ac fuse. The outputs of three secondaries of T1 are rectified and filtered to provide the $\pm 6V$ and $\pm 24V$ outputs as well as several other required bulk dc sources. A fourth secondary of T1 provides the unregulated 24 Vac output. Capacitor C17 is used in combination with a winding on T1 to resonate the transformer at the line frequency and provide the constant voltage characteristic. All the windings are tapped to allow change over between 50 and 60 Hz line operation. Transformer T2 is used by the line sense circuitry to monitor the input ac line.

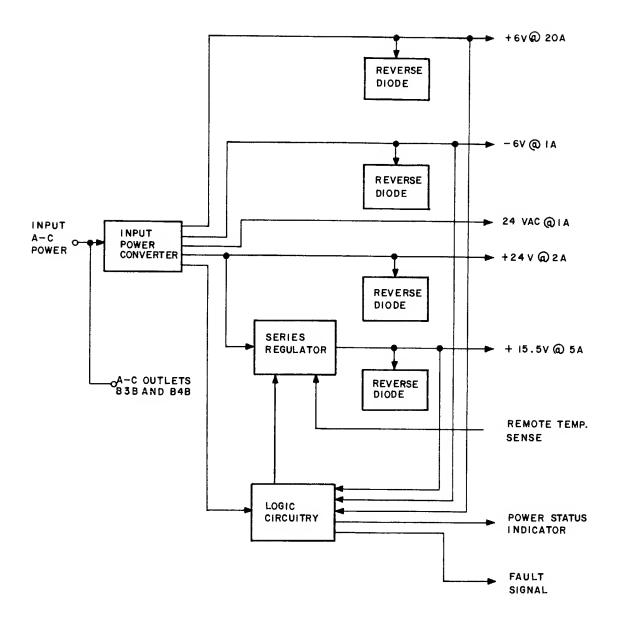
Reference Voltages

Figure 4-3 shows the positive and negative reference sources required by the +15.5V turn-on delay circuit and the +15.5V overvoltage circuit. The rectified voltage from A2 is filtered by R2 and C2 and applied to zener diode CR6, which provides the positive reference voltage. Similarly, the rectified voltage from CR3 and CR4 is filtered by R1 and C1 and applied to zener diode CR5, which provides the negative reference voltage.

+15.5V Series Regulator

The +15.5V series regulator and the turn-on control circuitry for the +15.5V output is shown in Figure 4-4.

Turn-on Control. -- The turn-on control circuitry is indicated by the dashed lines in Figure 4-4. Whenever Q6 is on, Q7 is on, which provides a drive current source for the +15.5V series regulator. In this condition Q12 is also on, preventing CR12 from conducting. Whenever Q6 is turned off, however, Q7 is also turned off, removing the drive current to the +15.5V series regulator, and turning it off. It also turns Q12 off, which causes CR12 to



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Figure 4-1. Power Supply Block Diagram

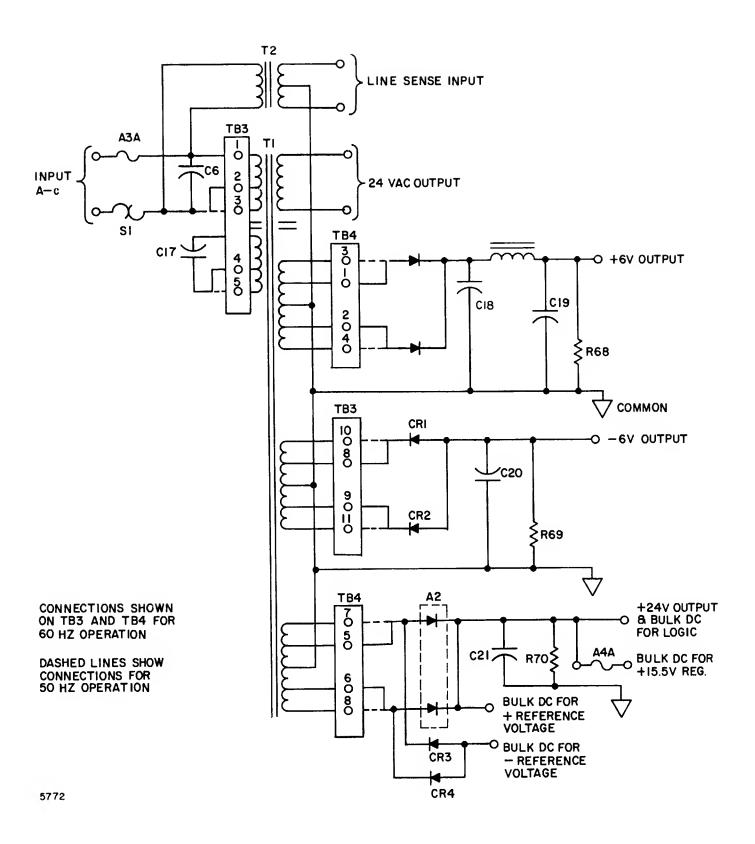


Figure 4-2. Input Power Converter

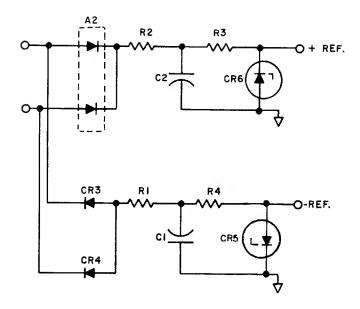


Figure 4-3. Positive and Negative Reference Sources

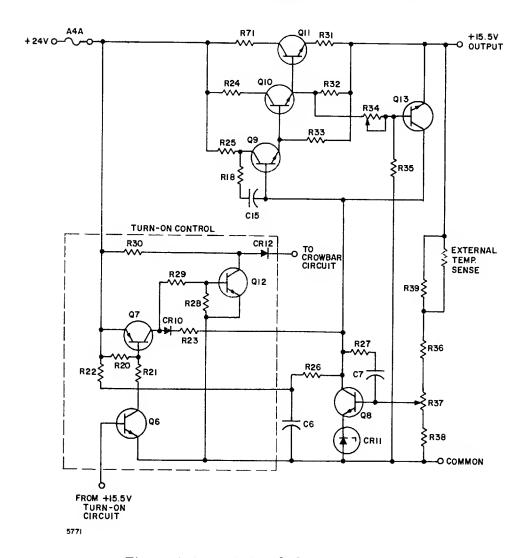


Figure 4-4. +15.5-Volt Series Regulator

conduct. This fires the crowbar SCR in the +15.5V overvoltage circuit, which shuts down the 15.5V output. During initial turn-on of the supply, this circuit attempts to fire the crowbar SCR, which would prevent turn-on. However, since no output voltage is present then, the crowbar SCR cannot turn on.

Series Regulator Operation. -- The output voltage appears across a voltage divider consisting of R36, R37, R38 and R39, and an external temperature programming resistor. The wiper voltage of R37 is compared to the reference voltage across zener diode CR11 by transistor Q8. Q8 controls the series regulator by shunting a portion of the base drive current for Q9 (provided by R23) away from Q9. (It is assumed that the turn-on control circuitry has already indicated turn-on). Q9 in turn controls the conductivity of Q10 and the pass transistor, Q11, which controls the load current.

Current limiting is provided by the circuit consisting of R31, R34, R35, and Q13. The current level is sensed by R31. The voltage across R31 is compared to a fixed voltage across R34 by transistor Q13. Whenever the maximum allowed current is reached, the voltage across R31 exceeds the voltage across R34. This causes Q13 to conduct, shunting away a portion of the base drive current for Q9, thus reducing the load current. The overload characteristic is shown in Figure 4-5.

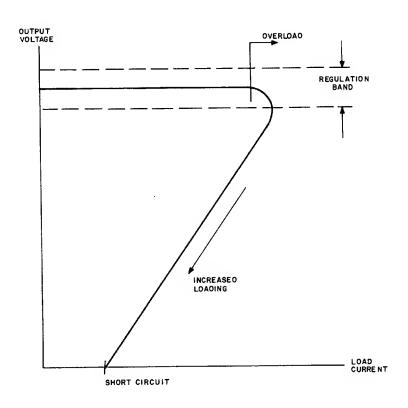


Figure 4-5. Output Voltage/Current Overload Characteristic

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Reverse Diodes

Diodes CR32, CR33, CR34, and CR35 are connected across the +6V, -6V, +24V and +15.5V outputs, respectively, to prevent accidental reversal of polarity in excess of two volts on any of these outputs.

Logic Circuitry

The logic circuitry consists of a line sense circuit, a +15.5V turn-on delay circuit and an overvoltage circuit for the +15.5V output.

<u>Line Sense Circuit.</u> -- The line sense circuit (refer to Figure 4-6) initiates turn-off of the power supply if ac input voltage is below allowable limits.

The ac input voltage is sensed by transformer T2. The secondary voltage is full-wave rectified by CR15 and CR16 to provide an unfiltered dc voltage across R46, R47 and R48. R47 is adjusted so that, when the peak ac input voltage rises above the low line limit, CR17 will conduct, turning on Q17 until the ac input voltage drops below this level again.

At the beginning of each half-cycle, C12 begins to charge at a rate determined by C12, R55 and the fixed reference voltage across zener diode CR19. Whenever C12 charges to the predetermined level, CR20 conducts, which causes SCR CR22, to fire. The charge rate is determined so that, if the ac input voltage is at low line or above, Q17 will be turned on due to the line sense voltage before C12 has charged to the level which causes CR20 to conduct. Transistor Q16 is held on by the full-wave rectified voltage at all times except for a short period as the ac input voltage passes through zero volts. At this time, Q16 turns on and discharges C12 to reset the line sense circuit.

Under normal ac input voltage conditions, Q17 clamps the gate of CR22 before it is fired (Figure 4-7 shows waveforms of the cathodes CR17 and CR20). However, if the ac input voltage fails to reach the low line level for one half-cycle, CR22 is fired, and the following sequence occurs:

- a. Coupling diode CR21 conducts, turning Q5 on, which activates the relay trip coil on the external input circuit breaker.
- b. Coupling diode CR23 also conducts, drawing current through R57 away from zener diode CR24. This turns CR24 off, which then turns Q18 off. After a short period, C14 charges sufficiently to cause zener diode CR25 to conduct and fire crowbar SCR CR14 in the +15.5V overvoltage circuit.
- c. Coupling diode CR26 also conducts, drawing current through R61 away from zener diode CR27, turning CR27 off, which then turns Q19 off. Relay Kl becomes deenergized and grounds the power status terminal. It also prevents CR29 from conducting, which turns CR30 and Q20 on. This causes the fault signal to appear (drop to ground).

In summary, whenever the ac input voltage fails to reach the low line limit for one half-cycle, the fault signal appears, the external input breaker is opened, the power status terminal is grounded, and, after a short time delay period, the +15.5V output is crowbarred.

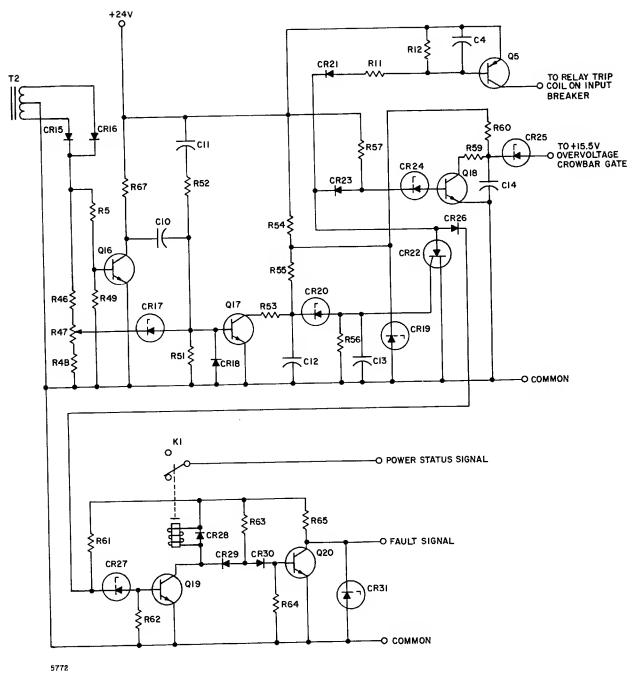


Figure 4-6. Line Sense Circuit

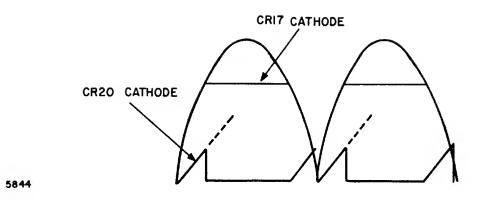


Figure 4-7. Line Sense Circuit Waveform

+15.5V Turn-on Delay Circuit. -- The +15.5V turn-on delay circuit (Refer to Figure 4-8) ensures that the +15.5V output is not allowed to turn on until the ± 6 V output voltages have both reached 90% of nominal.

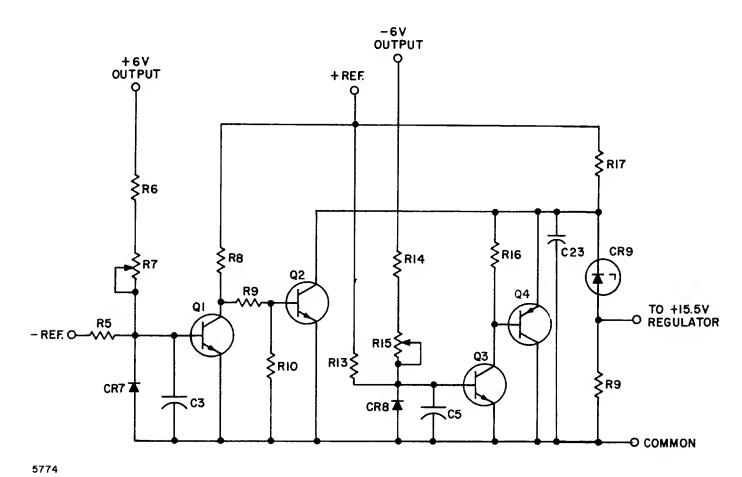
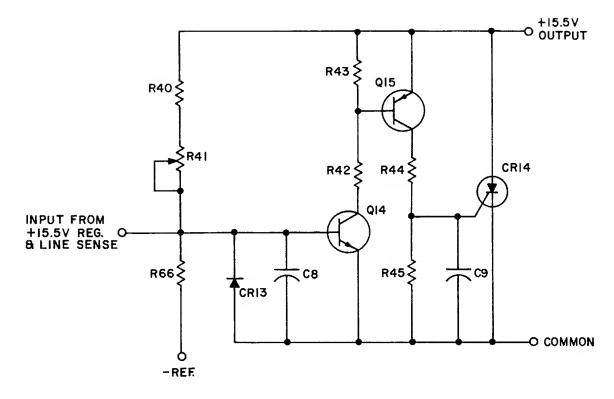


Figure 4-8. +15.5-Volt Turn-On Delay Circuit



5773

Figure 4-9. +15.5-Volt Overvoltage Circuit

The +6V output determines the current through resistors R6 and R7. This current is compared to the current through R5, which is determined by the negative reference voltage. Whenever the +6V output reaches its minimum allowed level, the current through R6 and R7 exceeds the current through R5, turning Q1 on, clamping Q2 off and allowing zener diode CR9 to conduct.

Similarly, the -6V output determines the current through R14 and R15. This current is compared with the current through R13, which is determined by the positive reference voltage. Whenever the -6V output reaches its minimum allowed level, the current through R14 and R15 exceeds the current through R13, turning Q3 off, turning Q4off, and allowing zener diode CR9 to conduct.

Whenever both the +6V and -6V outputs are above their minimum allowed levels, Q2 and Q4 are both off, and zener diode CR9 conducts to provide a turn-on signal for the +15.5V regulator. However, if either the +6V or -6V output is below its minimum allowed level, CR9 does not conduct. This removes the turn-on signal for the +15.5V regulator, which turns off the regulator and crowbars the +15.5V output.

+15.5V Overvoltage Circuit. -- The +15.5V overvoltage circuit (Refer to Figure 4-9) crowbars the +15.5V output via SCR CR14 whenever the +15.5V output exceeds its maximum allowed level or whenever a shut-down signal is received from the +15.5V regulator or the line sense circuit.

The +15.5V output determines the current through R40 and R41. This current is compared with the current through R66, which is determined by the negative reference voltage. Whenever the +15.5V output exceeds its maximum allowed level, the current through R40 and R41 exceeds the current through R66. This turns Q14 on, which turns Q15 on. This fires crowbar SCR CR14, which clamps the +15.5V output voltage to a low level. This circuit is also activated in the same manner whenever the +15.5V regulator or the line sense circuit provides a positive signal at the base of Q14.

MAINTENANCE

The only routine maintenance required for the power supply is periodic cleaning or replacement of the air filter. Adjustment procedures, a trouble shooting chart and interface connection data are described in the following paragraphs.

Replacement Parts

Replacement parts can be purchased directly from Honeywell Inc., Framingham, Mass. However, most of the components are standard electrical parts and might be obtained locally in less time.

Recommended Test Instruments

The following test instruments will be helpful in testing and adjusting the power supply:

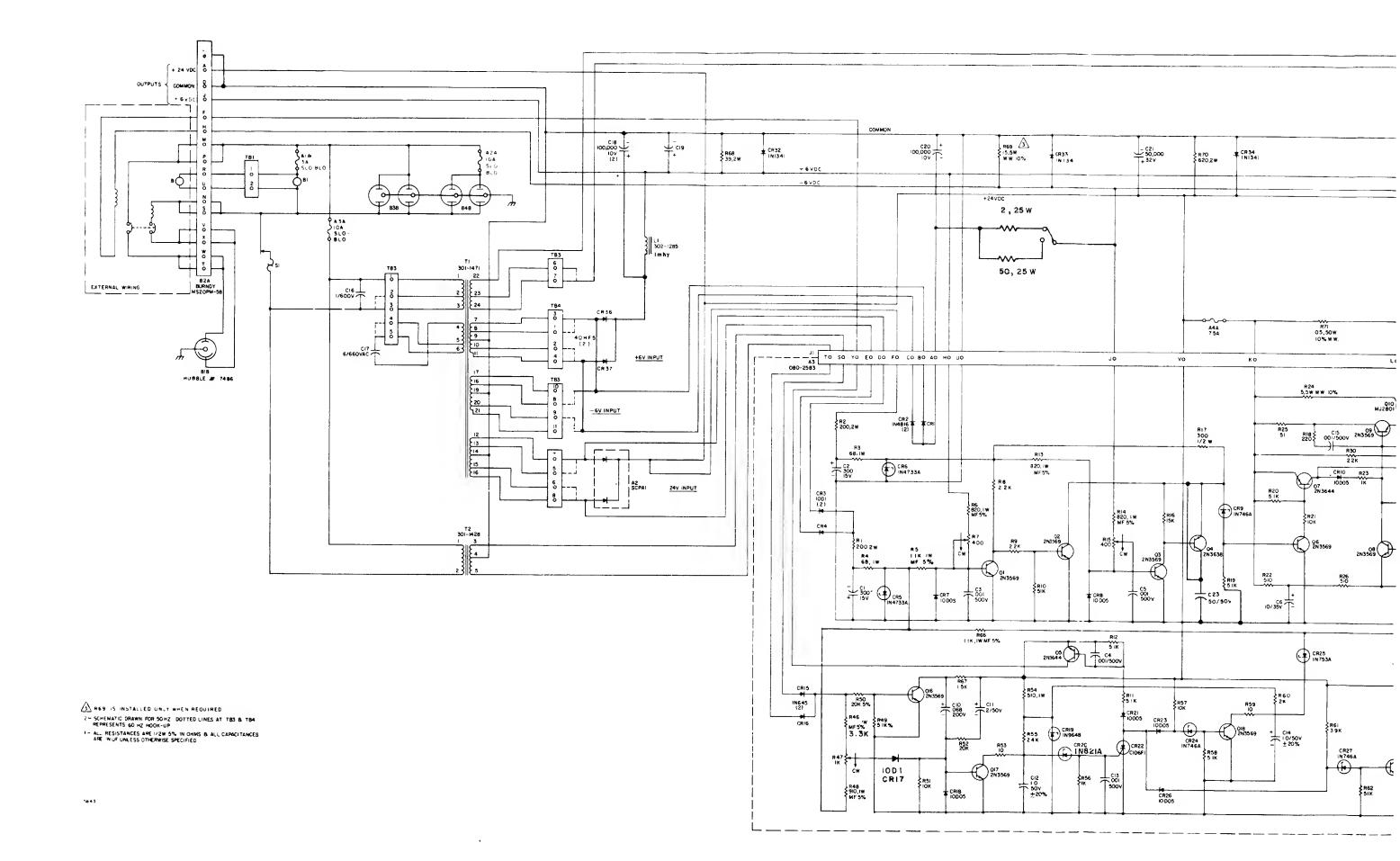
Voltmeter, ac/dc Ammeter, ac/dc Card Extender

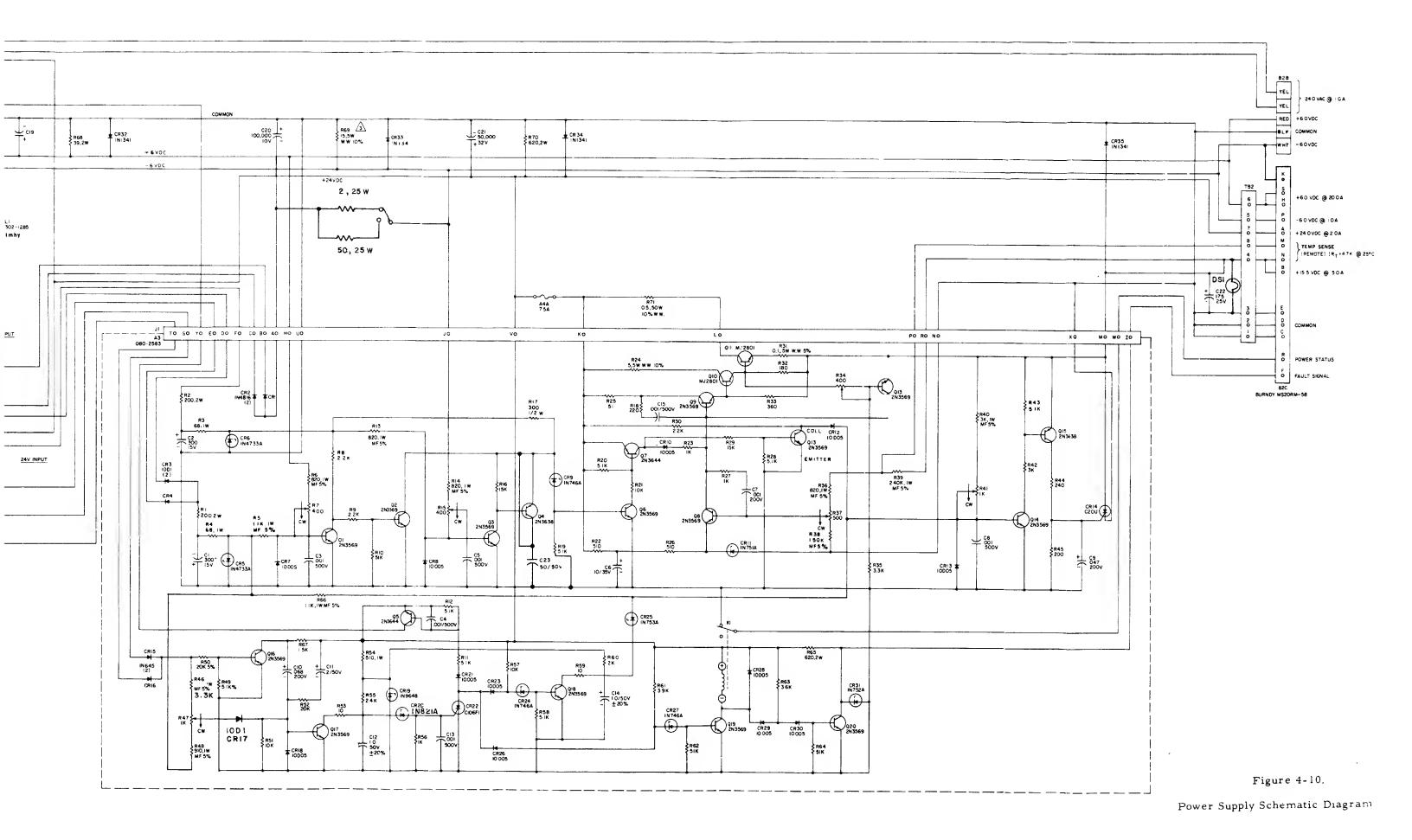
Troubleshooting Procedure

Use every safety precaution when troubleshooting the power supply. The supply should be visibly examined for broken, loose or damaged parts, or wire and foreign objects. In the event of an audibly or visually apparent malfunction, proceed directly to the affected area and perform the necessary repairs. Apparent circuit board failure may be caused by improperly adjusted potentiometers. This should be kept in mind when troubleshooting the power supply.

WARNING

The input transformer produces voltage in excess of 600 volts. Exercise extreme caution whenever the power supply cover is off. Remove any rings, watches or other metallic objects before installation or testing. Avoid contact with heat sinks or the input transformer, which operate at high temperatures.





Perform the following preliminary checks before troubleshooting the unit:

- a. Remove any foreign objects from the power supply.
- b. Since the power status signal is provided by a mercury relay, the power supply must be placed in an upright position to ensure proper operation.
 - c. Check all input and output connections.
 - d. Check the remote temperature sensing device connection.
 - e. Check for proper connections for 50 or 60 Hz operation

Table 4-1.
Troubleshooting Guide

SYMPTOM	POSSIBLE CAUSE	SUGGESTED ACTION
Power supply will not turn on.	a. No input ac power. b. Open thermostat S1. c. Blown fuse AlA or A3A	a. Check for input power.b. Check for proper cooling.c. Check fuses.
	d. Low ac line voltage. e. Faulty or misadjusted line sense circuit under low ac line condition.	 d. Check for faulty signal. e. Check ac line level and line sense circuit adjustment.
No +15.5V out- put voltage.	 a. Undervoltage on +6V or -6V output. b. Shorted output. c. Faulty or misadjusted turn-on delay circuit. 	 a. Check ±6V levels. b. Check with external loads removed. c. Check turn-on delay circuit.
Low +15.5V out- put voltage.	a. Improper adjustment. b. Blown fuse A4A c. Overloaded output. d. Misadjusted over- current limit.	a. Check output adjustment.b. Check fuse.c. Check with external load removed.d. Check adjustment.
Overvoltage occurs on +15.5V output.	 a. Misadjusted output. b. Shorted pass transistor Q11. c. Misadjusted overvoltage circuit. 	a. Check adjustment.b. Check Qll.c. Check adjustment of over-voltage circuit: Overvoltage may not be actually occuring.
False indication at power status terminal.	a. Power supply not in up- right position.	a. Check position of supply.

ADJUSTMENTS

50 or 60 Hz Operation Adjustment

Several tap changes are required on transformer T1 to convert from 60 Hz to 50 Hz operation. Figure 4-2 shows the correct wiring for 60 Hz operation. The dashed lines show the changes required for 50 Hz operation. Changing frequency operation also requires readjustment of the line sense circuit.

Output Voltage Adjustments

The +15.5V output is the only adjustable output. This voltage is controlled by potentiometer R37 where Clockwise rotation will increase the output voltage level.

+15.5V Overvoltage Adjustment

The +15.5V overvoltage adjustment is controlled by potentiometer R41. Proceed as follows:

- a. Turn R41 (maximum overvoltage setting) fully clockwise.
- b. Apply input ac power.
- c. Adjust the +15.5V output voltage to the desired overvoltage setting (18V) with the output voltage adjustment potentiometer R37. It may be necessary to replace the external thermistor with a decade box to reach this level.
 - d. Slowly turn R41 counterclockwise until the +15.5V output voltage drops to zero.
 - e. Remove input ac power.
 - f. Replace the external thermistor if it had been removed.
 - g. Turn R37 fully counterclockwise.
 - h. Apply input ac power.
 - i. Set the +15.5V output voltage to the desired operating level.

+15.5V Overcurrent Adjustment

Adjust the overload bendback point with potentiometer R34 using the following procedure:

- a. Turn R34 fully clockwise.
- b. Apply a load to the +15.5V output equal to the desired overcurrent setting.
- c. Apply input ac power.
- d. Slowly turn R34 counterclockwise until the +15.5V output voltage starts to drop.
- e. Remove input ac power and remove the load.

Line Sense Circuit Adjustment

The line sense circuit is adjusted by potentiometer R47. This adjustment is required

whenever a change is made between 50 Hz and 60 Hz opera on. Proceed as follows:

- a. Turn R47 fully clockwise.
- b. Apply 95 Vac (low line) to the input power terminals.
- c. Slowly turn R47 counterclockwise until the fault signal appears.
- d. Remove input ac power.

±6V Undervoltage Adjustment

The +15.5V turn-on delay circuit contains ±6V undervoltage sensors. These sensors have been adjusted at the factory and should normally require no adjustment. However, if adjustment should become necessary, proceed as follows:

+6V Output Adjustment Procedure

- a. Turn R7 fully counterclockwise.
- b. Disconnect the lead from connector J1-H to capacitor C18 (positive terminal) at the capacitor.
- c. Connect the disconnected lead to a positive voltage source of the desired undervoltage level.
 - d. Apply input ac power.
 - e. Slowly turn R7 clockwise until the +15.5V output drops to zero.
 - f. Remove input ac power.
 - g. Remove the external voltage source and reconnect the lead to C18.

-6V Output Adjustment Procedure

- a. Turn R15 fully counterclockwise.
- b. Disconnect the lead from connector ${\tt J1-J}$ to capacitor C20 (negative terminal) at the capacitor.
- c. Connect the disconnected lead to a negative voltage source of the desired under-voltage level.
 - d. Apply input ac power.
 - e. Slowly turn R15 clockwise until the +15.5V output drops to zero.
 - f. Remove input ac power.
 - g. Remove the external voltage source and reconnect the lead to C20.

CONNECTOR INTERFACE DATA

All inputs and outputs are made via the four connectors on the power supply. The pin connections are tabulated below. The connector number precedes the pin number; for example,

B2A-A refers to pin A or connector B2A.

Terminal	Identification
BlB	AC Input Power
B2A-A	+24 Vdc Output
B2A-D	Common
B2A-F	To relay trip coil on circuit breaker
B2A-H	To relay trip coil on circuit breaker
B2A-J	+6V Output
B2A-M	From input circuit breaker
B2A-N	From input circuit breaker
B2A-P	From input circuit breaker
B2A-S	From input circuit breaker
B2A-R	To Fan
B2A-U	To Fan
B2A-T	To input circuit breaker
B2A-V	To input circuit breaker
B2A-W	To input circuit breaker
B2A-X	To input circuit breaker
B2B-YEL	24 Vac Output
B2B-RED	+6 Vdc Output
B2B-BLK	-6 Vdc Output
B2B-WHT	Common
B3B	Ac outlet, non-fused
B4B	Ac outlet, fused
B2C-A	+24 Vdc Output
B2C-B	+15.5 Vdc Output
B2C-C	Common
B2C-D	Common
B2C-E	Common
B2C-F	Line fault signal
B2C-H	+6 Vdc Output
B2C-M	Temperature sense element
B2C-N	Temperature sense element
B2C-P	-6Vdc Output
B2C-R	Power status terminal
B2C-S	+6 Vdc output

SPECIFICATIONS

Input Power

95-130 VRMS, 50 or 60 Hz $^{\pm}1$ Hz, single phase.

Output Power

Output Voltage	Current Range	Regulation Band	Set Current	Ripple (p-p)
+24 Vdc	0 - 2A	±5%*	1.5A	5%
+15.5Vdc	2 - 5A	±5%		2%
+6Vdc	8 - 20A	±6%*	15A	2%
-6Vdc	0 - 1A	±6%*	0. 5A	2%
24Vac	0 - 1A			

*Regulation of +24V, +6V and -6V includes static line voltage changes (at set current) and ripple only.

Adjustment Range

The +15.5V output is adjustable to nominal.

Temperature Compensation

The +15.5V output is remotely controlled by a temperature sensing device (Honeywell P/N 70 932 305 001) at a nominal rate of -0.5% per °C from 0-60°C. The bandwidth allowed is $\pm 4\%$ deviation from linearity below 25°C and $\pm 2\%$ deviation from linearity above 25°C.

Overvoltage Protection

Turn-on and turn-off will not cause the +15.5V output to exceed 18V nor the $\pm6V$ outputs to exceed nominal by more than 20%.

An overvoltage crowbar circuit prevents the +15.5V output from exceeding 18V in the event of a regulator component failure.

Overcurrent Protection

Fuses are provided for input ac power, the internal fan, bulk dc power for the +15.5V regulator and two ac auxiliary outputs. Current limiting circuitry is incorporated in the +15.5V regulator.

Output Voltage Reversal

Reverse diodes are included across each dc output to prevent any voltage from reversing polarity by more than 2.0 volts.

Thermal Cutout

A thermal cutout is included to remove input ac power to the power supply if unsafe temperature is exceeded.

Operating Temperature

 $0 - 60^{\circ}C$

Efficiency

50% or greater when fully loaded.

Turn-on Turn-off Sequencing

The following turn-on and turn-off sequencing is provided under all rated load conditions:

- During turn-on, the +15.5V output will not rise above 20% of nominal until the ±6V outputs are above 90% of nominal. The ±6V outputs are energized when power is applied.
- 2. During turn-off, the ±6V outputs shall remain above 90% of nominal until the +15.5V output drops below 20% of nominal.
- 3. A +5 to +6 volt fault signal rated at 10 mA is provided whenever input ac power is within acceptable limits. The +15.5V output will remain within regulation for a minimum of 1.0 ms after loss of this signal, and the ±6V outputs will remain in regulation for at least 2 ms.
- 4. The fault signal will fall to ground level within 1/2 cycle of the loss of input ac power. Removing the fault signal also trips the input ac circuit breaker.

SECTION 2 ILLUSTRATED PARTS BREAKDOWN

This section contains the illustrated parts breakdown (IPB) of the power supply for both rack-mounted and table top models of the H316 General Purpose Computer.

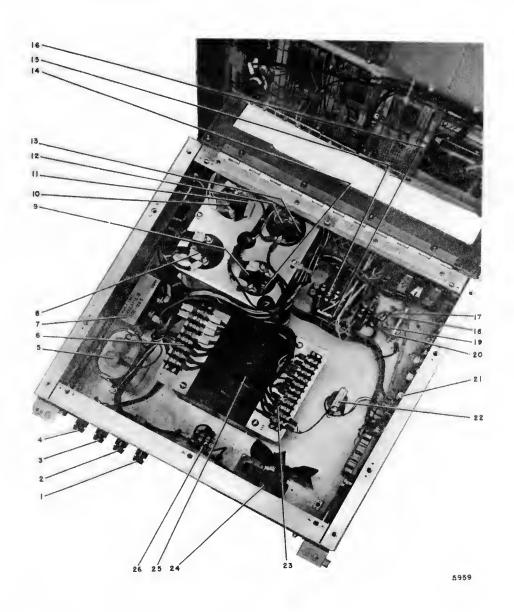


Figure 4-11. Power Supply, Rack-Mounted Configuration (Part 1 of 2)

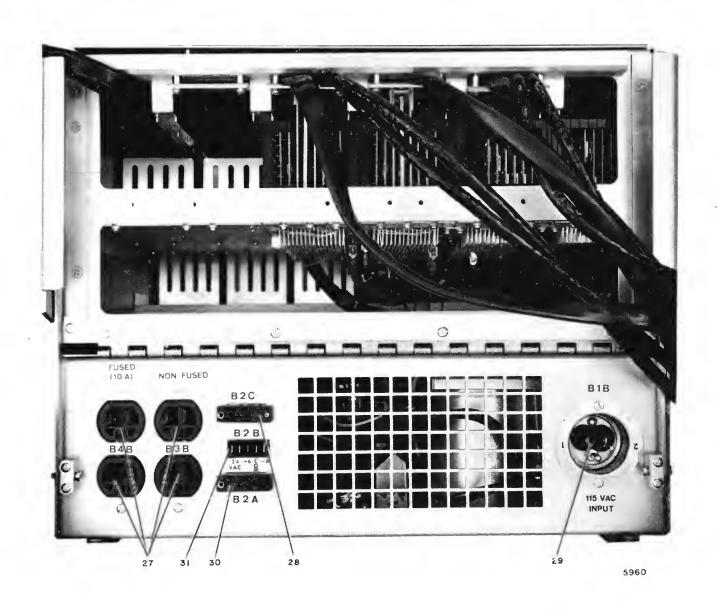


Figure 4-11. Power Supply, Table Top Configuration (Part 2 of 2)

Fig. & Index No.	Designation	AULT Mfg. Co. Part No.	Inden- ture	Description	Qty per Ass'y
4-11	А3	950061001*	С	POWER SUPPLY - AULT Mfg; No. PR 100-A1 2 (Refer to Figure 3-1-4 and 3-2-5 for NHA).	Ref
-1	AlA	6221293	D	FUSE, CARTRIDGE - 3A, Slo-Blo	1
-2	A2A	6221294	D	FUSE, CARTRIDGE - 10A, Slo-Blo	2
-3	A3A	6221294	D	FUSE, CARTRIDGE - Same as A2A	Ref
-4	A4A	62211002	D	FUSE, CARTRIDGE - 7.5A	1
- 5	C22	4001540	D	CAPACITOR, FXD, ELECTROLYTIC - 175 µF, 25V	1
-6	TB4	6201601	D	TERMINAL BOARD - barrier type	2
-7	Ll	3021285	D	CHOKE	1
-8	C19	4001278	D	CAPACITOR, ELECTROLYTIC - 100,000 µF, 10V	3
- 9	C20	4001278	D	CAPACITOR, ELECTROLYTIC - same as C19	Ref
-10	C18	4001278	D	CAPACITOR, ELECTROLYTIC - same as C19	Ref
-11	R 69	5804601	D	RESISTOR, FXD, WIREWOUND - 15 ohms, 5W ±10%	1
-12	C21	4001283	D	CAPACITOR, FXD, ELECTROLYTIC - 50,000 µF, 32V	1
-13	R70	5003083	D	RESISTOR, FXD, FILM - 620 ohms, 2W, ±5%	1
-14	R68	5003054	D	RESISTOR, FXD, FILM - 39 ohms, 2W, ±5%	1
-15	TB2	6201601	D	TERMINAL BOARD - same as TB4	1
-16	C17	4061414	D	CAPACITOR, FXD - 6 µF, 660V	1
-17	CR32	6031033	D	SEMICONDUCTOR DEVICE, DIODE - type 1N1341	4
-18	CR33	6031033	D	SEMICONDUCTOR DEVICE, DIODE - same as CR 32	Ref
-19	CR34	6031033	D	SEMICONDUCTOR DEVICE, DIODE - same as CR32	Ref
-20	CR35	6031033	D	SEMICONDUCTOR DEVICE, DIODE - same as CR32	Ref
-21	A3	0802583	D	CIRCUIT CARD ASSEMBLY (See Figure 4-12 for breakdown)	1
-22	T2	3011428A	D	TRANSFORMER	1
-23	TB3	6201158	D	TERMINAL BOARD - barrier type	1
-24	Bl	6281011	D	FAN, AXIAL	1
-25	Τl	3011471B	D	TRANSFORMER, CONSTANT VOLTAGE	1
-26	TBI	6201132	D	TERMINAL BOARD - barrier type; C-J type 2-140	1

*CCD part number assignment

Fig. & Index		AULT Mfg. Co.	Inden-		Qty
No.	Designation	Part No.	ture	Description	Ass'y
4-11	CR36, CR37 (not shown)	60311881	D	SEMICONDUCTOR DEVICE, DIODE - type 40HF5	2
	A2 (not shown)	6061092	D	RECTIFIER	1
	C16 (not shown)	4061102	D	CAPACITOR, FXD, ELECTROLYTIC - 0.1 µF, 600V	1
	R71 (not shown)	5808201	D	RESISTOR, FXD, WW - 0.5 ohm, 50W 10%	1
-27	в3в, в4в	62015502	D	CONNECTOR, RECEPTACLE, ELEC - 2 section w/2 female parallel contact and 1 gnd pin contact, Hubbell type 5262	2
-28	B2C	62012402	D	CONNECTOR, RECEPTACLE, ELEC - Burndy type, MS20RM58	2
-29	BlB		D	CONNECTOR, AC, PWR-Hubbel P/N 7486	1
-30	B2A	62012402	D	CONNECTOR, RECEPTACLE, ELEC - same as B2C	Ref
-31	B2B		D	CONNECTOR RECEPTACLE - consisting of 5 contacts: two DC2025 yellow; one DC2025 red; one DC2025 black; one DC2025 white, Heyco type	1

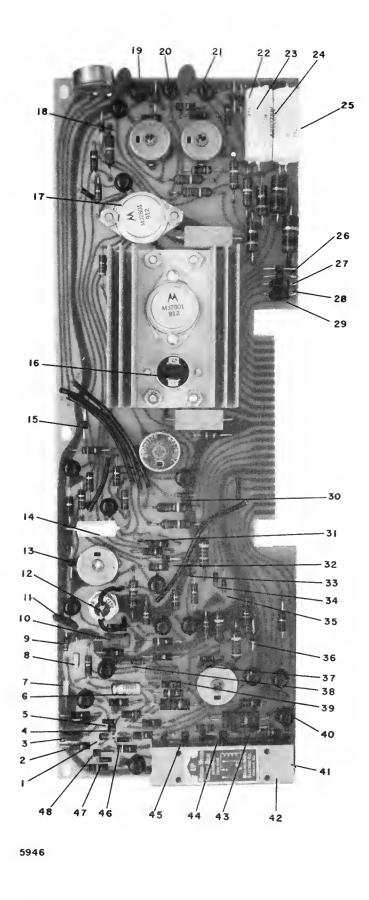


Figure 4-12. Printed Circuit Card (Part 1 of 2)

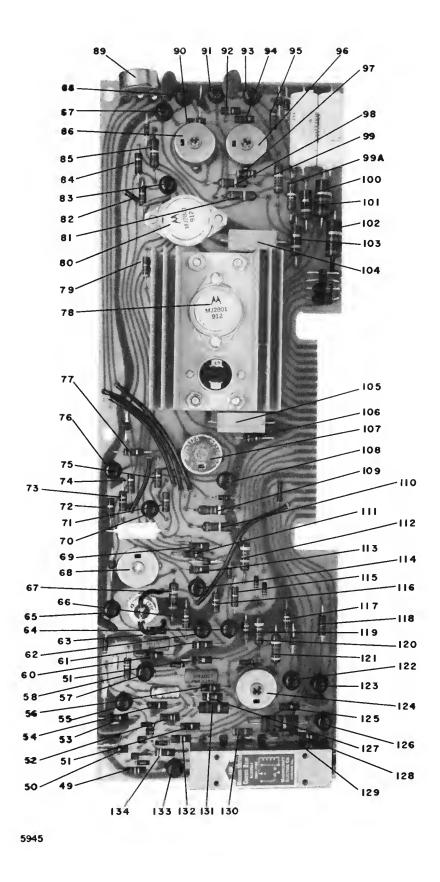


Figure 4-12. Printed Circuit Card (Part 2 of 2)

Fig. & Index No.	Designation	AULT Mfg. Co. Part No.	Inden- ture	Description	Qty per Ass'y
4-12-	A3	0802583	D	CIRCUIT CARD ASSEMBLY (Refer to Figure 4-11-21 for NHA)	Ref
- l	CR23	6031300	E	SEMICONDUCTOR DEVICE, DIODE - type 10D05	10
-2	CR22	6001072	E	SEMICONDUCTOR DEVICE, DIODE - SCR type C106F1	1
-3	C13	4061239	E	CAPACITOR - 0.002 µF, 500V	6
-4	CR21	6031300	E	SAME AS CR23	1
- 5	CR20	60511002	E	SEMICONDUCTOR DEVICE, DIODE - type 1N753A	2
-6	C11	4001069	E	CAPACITOR - 2 µF, 50V	1
-7	C14	4041018	E	CAPACITOR - 1.0 μF, 50V	2
-8	C12	4041010	E	CAPACITOR - same as C14	Ref
-9	CR25	60511002	E	SEMICONDUCTOR DEVICE, DIODE - same as CR20	Ref
-10	C 9	4061138	E	CAPACITOR - 0.047 µF, 200V	1
-11	C8	4061239	E	CAPACITOR - same as C13	Ref
-12	CR14	6001038	Æ	SEMICONDUCTOR DEVICE, DIODE - SCR type C20U	1
-13	CR13	6051300	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-14	C6	4001542	E	CAPACITOR - 10 μF, 35V	1
-15	CR12	6031300	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-16	Sl	62610945	E	THERMOSTAT	1
-17	C15	4061239	E	CAPACITOR - same as C13	Ref
-18	CR5	6051215	E	SEMICONDUCTOR DEVICE, DIODE - type 1N4733A	2
-19	C5	4061239	E	CAPACITOR - same as C13	Ref
-20	CR8	6031300	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-21	C3	4061239	E	CAPACITOR - same as C13	Ref
-22	CR7	6031300	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-23	CR6	6051215	E	SEMICONDUCTOR DEVICE, DIODE - same as CR5	Ref
-24	C2	4001539	E	CAPACITOR - 300 μF, 15V	2
-25	C1	400153)	E	CAPACITOR - same as C2	Ref
-26	CR4	6031290	E	SEMICONDUCTOR DEVICE, DIODE - type 10D1	2
-27	CR3	6031290	E	SEMICONDUCTOR DEVICE, DIODE - same as CR4	Ref
-28	CR2	6031301	E	SEMICONDUCTOR DEVICE, DIODE - type 1N4816	2

Fig. & Index No.	Designation	AULT Mfg. Co. Part No.	Inden- ture	Description	Qty per Ass'y
			E		Ref
-29	CR1	6031301	E	SEMICONDUCTOR DEVICE, DIODE - same as CR2	Rei
-30	CR11	605110037	E	SEMICONDUCTOR DEVICE, DIODE - type 1N751A	1
-31	C7	4061132	E	CAPACITOR - 0.001 µF, 200V	1
-32	CR10	6031300	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-33	CR9	605110030	E	SEMICONDUCTOR DEVICE, DIODE - type 1N746A	4
-34	CR15	6031172	E	SEMICONDUCTOR DEVICE, DIODE - type 1N645	1
-35	CR16	6031172	E	SEMICONDUCTOR DEVICE, DIODE - type 1N645	1
-36	CR18	6031300	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-37	CR17	605110020	E	SEMICONDUCTOR DEVICE, DIODE - type 1N752A	2
-38	CR 19	605110028	E	SEMICONDUCTOR DEVICE, DIODE - type 1N964B	1
-39	C10	4061142	E	CAPACITOR - 0.068 µF, 200V	1
-40	C4	4061239	E	CAPACITOR - same as C13	Ref
-41	CR31	605110020	E	SEMICONDUCTOR DEVICE, DIODE - same as CR17	Ref
-42	Kl	6241104	E	RELAY, MERCURY WETTED	1
-43	CR 30	6031300	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-44	CR29	6031300	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-45	CR28	6031300	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-46	CR24	605110030	E	SEMICONDUCTOR DEVICE, DIODE - same as CR9	Ref
-47	CR27	605110030	E	SEMICONDUCTOR DEVICE, DIODE - same as CR9	Ref
-48	CR26	605110030	E	SEMICONDUCTOR DEVICE, DIODE - same as CR9	Ref
-49	R62	5001129	E	RESISTOR, FXD, COMP - 51K ohms, 1/2W, 5%	3
-50	R58	5001105	E	RESISTOR, FXD, COMP - 5.1K ohms, 1/2W, 5%	8
-51	R53	5001040	E	RESISTOR, FXD, COMP - 10 ohms, 1/2W, 5%	2
-52	R 60	5001095	E	RESISTOR, FXD, COMP - 2K ohms, 1/2W, 5%	1
-53	R56	5001088	E	RESISTOR, FXD, COMP - 1K ohms, 1/2W, 5%	3

Fig. & Index No.	Designation	AULT Mfg. Co. Part No.	Inden- ture	Description	Qty per Ass'y
-54	R59	5001040	E	RESISTOR, FXD, COMP - same as R53	Ref
-55	Q18	6011075	E	TRANSISTOR, type 2N3569	14
-56	R52	5001119	E	RESISTOR, FXD, COMP - 20K ohms, 1/2W, 5%	2
-57	Q16	6011075	E	TRANSISTOR - same as Ol8	Ref
-58	R67	5001092	E	RESISTOR, FXD, COMP - 1.5 ohms, 1/2W, ±5%	1
-59	R49	5001105	E	RESISTOR, FXD, COMP - same as R58	Ref
-60	R45	5001071	E	RESISTOR, FXD, COMP - 200 ohms, $1/2$ W, 5%	1
-61	R44	5001073	E	RESISTOR, FXD, COMP - 240 ohms, $1/2W$, 5%	1
-62	Q15	6011151	E	TRANSISTOR - type 2N3638	2
-63	R42	5001099	E	RESISTOR, FXD, COMP - $3K$ ohms, $1/2W$, 5%	1
-64	Q6	6011075	E	TRANSISTOR - same as Q18	Ref
-65	Q14	6011075	E	TRANSISTOR - same as Q18	Ref
- 66	R43	5001105	E	RESISTOR, FXD, COMP - same as R58	Ref
-67	R40	5303099	E	RESISTOR, FXD, FILM - 3K ohms, 1W, 5%	1
-68	R41	59013526	E	RESISTOR, VARIABLE - 1K ohm	2
-69	R27	5001088	E	RESISTOR, FXD, COMP - same as R56	Ref
-70	Q8	6011075	E	TRANSISTOR - same as Q18	Ref
-71	R26	5001081	E	RESISTOR, FXD, COMP - 510 ohms, 1/2W, 5%	2
-72	R28	5001105	E	RESISTOR, FXD, COMP - same as R58	Ref
-73	R29	5001116	E	RESISTOR, FXD, COMP - 15K ohms, 1/2W, 5%	2
-74	R30	5001096	E	RESISTOR, FXD, COMP - 2.2K ohms, 1/2W, 5%	3
-75	R22	5001081	E	RESISTOR, FXD, COMP - same as R26	Ref
- 76	Q12	6011075	E	TRANSISTOR - same as Q18	Ref
-77	R35	5001100	E	RESISTOR, FXD, COMP - 3.3K ohms, 1/2W, 5%	1
-78	Q11	6011133	E	TRANSISTOR - type MJ2801	2
-7 9	R33	5001077	E	RESISTOR, FXD, COMP - 360 ohms, 1/2W, 5%	1
-80	Q10	6011133	E	TRANSISTOR - same as Qll	Ref
-81	R14	5303086	E	RESISTOR, FXD, FILM - 820 ohms, 1W, 5%	3
-82	R18	5001072	E	RESISTOR, FXD, COMP - 220 ohms, 1/2W, 5%	1
-83	Q9	6011075	E	TRANSISTOR - same as Q18	Ref

Fig. & Index No.	Designation	AULT Mfg. Co. Part No.	Inden- ture	Description	Qty per Ass'y
-84	R25	5001057	Е	RESISTOR, FXD, COMP - 51 ohms, 1/2W, 5%	1
-85	R66	5303089	E	RESISTOR, FXD, FILM - 1.1K ohms, 1W, 5%	2
-86	R15	5901128	E	RESISTOR, VARIABLE - 400 ohms	3
-87	Q4	6011151	E	TRANSISTOR - same as Q15	Ref
-88	Q3	6011075	E	TRANSISTOR - same as Q18	1
-89	R37	5 701132	E	RESISTOR, VARIABLE - 500 ohms	1
-90	R16	5001116	E	RESISTOR, FXD, COMP - same as R29	Ref
-91	Q2	6011075	E	TRANSISTOR - same as Q18	Ref
-92	R10	5001129	E	RESISTOR, FXD, COMP - same as R62	
-93	Ql	6011075	E	TRANSISTOR - same as Q18	Ref
-94	R9	5001096	E	RESISTOR, FXD, COMP - same as R30	Ref
-95	R8	5001096	E	RESISTOR, FXD, COMP - same as R30	Ref
-96	R7	5901128	E	RESISTOR, VARIABLE - same as R15	Ref
-97	R17	5001075	E	RESISTOR, FXD, COMP - 300 ohms, 1/2W, 5%	1
-98	R13	5303086	E	RESISTOR, FXD, FILM - same as R14	Ref
-99	R6	5303086	E	RESISTOR, FXD, FILM - same as R14	Ref
-99A	R5	5303089	E	RESISTOR, FXD, FILM - same as R66	Ref
-100	R2	5003071	E	RESISTOR, FXD, COMP - 200 ohms, 2W, ±5%	2
-101	R3	5002060	E	RESISTOR, FXD, COMP - 68 ohms, 1W, ±5%	1
-102	Rl	5003071	E	RESISTOR, FXD, COMP - same as R2	Ref
-103	R4	5002060	E	RESISTOR, FXD, COMP - same as R3	Ref
-104	R24	5804602	E	RESISTOR, FXD, WW - 5 ohms, 5W, ±10%	1
-105	R31	5804455	E	RESISTOR, FXD, WW - 0.1 ohm, 5W, ±5%	1
-106	R32	5001070	E	RESISTOR, FXD, COMP - 180 ohms, 1/2W, ±5%	1
-107	R34	5901128	E	RESISTOR, VARIABLE - same as R15	Ref
-108	Q13	6011075	E	TRANSISTOR - same as Q18	Ref
-109	R38	5303092	E	RESISTOR, FXD, FILM - 1.5K ohms, 1W, ±5%	2
-110	R36	5303086	E	RESISTOR, FXD, FILM - 820 ohms, 1W, ±5%	1
-111	R23	5001088	E	RESISTOR, FXD, COMP - same as R56	Ref
-112	R39	5303097	E	RESISTOR, FXD, FILM - 2.4K ohms, 1W, ±5%	1
-113	R20	5001105	E	RESISTOR, FXD, FILM - same as R58	Ref

Fig. & Index No.	Designation	AULT Mfg. Co. Part No.	Inden- ture	Description	Qty per Ass'y
-114	Q7	6011153	E	TRANSISTOR - type 2N3644	2
-115	R19	5001105	E	RESISTOR, FXD, COMP - same as R58	Ref
-116	R21	5001112	E	RESISTOR, FXD, COMP - 10K ohms, 1/2W, ±5%	3
-117	R51	5001112	E	RESISTOR, FXD, COMP - same as R21	Ref
-118	R12	5001105	E	RESISTOR, FXD, COMP - same as R58	Ref
-119	R50	5001119	E	RESISTOR, FXD, COMP - same as R52	Ref
-120	R46	5303092	E	RESISTOR, FXD, FILM - same as R38	Ref
-121	R48	5303087	E	RESISTOR, FXD, FILM - 910 ohms, 1W, ±5%	1
-122	Q17	6011075	E	TRANSISTOR - same as Q18	Ref
-123	Q5	6011153	E	TRANSISTOR - same as Q7	Ref
-124	R47	59013526	E	RESISTOR, VARIABLE - same as R41	Ref
-125	Rll	5001105	E	RESISTOR, FXD, COMP - same as R58	Ref
-126	Q20	6011075	E	TRANSISTOR - same as Q18	Ref
-127	R55	5001097	E	RESISTOR, FXD, COMP - 2.4K ohms, 1/2W, 5%	1
-128	R65	5003083	E	RESISTOR, FXD, FILM - 620 ohms, 2W, ±5%	1
-129	R64	5001129	E	RESISTOR, FXD, COMP - same as R62	Ref
-130	R63	5001101	E	RESISTOR, FXD, COMP - 3.6 ohms, $1/2W$, $\pm 5\%$	1
-131	R54	5002081	E	RESISTOR, FXD, COMP - 510 ohms, 1W, ±5%	1
-132	R57	5001112	E	RESISTOR, FXD, COMP - same as R21	Ref
-133	Q19	6011075	E	TRANSISTOR - same as Q18	Ref
-134	R61	5001102	E	RESISTOR, FXD, COMP - 3.9K ohms, 1/2W, ±5%	1
	C23	4001061	E	CAPACITOR, FXD - 50 µF, 50V Sprague type TE	1

PART II AULT POWER SUPPLY, MODEL PR-130

Part II contains two sections presenting the assembly description and illustrated parts breakdown for Ault Model PR-130. Two versions of this power supply were manufactured per Honeywell SCD No. 950 061 002; Serial No. 0 through 570, and 571 through 589. Component differences are presented in Figure 4-22 and listed in Table 4-3.

SECTION I ASSEMBLY DESCRIPTION

This section presents the theory of operation, maintenance, troubleshooting procedure and adjustments for Model PR-130 Power Supply.

Model PR-130 Power Supply is designed to provide operating voltages for the H316 computer as follows:

24 Vac	l ampere
+6.5 Vdc	8-20 amperes
-6 Vdc	l ampere (max)
+15.5 Vdc	0.2 - 5 amperes
+24 Vdc	2 amperes (max)

A multiple secondary constant voltage transformer is used to provide these required operating potentials using an input line of 95 to 130 Vac at either 50 or 60 Hz. Logic circuitry is included in the power supply to control the turn on procedure. Circuit protection devices include fuses, a low line voltage sensing circuit, and a thermostat switch.

PHYSICAL LAYOUT

The Power Supply measures approximately 17 inches wide by 17 1/2 inches deep by 5 inches high, and it is available for mounting with either the rack-mounted or table top computer configuration. The table top configuration uses the power supply as the computer base, with the mainframe hinged to the top of the power supply. The rack-mounted configuration places the power supply below the mainframe and separately attached to the mounting rack. Cooling is provided by a built in fan and four connectors are used for input and output voltages.

THEORY OF OPERATION

The Power Supply converts ac input power into four regulated dc outputs and one nonregulated 24 Vac output. A block diagram of the power supply is shown in Figure 4-13. Input ac power is supplied to a constant voltage transformer in the input power converter. Three secondaries of the constant voltage transformer provide the +6.5V, -6V and +24V output voltages. The +24V winding also provides bulk ac power to a series regulator which regulates the +15.5V output voltage. A fourth secondary provides the 24 Vac output. The logic circuitry provides the required sequencing, line sensing and overvoltage protection. Reverse diodes are included across each output to prevent accidental reversal of polarity.

Input Power Converter

Input ac power is supplied to the primary of constant voltage transformer T1. (Refer to Figure 4-14). Thermostat switch S1 interrupts ac power if the ambient temperature reaches an unsafe operating level. A3A is the input ac fuse. The outputs of three secondaries of T1 are rectified and filtered to provide the +6.5V, -6V, and +24V outputs as well as several other required bulk dc sources. A fourth secondary of T1 provides the unregulated 24 Vac output. Capacitor C17 is used in combination with a winding of T1 to resonate the transformer at the line frequency and provide the constant voltage characteristic. All the windings are tapped to allow change over between 50 and 60 Hz line operation. Transformer T2 is used by the line sense circuitry to monitor the input ac line.

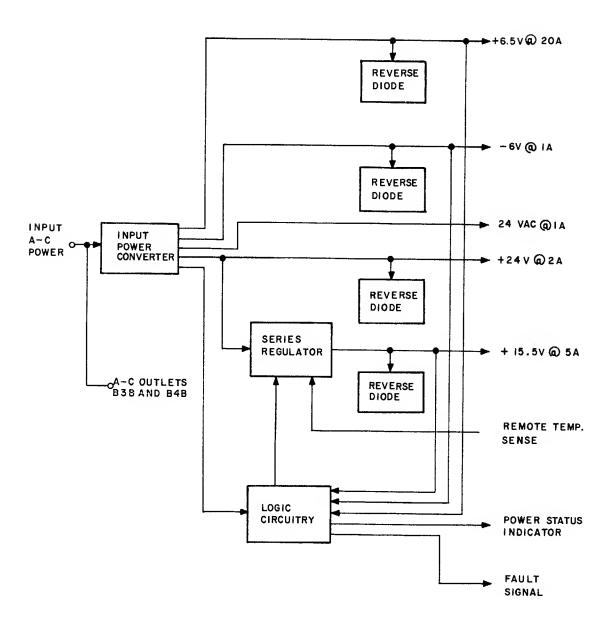
Reference Voltages

Figure 4-15 shows the positive and negative reference sources required by the +15.5V turn-on delay circuit and the +15.5V overvoltage circuit. The rectified voltage from A2 is filtered by R2 and C2 and applied to zener diode CR6, which provides the positive reference voltage. Similarly, the rectified voltage from CR3 and CR4 is filtered by R1 and C1 and applied to zener diode CR5, which provides the negative reference voltage.

+15.5V Series Regulator

The +15.5V series regulator and the turn-on control circuitry for the +15.5V output is shown in Figure 4-16.

Turn-on Control. -- The turn-on control circuitry is indicated by the dashed lines in Figure 4-16. Whenever Q6 is on, Q7 is on, which provides a drive current source for the +15.5V series regulator. In this condition Q12 is also on, preventing CR12 from conducting. Whenever Q6 is turned off, however, Q7 is also turned off, removing the drive current to the +15.5V series regulator, and turning it off. It also turns Q12 off, which causes CR12 to conduct. This fires the crowbar SCR in the +15.5V overvoltage circuit, which shuts down the 15.5V output. During initial turn-on of the supply, this circuit attempts to fire the crowbar SCR, which would prevent turn-on. However, since no output voltage is present then, the crowbar SCR cannot turn on.



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Figure 4-13. Power Supply Block Diagram

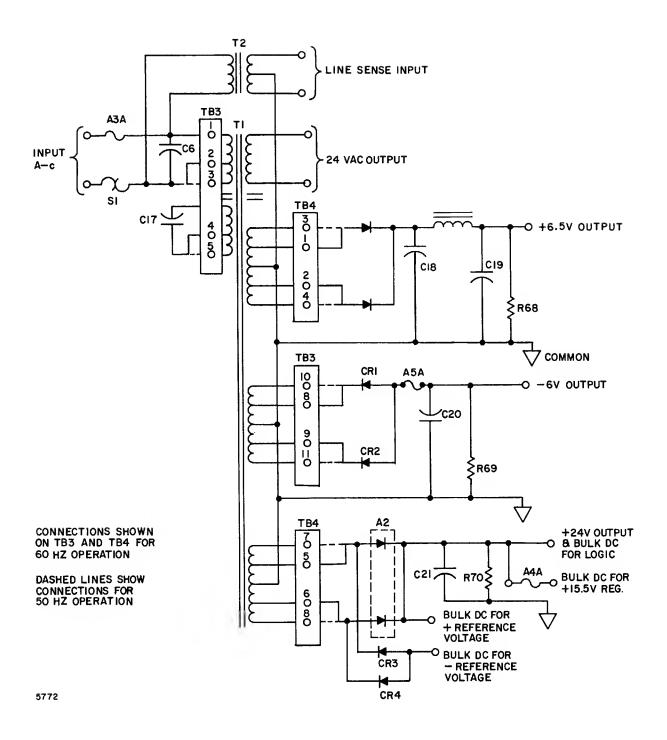


Figure 4-14. Input Power Converter

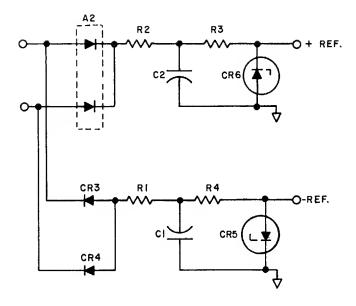


Figure 4-15. Positive and Negative Reference Sources

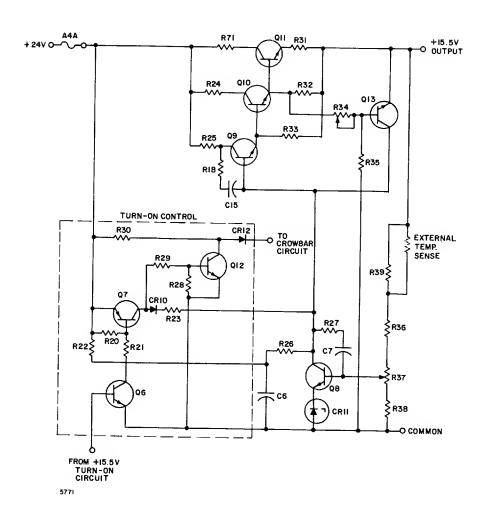


Figure 4-16. +15.5-Volt Series Regulator

Series Regulator Operation. -- The output voltage appears across a voltage divider consisting of R36, R37, R38 and R39, and an external temperature programming resistor. The wiper voltage of R37 is compared to the reference voltage across zener diode CR11 by transistor Q8. Q8 controls the series regulator by shunting a portion of the base drive current for Q9 (provided by R23) away from Q9. (It is assumed that the turn-on control circuitry has already indicated turn-on). Q9 in turn controls the conductivity of Q10 and the pass transistor, Q11, which controls the load current.

Current limiting is provided by the circuit consisting of R31, R34, R35, and Q13. The current level is sensed by R31. The voltage across R31 is compared to a fixed voltage across R34 by transistor Q13. Whenever the maximum allowed current is reached, the voltage across R31 exceeds the voltage across R34. This causes Q13 to conduct, shunting away a portion of the base drive current for Q9, thus reducing the load current. The overload characteristic is shown in Figure 4-17.

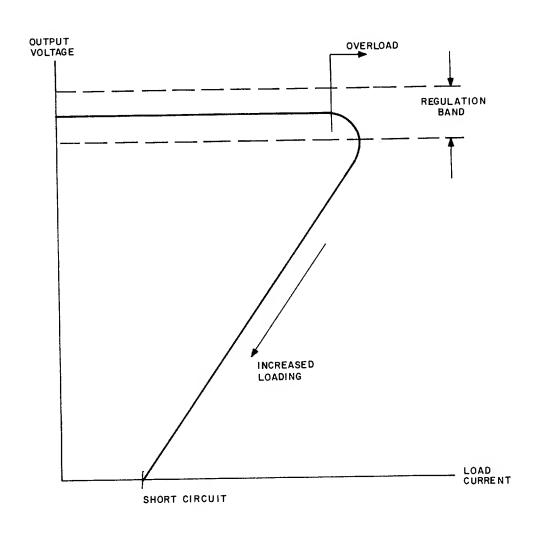


Figure 4-17. Output Voltage/Current Overload Characteristic

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Reverse Diodes

Diode assembly SCDA-1 (A4) is connected across the +6.5V and -6V line: while SCNA-1 (A5) is connected across the +24V and +15.5V outputs respectively, to prevent accidental reversal of polarity in excess of two volts on any of these outputs.

Logic Circuitry

The logic circuitry consists of a line sense circuit, a +15.5V turn-on delay circuit and an overvoltage circuit for the +15.5V output.

<u>Line Sense Circuit.</u> -- The line sense circuit (refer to Figure 4-18) initiates turn-off of the power supply if ac input voltage is below allowable limits.

The ac input voltage is sensed by transformer T2. The secondary voltage is full-wave rectified by CR15 and CR16 to provide an unfiltered dc voltage across R46, R47 and R48. R47 is adjusted so that, when the peak ac input voltage rises above the low line limit, Q17 will be turned on until the ac input drops to normal again.

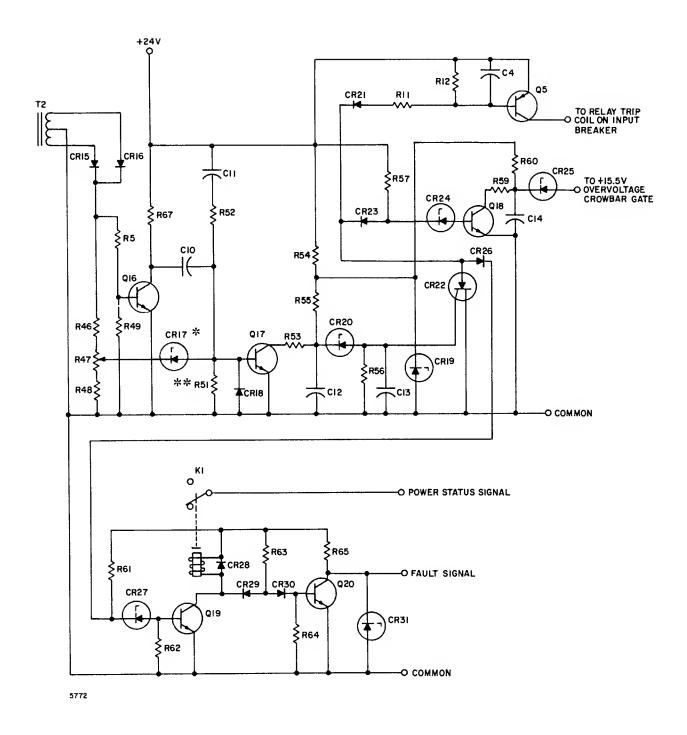
At the beginning of each half-cycle, C12 begins to charge at a rate determined by C12, R55 and the fixed reference voltage across zener diode CR19. Whenever C12 charges to the predetermined level, CR20 conducts, which causes SCR CR22, to fire. The charge rate is determined so that, if the ac input voltage is at low line or above, Q17 will be turned on due to the line sense voltage before C12 has charged to the level which causes CR20 to conduct. Transistor Q16 is held on by the full-wave rectified voltage at all times except for a short period as the ac input voltage passes through zero volts. At this time, Q16 turns on and discharges C12 to reset the line sense circuit.

Under normal ac input voltage conditions, Q17 clamps the gate of CR22 before it is fired (Figure 4-19 shows waveforms of the cathodes CR17* and CR20). However, if the ac input voltage fails to reach the low line level for one half-cycle, CR22 is fired, and the following sequence occurs:

- a. Coupling diode CR21 conducts, turning Q5 on, which activates the relay trip coil on the external input circuit breaker.
- b. Coupling diode CR23 also conducts, drawing current through R57 away from zener diode CR24. This turns CR24 off, which then turns Q18 off. After a short period, C14 charges sufficiently to cause zener diode CR25 to conduct and fire crowbar SCR CR14 in the +15.5V overvoltage circuit.
- c. Coupling diode CR26 also conducts, drawing current through R61 away from zener diode CR27, turning CR27 off, which then turns Q19 off. Relay K1 becomes deenergized and grounds the power status terminal. It also prevents CR29 from conducting, which turns CR30 and Q20 on. This causes the fault signal to appear (drop to ground).

In summary, whenever the ac input voltage fails to reach the low line limit for one half-cycle, the fault signal appears, the external input breaker is opened, the power status terminal is grounded, and, after a short time delay period, the +15.5V output is crowbarred.

^{*}For Serial No. 0 through 570 operation only.



*CR17 is replaced with resistor R76 for Serial No. 570 and beyond. **R51 is omitted for Serial No. 570 and beyond.

Figure 4-18. Line Sense Circuit

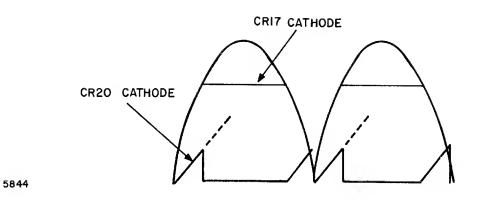


Figure 4-19. Line Sense Circuit Waveform

 $\pm 15.5 \text{V}$ Turn-on Delay Circuit. -- The +15.5V turn-on delay circuit (Refer to Figure 4-20) ensures that the +15.5V output is not allowed to turn on until the $\pm 6 \text{V}$ output voltages have both reached 90% of nominal.

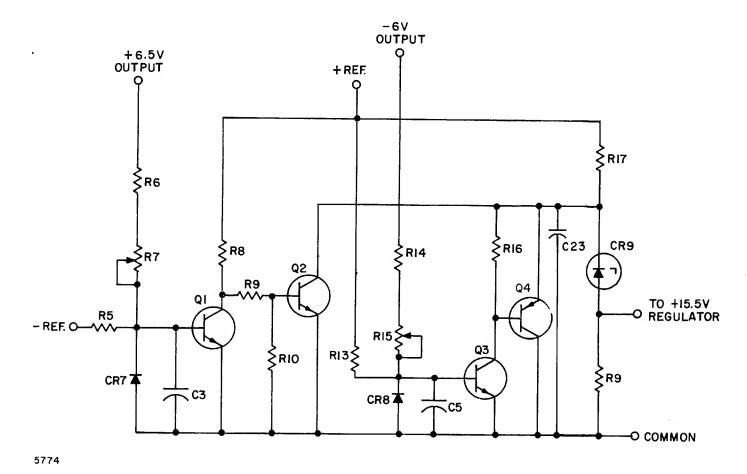


Figure 4-20. +15.5-Volt Turn-On Delay Circuit

The +6.5V output determines the current through resistors R6 and R7. This current is compared to the current through R5, which is determined by the negative reference voltage. Whenever the +6.5V output reaches its minimum allowed level, the current through R6 and R7 exceeds the current through R5, turning Q1 on, clamping Q2 off and allowing zener diode CR9 to conduct.

Similarly, the -6V output determines the current through R14 and R15. This current is compared with the current through R13, which is determined by the positive reference voltage. Whenever the -6V output reaches its minimum allowed level, the current through R14 and R15 exceeds the current through R13, turning Q3 off, turning Q4 off, and allowing zener diode CR9 to conduct.

Whenever both the +6.5V and -6V outputs are above their minimum allowed levels, Q2 and Q4 are both off, and zener diode CR9 conducts to provide a turn-on signal for the +15.5V regulator. However, if either the +6.5V or -6V output is below its minimum allowed level, CR9 does not conduct. This removes the turn-on signal for the +15.5V regulator, which turns off the regulator and crowbars the +15.5V output.

+15.5V Overvoltage Circuit. -- The +15.5V overvoltage circuit (refer to Figure 4-21) crowbars the +15.5V output via SCR CR14 whenever the +15.5V output exceeds its maximum allowed level or whenever a shut-down signal is received from the +15.5V regulator or the line sense circuit.

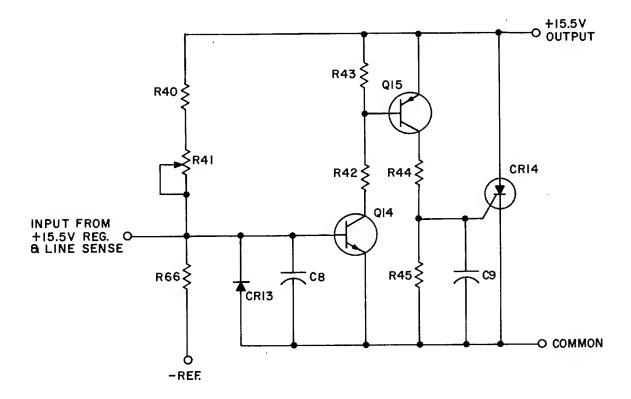


Figure 4-21. +15.5-Volt Overvoltage Circuit

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The +15.5V output determines the current through R40 and R41. This current is compared with the current through R66, which is determined by the negative reference voltage. Whenever the +15.5V output exceeds its maximum allowed level, the current through R40 and R41 exceeds the current through R66. This turns Q14 on, which turns Q15 on. This fires crowbar SCR CR14, which clamps the +15.5V output voltage to a low level. This circuit is also activated in the same manner whenever the +15.5V regulator or the line sense circuit provides a positive signal at the base of Q14.

MAINTENANCE

The only routine maintenance required for the power supply is periodic cleaning or replacement of the air filter. Adjustment procedures, a trouble shooting chart and interface connection data are described in the following paragraphs.

Replacement Parts

Replacement parts can be purchased directly from Honeywell Inc., Framingham, Mass. However, most of the components are standard electrical parts and might be obtained locally in less time.

Recommended Test Instruments

The following test instruments will be helpful in testing and adjusting the power supply:

Voltmeter, ac/dc Ammeter, ac/dc Card Extender

Troubleshooting Procedure

Use every safety precaution when troubleshooting the power supply. The supply should be visibly examined for broken, loose or damaged parts, or wire and foreign objects. In the event of an audibly or visually apparent malfunction, proceed directly to the affected area and perform the necessary repairs. Apparent circuit board failure may be caused by improperly adjusted potentiometers. This should be kept in mind when troubleshooting the power supply.

WARNING

The input transformer produces voltage in excess of 600 volts. Exercise extreme caution whenever the power supply cover is off. Remove any rings, watches or other metallic objects before installation or testing. Avoid contact with heat sinks or the input transformer, which operate at high temperatures.

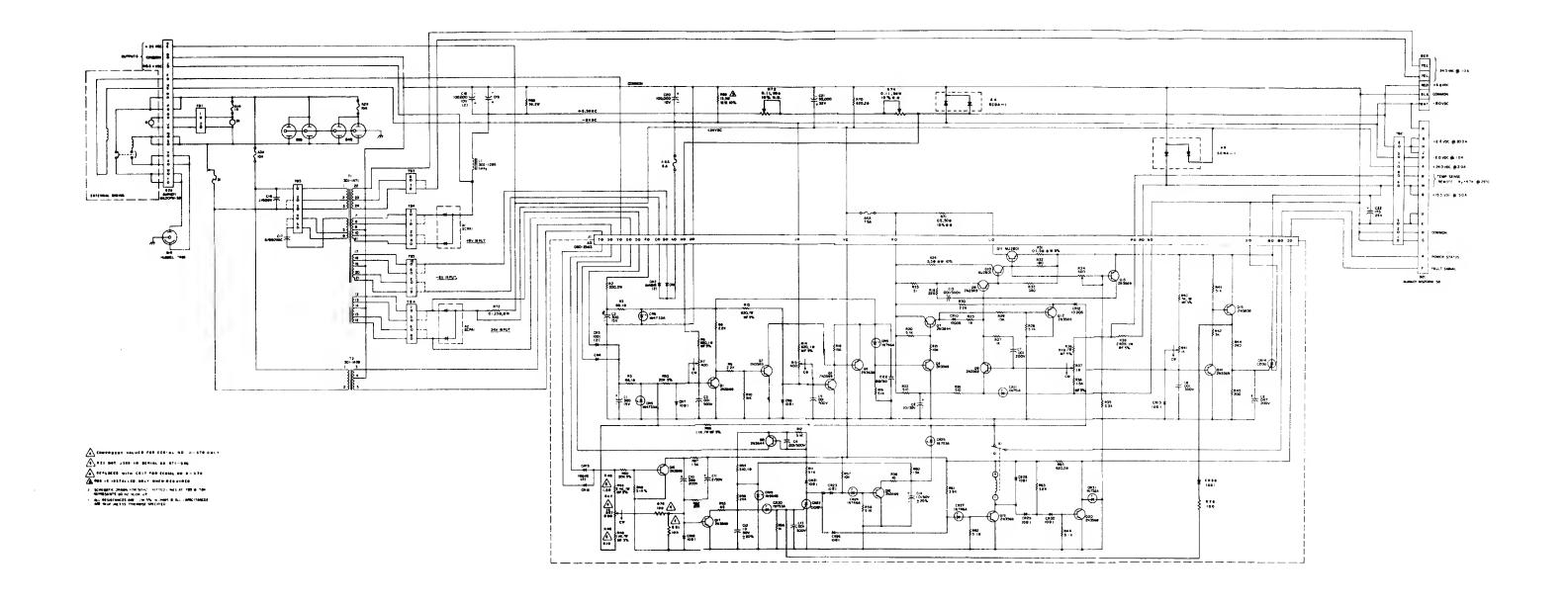


Figure 4-22. Power Supply Schematic Diagram

Perform the following preliminary checks before troubleshooting the unit:

- a. Remove any foreign objects from the power supply.
- b. Since the power status signal is provided by a mercury relay, the power supply must be placed in an upright position to ensure proper operation.
 - c. Check all input and output connections.
 - d. Check the remote temperature sensing device connection.
 - e. Check for proper connections for 50 or 60 Hz operation

Table 4-2.
Troubleshooting Guide

SYMPTOM	POSSIBLE CAUSE	SUGGESTED ACTION
Power supply will not turn on.	a. No input ac power. b. Open thermostat S1. c. Blown fuse A1A or A3A	a. Check for input power.b. Check for proper cooling.c. Check fuses.
	d. Low ac line voltage. e. Faulty or misadjusted line sense circuit under low ac line condition.	d. Check for faulty signal. e. Check ac line level and line sense circuit adjustment.
No +15.5V out- put voltage.	a. Undervoltage on +6.5V or -6V output. b. Shorted output.	a. Check +6.5V or -6V levels.b. Check with external loads removed.
	c. Faulty or misadjusted turn-on delay circuit.	c. Check turn-on delay circuit.
Low +15.5V out- put voltage.	 a. Improper adjustment. b. Blown fuse A4A c. Overloaded output. d. Misadjusted overcurrent limit. 	 a. Check output adjustment. b. Check fuse. c. Check with external load removed. d. Check adjustment.
Overvoltage occurs on +15.5V output.	 a. Misadjusted output. b. Shorted pass transistor Q11. c. Misadjusted overvoltage circuit. 	 a. Check adjustment. b. Check Qll. c. Check adjustment of over-voltage circuit: Overvoltage may not be actually occuring.
False indication at power status terminal.	a. Power supply not in upright position.	a. Check position of supply.

ADJUSTMENTS

50 or 60 Hz Operation Adjustment

Several tap changes are required on transformer T1 to convert from 60 Hz to 50 Hz operation. Figure 4-14 shows the correct wiring for 60 Hz operation. The dashed lines show the changes required for 50 Hz operation. Changing frequency operation also requires readjustment of the line sense circuit.

Output Voltage Adjustments.

The +15.5V output is controlled by potentiometer R37 (clockwise rotation increases the output voltage level). The +6.5V output is controlled by potentiometers R72 and R74. The -6V output is adjusted by wirewound resistor R80 or R81. The Power Supply is normally delivered with R81 connected as the -6V adjustment. However, R80 must be used if the -6V cannot be adjusted using R81. In this case, the lead at point A, R81, must be moved to point B, R80. (See Figure 4-29.)

+15.5V Overvoltage Adjustment

The +15.5V overvoltage adjustment is controlled by potentiometer R41. Proceed as follows:

- a. Turn R41 (maximum overvoltage setting) fully clockwise.
- b. Apply input ac power.
- c. Adjust the +15.5V output voltage to the desired overvoltage setting (18V) with the output voltage adjustment potentiometer R37. It may be necessary to replace the external thermistor with a decade box to reach this level.
 - d. Slowly turn R41 counterclockwise until the +15.5V output voltage drops to zero.
 - e. Remove input ac power.
 - Replace the external thermistor if it had been removed.
 - g. Turn R37 fully counterclockwise.
 - h. Apply input ac power.
 - Set the +15.5V output voltage to the desired operating level.

+15.5V Overcurrent Adjustment

Adjust the overload bendback point with potentiometer R34 using the following procedure:

- Turn R34 fully clockwise.
- b. Apply a load to the +15.5V output equal to the desired overcurrent setting.
- c. Apply input ac power.
- d. Slowly turn R34 counterclockwise until the +15.5V output voltage starts to drop.
- e. Remove input ac power and remove the load.

Line Sense Circuit Adjustment

The line sense circuit is adjusted by potentiometer R47. This adjustment is required whenever a change is made between 50 Hz and 60 Hz operation. Proceed as follows:

- a. Turn R47 fully clockwise.
- b. Apply 95 Vac (low line) to the input power terminals.
- c. Slowly turn R47 counterclockwise until the fault signal appears.
- d. Remove input ac power.

+6.5V or -6V Undervoltage Adjustment

The +15.5V turn-on delay circuit contains +6.5V or -6V undervoltage sensors. These sensors have been adjusted at the factory and should normally require no adjustment. However, if adjustment should become necessary, proceed as follows:

+6.5V Output Adjustment Procedure

- a. Turn R7 fully counterclockwise.
- b. Disconnect the lead from connector J1-H to capacitor C18 (positive terminal) at the capacitor.
- c. Connect the disconnected lead to a positive voltage source of the desired under-voltage level.
 - d. Apply input ac power.
 - e. Slowly turn R7 clockwise until the +15.5V output drops to zero.
 - f. Remove input ac power.
 - g. Remove the external voltage source and reconnect the lead to C18.

-6V Output Adjustment Procedure

- a. Turn R15 fully counterclockwise.
- b. Disconnect the lead from connector J1-J to capacitor C20 (negative terminal) at the capacitor.
- c. Connect the disconnected lead to a negative voltage source of the desired undervoltage level.
 - d. Apply input ac power.
 - e. Slowly turn R15 clockwise until the +15.5V output drops to zero.
 - f. Remove input ac power.
 - g. Remove the external voltage source and reconnect the lead to C20.

CONNECTOR INTERFACE DATA

All inputs and outputs are made via the four connectors on the power supply. The pin connections are tabulated below. The connector number precedes the pin number; for example, B2A-A refers to pin A or connector B2A.

Terminal	Identification
B1B	AC Input Power
B2A-A	+24 Vdc Output
B2A-D	Common
B2A-F	To relay trip coil on circuit breaker
в2А-Н	To relay trip coil on circuit breaker
B2A-J	+6.5 V Output
B2A-M	From input circuit breaker
B2A-N	From input circuit breaker
B2A-P	From input circuit breaker
B2A-S	From input circuit breaker
B2A-R	To Fan
B2A-U	To Fan
B2A-T	To input circuit breaker
B2A-V	To input circuit breaker
B2A-W	To input circuit breaker
B2A-X	To input circuit breaker
B2B-YEL	24 Vac Output
B2B-RED	+6.5 Vdc Output
B2B-BLK	-6 Vdc Output
B2B-WHT	Common
B3B	Ac outlet, non-fused
B4B	Ac outlet, fused
B2C-A	+24 Vdc Output
B2C-B	+15.5 Vdc Output
B2C-C	Common
B2C-D	Common
B2C-E	Common
B2C-F	Line fault signal
B2C-H	+6.5 Vdc Output
B2C-J	B2C-J
B2C-K	B2C -K
B2C-M	Temperature sense element
B2C-N	Temperature sense element
B2C-P	-6 Vdc Output
B2C-R	Power status terminal
B2C-S	+6.5 Vdc output

SPECIFICATIONS

Input Power

95-130 VRMS, 50 or 60 Hz \pm 1 Hz, single phase.

Output Power

Output Voltage	Current Range	Regulation Band	Set Current	Ripple (p-p)
+24 Vdc	0 - 2A	±5%*	1.5A	5%
+15.5Vdc	2 - 5A	± 5%		2%
+6.5 Vdc	8 - 20A	±6%*	15A	2%
-6Vdc	0 - 1A	±6%*	0.5A	2%
24Vac	0 - 1A			

*Regulation of +24V, +6.5V and -6V includes static line voltage changes (at set current) and ripple only.

Adjustment Range

The +15.5V output is adjustable to nominal.

Temperature Compensation

The +15.5V output is remotely controlled by a temperature sensing device (Honeywell P/N 70 932 305 001) at a nominal rate of -0.5% per °C from 0-60°C. The bandwidth allowed is $\pm 4\%$ deviation from linearity below 25°C and $\pm 2\%$ deviation from linearity above 25°C.

Overvoltage Protection

Turn-on and turn-off will not cause the +15.5V output to exceed 18V nor the +6.5V and -6V outputs to exceed nominal by more than 20%.

An overvoltage crowbar circuit prevents the +15.5V output from exceeding 18V in the event of a regulator component failure.

Overcurrent Protection

Fuses are provided for input ac power, the internal fan, bulk dc power for the ± 15.5 V regulator and two ac auxiliary outputs. Current limiting circuitry is incorporated in the ± 15.5 V regulator.

Output Voltage Reversal

Reverse diodes are included across each dc output to prevent any voltage from reversing polarity by more than 2.0 volts.

Thermal Cutout

A thermal cutout is included to remove input ac power to the power supply if unsafe temperature is exceeded.

Operating Temperature

0 - 60°C.

Efficiency

50% or greater when fully loaded.

Turn-on Turn-off Sequencing

The following turn-on and turn-off sequencing is provided under all rated load conditions:

- 1. During turn-on, the +15.5V output will not rise above 20% of nominal until the +6.5V and -6V outputs are above 90% of nominal. The +6.5V and -6V outputs are energized when power is applied.
- 2. During turn-off, the +6.5V and -6V outputs shall remain above 90% of nominal until the +15.5V output drops below 20% of nominal.
- 3. A +5 to +6 volt fault signal rated at 10 mA is provided whenever input ac power is within acceptable limits. The +15.5V output will remain within regulation for a minimum of 1.0 ms after loss of this signal, and the +6.5V and -6V outputs will remain in regulation for at least 2 ms.
- 4. The fault signal will fall to ground level within 1/2 cycle of the loss of input ac power. Removing the fault signal also trips the input ac circuit breaker.

Fig. & Index	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-24-	A3	950061002	С	POWER SUPPLY - AULT Mfg. No. PR-130	Ref
-1	A5A	6221082	D	FUSE, CARTRIDGE - 3A	1
-2	AlA	6221293	D	FUSE, CARTRIDGE - 3A, Slo-Blo	1
-3	A2A	6221294	D	FUSE, CARTRIDGE - 10A, Slo-Blo	2
-4	A3A	6221294	D	FUSE, CARTRIDGE - Same as A2A	Ref
-5	A4A	62211002	D	FUSE, CARTRIDGE - 7.5A	1
-6	R74	580-84001	D	RESISTOR, VARIABLE, WIREWOUND - 0.11 ohms, 50W ±10%	2
-7	R72	580-84001	D	RESISTOR, VARIABLE, WIREWOUND - Same as R74	Ref
-8	C17	4061414	D	CAPACITOR, FXD: 6 µF, 660V	2
-9	TB4	6201601	D	TERMINAL BOARD - barrier type	2
-10	Ll	3021285	D	CHOKE	1
-11	C19	4001278	D	CAPACITOR, ELECTROLYTIC - 100,000 µF, 10V	3
-12	C21	4001283	D	CAPACITOR, ELECTROLYTIC - 50,000 µF, 32V	1
-13	C18	4001278	D	CAPACITOR, ELECTROLYTIC - Same as C19	Ref
-14	R69	5804601	D	RESISTOR, FXD, WIREWOUND - 15 ohms, 5W±10%	1
-15	C20	4001278	D	CAPACITOR, ELECTROLYTIC - Same as C19	Ref
-16	R68	5003054	D	RESISTOR, FXD, FILM - 39 ohms, 2W, ±5%	1
-17	R70	5003083	D	RESISTOR, FXD, FILM - 620 ohms, 2W, ±5%	1
-18	TB2	6201601	D	TERMINAL BOARD - same as TB4	1
-19	C22	4001540	D	CAPACITOR, FXD, ELECTROLYTIC - 125 µF, 25V	1
-20	A4	60611601	D	DIODE ASSEMBLY - Type SCDA1	l
-21	A5	60610971	D	DIODE ASSEMBLY - Type SCNA1	1
-22	A3	0802583	D	CIRCUIT CARD ASSEMBLY (See Figure 4-12 for breakdown)	1
-23	Т2	3011428	D	TRANSFORMER	1
-24	ТВ3	6201158	D	TERMINAL BOARD - barrier type	1 1
-25	В1	6281011	D	FAN, AXIAL	1
-26	Τl	3011522	D	TRANSFORMER, CONSTANT VOLTAGE	1
-27	TBl	6201132	D	TERMINAL BOARD - barrier type; C-J type 2-140	1

Fig. & Index	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
4-24	CR 36, CR 37*	60311881	D	SEMICONDUCTOR DEVICE, DIODE - type 40HF5	2
	A2*	6061001	D	DIODE - Assembly type SCPA1	1
	C16*	4061171	D	CAPACITOR, FXD, ELECTROLYTIC - 0.1 µF, 600V	1
	R71*	58078805	ם	RESISTOR, FXD, WIREWOUND - 0.5 ohm, 50W 10%	1
-28	BlB		D	CONNECTOR, AC, PWR - Hubbell P/N 8486	1
-29	B2C	62012401	D	CONNECTOR, RECEPTACLE, ELEC - Burndy type, MS20RM58	2
-30	B2A	62012401	D	CONNECTOR, RECEPTACLE, ELEC - Same as B2C	Ref
-31	B2B		D	CONNECTOR, RECEPTACLE - consisting of 5 contacts: two DC2025 yellow; one DC2025 red; one DC2025 black; one DC2025 white, Heyco type	1
-32	B3B, B4B	62015502	D	CONNECTOR, RECEPTACLE, ELEC - 2 section w/2 female parallel contact and 1 gnd pin contact, Hubbell type 5262	2
	-				
		<u> </u>			

*Not shown

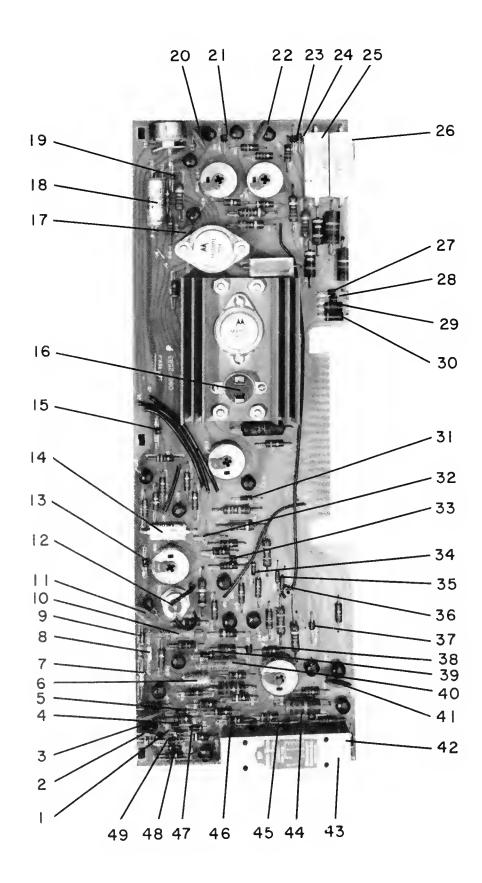


Figure 4-25. Printed Circuit Card (Part 1 of 2)

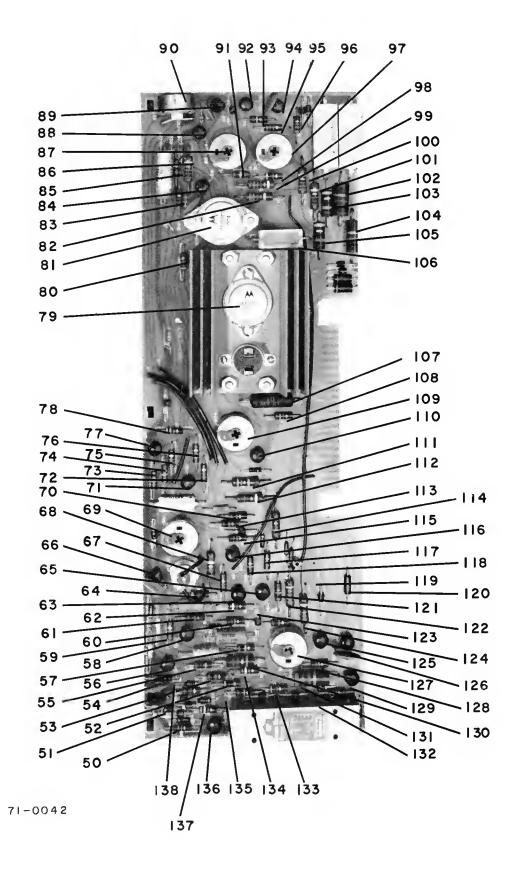


Figure 4-25. Printed Circuit Card (Part 2 of 2)

Fig. &		AULT			
Index	Desig-	Mfg. Co.	Inden-		Qty per
No.	nation	Part No.	ture	Description	Ass'y
4-25	A3	0802583	D	CIRCUIT CARD ASSEMBLY (Refer to Figure 4-24-22 for NHA)	Ref
-1	CR23	6032201	E	SEMICONDUCTOR DEVICE, DIODE - type 10D1	12
-2	CR22	6001072	E	SEMICONDUCTOR DEVICE, DIODE - SCR type C106F1	1
-3	C13	4061239	E	CAPACITOR - 0.001 µF, 500V	6
-4	CR21	60312201	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	1
- 5	CR20	60511002	E	SEMICONDUCTOR DEVICE, DIODE - type 1N753A	2
-6	C11	4001069	E	CAPACITOR - 2 µF, 50V	1
-7	C14	4041018	E	CAPACITOR - 1.0 µF, 50V	2
-8	C12	4041018	E	CAPACITOR - same as C14	Ref
-9	CR 25	60511002	E	SEMICONDUCTOR DEVICE, DIODE - same as CR20	Ref
-10	C9	4061138	E	CAPACITOR - 0.047 µF, 200V	1
-11	C8	4061239	E	CAPACITOR - same as C13	Ref
-12	CR 14	6001038	E	SEMICONDUCTOR DEVICE, DIODE - SCR type C20U	1
-13	CR13	6052201	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-14	C6	4001542	E	CAPACITOR - 10 μF, 35V	1
- 15	CR 12	6032201	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-16	Sl	62610945	E	THERMOSTAT	1
-17	C15	4061239	E	CAPACITOR - same as C13	Ref
-18	C23	4001961	E	CAPACITOR, FXD - 50 µF, 50V Sprague Type TE	1
-19	CR5	6051215	E	SEMICONDUCTOR DEVICE, DIODE - type 1N4733A	2
-20	C5	4061239	E	CAPACITOR - same as C13	Ref
-21	CR8	60312201	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-22	C3	4061239	E	CAPACITOR - same as C13	Ref
-23	CR7	60312201	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
-24	CR6	6051215	E	SEMICONDUCTOR DEVICE, DIODE - same as CR5	Ref
-25	C2	4001539	E	CAPACITOR - 300 µF, 15V	2
-26	C1	4001539	E	CAPACITOR - same as C2	Ref
-27	CR4	60312201	E	SEMICONDUCTOR DEVICE 7-1-1	Ref

	Fig. & Index No.	Desig- nation	AULT Mfg. Co. Part No.	Inden- ture	Description	Qty per Ass'y
	-28	CR3	60312201	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
	-29	CR2	6031301	E	SEMICONDUCTOR DEVICE, DIODE type 1N4816	2
	-30	CRl	6031301	E	SEMICONDUCTOR DEVICE, DIODE - same as CR2	Ref
	-31	CRll	605110037	E	SEMICONDUCTOR DEVICE, DIODE - type 1N751A	1
١	-32	C7	4061132	E	CAPACITOR - 0.001 μF, 200V	1
	-33	CR10	6032201	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
	-34	CR9	605110030	E	SEMICONDUCTOR DEVICE, DIODE - type 1N746A	4
	-35	CR 15	6031171	E	SEMICONDUCTOR DEVICE, DIODE - type 1N645	2
	-36	CR16	6031171	E	SEMICONDUCTOR DEVICE, DIODE - same as CR 15	Ref
	-37	CR 18	60312201	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
▲	-38	CR 17	605110020	E	SEMICONDUCTOR DEVICE, DIODE - type 1N752A	2
	-39	CR 19	60511028	E	SEMICONDUCTOR DEVICE, DIODE - type 1N964B	1
	-40	C10	4061142	E	CAPACITOR - 0.068 µF, 200V	1
	-41	C4	4061239	E	CAPACITOR - same as C13	Ref
	-42	1	605110020	E	SEMICONDUCTOR DEVICE, DIODE - same as CR 17	Ref
	-43	Kl	6241104	E	RELAY, MERCURY WETTED	1
	-44	CR 30	60312201	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
	-45	CR29	60312201	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
	-46	CR28	60312201	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
	-47	CR24	605110030	E	SEMICONDUCTOR DEVICE, DIODE - same as CR9	Ref
	-48	CR27	605110030	E	SEMICONDUCTOR DEVICE, DIODE - same as CR9	Ref
	-49	CR26	60312201	E	SEMICONDUCTOR DEVICE, DIODE - same as CR23	Ref
	-50	R62	5001105	` E	RESISTOR, FXD, COMP - 5.1K ohms, 1/2W, 5%	11
	-51	R58	5001105	E	RESISTOR, FXD, COMP - same as R62	Ref
	-52		5001051	E	RESISTOR, FXD, COMP - 30 ohms, 1/2W, 5%	2

▲ See Table 4-3 at end of this section.

Fig. & Index	Desig-	AULT Mfg. Co.	Inden-		Qty
No.	nation	Part No.	ture	Description	per Ass'y
-53	R60	5001095	E	RESISTOR, FXD, COMP - 2K ohms, 1/2W, 5%	1
-54	R56	5001088	E	RESISTOR, FXD, COMP - 1K ohms, 1/2W, 5%	3
-55	R59	5001040	E	RESISTOR, FXD, COMP - 10 ohms, 1/2W, 5%	1
-56	Q18	6011075	E	TRANSISTOR - type 2N3569	14
-57	R52	5001119	E	RESISTOR, FXD, COMP - 20K ohms, 1/2W, 5%	2
-58	Q16	6011075	E	TRANSISTOR - same as Q18	Ref
-59	R67	5001092	E	RESISTOR, FXD, COMP - 1.5K ohms, 1/2W, ±5%	1
-60	R49	5001105	E	RESISTOR, FXD, COMP - same as R58	Ref
-61	R45	5001071	E	RESISTOR, FXD, COMP - 200 ohms, 1/2W, 5%	1
-62	R44	5001073	E	RESISTOR, FXD, COMP - 240 ohms, 1/2W, 5%	1
- 63	Q15	6011151	E	TRANSISTOR - type 2N3638	2
-64	R42	5001099	E	RESISTOR, FXD, COMP - 3K ohms, 1/2W, 5%	1
-65	Q6	6011075	E	TRANSISTOR - same as Q18	Ref
-66	Q14	6011075	E	TRANSISTOR - same as Q18	Ref
-67	R43	5001105	E	RESISTOR, FXD, COMP - same as R58	Ref
-68	R40	6403099	E	RESISTOR, FXD, FILM - 3K ohms, 1W, 5%	1
-69	R41	59013526	E	RESISTOR, VARIABLE - 1K ohm	2
-70	R27	5001088	E	RESISTOR, FXD, COMP - same as R56	Ref
-71	Q8	6011075	E	TRANSISTOR - same as Q18	Ref
-72	R26	5001081	E	RESISTOR, FXD, COMP - 510 ohms, 1/2W, 5%	2
-73	R28	5001105	E	RESISTOR, FXD, COMP - same as R58	Ref
-74	R29	5001116	E	RESISTOR, FXD, COMP - 15K ohms, 1/2W, 5%	2
- 75	R 30	5001096	E	RESISTOR, FXD, COMP - 2.2K ohms, 1/2W, 5%	3
-76	R22	5001081	E	RESISTOR, FXD, COMP - same as R26	Ref
-77	Q12	6011075	E	TRANSISTOR - same as Q18	Ref
-78	R35	5001100	E	RESISTOR, FXD, COMP - 3.3K ohms, 1/2W, 5%	1
-79	Qll	6011133	E	TRANSISTOR - type MJ2801	2
-80	R33	5001077	E	RESISTOR, FXD, COMP - 360 ohms, 1/2W, 5%	1
-81	Q10	6011133	E	TRANSISTOR - same as Qll	Ref

Fig. & Index No.	Desig-	AULT Mfg. Co. Part No.	Inden-	Description	Qty per Ass'y
				-	3
-82	R 14	5303086	E	RESISTOR, FXD, FILM - 820 ohms, 1W, 5%	3
-83	R18	5001072	E	RESISTOR, FXD, COMP - 220 ohms, 1/2W, 5%	1
-84	Q9	6011075	E	TRANSISTOR - same as Q18	Ref
-85	R25	5001057	E	RESISTOR, FXD, COMP - 51 ohms, 1/2W, 5%	1
-86	R66	5303089	E	RESISTOR, FXD, FILM - 1.1K ohms, 1W, 5%	2
-87	R15	59013524	E	RESISTOR, VARIABLE - 400 ohms	3
-88	Q4	6011151	E	TRANSISTOR - same as Q15	Ref
-89	Q3	6011075	E	TRANSISTOR - same as Q18	1
-90	R37	59013546	E	RESISTOR, VARIABLE - 1K ohms	1
-91	R16	5001116	E	RESISTOR, FXD, COMP - same as R29	Ref
-92	Q2	6011075	E	TRANSISTOR - same as Q18	Ref
-93	R10	5001129	E	RESISTOR, FXD, COMP - 51 ohms, 1/2W ±5%	1
-94	Q1	6011075	E	TRANSISTOR - same as Q18	Ref
-95	R9	5001096	E	RESISTOR, FXD, COMP - same as R30	Ref
-96	R8	5001096	E	RESISTOR, FXD, COMP - same as R30	Ref
-97	R7	59013524	E	RESISTOR, VARIABLE - same as R15	Ref
-98	R17	5001075	E	RESISTOR, FXD, COMP - 300 ohms, 1/2W, 5%	1
-99	R13	5303086	E	RESISTOR, FXD, FILM - same as R14	Ref
-100	R6	5303086	E	RESISTOR, FXD, FILM - same as R14	Ref
-101	R5	5303089	E	RESISTOR, FXD, FILM - same as R66	Ref
-102	R2	5003071	E	RESISTOR, FXD, COMP - 200 ohms, 2W, ±5%	2
-103	R3	5002060	E	RESISTOR, FXD, COMP - 68 ohms, 1W, ±5%	1
-104	Rl	5003071	E	RESISTOR, FXD, COMP - same as R2	Ref
-105	R4	5002060	E	RESISTOR, FXD, COMP - same as R3	Ref
-106	R24	5804602	E	RESISTOR, FXD, WIREWOUND - 5 ohms, 5W, ±10%	1 1
-107	R31	5804455	E	RESISTOR, FXD, WIREWOUND -0.1 ohm, 5W, ±5%	1
-108	R32	5001070	E	RESISTOR, FXD, COMP - 180 ohms, 1/2W, ±5%	1
-109	R34	59013524	E	RESISTOR, VARIABLE - same as R 15	Ref
-110	Q13	6011075	E	TRANSISTOR - same as Q18	Ref
-111	R38	5303091	E	RESISTOR, FXD, FILM - 1.3K ohms, 1W, ±5%	2
					<u> </u>

•	Fig. & Index No.	Desig- nation	AULT Mfg. Co. Part No.	Inden- ture	Description	Qty per Ass'y
	-112	R36	5303081	E	RESISTOR, FXD, FILM - 510 ohms, 1W, ±5%	1
	-113	R23	5001088	E	RESISTOR, FXD, COMP - same as R56	Ref
	-114	R39	5303097	E	RESISTOR, FXD, FILM - 2.4K ohms, 1W, ±5%	1
	-115	R20	5001105	E	RESISTOR, FXD, FILM - same as R58	Ref
	-116	Q7	6011153	E	TRANSISTOR - type 2N3644	2
	-117	R19	5001105	E	RESISTOR, FXD, COMP - same as R58	Ref
	-118	R21	5001112	E	RESISTOR, FXD, COMP - 10K ohms, $1/2W$, $\pm 5\%$	3
▲	-119	R51	5001112	E	RESISTOR, FXD, COMP - same as R21	Ref
	-120	R12	5001105	E	RESISTOR, FXD, COMP - same as R58	Ref
	-121	R50	5001119	E	RESISTOR, FXD, COMP - same as R52	Ref
•	-122	R46	5303092	E	RESISTOR, FXD, FILM - 1.5K ohms, 1/2 W ±5%	1
	-123	CR38	60312201	E	SEMICONDUCTOR DEVICE DIODE - Same as CR23	Ref
A	-124	R48	5303087	E	RESISTOR, FXD, FILM - 910 ohms, 1W, ±5%	1
	-125	Q17	6011075	E	TRANSISTOR - same as Q18	Ref
	-126	Q5	6011153	E	TRANSISTOR - same as Q7	Ref
A	-127	R47	5901125	E	RESISTOR, VARIABLE - 1K ohms	1
	-128	Rll	5001105	E	RESISTOR, FXD, COMP - same as R58	Ref
	-129	Q20	6011075	E	TRANSISTOR - same as Q18	Ref
	-130	R55	5001097	E	RESISTOR, FXD, COMP - 2.4K ohms, 1/2W, 5%	1
	-131	R65	5003083	E	RESISTOR, FXD, FILM - 620 ohms, 2W, ±5%	1
	-132	R64	5001105	E	RESISTOR, FXD, COMP - same as R62	Ref
	-133	R63	5001101	E	RESISTOR, FXD, COMP - 3.6K ohms, 1/2W, ±5%	1
	-134	R54	5002081	E	RESISTOR, FXD, COMP - 510 ohms, 1W, ±5%	1
	-135	R57	5001112	E	RESISTOR, FXD, COMP - same as R21	Ref
	-136	Q19	6011075	E	TRANSISTOR - same as Q18	Ref
	-137	R61	5001102	E	RESISTOR, FXD, COMP - 3.9K ohms, 1/2W, ±5%	1
	-138	R75	5001064	E	RESISTOR, FXD, COMP - 100 ohms, 1/2W ±5%	1
		4 2 ct and				

▲ See Table 4-3 at end of this section.

Table 4-3.
Component Changes Per Serial Number

Fig &	Serial No. 0 through 570				Serial No. 571 through 589			
Index No.	Desig	Description	Part No.	Desig	Description	Part No.		
4-25								
-38	CR 17	SEMICONDUCTOR DEVICE, DIODE - Type 1N752A	605110020	R76	RESISTOR, FXD, COMP - 100 ohms 1/2W ±5%	5001064		
-119	R51	RESISTOR, FXD, FILM - 10K, 1/2W ±5%	5001112		Not Used			
-122	R46	RESISTOR, FXD, FILM - 1.5K, 1/2W ±5%	5303092	R46	RESISTOR, FXD, FILM - 2.4K, 1W ±5%	5303097		
-124	R48	RESISTOR, FXD, FILM - 910 ohms 1W ±5%	8303087	R48	RESISTOR, FXD, FILM - 1.1K, 1W ±5%	5303089		
-127	R47	RESISTOR, VARIABLE -	5901125	R47	RESISTOR, VARIABLE - 500 ohms	5901352		

PART III AULT POWER SUPPLY, MODELS PR-136/PR-143

Part III contains one section presenting the illustrated parts breakdown and schematic diagram for Models PR-136 and PR-143 Power Supplies, manufactured by Ault Inc. per Honeywell SCDs 950 061 003 and 950 061 004, respectively. The operation of both models (PR-136 and PR-143) is similar to Ault Model PR-130. Therefore, refer to Part II, Section 1, for the physical layout, theory of operation, maintenance, troubleshooting procedure, and adjustments for Models PR-136 and PR-143 Power Supplies.

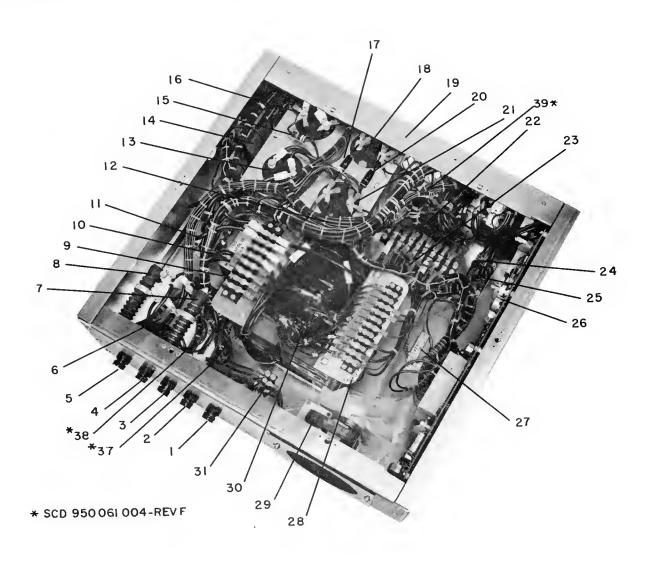
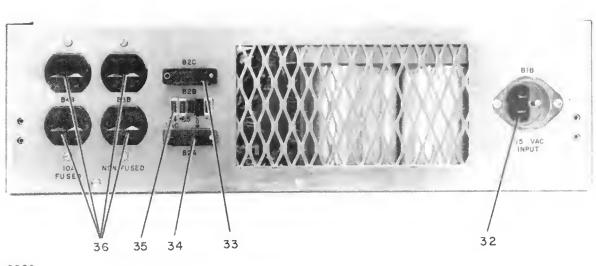


Figure 4-26. Power Supply, Rack-Mounted Configuration (Part 1 of 2)



71-0028

Figure 4-26. Power Supply, Table Top Configuration (Part 2 of 2)

Fig. & Index No.	Desig- nation	AULT Mfg. Co. Part No.	Inden- ture	Description	Qty per Ass'y
4-26		950061003*	С	POWER SUPPLY - AULT Mfg No. PR136-A1	Ref
- 1	A5A	6221082	D	FUSE, CARTRIDGE - 3A	1
-2	AlA	6221203	D	FUSE, CARTRIDGE - 3A, Slo-Blo	1
-3	A2A	6221294	D	FUSE, CARTRIDGE - 10A, Slo-Blo	2
-4	A3A	6221294	D	FUSE, CARTRIDGE - Same as A2A	Ref
- 5	A4A	62211002	D	FUSE, CARTRIDGE - 7.5A	1
-6	C17	4061414	D	CAPACITOR - 6 µF, 660V	1
-7	R74	580-84001	D	RESISTOR, VARIABLE, WIREWOUND - 0.11 ohms 50W ±10%	2
-8	R72	580-84001	D	RESISTOR, VARIABLE, WIREWOUND - same as R74	Ref
-9	TB4	6201601	D	TERMINAL BOARD - Barrier Type	2
-10	Ll	3021285	D	CHOKE	1
-11	CR36, CR37	60311881	D	RECTIFIER - 40 HF5	2
-12	R70 (Hidden)	5003083	D	RESISTOR, FIXED, COMPOSITION - 620 ohms, 2W, 5%	1
-13	C18	4001278	D	CAPACITOR - 100,000 μF, 10V	3
-14	A2	60610981	D	DIODE ASSEMBLY - SCPA1	1
-15	R68	5003054	D	RESISTOR, FIXED, COMPOSITION - 39 ohms, 2W, 5%	1
-16	C19	4001278	D	CAPACITOR - Same as C18	Ref
-17	R79	580842023	D	RESISTOR, WIREWOUND - 200 ohms, 10W, 10%	1
-18	C20	4001278	D	CAPACITOR - Same as C18	Ref
- 19	R69 (Hidden)	5804601	D	RESISTOR, WIREWOUND - 15 ohms, 5W, 10%	1
-20	R78	5003056	D	RESISTOR, FIXED, COMPOSITION - 47 ohms, 2W, 5%	1
-21	C21	4001283	D	CAPACITOR - 50,000 µF, 32V	1
-22	TB2	6201158	D	TERMINAL BOARD - Barrier Type	1
-23	C22	4001540	D	CAPACITOR - 175 μF, 25V	1
-24	A4	60611601	D	DIODE ASSEMBLY - SCDA1	1
-25	A5	60610971	D	DIODE ASSEMBLY - SCNA1	l
-26	A3	080253	D	CIRCUIT CARD ASSEMBLY	l
-27	T2	3011428	D	TRANSFORMER	1
-28	TB3	6201158	D	TERMINAL BOARD - Barrier Type	1
-29	Bl	1018418	D	FAN ASSEMBLY - Modified	1
-30	Tl	3011522	D	TRANSFORMER	1
-31	TBl	6201132	D	TERMINAL BOARD - Barrier Type	1

Fig. & Index No.	Desig- nation	AULT Mfg. No. Part No.	Inden- ture	Description	Qty per Ass'y
-32	BlB	62015503	D	INLET, ELECTRICAL - Hubbell Type 5240	1
-33	B2C	62012401	D	CONNECTOR, RECEPTACLE, ELECTRICAL - Same as B2A	Ref
-34	B2A	62012401	D	CONNECTOR, RECEPTACLE, ELECTRICAL - Burndy Type MS20RM58	2
-35	в2в	620-1643 (Blk) 620-1644(Yel) 620-1645(Red)		CONNECTOR, RECEPTACLE, ELECTRICAL - Heyco Type DC202-1	1
-36	B3B, B4B	62015502	D	CONNECTOR, RECEPTACLE, ELECTRICAL - Hubbell Type 5262	2
*-37	R80 (not shown)	580-6553	D	RESISTOR, VARIABLE, WIREWOUND 5 ohms, 25W	1
* -38	R81 (not shown)	580-6557	D	RESISTOR, VARIABLE, WIREWOUND 50 ohms, 25W	1
* -39	DS1 (not shown)	62S-1033-041	D	LIGHT, MINIATURE, HM 550	1

^{*}SCD 950 061 004, Rev. F

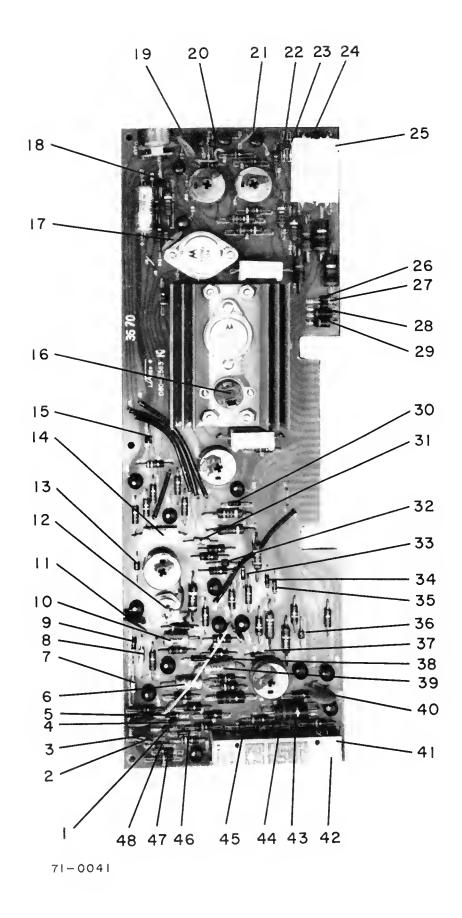


Figure 4-27. Printed Circuit Card (Part 1 of 2)

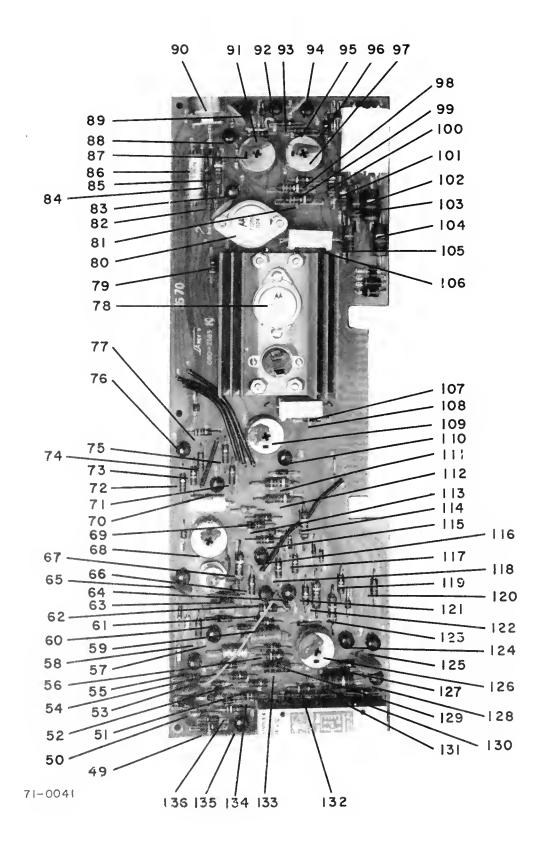


Figure 4-27. Printed Circuit Card (Part 2 of 2)

Fig. & Index No.	Desig- nation	AULT Mfg. Co. Part No.	Inden- ture	Description	Qty per Ass'y
4-27	A3	1802584	D	CIRCUIT CARD ASSEMBLY (Refer to Figure 4-27 for NHA)	Ref
-1	CR23	60312201	E	SEMICONDUCTOR DEVICE, DIODE - Type 10D01	15*
-2	CR22	6001072	E	SEMICONDUCTOR DEVICE, DIODE - Type SCR C106F1	1
-3	C13	406-1239	E	CAPACITOR - 0.001 µF, 500V	6
-4	CR21	60312201	E	Same as CR-23	Ref
- 5	CR20	60511002	E	SEMICONDUCTOR DEVICE, DIODE - Zener - Type 1N753A	2
-6	C11	4001069	E	CAPACITOR - 2 μF, 50V	1
-7	C14	4041018	E	CAPACITOR - 1.0 μF, 50V	2
-8	C12	4041018	E	CAPACITOR - same as C14	Ref
-9	CR 25	60511002	E	Same as CR20	Ref
-10	C9	4061138	E	CAPACITOR - 0.047 µF, 200V	1
-11	C8	4061239	E	CAPACITOR - same as C13	Ref
-12	CR14	6001038	E	SEMICONDUCTOR DEVICE, DIODE - Type C20U	1
-13	CR13	60312201	E	SEMICONDUCTOR DEVICE - same as CR23	Ref
-14	C6	4001542	E	CAPACITOR - 10 μF, 35V	1
-15	CR 12	4041018	E	CAPACITOR - 1.0 μF, 50V	2
-16	Sl	62610945	E	THERMOSTAT	1
-17	C15	4061239	E	CAPACITOR - same as C13	Ref
-18	CR5	6051215	E	SEMICONDUCTOR DEVICE, DIODE - Type 1N4733A	2
-19	C5	4061239	E	CAPACITOR - same as C13	Ref
-20	CR8	60312201	E	SEMICONDUCTOR DEVICE - same as CR23	Ref
-21	C3	4061239	E	CAPACITOR - Same as C13	Ref
-22	CR7	60312201	E	SEMICONDUCTOR DEVICE - same as CR23	Ref
-23	CR6	6051215	E	SEMICONDUCTOR DEVICE - same as CR5	Ref
-24	C2	4001539	E	CAPACITOR - 300 μF, 15V	2
-25	Cl	4001539	E	CAPACITOR - same as C2	Ref
-26	CR4	60312201	E	SEMICONDUCTOR DEVICE - same as CR23	Ref
-27	CR3	60312201	E	SEMICONDUCTOR DEVICE - same as CR23	Ref
-28	CR2	6031301	E	RECTIFIER - 1N4816	,
-29	CR l	6031301	E	RECTIFIER - same as CR2	2 Ref

^{*}SCD 950 061 004--Change qty 15 to 16.

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
-30	CR11	605110037	E	SEMICONDUCTOR DEVICE, DIODE - Type 1N751A	1
- 31	C7	4061132	E	CAPACITOR - 0.001 µF, 200V	1
-32	CR10	60312201	E	SEMICONDUCTOR DEVICE - same as CR23	Ref
- 33	CR9	605110030	E	SEMICONDUCTOR DEVICE, DIODE - Type 1N746A	3
-34	CR15	6031171	E	SEMICONDUCTOR DEVICE, DIODE - Type 1N645	2
-35	CR16	6031171	E	SEMICONDUCTOR DEVICE - same as CR 15	Ref
-36	CR18	60312201	E	SEMICONDUCTOR DEVICE - same as CR23	Ref
*-37	R76	5001064	E	RESISTOR, FIXED, COMPOSITION - 100 ohms, 1/2W, 5%	2
-38	CR19	605110028	E	SEMICONDUCTOR DEVICE, DIODE - Type 1N964B	1
-39	C10	4061239	E	CAPACITOR - 0.068 μF, 200V	1
-40	C4	4061239	E	CAPACITOR - same as C13	Ref
-41	CR31	605110020	E	SEMICONDUCTOR DEVICE, DIODE - Type 1N752A	1
-42	Kl	6241104	E	RELAY	1
-43	CR 30	60312201	E	SEMICONDUCTOR DEVICE - same as CR23	Ref
-44	CR29	60312201	E	SEMICONDUCTOR DEVICE - same as CR 23	Ref
-45	CR28	60312201	E	SEMICONDUCTOR DEVICE - same as CR23	Ref
-46	CR24	605110030	E	SEMICONDUCTOR DEVICE - same as CR9	Ref
-47	CR27	605110030	E	SEMICONDUCTOR DEVICE - same as CR9	Ref
-48	CR26	60312201	E	SEMICONDUCTOR DEVICE - same as CR23	Ref
-49	R62	5001105	E	RESISTOR, FIXED, COMPOSITION - 5.1K ohms, 1/2W, 5%	10
-50	R58	5001105	E	RESISTOR - same as R62	Ref
-51	R53	5001051	E	RESISTOR, FIXED, COMPOSITION - 30 ohms, 1/2W, 5%	1
-52	R60	5001095	E	RESISTOR, FIXED, COMPOSITION - 2K ohms, 1/2W, 5%	1
-53	R56	5001088	E	RESISTOR, FIXED, COMPOSITION - 1/2W, 5%	3
-54	R59	5001040	E	RESISTOR, FIXED, COMPOSITION - 10 ohms, 1/2W, 5%	1

^{*}SCD 950 061 004--Replace R76 with CR39, Part No. 60312201, same as CR23.

Fig. & Index	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
-55	Q18	6011075	E	SEMICONDUCTOR DEVICE, TRANSISTOR Type 2N3569	
-56	R 52	5001119	E	RESISTOR, FIXED, COMPOSITION - 20K ohms, 1/2W, 5%	2
-57	Q16	6011075	E	SEMICONDUCTOR DEVICE, TRANSISTOR same as O18	Ref
-58	R 67	5001092	E	RESISTOR, FIXED, COMPOSITION - 1.5K ohms, 1/2W, 5%	1
- 59	R49	5001105	E	RESISTOR - same as R62	Ref
-60	R45	5001071	E	RESISTOR, FIXED, COMPOSITION - 200 ohms, 1/2W, 5%	1
-61	R44	5001073	E	RESISTOR, FIXED, COMPOSITION - 240 ohms, 1/2W, 5%	1
-62	Q15	6011151	E	SEMICONDUCTOR DEVICE, TRANSISTOR Type 2N3638	2
-63	R42	5001099	E	RESISTOR, FIXED, COMPOSITION - 3K ohms, 1/2W, 5%	1
-64	Q6	6011075	E	SEMICONDUCTOR DEVICE - same as Q18	Ref
-65	Q14	6011075	E	SEMICONDUCTOR DEVICE - same as Q18	Ref
-66	R43	5001105	E	RESISTOR - same as R62	Ref
-67	R40	5303099	E	RESISTOR, FIXED, FILM - 3K ohms, 1W, 5%	1
-68	R41	59013526	E	POTENTIOMETER - lK ohm	1
-69	R27	5001080	E	RESISTOR - same as R56	Ref
-70	Q8	6011075	E	SEMICONDUCTOR DEVICE - same as Q18	Ref
-71	R26	5001081	E	RESISTOR, FIXED, COMPOSITION - 510 ohms, 1/2W, 5%	2
-72	R28	5001105	E	RESISTOR - same as R62	Ref
-73	R29	5001116	E	RESISTOR, FIXED, COMPOSITION - 15K ohms, 1/2W, 5%	2
-74	R 30	5001096	E	RESISTOR, FIXED, COMPOSITION - 2.2K ohms, 1/2W, 5%	3
-75	R22	5001081	E	RESISTOR - same as R26	Ref
-76	Q12	6011075	E	SEMICONDUCTOR DEVICE - same as Q18	Ref
-77	R 35	5001100	E	RESISTOR, FIXED, COMPOSITION - 3.3K 1/2W, 5%	1
-78	Qll	6011133	E	SEMICONDUCTOR DEVICE, TRANSISTOR Type MJ2801	2
-79	R 33	5001077	E	RESISTOR, FIXED, COMPOSITION - 360 ohms, 1/2W, 5%	1

Fig. & Index No.	Desig- nation	Part No.	Inden- ture	Description	Qty per Ass'y
-80	Q10	6011133	E	SEMICONDUCTOR DEVICE - same as Q11	Ref
-81	R14	5303086	E	RESISTOR, FIXED, FILM - 820 ohms, 1W, 5%	3
-82	R18	5001072	E	RESISTOR, FIXED, COMPOSITION - 220 ohms, 1/2W, 5%	1
-83	Q9	6011075	E	SEMICONDUCTOR DEVICE - same as Q18	Ref
-84	R25	5001057	E	RESISTOR, FIXED, COMPOSITION - 51 ohms, 1/2W, 5%	1
-85	R66	5303089	С	RESISTOR, FIXED, FILM - 1.1K ohms, 1W, 5%	3
-86	C23	4001061	E	CAPACITOR - 50 µF, 50V	1
-87	R 15	59013524	E	POTENTIOMETER - 400 ohms	3
-88	Q4	6011151	E	SEMICONDUCTOR DEVICE - same as Q15	Ref
-89	Q3	6011075	E	SEMICONDUCTOR DEVICE - same as Q8	Ref
-90	R37	59013546	E	POTENTIOMETER - lK ohms	1
-91	R16	5001116	E	RESISTOR - same as R29	Ref
-92		6011075	E	SEMICONDUCTOR DEVICE - same as Q8	Ref
-93	R10	5001129	E	RESISTOR, FIXED, COMPOSITION - 51K ohms, 1/2W, 5%	1
-94	Ql	6011075	E	SEMICONDUCTOR DEVICE - same as Q8	Ref
- 95	R9	5001096	E	RESISTOR - same as R30	Ref
-96		5001096	E	RESISTOR - same as R30	Ref
-97		59013524	E	POTENTIOMETER - same as R15	Ref
-98	R17	5001075	E	RESISTOR, FIXED, COMPOSITION - 300 ohms, 1/2W, 5%	1
-99	R13	5303086	E	RESISTOR - same as R14	Ref
-100		5303086	E	RESISTOR - same as R13	Ref
-101		5303089	E	RESISTOR - same as R66	Ref
-102	R2	5003071	E	RESISTOR, FIXED, COMPOSITION - 200 ohms, 2W, 5%	2
-103	R 3	5002060	E	RESISTOR, FIXED, COMPOSITION - 68 ohms, 1W, 5%	2
-104	Rl	5003071	E	RESISTOR - same as R2	Ref
-105	1	5002060	E	RESISTOR - same as R3	Ref
-106		5804602	E	RESISTOR, WIREWOUND - 5 ohms, 5W, 10%	1
-107	R31	5804455	E	RESISTOR, WIREWOUND - 0.1 ohm, 5W, 5%	1

-108 R32 5001070 E RESISTOR, FIXED, COMPOSITION - 109 R34 59013524 E POTENTIOMETER - same as R15 -110 Q13 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -111 R38 5303091 E RESISTOR, FIXED, FILM - 1.3K ohms, 1/2, 5% -112 R36 5303081 E RESISTOR, FIXED, FILM - 510 ohms, 1/4, 5% -113 R23 501088 E RESISTOR, FIXED, COMPOSITION - 2.40K, 1W, 5% -115 R20 5001105 E RESISTOR, FIXED, COMPOSITION - 2.40K, 1W, 5% -116 Q7 6011153 E SEMICONDUCTOR DEVICE, TRANSISTOR Type 2N3644 -117 R19 5001105 E RESISTOR - same as R62 -118 R21 5001112 E RESISTOR - same as R62 -120 R50 5001119 E RESISTOR - same as R62 -121 R46 5305097 E RESISTOR - same as R62 -122 R48 5303089 E RESISTOR - same as R66 -123 Q17 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -124 Q5 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -125 R47 59013525 E POTENTIOMETER, 500 ohms -126 R11 5001105 E RESISTOR - same as R62 -127 Q20 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -128 R55 5001097 E RESISTOR - same as R62 -129 R65 5003083 E RESISTOR - same as R62 -129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -130 R64 5001105 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5% -133 R57 5001112 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5% -133 R57 5001112 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5% -133 R57 5001112 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	Qty per Ass'y
-110 Q13 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -111 R38 5303091 E RESISTOR, FIXED, FILM - 1.3K ohms, 1W, 5% -112 R36 5303081 E RESISTOR, FIXED, FILM - 510 ohms, 1W, 5% -113 R23 501088 E RESISTOR - same as R56 -114 R39 5303097 E RESISTOR, FIXED, COMPOSITION - 2.40K, 1W, 5% -115 R20 5001105 E RESISTOR - same as R62 -116 Q7 6011153 E SEMICONDUCTOR DEVICE, TRANSISTOR Type 273644 -117 R19 5001105 E RESISTOR - same as R62 -118 R21 5001112 E RESISTOR - same as R62 -119 R12 5001105 E RESISTOR - same as R62 -120 R50 5001119 E RESISTOR - same as R62 -121 R46 5305097 E RESISTOR - same as R52 -121 R46 5303089 E RESISTOR - same as R64 -122 R48 5303089 E RESISTOR - same as R66 -123 Q17 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -124 Q5 6011153 E SEMICONDUCTOR DEVICE - same as Q8 -125 R47 59013525 E POTENTIOMETER, 500 ohms -126 R11 5001105 E RESISTOR - same as R62 -127 Q20 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -128 R55 5001097 E RESISTOR - same as R62 -129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -130 R64 5001105 E RESISTOR, FIXED, COMPOSITION - 620 ohms, 2W, 5% -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	1
-111 R38 5303091 E RESISTOR, FIXED, FILM - 1.3K ohms, 1W, 5% -112 R36 5303081 E RESISTOR, FIXED, FILM - 510 ohms, 1W, 5% -113 R23 501088 E RESISTOR - same as R56 -114 R39 5303097 E RESISTOR - same as R56 -114 R39 5303097 E RESISTOR - same as R62 -115 R20 5001105 E RESISTOR - same as R62 -116 Q7 6011153 E SEMICONDUCTOR DEVICE, TRANSISTOR Type 2N3644 -117 R19 5001105 E RESISTOR - same as R62 -118 R21 5001112 E RESISTOR, FIXED, COMPOSITION - 10K ohms, 1/2W, 5% -119 R12 5001105 E RESISTOR - same as R62 -120 R50 5001119 E RESISTOR - same as R62 -121 R46 5305097 E RESISTOR - same as R62 -122 R48 5303089 E RESISTOR - same as R64 -123 Q17 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -124 Q5 6011153 E SEMICONDUCTOR DEVICE - same as Q8 -125 R47 59013525 E POTENTIOMETER, 500 ohms -126 R11 5001105 E RESISTOR - same as R62 -127 Q20 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -128 R55 5001097 E RESISTOR - same as R62 -129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -130 R64 5001105 E RESISTOR, FIXED, COMPOSITION - 620 ohms, 2W, 5% -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	Ref
1W, 5% RESISTOR, FIXED, FILM - 510 ohms, 1W, 5% RESISTOR - same as R56	Ref
1W, 5% 1W, 5% 1W, 5% 1W, 5% 1W, 5% 1W, 5% 1	1
-114 R39 5303097 E RESISTOR, FIXED, COMPOSITION - 2.40K, 1W, 5% -115 R20 5001105 E RESISTOR - same as R62 -116 Q7 6011153 E SEMICONDUCTOR DEVICE, TRANSISTOR Type 2N3644 -117 R19 5001105 E RESISTOR - same as R62 -118 R21 5001112 E RESISTOR, FIXED, COMPOSITION - 10K ohms, 1/2W, 5% -119 R12 5001105 E RESISTOR - same as R62 -120 R50 5001119 E RESISTOR - same as R52 -121 R46 5305097 E RESISTOR - same as R52 -122 R48 5303089 E RESISTOR - same as R66 -123 Q17 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -124 Q5 6011153 E SEMICONDUCTOR DEVICE - same as Q7 -125 R47 59013525 E POTENTIOMETER, 500 ohms -126 R11 5001105 E RESISTOR - same as R62 -127 Q20 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -128 R55 5001097 E RESISTOR - same as R62 -129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -130 R64 5001105 E RESISTOR, FIXED, COMPOSITION - 620 ohms, 2W, 5% -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	1
2.40K, 1W, 5%	Ref
-116 Q7 6011153 E SEMICONDUCTOR DEVICE, TRANSISTOR Type 2N3644 -117 R19 5001105 E RESISTOR - same as R62 -118 R21 5001112 E RESISTOR, FIXED, COMPOSITION - 10K ohms, 1/2W, 5% -119 R12 5001105 E RESISTOR - same as R62 -120 R50 5001119 E RESISTOR - same as R52 -121 R46 5305097 E RESISTOR - same as R39 -122 R48 5303089 E RESISTOR - same as R66 -123 Q17 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -124 Q5 6011153 E SEMICONDUCTOR DEVICE - same as Q7 -125 R47 59013525 E POTENTIOMETER, 500 ohms -126 R11 5001105 E RESISTOR - same as R62 -127 Q20 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -128 R55 5001097 E RESISTOR - same as R62 -129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -130 R64 5001101 E RESISTOR - same as R62 -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	2
Type 2N3644 -117 R19 5001105 E RESISTOR - same as R62 -118 R21 5001112 E RESISTOR, FIXED, COMPOSITION - 10K ohms, 1/2W, 5% -119 R12 5001105 E RESISTOR - same as R62 -120 R50 5001119 E RESISTOR - same as R52 -121 R46 5305097 E RESISTOR - same as R39 -122 R48 5303089 E RESISTOR - same as R66 -123 Q17 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -124 Q5 6011153 E SEMICONDUCTOR DEVICE - same as Q7 -125 R47 59013525 E POTENTIOMETER, 500 ohms -126 R11 5001105 E RESISTOR - same as R62 -127 Q20 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -128 R55 5001097 E RESISTOR - same as R62 -129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -130 R64 5001101 E RESISTOR, FIXED, COMPOSITION - 620 ohms, 2W, 5% -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	Ref
-118 R21 5001112 E RESISTOR, FIXED, COMPOSITION - 119 R12 5001105 E RESISTOR - same as R62 -120 R50 5001119 E RESISTOR - same as R52 -121 R46 5305097 E RESISTOR - same as R39 -122 R48 5303089 E RESISTOR - same as R66 -123 Q17 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -124 Q5 6011153 E SEMICONDUCTOR DEVICE - same as Q7 -125 R47 59013525 E POTENTIOMETER, 500 ohms -126 R11 5001105 E RESISTOR - same as R62 -127 Q20 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -128 R55 5001097 E RESISTOR - same as R62 -129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -130 R64 5001105 E RESISTOR, FIXED, COMPOSITION - 620 ohms, 2W, 5% -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	2
10K ohms, 1/2W, 5% RESISTOR - same as R62	Ref
-120 R50 5001119 E RESISTOR - same as R52 -121 R46 5305097 E RESISTOR - same as R39 -122 R48 5303089 E RESISTOR - same as R66 -123 Q17 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -124 Q5 6011153 E SEMICONDUCTOR DEVICE - same as Q7 -125 R47 59013525 E POTENTIOMETER, 500 ohms -126 R11 5001105 E RESISTOR - same as R62 -127 Q20 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -128 R55 5001097 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 620 ohms, 2W, 5% -130 R64 5001105 E RESISTOR - same as R62 -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	2
-121 R46 5305097 E RESISTOR - same as R39 -122 R48 5303089 E RESISTOR - same as R66 -123 Q17 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -124 Q5 6011153 E SEMICONDUCTOR DEVICE - same as Q7 -125 R47 59013525 E POTENTIOMETER, 500 ohms -126 R11 5001105 E RESISTOR - same as R62 -127 Q20 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -128 R55 5001097 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 620 ohms, 2W, 5% -130 R64 5001105 E RESISTOR - same as R62 -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	Ref
-122 R48 5303089 E RESISTOR - same as R66 -123 Q17 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -124 Q5 6011153 E SEMICONDUCTOR DEVICE - same as Q7 -125 R47 59013525 E POTENTIOMETER, 500 ohms -126 R11 5001105 E RESISTOR - same as R62 -127 Q20 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -128 R55 5001097 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 620 ohms, 2W, 5% -130 R64 5001105 E RESISTOR - same as R62 -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	Ref
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-126 R11 5001105 E RESISTOR - same as R62 -127 Q20 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -128 R55 5001097 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 620 ohms, 2W, 5% -130 R64 5001105 E RESISTOR - same as R62 -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	Ref
-127 Q20 6011075 E SEMICONDUCTOR DEVICE - same as Q8 -128 R55 5001097 E RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, 5% -129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 620 ohms, 2W, 5% -130 R64 5001105 E RESISTOR - same as R62 -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	1
Q8	Ref
-129 R65 5003083 E RESISTOR, FIXED, COMPOSITION - 620 ohms, 2W, 5% -130 R64 5001105 E RESISTOR - same as R62 -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	Ref
-130 R64 5001105 E RESISTOR - same as R62 -131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	1
-131 R63 5001101 E RESISTOR, FIXED, COMPOSITION - 3.6K ohms, 1/2W, 5% -132 R54 5002081 E RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	1
-132 R54 5002081 E 3.6K ohms, 1/2W, 5% RESISTOR, FIXED, COMPOSITION - 510 ohms, 1W, 5%	Ref
510 ohms, 1W, 5%	1
-133 R57 5001112 E RESISTOR - same as R21	1
	Ref
-134 Q19 5011075 E SEMICONDUCTOR DEVICE - same as Q8	Ref
-135 C23 4001061 E CAPACITOR - 50 μF, 50V	1

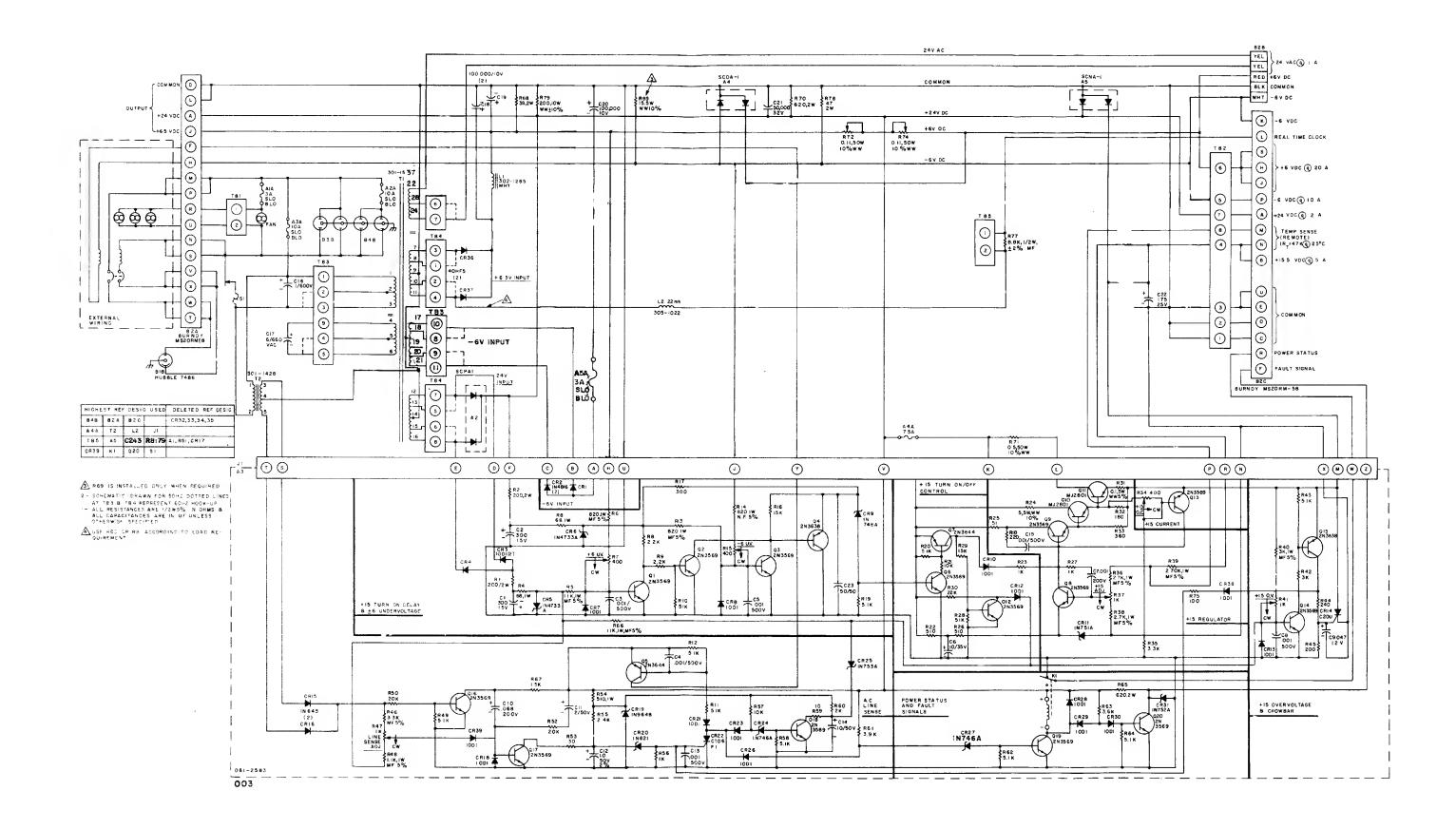


Figure 4-28. Model PR-136 Power Supply, Schematic Diagram (SCD 950 061 003)

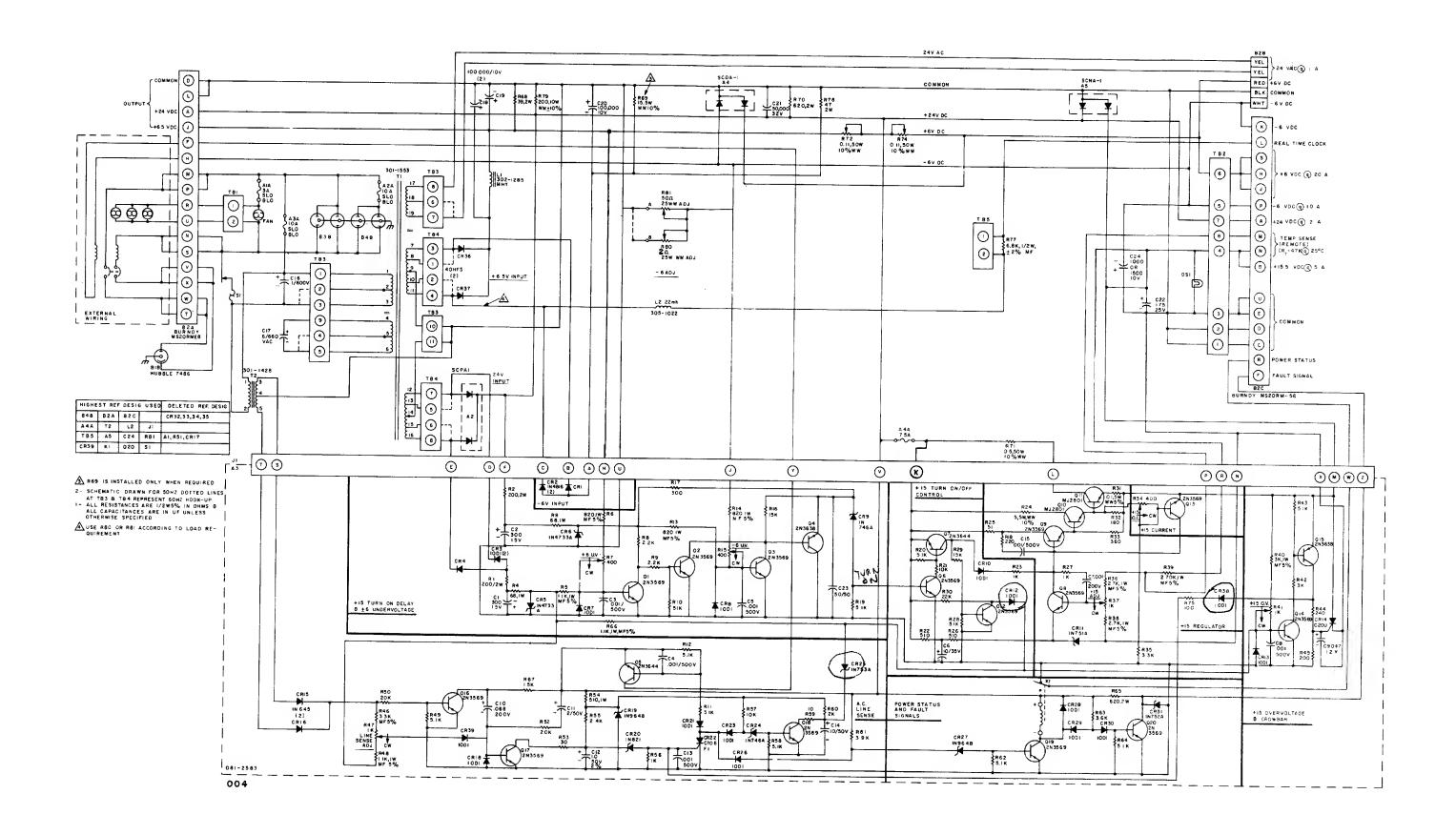


Figure 4-29. Model PR-143-Al Power Supply, Schematic Diagram (SCD 950 061 004, Rev F)

APPENDIX B ACME POWER SUPPLIES

CHAPTER V ACME POWER SUPPLIES

This chapter is divided into two parts. Each part contains information for the power supplies manufactured by Acme Electric Corporation, and used in the H316 General Purpose Computer.

Part I contains operating instructions and illustrated parts breakdown (IPB) for Acme Model PS-1-59307, manufactured per Honeywell Specification Control Drawing (SCD) No. 950061001.

Part II contains the IPB and schematic diagram for Acme Model PS-2-59307, manufactured per Honeywell SCD No. 950061003.

PART I ACME POWER SUPPLY, MODEL PS-1-59307

SECTION 1 ASSEMBLY DESCRIPTION

The H316 Power Supply is designed to provide operating voltages for the H316 computer as follows:

24 Vac	l ampere (max)
+6 Vdc	8-20 amperes
+6.5 Vdc*	8-20 amperes
-6 Vdc	l ampere (max)
+15.5 Vdc	0.2-5 amperes
+24 Vdc	2 amperes (max)

A multiple secondary constant voltage transformer is used to provide these required operating potential using an input line of 95 to 130 Vac at either 50 or 60 Hz. Logic circuitry is included in the power supply to control the turn on procedure. Circuit protection devices include fuses, a low line voltage sensing circuit, and a thermostat switch.

PHYSICAL LAYOUT

The power supply measures 17.28 inches wide by 17.19 inches deep by 5.15 inches high, and it is available for mounting with either the rack-mounted or table top computer configuration. The table top configuration uses the power supply as the computer base, with the mainframe hinged to the top of the supply. The rack-mounted configuration places the power supply below the mainframe and separately attached to the mounting rack. Cooling is provided by a built in fan and three connectors are used for input and output voltages. This power supply consists of the basic power unit Figure 5-1, +15.5 Vdc circuit (printed circuit board) Figure 5-2, and a line sensing circuit (printed circuit board) Figure 5-3.

*For Model PS-2-59307 only

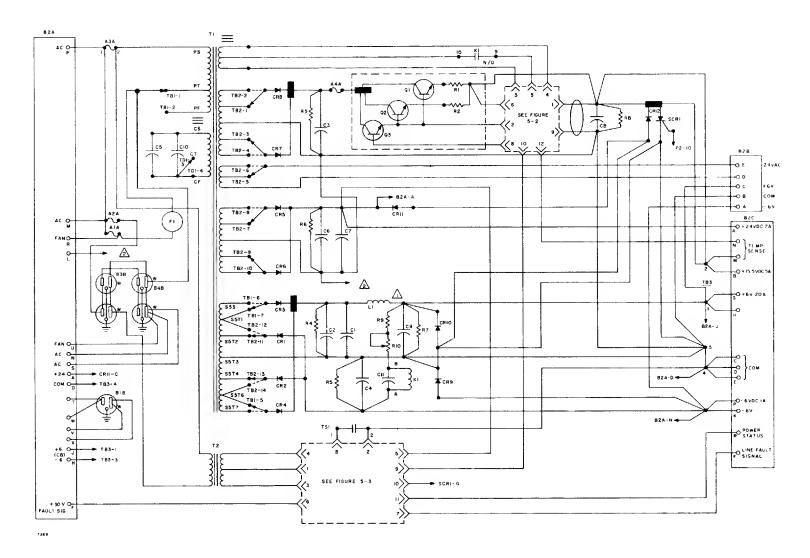


Figure 5-1. Basic Power Supply Schematic

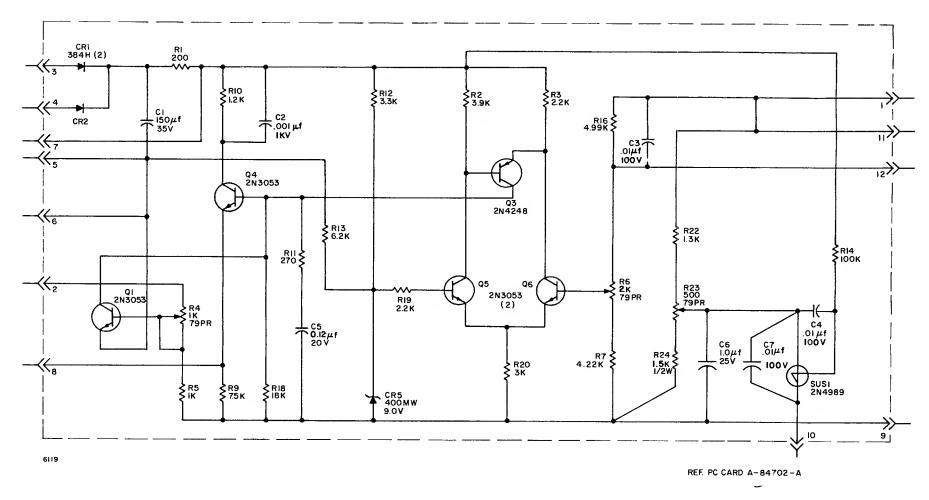


Figure 5-2. Power Supply +15.5 Vdc Circuit Schematic (Printed Circuit Card A-84702-A)

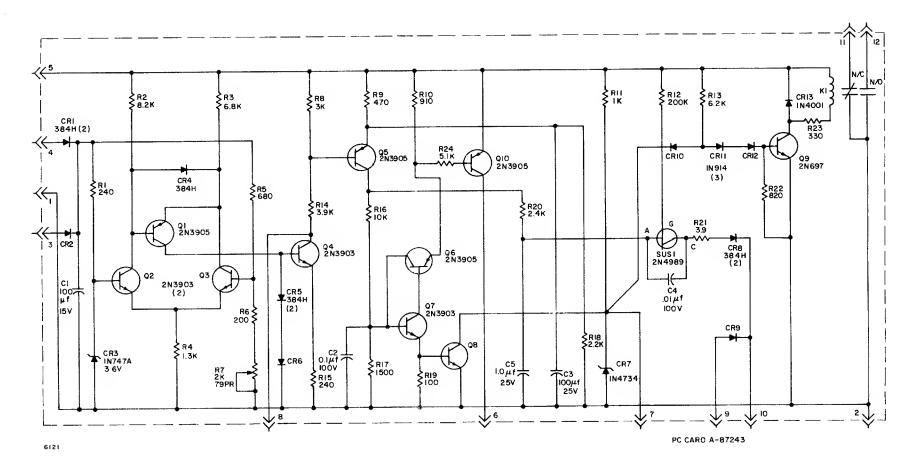


Figure 5-3. Line Sensing Circuit Schematic (Printed Circuit Card A-87249)

THEORY OF OPERATION

The power supply converts ac input power into four regulated dc outputs and one nonregulated 24 Vac output. A block diagram of the power supply is shown in Figure 5-4. Input ac power is supplied to a constant voltage transformer in the input power converter. Three secondaries of the constant voltage transformer provide the +6V, -6V, and +24V output voltages. The +24V winding also provides bulk ac power to a series regulator which regulates the +15.5 output voltage. A fourth secondary provides the 24 Vac output. The logic circuitry provides the required sequencing, line sensing, and overvoltage protection. Reverse diodes are included across each output to prevent accidental reversal of polarity.

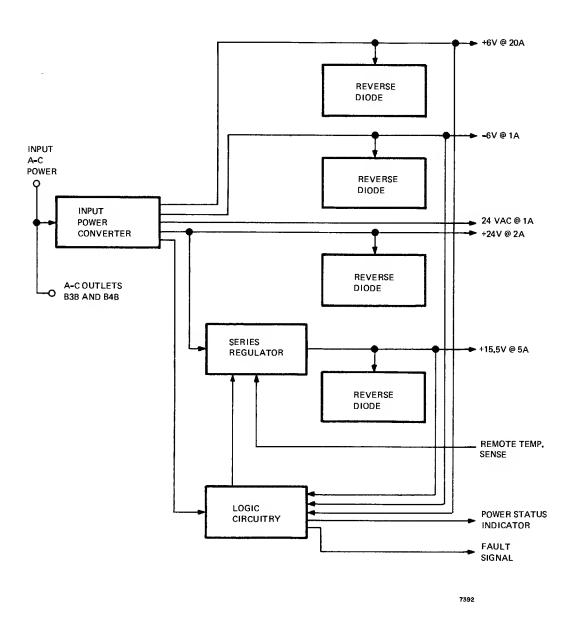


Figure 5-4. Power Supply Block Diagram

Input Power Converter

Input ac power is supplied to the primary of constant voltage transformer T1. (Refer to Figure 5-5.) A line voltage sensing circuit provides a "fault signal" to indicate whether the ac line voltage is above or below line limits. A3A is the input ac fuse. The outputs of three secondaries of T1 are rectified and filtered to provide the ±6V and +24V outputs as well as several other required bulk dc sources. A fourth secondary of T1 provides the unregulated 24 Vac output. A capacitor is used in combination with a winding on T1 to resonate the transformer at the line frequency and provide the constant voltage characteristic. All the windings are tapped to allow change over between 50 and 60 Hz line operation. Transformer T2 is used by the line sense circuitry to monitor the input ac line.

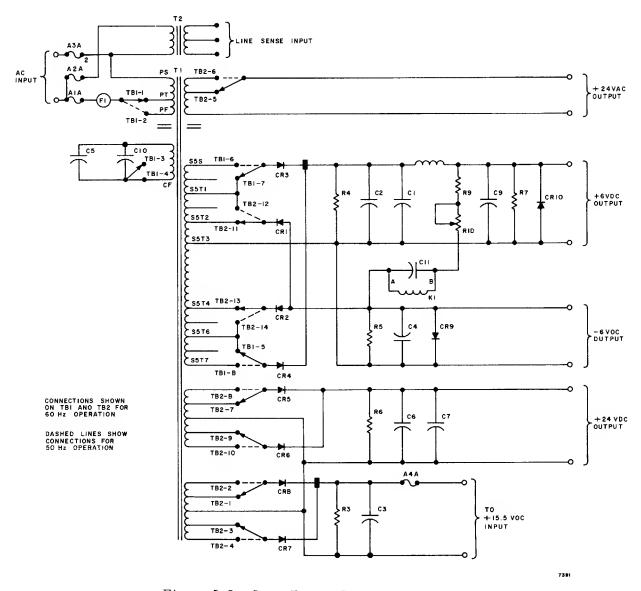
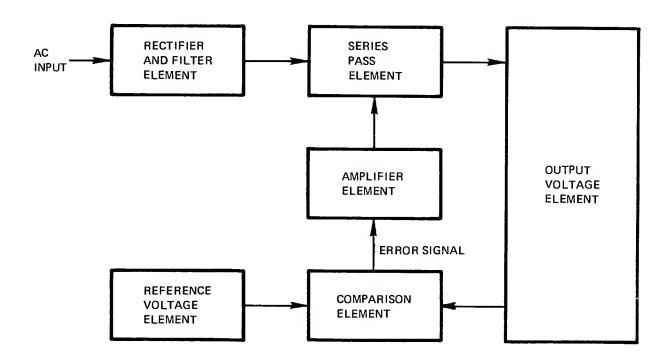


Figure 5-5. Input Power Converter Diagram

+15.5 Vdc Supply Circuit

The +15.5 Vdc supply is controlled by a remote temperature sensing device. This supply is a basic series regulator containing a temperature sensitive voltage adjustment, an overvoltage circuit, and a current limit circuit.

The basic series regulator, Figures 5-6 and 5-7, consists of a comparison element which compares a portion of the output voltage with the reference voltage, and generates an error signal. This signal is amplified and applied to the base of a series pass element which increases or decreases the output in response to the error signal.



7390

Figure 5-6. Series Regulator Circuit Block Diagram

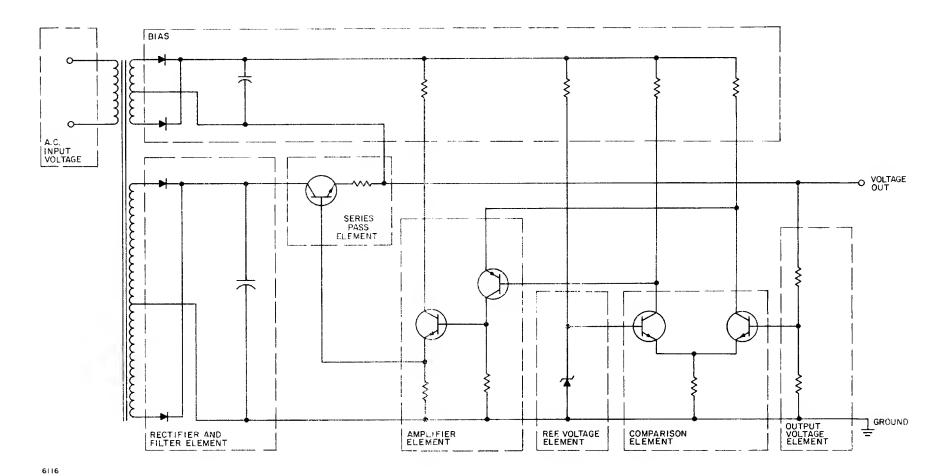


Figure 5-7, Series Regulator Circuit Schematic

The basic schematic of the regulator for the +15.5 Vdc power supply is presented in Figure 5-8. This unit contains the temperature sensitive voltage circuit, the overvoltage firing circuit, and the current limit circuit.

The remote temperature sensing device (Honeywell P/N 70 932 305 001) is a thermistor that provides a nominal temperature coefficient of $-0.5\%/^{\circ}$ C. This device is included in the output voltage circuit that changes the output as the resistance of the device changes. The overvoltage circuit is designed to limit the output voltage to less than +18 Vdc. The current cutback circuit limits the output current to less than 6 amperes.

Turn-on, Turn-off Sequence. -- The turn-on sequence of the +15.5 Vdc supply provides a delay (see Figure 5-8 relay K1) so that the +6V and -6V supplies exceeds 90% of nominal before the +15.5V supply exceeds 20% of normal. The turn-off sequence of this supply starts to crowbar at 1 ms after the "fault signal" goes to common. The +15.5V supply will be reduced to 20% of normal before the +6V or -6V supplies have changed by 10%.

Line Voltage Sensing Circuit

The line voltage sensing circuit provides a "fault signal" to indicate whether the ac line voltage is above the low line limit. The comparison element, Figures 5-9 and 5-10, compares a portion of a voltage that is directly proportional to the line voltage with a reference voltage. If the line voltage falls below the specified low line limit, the "fault signal" (5 to 6 Vdc) is reduced to zero. Thus, the power status is shorted to common through a set of relay contacts and a signal (approximately 30 Vdc) is applied to the input circuit breaker relay trip coil that shuts down the input power (see Figure 5-11).

MAINTENANCE

The only routine maintenance required for the power supply is periodic cleansing or replacement of the air filter. Adjustment procedures, a trouble shooting chart and interface connection data are described in the following paragraphs.

Replacement Parts

Replacement parts can be purchased directly from Honeywell Inc., Framingham, Mass. However, most of the components are standard electrical parts and might be obtained locally in less time.

Recommended Test Instruments

The following test instruments will be helpful in testing and adjusting the power supply:

Voltmeter, ac/dc Ammeter, ac/dc Card Extender

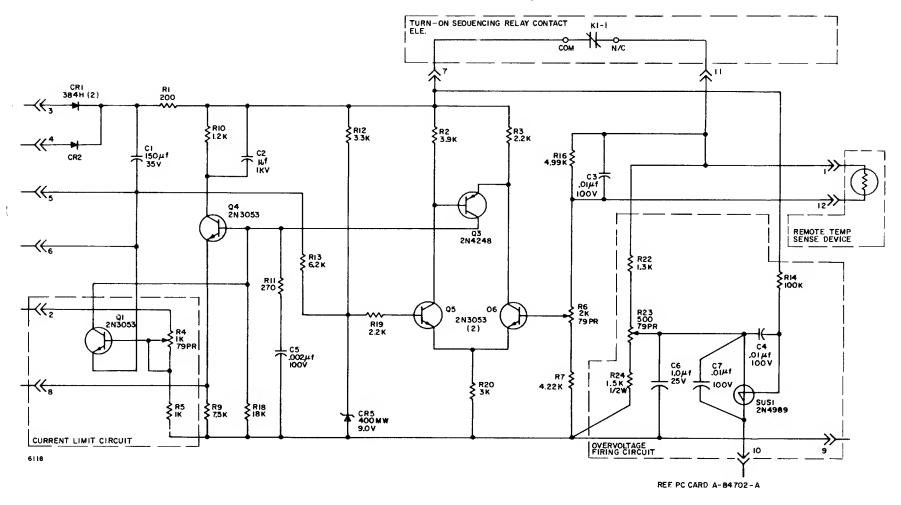


Figure 5-8. Schematic of +15.5 Vdc Power Supply Regulator

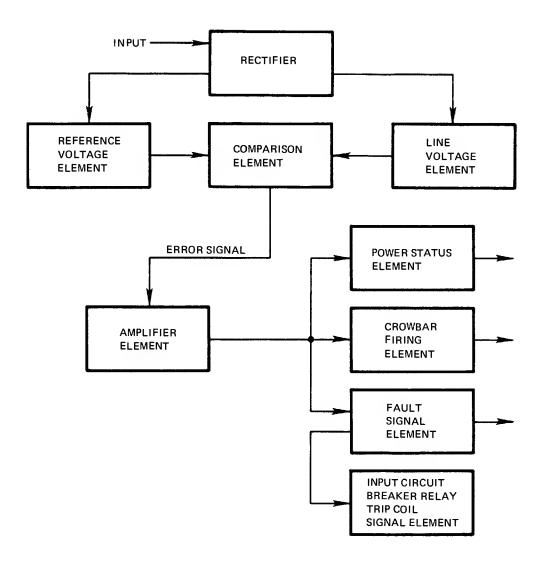


Figure 5-9. Line Voltage Sensing Circuit Block Diagram

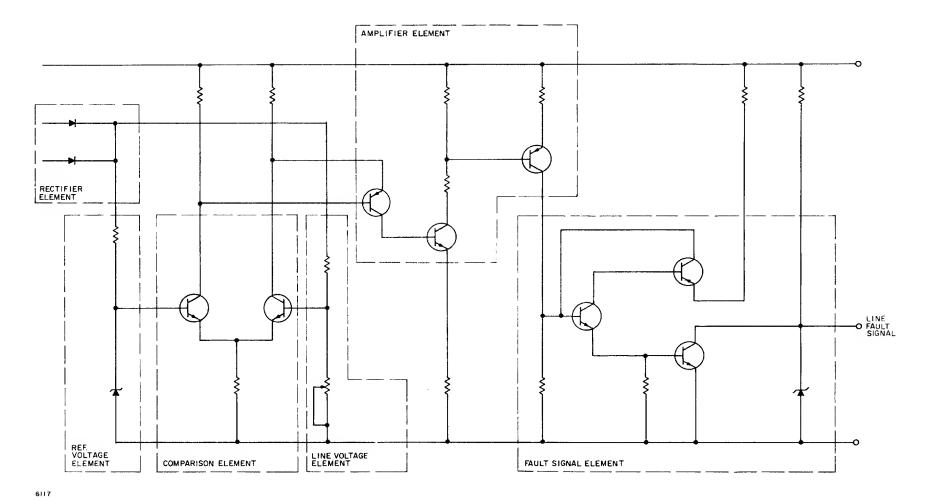


Figure 5-10. Line Voltage Sensing Circuit Schematic

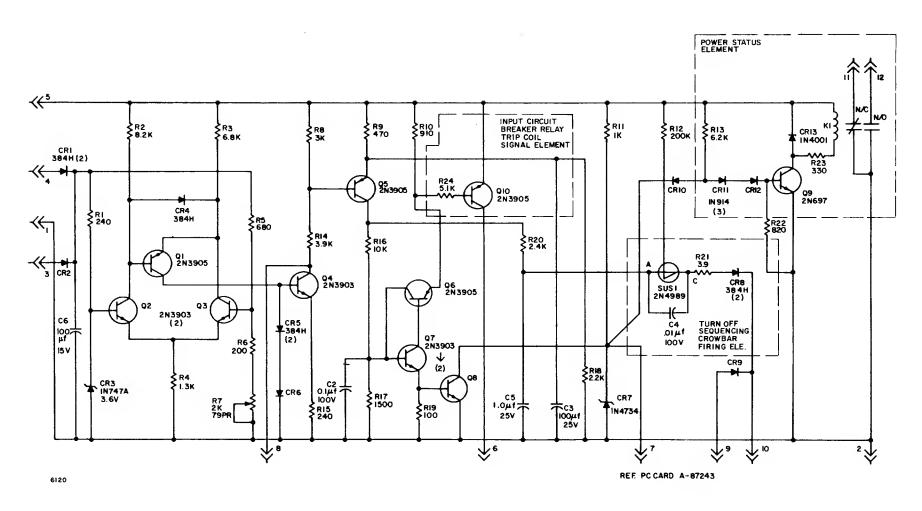


Figure 5-11. Line Sensing Circuit

Troubleshooting Procedure

Use every safety precaution when troubleshooting the power supply. The supply should be visibly examined for broken, loose or damaged parts, or wire and foreign objects. In the event of an audibly or visually apparent malfunction, proceed directly to the affected area and perform the necessary repairs. Apparent circuit board failure may be caused by improperly adjusted potentiometers. This should be kept in mind when troubleshooting the power supply.

WARNING

The input transformer produces voltage in excess of 600 volts. Exercise extreme caution whenever the power supply cover is off. Remove any rings, watches or other metallic objects before installation or testing. Avoid contact with heat sinks or the input transformer, which operate at high temperatures.

Perform the following preliminary checks before troubleshooting the unit:

- a. Remove any foreign objects from the power supply.
- b. Check all input and output connections.
- c. Check the remote temperature sensing device connection.
- d. Check for proper connections for 50 or 60 Hz operation.

Table 5-1.
Troubleshooting Guide

SYMPTOM	POSSIBLE CAUSE	SUGGESTED ACTION
Power supply will not turn on,	a. No input ac power.b. Blown fuse AlA, A2A, or A3A	a. Check for input power.b. Check fuses.
	c. Low ac line voltage. d. Faulty or misadjusted line sense circuit under low ac line condition.	c. Check for faulty signal.d. Check ac line level and line sense circuit adjustment.
No +15.5V out- put voltage.	 a. Under voltage on +6V or -6V output. 	a. Check ±6V levels.
put voitage.	b. Shorted output	 b. Check with external loads removed.
	 c. Faulty or misadjusted turn-on delay circuit. 	c. Check turn-on delay circuit.
Low +15.5V out- put voltage.	a. Improper adjustment.b. Blown fuse A4A.c. Overloaded output.	a. Check output adjustment.b. Check fuse.c. Check with external load removed.
	d. Misadjusted over current limit.	d. Check adjustment.
Overvoltage occurs on +15.5V output.	a. Misadjusted output. b. Shorted pass transistor O2.	a. Check adjustment.b. Check Q2.
	c. Misadjusted overvoltage circuit.	 c. Check adjustment of overvoltage circuit: Overvoltage may not be actually occurring.

ADJUSTMENTS

50 or 60 Hz Operation Adjustment

Several tap changes are required on transformer Tl to convert from 60 Hz to 50 Hz operation. Figure 5-5 shows the correct wiring for 60 Hz operation. The dashed lines show the changes required for 50 Hz operation. Changing frequency operation also requires readjustment of the line sense circuit.

Output Voltage Adjustments

The +15.5V output is the only adjustable output. This voltage is controlled by potentiometer R6 (Figure 5-2) where clockwise rotation will increase the output voltage level.

+15.5V Overvoltage Adjustment

The +15.5V overvoltage adjustment is controlled by potentiometer R23. Proceed as follows:

- a. Turn R23 (maximum overvoltage setting) fully clockwise.
- b. Apply input ac power.
- c. Adjust the +15.5V output voltage to the desired overvoltage setting (18V) with the output voltage adjustment potentiometer R6. It may be necessary to replace the external thermistor with a decade box to reach this level.
 - d. Slowly turn R23 counterclockwise until the +15.5V output voltage drops to zero.
 - e. Remove input ac power.
 - f. Replace the external thermistor if it had been removed.
 - g. Turn R6 fully counterclockwise.
 - h. Apply input ac power.
 - i. Set the +15.5V output voltage to the desired operating level.

+15.5V Overcurrent Adjustment

Adjust the overload bendback point with potentiometer R34 using the following procedure:

- a. Turn R4 fully clockwise.
- b. Apply a load to the +15.5V output equal to the desired overcurrent setting.
- c. Apply input ac power.
- d. Slowly turn R4 counterclockwise until the +15.5V output voltage starts to drop.
- e. Remove input ac power and remove the load.

Line Sense Circuit Adjustment

The line sense circuit is adjusted by potentiometer R7. This adjustment is required whenever a change is made between 50 Hz and 60 Hz operation. Proceed as follows:

- a. Turn R7 fully clockwise.
- b. Apply 95 Vac (low line) to the input power terminals.
- c. Slowly turn R7 counterclockwise until the fault signal goes to ground.
- d. Remove input ac power.

±6V Undervoltage Adjustment

The ± 15.5 V turn-on delay circuit contains ± 6 V undervoltage sensors. These sensors have been adjusted at the factory and should normally require no adjustment. However, if adjustment should become necessary, proceed as follows:

±6V Undervoltage Adjustment Procedure (for Model PS-1-59307 only)

- a. Turn R10 fully counterclockwise.
- b. Disconnect one lead of resistor R9 at junction (capacitor C9 and resistor R7).
- c. Connect the disconnected lead to a positive voltage source of the desired undervoltage level.
 - d. Apply input ac power.
 - e. Slowly turn R10 clockwise until the +15.5V output drops to zero.
 - f. Remove input ac power.
 - g. Remove the external voltage source and reconnect the lead.

+6.5V Output Adjustment Procedure (for Model PS-2-59307 only)

- a. Turn off power to system.
- b. Place a suitable meter on pin B2CS and adjust slide-wire resistor R11 (Figures 5-15 and 5-19).
 - c. Turn on power to system and read meter.
 - d. Turn off power to system and adjust slidewire resistor R11.
 - e. Repeat steps b, c, and d until meter reading is 6.5 Vdc.

CONNECTOR INTERFACE DATA

All inputs and outputs are made via the three connectors on the power supply. The pin connections are tabulated in Table 5-2. The connector number precedes the pin number; for example, B2A-A refers to pin A or connector B2A.

SPECIFICATIONS

Input Power

95-130 VRMS, 50 or 60 Hz \pm 1 Hz, single phase.

Output Power

Output Voltage	Current Range	Regulation Band	Set Current	Ripple _(p-p)_	Overvoltage Protection Max. Voltage
+24 Vdc	0 - 2A	±5%*	1.5A	5%	
+15.5 Vdc	0.2 - 5A	±5%		2%	+18
+6 Vdc	8 - 20A	±6%*	15A	2%	
-6 Vdc	0 - 1A	±6%*	0.5A	2%	
+6.5 Vdc	8 - 20A	±6%**	15A	2%	
24 Vac	0 - 1A				

^{*}Regulation of +24V, +6V and -6V includes static line voltage changes (at set current) and ripple only.
**For Model PS-2-59307 only.

Table 5-2.
Pin Connections*

Terminal	Identification
B2A-A	+24 Vdc Output
B2A-D	Common
B2A-F	+30V fault signal
B2A-H	-6V Output
B2A-J	+6V Output (+6.5V)
B2A-L	Junction 🖄
B2A-M	AC fused
B2A-N	To AC B4B
B2A-P	AC Outlet fused B3B
B2A-S	To AC B4B
B2A-R	To Fan
B2A-U	To Fan
B2A-T	To AC BlB
B2A-V	To AC BlB-W
B2A-W	To AC BlB
B2A-X	To AC BlB-W
B2B-E	24 Vac Output
B2B-C	+6 Vdc Output (+6.5V)
B2B-A	-6 Vdc Output
B2B-B	Common
взв	AC Outlet, fused
B4B	AC Outlet, fused
B2C-A	+24 Vdc Output
B2C-B	+15.5 Vdc Output
B2C-C	Common
B2C-D	Common
B2C-E	Common
B2C-F	Line fault signal
B2C-H	+6 Vdc Output (+6.5V)
B2C-K	-6 Vdc Output
B2C-M	Temperature sense element
B2C-N	Temperature sense element
B2C-P	-6 Vdc Output
B2C-R	Power status terminal
B2C-S	+6 Vdc Output for Model PS-1-59307
	+6.5 Vdc Output for Model PS-2-59307

^{*} For Model PS-1-59307 See Figure 5-1 For Model PS-2-59307 See Figure 5-19

The +15.5V supply regulation is $\pm 5\%$ for:

- 1. Line Change (95 130 Vac).
- 2. A 2.6 Ampere load step in the range above 0.3 Ampere.
- 3. Temperature drift over a 90 day period.

The voltage level of the +15.5V supply is remotely controlled by a temperature sensing device.

Line Voltage Sensing

Circuitry is included to provide a "fault signal" to indicate whether the ac line voltage is above the low line limit.

```
("fault signal" is 5 to 6 Vdc when the input is above low line) ("fault signal" is 0 when the line is below low line)
```

Overvoltage Protection

Turn-on and turn-off will not cause the $+15.5 \, \mathrm{V}$ output to exceed 18V nor the $\pm 6 \, \mathrm{V}$ outputs to exceed nominal by more than 20%.

An overvoltage crowbar circuit prevents the +15.5V output from exceeding 18V in the event of a regulator component failure.

Overcurrent Protection

Fuses are provided for input ac power, the internal fan, bulk dc power for the +15.5V regulator and two ac auxiliary outputs. Current limiting circuitry is incorporated in the +15.5V regulator.

Output Voltage Reversal

Diodes are across each output to prevent a reverse voltage of greater than 2.0V.

Excess Temperature

A temperature sensitive switch is located on the transistor heat sink which will send the "fault signal" to 0 in the event of excess temperature. Normal operating temperature is $0 - 60^{\circ}$ C.

SECTION 2 ILLUSTRATED PARTS BREAKDOWN

This section contains the illustrated parts breakdown (IPB) of the Acme Electric Corporation Power Supply, Model PS-1-59307 used on both the rack-mounted and table top models of the H316 General Purpose Computer.

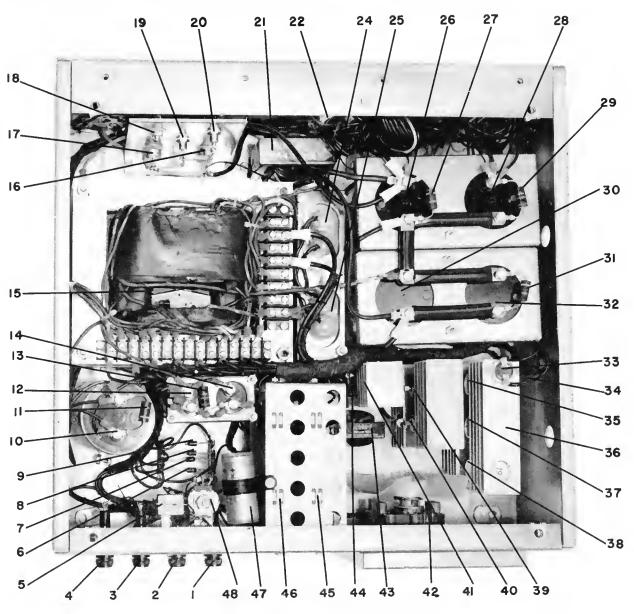


Figure 5-12. Power Supply, Acme Model PS-1-59307, Parts Location Diagram (Sheet 1 of 2)

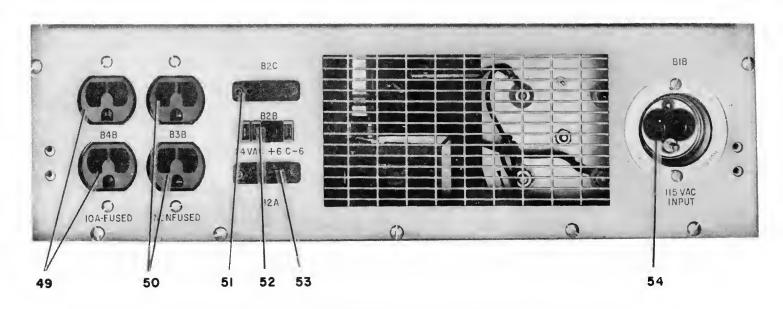


Figure 5-12. Power Supply, Acme Model PS-1-59307, Parts Location Diagram (Sheet 2 of 2)

			T			
	g. & ndex		Acme	Inden-		Qty
1	No.	Designation	Part No.	ture	Description	per A ss'y
5-17	2	DEF1 through DEF3	70950061 -* 001	С	POWER SUPPLY-Acme Elec. Corp. Part No. PS-1-59307 (Ref. to Figs. 3-1-4 and 3-2-5 for NHA)	A/R
	- 1	Al A	A-25-74310	D	FUSE, CARTRIDGE - 1A; Bussman MDA10A; slow-blowing type	1
	-2	A2A	A-32-74310	D	FUSE, CARTRIDGE — 2A; Bussman MDA2A; slow-blowing type	1
	-3	A3A	A-31-74310	D	FUSE, CARTRIDGE — 8A; Bussman MDA8A, slow-blowing type	1
	- 4	A4A	A-10-23108	D	FUSE, CARTRIDGE - 8A; Bussman ABC8A; fast-blowing type	1
	- 5	Kl	A-5-89745	D	RELAY, ARMATURE - spdt; coil, Hart- Advance 67DP-D-203, res. ohms 185	1
	-6	CR6	A-2-81259	D	SEMICONDUCTOR DEVICE, DIODE - Westinghouse type 1 N5401	4
	- 7	CR5	A-2-81259	D	SEMICONDUCTOR DEVICE, DIODE - same as CR6	Ref
	-8	CR2	A-2-81259	D	SEMICONDUCTOR DEVICE, DIODE - same as CR6	Ref
	-9	CRI	A-2-81259	D	SEMICONDUCTOR DEVICE, DIODE - same as CR6	Ref
	-10	C3	A-60-74243	D	CAPACITOR, FIXED, ELECT - 21,500 µF; 40V; Mallory type CGS	1
	-11	R 3	A-67-41321	D	RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 2W; ±5%	3
	-12	C7	A-57-74243	D	CAPACITOR, FIXED, ELECT - 6000 µF, 40V	2
	-13	R6	A-59-41321	D	RESISTOR, FIXED, COMPOSITION - 1K ohm, 2W, ±5%	3
	-14	C6	A-57-74243	D	CAPACITOR, FIXED, ELECT — same as C7	Ref
	-15	T1	T-65717	D	TRANSFORMER, POWER	1
	-16	SCRI	A-2-61908	D	THYRISTOR-type 2N682, GEC35Fx50 F964	1
		CR10	A-2-41409	D	SEMICONDUCTOR DEVICE, DIODE - Westinghouse type 1N1184A	3
		CR9	A-2-92571	D	SEMICONDUCTOR DEVICE, DIODE - Westinghouse type 368B VW	2
		CR11	A-4-92571	D	SEMICONDUCTOR DEVICE, DIODE - Westinghouse type 368B VW	3
		CR12	A-2-93571	D	SEMICONDUCTOR DEVICE, DIODE - same as CR9	Ref
		Ll	T-15-56515	D	TRANSFORMER	1
		C8	A-55-74243	D	CAPACITOR, FIXED, ELECT - 2000 μF, 40V; Mallory type CGS	1
	-23	R8 (not shown)	A-59-41321	D	RESISTOR, FIXED, COMPOSITION — same as R6	Ref

^{*}Honeywell part no. assignment

Fig. & Index No.	Designation	Acme Part No.	Inden- ture	Description	Qty per Ass'y
-24	C10	A-5-81411	D	CAPACITOR, FIXED, ELECT — 5 µF, 660V	2
-25	C5	A-5-81411	D	CAPACITOR, FIXED, ELECT — same as C10	Ref
-26	C9	A-25-74243	D	CAPACITOR, FIXED, ELECT - 76,000 μF, 15V; Sangamo type 500	4
-27	R7	A-67-41321	D	RESISTOR, FIXED, COMPOSITION — same as R3	Ref
-28	C4	A-25-74243	D	CAPACITOR, FIXED, ELECT — same as C9	Ref
-29	R5	A-59-41321	D	RESISTOR, FIXED, COMPOSITION – same as R6	Ref
-30	C1	A-25-74243	D	CAPACITOR, FIXED, ELECT — same as C9	Ref
-31	R 4	A-67-41321	D	RESISTOR, FIXED, COMPOSITION — same as R3	Ref
-32	C2	A-25-74243	D	CAPACITOR, FIXED, ELECT - same as C9	Ref
-33	TS1	A-5-78408	D	THERMOSTAT - opens 160°F ±8°; closes 180°F ±8°; Elmwood Sensor Series (F180 88-58)	1
-34	R1 (not shown)	A-8-62377	D	RESISTOR, FIXED, FILM — 0.2 ohm, 5W, ±3%; Tepro type TS5W	2
-35	Ql	A-1-67703	D	TRANSISTOR — Westinghouse type 2N3055	3
-36	R2 (not shown)	A-8-62377	D	RESISTOR, FIXED, FILM - same as Rl	Ref
-37	Q2	A-1-67703	D	TRANSISTOR — same as Ql	Ref
-38	Q3	A-1-67703	D	TRANSISTOR — same as Ql	Ref
-39	CR4	A-2-41409	D	SEMICONDUCTOR DEVICE, DIODE — same as CR10	Ref
-40	CR3	A-2-41409	D	SEMICONDUCTOR DEVICE, DIODE - same as CR10	Ref
-41	CR8	A-4-92571	D	SEMICONDUCTOR DEVICE, DIODE - same as CR11	Ref
-42	Fl	A-81342	D	FAN, AXIAL - 0.003 HP, 16W, 115V, 60 Hz; Howard Industries Model 1075-3038	1
-43	T2	T-66620	D	TRANSFORMER	1
-44		A-4-92571	D	SEMICONDUCTOR DEVICE, DIODE - same as CR11	R ef
-45	PC2	A-87243-B	D	PRINTED WIRING ASSY - (See Figure 5-13 for additional parts breakdown)	1

Fig. & Index No.	Designation	Acme Part No.	Inden-	Description	Qty per
- 46	PC1	A-84702-A	D	PRINTED WIRING ASSY - (See Figure	Ass'y
- 47	C11	A-5-80289	D	5-14 for additional parts breakdown) CAPACITOR, FIXED, ELECT - 4000 µF, 15V; Sprague type 39D	1
- 48	R10	A-1-82119	D	RESISTOR, VARIABLE - 50 ohms, 2W	,
-49	B4B	A-55703	D	CONNECTOR, RECEPTACLE, ELECT – Hubbell P/N 5252	1 2
-50	взв	A-55703	D	CONNECTOR, RECEPTACLE, ELECT - same as B4B	Ref
-51	B2C	A-3-45705	D	CONNECTOR, RECEPTACLE - Burndy type MS-20RM-58	2
-52	B2B	A-11-58608	D	CONNECTOR, RECEPTACLE — c/o Heyco DC-202 and Acme Housing P/N A-6-58608-01	1
- 53	B2A	A-3-45705	D	CONNECTOR, RECEPTACLE — same as B2C	Ref
- 54	BlB	A-89705	D	CONNECTOR, RECEPTACLE, ELECT- Hubbell Type P/N 5278	1
	R11	A-2-67813	D	RESISTOR, VARIABLE - 0.15 ohm, 105W	1
	R12	A-1-57288	D	RESISTOR, VARIABLE - 1 ohm, 12W	l
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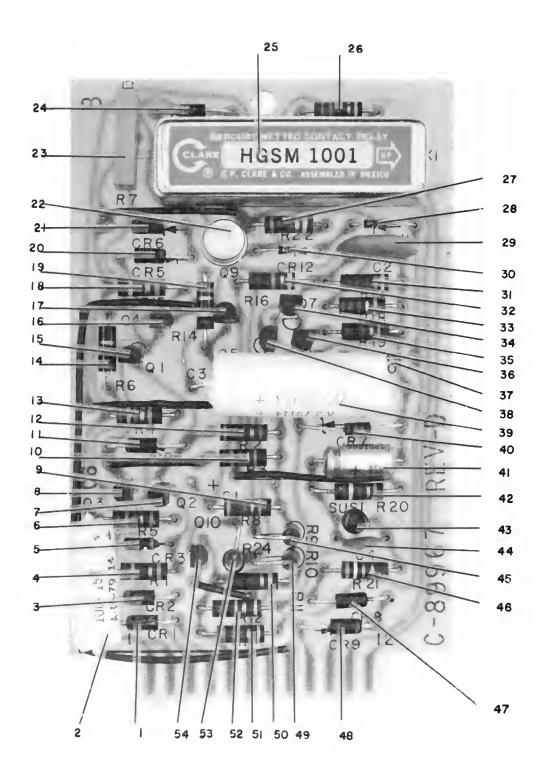


Figure 5-13. Printed Circuit Board (PC2), Parts Location Diagram

Fig. & Index No.	Designation	Acme Part No.	Inden-		Qty per
140.	Designation	Fart No.	ture	Description	Ass'y
5-13	PC2	A-87243-B	D	PRINTED WIRING ASSY — (Refer to Figure 5-12-45 for the next higher assembly)	Ref
-1	CR1	A-4-82573	F	SEMICONDUCTOR DEVICE, DIODE - Westinghouse type 1 N5395	7
-2	C6	A-16-79114	E	CAPACITOR, FIXED - 100 μF 15V	7
-3	CR2	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE — same as CR1	Ref
- 4	R1	A-86-44507	E	RESISTOR, FIXED, COMPOSITION - 240 ohms, 2W, ±5%	2
- 5	CR3	A-4-50538	E	SEMICONDUCTOR DEVICE, DIODE - type 1 N747A	1
-6	R5	A-19-44507	E	RESISTOR, FIXED, COMPOSITION - 680 ohms, 1/2W, ±5%	1
- 7	Q2	A-1-80269	E	TRANSISTOR - Motorola type 2N3903	4
-8	Q3	A-1-80269	E	TRANSISTOR — same as Q2	Ref
-9	R8	A-48-44507	E	RESISTOR, FIXED, COMPOSITION - 3K ohms, 1/2W, ±5%	1
-10	R3	A-17-44507	E	RESISTOR, FIXED, COMPOSITION - 6.8K ohms, 1/2W, ±5%	1
-11	CR4	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE — same as CR1	Ref
-12	R2	A-33-44507	E	RESISTOR, FIXED, COMPOSITION - 8.2K ohms, 1/2W, ±5%	1
-13	R4	A-50-44507	E	RESISTOR, FIXED, COMPOSITION - 1.3K ohms, 1/2W, ±5%	1
-14	R6	A-40-44507	E	RESISTOR, FIXED, COMPOSITION - 200 ohms, 1/2W, ±5%	1
-15	Q1	A-1-80270	E	TRANSISTOR - Motorola type 2N3905	4
-16	Q4	A-1-80269	E	TRANSISTOR - same as Q2	Ref
-17	Q 5	A-1-80270	E	TRANSISTOR - same as Q1	Ref
-18	R15	A-86-44507	E	RESISTOR, FIXED, COMPOSITION - same as R1	Ref
-19	R14	A-21-44507	Е	RESISTOR, FIXED, COMPOSITION - 3,9K ohms, 1/2W, ±5%	1
-20	CR5	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE - same as CR1	Ref
-21	CR6	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE — same as CR1	Ref
-22	Q 9	A-2-80115	E	TRANSISTOR - type 2N697	1
-23	R7	A-8-81756	E	RESISTOR, VARIABLE - 2K ohms	1
-24	CR13	A-1-86133	E	SEMICONDUCTOR DEVICE, DIODE - type 1N4001	1

Fig. & Index No.	Designation	Acme Part No.	Inden- ture	Description	Qty per Ass'y
-25	Kl	A-89760	E	RELAY, MERCURY, WETTED - C. P. Clare P/N HGSM1001	1
-26	R23	A-18-44507	E	RESISTOR, FIXED, COMPOSITION $-$ 330 ohms, $1/2W$, $\pm 5\%$	1
-27	R22	A-58-44507	E	RESISTOR, FIXED, COMPOSITION — 820 ohms, 1/2W, ±5%	1
-28	CR11	A-89761	E	SEMICONDUCTOR DEVICE, DIODE - type 1N914	1
-29	C2	A-6-88012	E	CAPACITOR, FIXED, CERAMIC - 0.1 µF, 100V	1
-30	CR12	A-89761	E	SEMICONDUCTOR DEVICE, DIODE — same as CR11	Ref
-31	R17	A-6-44507	E	RESISTOR, FIXED, COMPOSITION — 1.5K ohms, 1/2W, ±5%	1
-32	R16	A-43-44507	E	RESISTOR, FIXED, COMPOSITION - 10K ohms, 1/2W, ±5%	1
-33	R18	A-22-44507	E	RESISTOR, FIXED, COMPOSITION — 2.2K ohms, 1/2W, ±5%	Ref
-34	Q7	A-1-80269	E	TRANSISTOR — same as Q2	Ref
-35	R19	A-1-44507	E	RESISTOR, FIXED, COMPOSITION - 100 ohms, 1/2W, ±5%	1
-36	Q8	A-1-80269	E	TRANSISTOR - same as Q2	Ref
-37	CR10	A-89761	E	SEMICONDUCTOR DEVICE, DIODE - same as CR11	Ref
-38	Q6	A-1-80270	E	TRANSISTOR — same as Ql	Ref
-39	C3	A-3-79114	E	CAPACITOR, FIXED = 100 μF, 35V	1
-40	CR7	A-7-78467	E	SEMICONDUCTOR DEVICE, DIODE - type 1N4734A	1
-41	C5	A-1-51997	E	CAPACITOR, FIXED, ELECTRICAL - 1 µF, 25V, Sprague 30D, type TE1200	1
-42	R20	A-9-44507	E	RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, ±5%	1
-43	SUSI	A-3-82197	E	TRANSISTOR - type 2N4989	1
-44	C4	A-2-88012	E	CAPACITOR, FIXED, CERAMIC - 0.01 µF, 100V	1
-45	R9	A-53-44507	E	RESISTOR, FIXED, COMPOSITION – 470 ohms, 1/2W, ±5%	1
- 46	R21	A-44507	E	RESISTOR, FIXED, COMPOSITION – 3.9 ohms, 1/2W, ±5%	1
-47	CR8	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE-	Ref
-48	CR9	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE—same as CR1	Ref
-49	R10	A-44-44507	E	RESISTOR, FIXED, COMPOSITION- 910 ohms, 1/2W, ±5%	1

Fig. & Index No.	Designation	Acme Part No.	Inden- ture	Description	Qty per Ass'y
-50	R11	A-5-44507	E	RESISTOR, FIXED, COMPOSITION - 1K ohms, 1/2W, ±5%	1
-51	R13	A-32-44507	E	RESISTOR, FIXED, COMPOSITION - 6.2K ohms, 1/2W, ±5%	1
-52	R12	A-16-59094	E	RESISTOR, FIXED, COMPOSITION - 200K ohms, ±5%	1
-53	R24	A-31-44507	E	RESISTOR, FIXED, COMPOSITION - 5.1K ohms, 1/2W, ±5%	1
-54	Q10	A-1-80270	E	TRANSISTOR - same as Ql	Ref

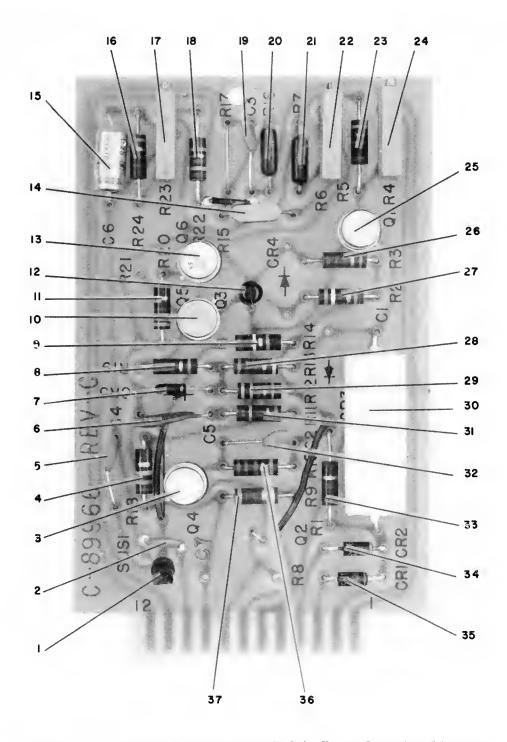


Figure 5-14. Printed Circuit Board (PCI), Parts Location Diagram

Fig. & Index No.	Designation	Acme Part No.	Inden-	Description	Qty per
110.	Designation	Tait No.	ture		Ass'y
5-14	PCl	A-84702-A	D	PRINTED WIRING ASSY — (Refer to Figure 5-12-46 for the next higher assembly)	Ref
-l	SUSI	A-3-82197	E	TRANSISTOR - type 2N4989	1
-2	C7	A-2-88012	E	CAPACITOR, FIXED, CERAMIC - 0.01 µF, 100V	3
- 3	Q4	A-1-73737	E	TRANSISTOR - type 2N3053	4
-4	R18	A-95-44507	E	RESISTOR, FIXED, COMPOSITION - 18K ohms, 1/2W, ±5%	1
- 5	C4	A-2-88012	E	CAPACITOR, FIXED, CERAMIC — same as C7	Ref
-6	C5	A-7-71984	E	CAPACITOR, FIXED, CERAMIC - 0.12 µF, 20V	1
-7	CR5	A-4-59072	E	SEMICONDUCTOR DEVICE, DIODE - type 1 N936	1
-8	R19	A-22-44507	E	RESISTOR, FIXED, COMPOSITION - 2.2K ohms, 1/2W, ±5%	1
-9	R14	A-9-59094	E	RESISTOR, FIXED, COMPOSITION - 100K ohms, 1/2W, ±5%	1
-10	Q5	A-1-73737	E	TRANSISTOR — same as Q4	Ref
-11	R20	A-48-44507	E	RESISTOR, FIXED, COMPOSITION — 3K ohms, 1/2W, ±5%	1
-12	Q3	A-1-83242	E	TRANSISTOR - type 2N4248	1
-13	Q6	A-1-51997	E	TRANSISTOR — same as Q4	Ref
-14	R 15	NOT	USED		!
-15	C6	A-1-51997	E	CAPACITOR, FIXED $-1~\mu\text{F}$, 25V, Sprague 30D, Type TE1200	1
-16	R24	A-24-44507	E	RESISTOR, FIXED, COMPOSITION - 1.5K ohms, 1/2W, ±5%	1
-17	R23	A-6-81756	E	RESISTOR, VARIABLE - 500 ohms	1
-18	R22	A-50-44507	E	RESISTOR, FIXED, COMPOSITION - 1.3K ohms, 1/2W, ±5%	1
-19	C3	A-2-88012	E	CAPACITOR, FIXED, CERAMIC - same as C7	Ref
-20	R16	A-36-76348	E	RESISTOR, FIXED, FILM -4.99 K ohms, $\pm 1\%$, type RN60D	1
-21	R7	A-34-76348	E	RESISTOR, FIXED, FILM — 4.87K ohms, ±1%, type RN60D	1
-22	R6	A-8-81756	E	RESISTOR, VARIABLE - 1K ohms	1
-23	R5	A-5-44507	E	RESISTOR, FIXED, COMPOSITION – 1K ohms, 1/2W, ±5%	1
-24	R4	A-7-81756	E	RESISTOR, VARIABLE - 1K ohms	1
-25	Ql	A-1-73737	E	TRANSISTOR — same as Q4	Ref
		1	ll		

Fig. & Index No.	Designation	Acme Part No.	Inden- ture	Description	Qty per Ass'y
-26	R3	A-22-44507	E	RESISTOR, FIXED, COMPOSITION – 2.2K ohms, 1/2W, ±5%	1
-27	R2	A-21-44507	E	RESISTOR, FIXED, COMPOSITION - 3.9K ohms, 1/2W, ±5%	1
-28	R13	A-32-44507	E	RESISTOR, FIXED, COMPOSITION - 6.2K ohms, 1/2W, ±5%	1
-29	R12	A-12-44507	E	RESISTOR, FIXED, COMPOSITION - 3.3K ohms, 1/2W, ±5%	1
-30	C1	A-1-79114	E	CAPACITOR, FIXED, ELECT- 150 µF, 35V	1
-31	Rll	A-38-44507	E	RESISTOR, FIXED, COMPOSITION - 270 ohms, 1/2W, ±5%	1
-32	C2	A-1-71984	E	CAPACITOR, FIXED, CERAMIC - 0.001 µF, 1 KV	1
-33	R1	A-40-44507	E	RESISTOR, FIXED, COMPOSITION - 200 ohms, 1/2W, ±5%	1
-34	CR2	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE - Westinghouse type 1 N5395	2
-35	CR1	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE — same as CR2	Ref
-36	R10	A-25-44507	E	RESISTOR, FIXED, COMPOSITION - 1.2K ohms, 1/2W, ±5%	1
-37	R9	A-56-44507	E	RESISTOR, FIXED, COMPOSITION - 7.5K ohms, 1/2W, ±5%	1

PART II ACME POWER SUPPLY, MODEL PS-2-59307

Part II contains one section presenting the illustrated parts breakdown and two schematics for Model PS-2-59307 manufactured by Acme Electric Corporation per Honeywell SCD 950 061 003. The operation of Model PS-2-59307 is similar to Acme Electric Model PS-1-59307. Therefore, refer to Part I, Section 1, for the physical layout, theory of operation, maintenance, troubleshooting procedure and adjustment for Model PS-2-59307 Power Supply.

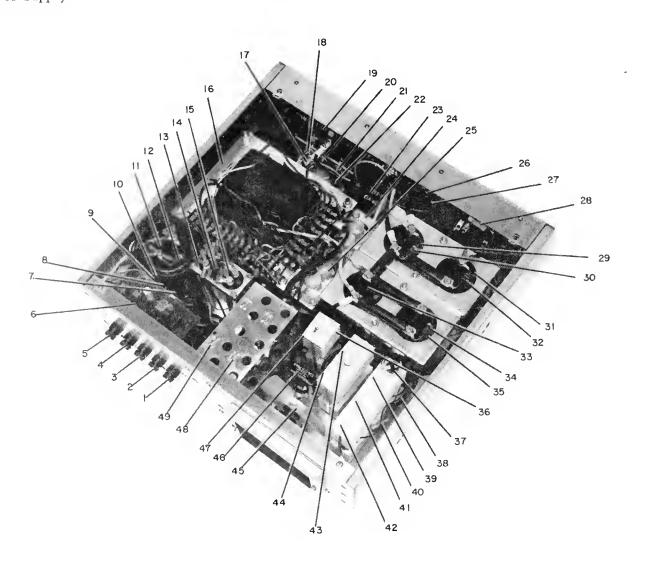


Figure 5-15. Power Supply, Acme Model PS-2-59307, Parts Location Diagram (Sheet 1 of 2)

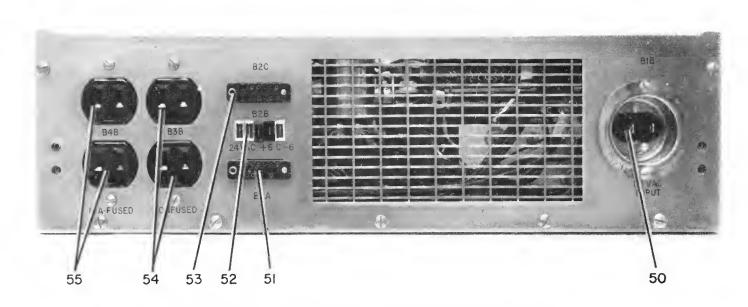


Figure 5-15. Power Supply, Acme Model PS-1-59307, Parts Location Diagram (Sheet 2 of 2)

Fig. & Index No.	Desig- nation	Acme Part No.	Inden- ture	Description	Qty per Ass'y
5-15		70950061003*	С	POWER SUPPLY, ACME ELEC CORP. Part No. PS-2-59307	
-1	A5A	A-7-27241	С	FUSE, CARTRIDGE - 1.5A Bussman AGC; fst-blowing type	1
-2	AlA	A-25-74310	D	FUSE, CARTRIDGE - 3A Bussman MDAA; slow-blowing type	1
-3	A2A	A-32-74310	D	FUSE, CARTRIDGE - 10A Bussman MDA10A; slow-blowing type	1
-4	A3A	A-31-74310	D	FUSE, CARTRIDGE - 8A Bussman MDA8A, slow-blowing type	1
-5	A4A	A-10-23108	D	FUSE, CARTRIDGE - 8A Bussman ABC8A; fast-blowing type	1
-6	PC3	A-1-95726	D	PRINTED CIRCUIT BOARD - (See Figure 5 for additional Parts Break- down)	1
-7	CR6	A-2-82573	D	SEMICONDUCTOR DEVICE, DIODE - Westinghouse type 1N5392	4
-8	CR5		D	SEMICONDUCTOR DEVICE, DIODE - same as CR6	Ref
-9	CR2		D	SEMICONDUCTOR DEVICE, DIODE - same as CR6	Ref
-10	CRI		D	SEMICONDUCTOR DEVICE, DIODE - same as CR6	Ref
-11	C3	A-60-74243	D	CAPACITOR, FIXED, ELECT - 21,500 µF; 40V; Mallory type CGS	1
-12	R3	A-47-41321	D	RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 2W ±5%	3
-13	C7	A-27-74243	D	CAPACITOR, FIXED, ELECT - 6000 μF, 40V	2
-14	R6	A-41-62377	D	RESISTOR, FIXED, COMPOSITION - 250 ohms, 5W, ±5%	3
-15	C6	A-57-74343	D	CAPACITOR, FIXED, ELECT - same as C7	Ref
-16	Τl	T-65717	D	TRANSFORMER, POWER	1
-17	CR10	A-2-41409	D	SEMICONDUCTOR DEVICE, DIODE - Westinghouse type 1N1184A	3
-18	CR9	A-2-92571	D	SEMICONDUCTOR DEVICE, DIODE - Westinghouse type 1N3616	2
-19	Rll	A-2-67813	D	RESISTOR, VARIABLE - 0.2 ohm, 105W	1
-20	CR 12	A-2-93571	D	SEMICONDUCTOR DEVICE, DIODE - same as CR9	Ref
-21	CRll	A-4-92571	D	SEMICONDUCTOR DEVICE, DIODE - Westinghouse type 1N3618	3
-22	SCR 1	A-2-61908	D	THYRISTOR - type 2N682, GEC35Fx50F964	1

*Honeywell Part Number

Fig. & Index	Desig- nation	Acme Part No.	lnden- ture	Description	Qty per Ass'y
-23	Ll	T-15-56515	D	CHOKE	l
-24	C10	A-5-81411	D	CAPACITOR, FIXED, ELECT - $5 \mu F$, $660 V$	2
-25	C5	A-5-81411	D	CAPACITOR, FIXED, ELECT - same as C10	Ref
-26	R8 (not shown)	A-59-41321	D	RESISTOR, FIXED, COMPOSITION - 1K ohm, 2W, ±5%	Ref
-27	C8	A-55-74243	D	CAPACITOR, FIXED, ELECT - 2000 µF, 40V; Mallory type CGS	1
-28	R12	A-157288	D	RESISTOR, VARIABLE - 2 ohms, 25W	1
-29	R7	A-67-41321	D	RESISTOR, FIXED, COMPOSITION - same as \mathbb{R}^3	Ref
-30	C9	A-25-74243	D	CAPACITOR, FIXED, ELECT - 76,000 µF, 15V; Sangamo type 500	4
-31	C4	A-25-74243	D	CAPACITOR, FIXED, ELECT - same as C9	Ref
-32	R 5	A-28-41321	D	RESISTOR, FIXED, COMPOSITION - 36 ohms, 2W	Ref
-33	Cl	A-25-74243	D	CAPACITOR, FIXED, ELECT - same as C9	Ref
-34	R4	A-67-41321	D	RESISTOR, FIXED, COMPOSITION - same as R3	Ref
-35	C2	A-25-74243	D	CAPACITOR, FIXED, ELECT - same as C9	Ref
-36	CR7	A-4-92571	D	SEMICONDUCTOR DEVICE, DIODE - same as CR11	Ref
-37	TS1	A-5-78408	D	THERMOSTAT - opens 160°F ±8°; closes 180°F ±8°; Elmwood Sensor Series (F180 88-58)	1
-38	R l (not shown)	A-8-62377	D	RESISTOR, FIXED, FILM - 0.2 ohm, 5W, ±3%, Tepro type TS5W	2
-39	Q1	A-1-67703	D	TRANSISTOR - Westinghouse type 1561-0604	3
-40	R2 (not shown)	A-8-62377	D	RESISTOR, FIXED, FILM - same as R1	Ref
-41	Q2	A-1-67703	D	TRANSISTOR - same as Ql	Ref
-42	Q3	A-1-67703	D	TRANSISTOR - same as Ql	Ref
-43	CR4	A-2-41409	D	SEMICONDUCTOR DEVICE, DIODE - same as CR10	Ref
-44	CR3	A-2-41409	D	SEMICONDUCTOR DEVICE, DIODE - same as CR10	Ref
-45	Fl	A-81342	D	FAN, AXIAL - 0.003 HP, 16W, 115V, 60 Hz; Howard Industries Model 6-218-152	1

	l				
Fig. & Index	Desig-		Inden-		Qty
No.	nation	Part No.	ture	Description	per Ass'y
14	TT 3	m (///20	n	TD AVGDON (TD	
-46	T2	T-66620	D	TRANSFORMER	1
47	CR8	A-4-92571	D	SEMICONDUCTOR DEVICE, DIODE - same as CR11	Ref
-48	PC2	A-1-87243B	D	PRINTED WIRING ASSY - (See Figure 5-13 for additional parts breakdown)	1
-49	PC l	A-1-74602A	D	PRINTED WIRING ASSY - (See Figure 5-14 for additional parts breakdown)	1
-50	BlB	A-89705	D	CONNECTOR, RECEPTACLE, ELECT- Hubbell Type P/N 5278	1
-51	B2A	A-3-45705	D	CONNECTOR, RECEPTACLE - Burndy type MS-20RM-58	2
-52	B2B	A-11-58608	D	CONNECTOR, RECEPTACLE - c/o Heyco DC-202 and Acme Housing P/N A-6-58608-01	1
-53	B2C	A-3-45705	D	CONNECTOR, RECEPTACLE - same as B2A	Ref
-54	B3B	A-55703	D	CONNECTOR, RECEPTACLE, ELECT- Hubbell P/N 5252	2
-55	B4B	A-55703	D	CONNECTOR, RECEPTACLE, ELECT- same as B3B	Ref
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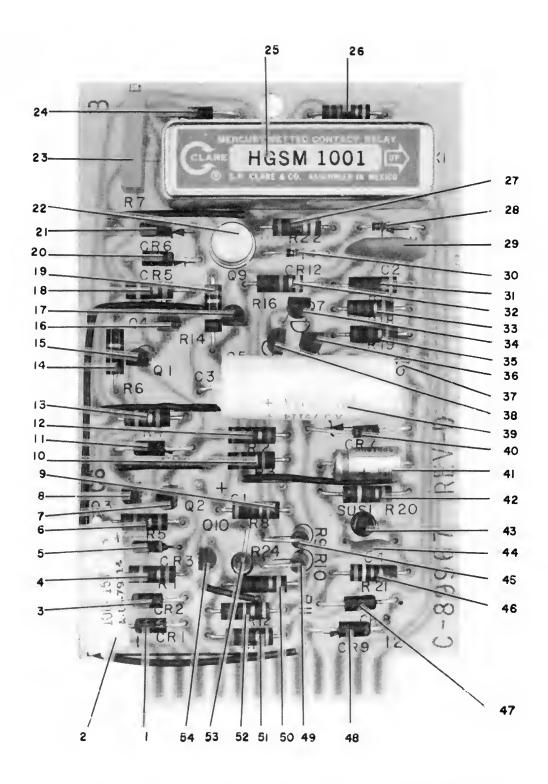


Figure 5-16. Printed Circuit Board (PC2), Parts Location Diagram

Fig. & Index No.	Desig- nation	Acme Part No.	Inden- ture	Description	Qty per Ass'y
5-16	PC2	A-87243	D	PRINTED CIRCUIT BOARD - (Refer to Figure 5-12-48 for the next higher assembly)	Ref
-1	CRI	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE- Westinghouse type 384H	7
-2	C6	A-16-79114	E	CAPACITOR, FIXED - 100 µF 15V	7
-3	CR2	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE — same as CR1	Ref
-4	R1	A-86-44507	E	RESISTOR, FIXED, COMPOSITION - 240 ohms, 2W, ±5%	2
-5	CR3	A-4-50538	E	SEMICONDUCTOR DEVICE, DIODE - type 1N747A	1
-6	R5	A-19-44507	E	RESISTOR, FIXED, COMPOSITION - 680 ohms, 1/2W, ±5%	1
-7	Q2	A-1-80269	E	TRANSISTOR - Motorola type 2N3903	4
-8	Q3	A-1-80269	E	TRANSISTOR — same as Q2	Ref
-9	R8	A-48-44507	E	RESISTOR, FIXED, COMPOSITION - 3K ohms, 1/2W, ±5%	1
-10	R3	A-17-44507	E	RESISTOR, FIXED, COMPOSITION $-$ 6.8K ohms, $1/2W$, $\pm 5\%$	1
-11	CR4	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE — same as CR1	Ref
-12	R2	A-33-44507	E	RESISTOR, FIXED, COMPOSITION - 8.2K ohms, 1/2W, ±5%	1
-13	R4	A-50-44507	E	RESISTOR, FIXED, COMPOSITION – 1.3K ohms, 1/2W, ±5%	1
-14	R6	A-40-44507	E	RESISTOR, FIXED, COMPOSITION — 200 ohms, 1/2W, ±5%	1
-15	Q1	A-1-80270	E	TRANSISTOR — Motorola type 2N3905	4
-16	Q4	A-1-80269	E	TRANSISTOR — same as Q2	Ref
-17	Q5	A-1-80270	E	TRANSISTOR — same as Q1	Ref
-18	R15	A-86-44507	E	RESISTOR, FIXED, COMPOSITION same as R1	Ref
-19	R14	A-21-44507	E	RESISTOR, FIXED, COMPOSITION 3.9K ohms, 1/2W, ±5%	1
-20	CR5	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE — same as CR1	Ref

Fig. & Index No.	Desig- nation	Acme Part No.	Inden- ture	Description	Qty per Ass'y
-21	CR6	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE — same as CR1	Ref
-22	Q9	A-2-80115	E	TRANSISTOR - type 2N697	1
-23	R7	A-8-81756	E	RESISTOR, VARIABLE - 2K ohms	1
-24	CR13	A-1-86133	E	SEMICONDUCTOR DEVICE, DIODE - type 1N4001	1
-25	K1	A-89760	E	RELAY, MERCURY, WETTED C.P. Clare P/N HGSM1001	1
-26	R23	A-18-44507	E	RESISTOR, FIXED, COMPOSITION - 330 ohms, 1/2W, ±5%	1
-27	R22	A-58-44507	E	RESISTOR, FIXED, COMPOSITION - 820 ohms, 1/2W, ±5%	1
-28	CR11	A-89761	E	SEMICONDUCTOR DEVICE, DIODE - type 1N914	1
-29	C2	A-6-88012	E	CAPACITOR, FIXED, CERAMIC — 0.1 µF, 100V	1
-30	CR12	A-89761	E	SEMICONDUCTOR DEVICE, DIODE — same as CR11	Ref
-31	R17	A-6-44507	E	RESISTOR, FIXED, COMPOSITION $-$ 1.5K ohms, $1/2W$, $\pm 5\%$	1
-32	R16	A-43-44507	E	RESISTOR, FIXED, COMPOSITION — 10K ohms, 1/2W, ±5%	1
-33	R18	A-22-44507	E	RESISTOR, FIXED, COMPOSITION - 2.2K ohms, 1/2W, ±5%	Ref
-34	Q7	A-1-80269	E	TRANSISTOR — same as Q2	Ref
-35	R19	A-1-44507	E	RESISTOR, FIXED, COMPOSITION - 100 ohms, 1/2W, ±5%	1
-36	Q8	A-1-80269	E	TRANSISTOR — same as Q2	Ref
-37	CR10	A-89761	E	SEMICONDUCTOR DEVICE, DIODE — same as CR11	Ref
-38	Q6	A-1-80270	E	TRANSISTOR — same as Q1	Ref
-39	C3	A-3-79114	E	CAPACITOR, FIXED - 100 μF, 35V	1
-40	CR7	A-7-78467	E	SEMICONDUCTOR DEVICE, DIODE - type 1N4734A	1
-41	C5	A-1-51997	E	CAPACITOR, FIXED, ELECTRICAL — 1 µF, 25V, Sprague 30D, type TE1200	1
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Fig. & Index No.	Desig- nation	Acme Part No.	Inden- ture	Description	Qty per Ass'y
-42	R20	A-9-44507	E	RESISTOR, FIXED, COMPOSITION - 2.4K ohms, 1/2W, ±5%	1
-43	SUS1	A-3-82197	E	TRANSISTOR - type 2N4989	1
-44	C4	A-2-88012	E	CAPACITOR, FIXED, CERAMIC - 0.01 µF, 100V	1
-45	R9	A-53-44507	E	RESISTOR, FIXED, COMPOSITION - 470 ohms, 1/2W, ±5%	1
-46	R21	A-44507	E	RESISTOR, FIXED, COMPOSITION - 3.9 ohms, 1/2W, ±5%	1
-47	CR8	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE — same as CR1	Ref
-48	CR9	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE — same as CR1	Ref
-49	R10	A-44-44507	E	RESISTOR, FIXED, COMPOSITION - 910 ohms, 1/2W, ±5%	1
- 50	R11	A-5-44507	E	RESISTOR, FIXED, COMPOSITION - 1K ohms, 1/2W, ±5%	1
-51	R13	A-32-44507	E	RESISTOR, FIXED, COMPOSITION - 6.2K ohms, 1/2W, ±5%	1
-52	R12	A-16-59094	E	RESISTOR, FIXED, COMPOSITION - 200K ohms, ±5%	1
-53	R24	A-31-44507	E	RESISTOR, FIXED, COMPOSITION - 5.1K ohms, 1/2W, ±5%	1
-54	Q10	A-1-80270	E	TRANSISTOR — same as Q1	Ref
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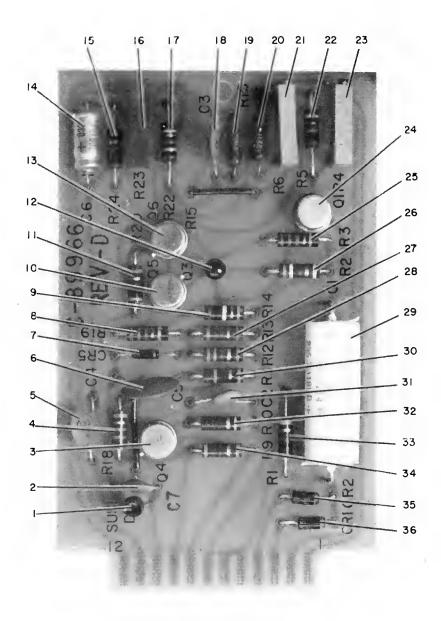


Figure 5-17. Printed Circuit Board (PC1), Parts Location Diagram

Fig. & Index No.	Desig- nation	Acme Part No.	Inden- ture	Description	Qty per Ass'y
5-17	PC1	A-84702-A	D	PRINTED CIRCUIT BOARD - (Refer to Figure 5-12-46 for the next higher assembly)	Ref
-1	SUSI	A-3-82197	E	TRANSISTOR - type 2N4989	1
-2	C7	A-2-75736	E	CAPACITOR, FIXED, CERAMIC - $0.01~\mu F$, $50V$	3
-3	Q4	A-1-73737	E	TRANSISTOR - type 2N3053	4
-4	R18	A-95-44507	E	RESISTOR, FIXED, COMPOSITION - $18K$ ohms, $1/2W$, $\pm 5\%$	1
- 5	C4	A-2-75736	E	CAPACITOR, FIXED, CERAMIC - same as C7	Ref
-6	C5	A-11-85474	E	CAPACITOR, FIXED, CERAMIC - 0.10 µF, 20V	1
-7	CR5	A-4-59072	E	SEMICONDUCTOR DEVICE, DIODE - type 1N936	1
-8	R19	A-22-44507	E	RESISTOR, FIXED, COMPOSITION - 2.2K ohms, $1/2W$, $\pm 5\%$	1
-9	R14	A-9-59095	E	RESISTOR, FIXED, COMPOSITION - $100K$ ohms, $1/2W$, $\pm 5\%$	1
-10	Q5	A-1-73737	E	TRANSISTOR - same as Q4	Ref
-11	R20	A-48-44507	E	RESISTOR, FIXED, COMPOSITION - 3K ohms, 1/2W, ±5%	1
-12	Q3	A-1-83242	E	TRANSISTOR - type 2N4248	1
-13	Q6	A-1-73737	E	TRANSISTOR - same as Q4	Ref
-14	C6	A-1-51997	E	CAPACITOR, FIXED - 1 µF, 25V, Sprague 30D, type TE1200	· 1
-15	R24	A-6-44507	E	RESISTOR, FIXED, COMPOSITION - 1.5K ohms, 1/2W, ±5%	, 1
-16	R23	A-6-81756	E	RESISTOR, VARIABLE - 500 ohms	1
-17	R22	A-50-44507	E	RESISTOR, FIXED, COMPOSITION - 1.3K ohms, 1/2W, ±5%	1
-18	C3	A-2-75736	E	CAPACITOR, FIXED, CERAMIC - same as C7	Ref
-19	R16	A-49-94562- 91	E	RESISTOR, FIXED, FILM - 499K ohms, ±1%, type RN60D	1
-20	R7	A-42-94562- 21	E	RESISTOR, FIXED, FILM - 4.22K ohms, ±1%, type RN60D	1
-21	R6	A-8-81756	E	RESISTOR, VARIABLE - 2K ohms	l
-22	R5	A-5-44507	E	RESISTOR, FIXED, COMPOSITION - 1K ohms, 1/2W, ±5%	1
-23	R4	A-7-81756	E	RESISTOR, VARIABLE - 1K ohms	l
-24	Ql	A-1-73737	E	TRANSISTOR - same as Q4	Ref
-25	R3	A-22-44507	E	RESISTOR, FIXED, COMPOSITION - 2.2K ohms, 1/2W, ±5%	1

Fig. & Index	Desig- nation	Acme Part No.	Inden- ture	Description	Qty per Ass'y
-26	R2	A-21-44507	E	RESISTOR, FIXED, COMPOSITION - 3.9K ohms, 1/2W, ±5%	1
-27	R13	A-32-44507	E	RESISTOR, FIXED, COMPOSITION - $6.2K$ ohms, $1/2W$, $\pm 5\%$	1
-28	R12	A-12-44507	E	RESISTOR, FIXED, COMPOSITION - $3.3K$ ohms, $1/2W$, $\pm 5\%$	1
-29	Cl	A-1-79114	E	CAPACITOR, FIXED, ELECT - 150 µF, 35V	1
-30	Rll	A-38-44507	E	RESISTOR, FIXED, COMPOSITION - 270 ohms, $1/2W$, $\pm 5\%$	1
-31	C2	A-1-71984	E	CAPACITOR, FIXED, CERAMIC - 0.001 µF, 1 kV	1
-32	R10	A-25-44507	E	RESISTOR, FIXED, COMPOSITION - 1.2K ohms, 1/2W, ±5%	1
-33	Rl	A-40-44507	E	RESISTOR, FIXED, COMPOSITION - 200 ohms, $1/2W$, $\pm 5\%$	1
-34	R9	A-56-44507	E	RESISTOR, FIXED, COMPOSITION - 7.5K ohms, 1/2W, ±5%	1
-35	CR2	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE - Westinghouse type 384H	2
-36	CR l	A-4-82573	E	SEMICONDUCTOR DEVICE, DIODE - same as CR2	Ref
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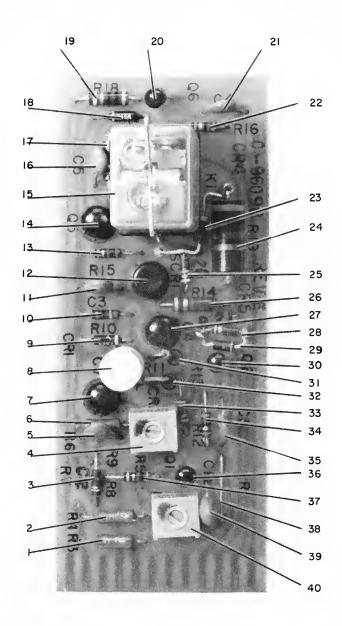


Figure 5-18. Printed Circuit Board (PC3), Part Location Diagram

PC3	Qty per Ass'y	Description	Inden- ture	Acme Part No.	Desig- nation	Fig. & Index No.
-2 R4 A-36-94562 E RESISTOR, FIXED, FILM - 365 ohms, 0.25W -3 R9 A-41-72691 E RESISTOR, FIXED, FILM - 120 ohms, 0.25W -4 R5 A-4-93416 D RESISTOR, FIXED - 100 pF, 1 kV -5 C2 A-30-71984 E CAPACITOR, FIXED - 100 pF, 1 kV -6 R6 A-33-94562 E RESISTOR, FIXED, FILM - 332 ohms, 0.25W -7 Q3 A-1-83243 E TRANSISTOR - Replacement type 2N5135 -8 C7 A-21-85850 E CAPACITOR, FIXED - 50 μH, 15 Vdc -9 CR1 A-2-50538 E DIODE - Replacement type 1N746A -10 R10 A-35-72691 E RESISTOR, FIXED, FILM - 68 ohms, 0.25W -11 C3 A-30-71984 E CAPACITOR, FIXED - 100 pF, 1 kV Same as C2 -12 SCR1 A-2-71320 E DIODE - C6F -13 R15 A-46-72691 E RESISTOR, FIXED, FILM - 200 ohms, 0.25W -14 Q5 A-1-83243 E TRANSISTOR - same as Q3 -15 K1 A-8-77170 E RELAY - 12 Vdc-T154-2C-12 Vdc -16 C5 A-30-71984 E CAPACITOR, same as C3 -17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR, same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	Ref	Figure 5-12-6 for the next higher	D	A-1-95726	PC3	5-18
-50	1		E	•	R3	-1
-4 R5 A-4-93416 D RESISTOR, POTENTIOMETER - 500 ohms, 1W -5 C2 A-30-71984 E CAPACITOR, FIXED - 100 pF, 1 kV -6 R6 A-33-94562 E RESISTOR, FIXED, FILM - 332 ohms, 0.25W -7 Q3 A-1-83243 E TRANSISTOR - Replacement type 2N5135 -8 C7 A-21-85850 E CAPACITOR, FIXED - 50 μH, 15 Vdc -9 CR1 A-2-50538 E DIODE - Replacement type 1N746A -10 R10 A-35-72691 E RESISTOR, FIXED, FILM - 68 ohms, 0.25W -11 C3 A-30-71984 E CAPACITOR, FIXED - 100 pF, 1 kV Same as C2 -12 SCR1 A-2-71320 E DIODE - C6F -13 R15 A-46-72691 E RESISTOR, FIXED, FILM - 200 ohms, 0.25W -14 Q5 A-1-83243 E TRANSISTOR - same as Q3 -15 K1 A-8-77170 E RELAY - 12 Vdc-T154-2C-12 Vdc -16 C5 A-30-71984 E CAPACITOR, same as C3 -17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - same as C2 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -23 CR4 A-1-82573 E DIODE - Replacement type 2N4248 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 0.25W -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 0.25W	1		E	,	R4	-2
500 ohms, 1W -5 C2 A-30-71984 E CAPACITOR, FIXED - 100 pF, 1 kV -6 R6 A-33-94562 E RESISTOR, FIXED, FILM - 332 ohms, 0.25W -7 Q3 A-1-83243 E TRANSISTOR - Replacement type 2N5135 -8 C7 A-21-85850 E CAPACITOR, FIXED - 50 μH, 15 Vdc -9 CR1 A-2-50538 E DIODE - Replacement type 1N746A -10 R10 A-35-72691 E RESISTOR, FIXED, FILM - 68 ohms, 0.25W -11 C3 A-30-71984 E CAPACITOR, FIXED - 100 pF, 1 kV Same as C2 -12 SCR1 A-2-71320 E DIODE - C6F -13 R15 A-46-72691 E RESISTOR, FIXED, FILM - 200 ohms, 0.25W -14 Q5 A-1-83243 E TRANSISTOR - same as Q3 -15 K1 A-8-77170 E RELAY - 12 Vdc-T154-2C-12 Vdc -16 C5 A-30-71984 E CAPACITOR, same as C3 -17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	1		E	A-41-72691	R9	-3
-6 R6 A-33-94562 E RESISTOR, FIXED, FILM - 332 ohms, 0.25W -7 Q3 A-1-83243 E TRANSISTOR - Replacement type 2N5135 -8 C7 A-21-85850 E CAPACITOR, FIXED - 50 μH, 15 Vdc -9 CR1 A-2-50538 E DIODE - Replacement type 1N746A -10 R10 A-35-72691 E RESISTOR, FIXED, FILM - 68 ohms, 0.25W -11 C3 A-30-71984 E CAPACITOR, FIXED - 100 pF, 1 kV Same as C2 -12 SCR1 A-2-71320 E DIODE - C6F -13 R15 A-46-72691 E RESISTOR, FIXED, FILM - 200 ohms, 0.25W -14 Q5 A-1-83243 E TRANSISTOR - same as Q3 -15 K1 A-8-77170 E RELAY - 12 Vdc - T154-2C - 12 Vdc -16 C5 A-30-71984 E CAPACITOR, same as C3 -17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	1		D	A-4-93416	R5	-4
-20 332 ohms, 0.25W -7 Q3 A-1-83243 E TRANSISTOR - Replacement type 2N5135 -8 C7 A-21-85850 E CAPACITOR, FIXED - 50 μH, 15 Vdc -9 CR1 A-2-50538 E DIODE - Replacement type 1N746A -10 R10 A-35-72691 E RESISTOR, FIXED, FILM - 68 ohms, 0.25W -11 C3 A-30-71984 E CAPACITOR, FIXED - 100 pF, 1 kV Same as C2 -12 SCR1 A-2-71320 E DIODE - C6F -13 R15 A-46-72691 E RESISTOR, FIXED, FILM - 200 ohms, 0.25W -14 Q5 A-1-83243 E TRANSISTOR - same as Q3 -15 K1 A-8-77170 E RELAY - 12 Vdc-T154-2C-12 Vdc -16 C5 A-30-71984 E CAPACITOR, same as C3 -17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.5W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	6	CAPACITOR, FIXED - 100 pF, 1 kV	E	A-30-71984	C2	- 5
-8 C7 A-21-85850 E CAPACITOR, FIXED - 50 μH, 15 Vdc -9 CR1 A-2-50538 E DIODE - Replacement type 1N746A -10 R10 A-35-72691 E RESISTOR, FIXED, FILM - 68 ohms, 0.25W -11 C3 A-30-71984 E CAPACITOR, FIXED - 100 pF, 1 kV Same as C2 -12 SCR1 A-2-71320 E DIODE - C6F -13 R15 A-46-72691 E RESISTOR, FIXED, FILM - 200 ohms, 0.25W -14 Q5 A-1-83243 E TRANSISTOR - same as Q3 -15 K1 A-8-77170 E RELAY - 12 Vdc-T154-2C-12 Vdc -16 C5 A-30-71984 E CAPACITOR, same as C3 -17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	1		E	· ·	R6	-6
-9 CR1 A-2-50538 E DIODE - Replacement type 1N746A -10 R10 A-35-72691 E RESISTOR, FIXED, FILM - 68 ohms, 0.25W -11 C3 A-30-71984 E CAPACITOR, FIXED - 100 pF, 1 kV Same as C2 -12 SCR1 A-2-71320 E DIODE - C6F -13 R15 A-46-72691 E RESISTOR, FIXED, FILM - 200 ohms, 0.25W -14 Q5 A-1-83243 E TRANSISTOR - same as Q3 -15 K1 A-8-77170 E RELAY - 12 Vdc-T154-2C-12 Vdc -16 C5 A-30-71984 E CAPACITOR, same as C3 -17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	3		E	A-1-83243	Q3	-7
-10 R10 A-35-72691 E RESISTOR, FIXED, FILM - 68 ohms, 0.25W -11 C3 A-30-71984 E CAPACITOR, FIXED - 100 pF, 1 kV Same as C2 -12 SCR1 A-2-71320 E DIODE - C6F -13 R15 A-46-72691 E RESISTOR, FIXED, FILM - 200 ohms, 0.25W -14 Q5 A-1-83243 E TRANSISTOR - same as Q3 -15 K1 A-8-77170 E RELAY - 12 Vdc-T154-2C-12 Vdc -16 C5 A-30-71984 E CAPACITOR, same as C3 -17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	1	CAPACITOR, FIXED - 50 µH, 15 Vdc	E	A-21-85850	C7	-8
0.25W -11 C3 A-30-71984 E CAPACITOR, FIXED - 100 pF, 1 kV Same as C2 -12 SCR1 A-2-71320 E DIODE - C6F -13 R15 A-46-72691 E RESISTOR, FIXED, FILM - 200 ohms, 0.25W -14 Q5 A-1-83243 E TRANSISTOR - same as Q3 -15 K1 A-8-77170 E RELAY - 12 Vdc-T154-2C-12 Vdc -16 C5 A-30-71984 E CAPACITOR, same as C3 -17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	2	DIODE - Replacement type 1N746A	E	A-2-50538	CR l	-9
Same as C2 -12 SCR1	1		E	A-35-72691	R10	-10
-13 R15 A-46-72691 E RESISTOR, FIXED, FILM - 200 ohms, 0.25W -14 Q5 A-1-83243 E TRANSISTOR - same as Q3 -15 K1 A-8-77170 E RELAY - 12 Vdc-T154-2C-12 Vdc -16 C5 A-30-71984 E CAPACITOR, same as C3 -17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	Ref		E	A-30-71984	C3	-11
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-15 K1 A-8-77170 E RELAY - 12 Vdc-T154-2C-12 Vdc -16 C5 A-30-71984 E CAPACITOR, same as C3 -17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	1		E	A-46-72691	R 15	-13
-16 C5 A-30-71984 E CAPACITOR, same as C3 -17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	Ref	TRANSISTOR - same as Q3	E	A-1-83243	Q 5	-14
-17 R17 A-5944507 E RESISTOR, FIXED, FILM - 510 ohms, 0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	1	RELAY - 12 Vdc-T154-2C-12 Vdc	E	A-8-77170	Kl	-15
0.5W -18 CR2 A-2-50538 E DIODE - same as CR1 -19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	Ref	CAPACITOR, same as C3	E	A-30-71984	C5	-16
-19 R18 A-71-4407 E RESISTOR, FIXED, FILM - 30 ohms, 0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	1		E	A-5944507	R17	-17
0.5W -20 Q6 A-1-83242 E TRANSISTOR - Replacement type 2N4248 -21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	Ref	DIODE - same as CR l	E	A-2-50538	CR2	-18
-21 C4 A-30-71984 E CAPACITOR - same as C2 -22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	1		E	A-71-4407	R18	-19
-22 R16 A37-72691 E RESISTOR, FIXED, FILM - 82 ohms, 0.25W -23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	3	TRANSISTOR - Replacement type 2N4248	E	A-1-83242	Q6	-20
-23 CR4 A-1-82573 E DIODE - Replacement type 1N5392 -24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	Ref	CAPACITOR - same as C2	E	A-30-71984	C4	-21
-24 R19 A-49-41321 E RESISTOR, FIXED, FILM - 300 ohms, 2W	2		E	A37-72691	R 16	-22
2 W	3	DIODE - Replacement type 1N5392	E	A-1-82573	CR4	-23
-25 R20 A-1-72692 E RESISTOR, FIXED, FILM - 10K, 0.25W	1		E	A-49-41321	R 19	-24
· · · · · · · · · · · · · · · · · · ·	l	RESISTOR, FIXED, FILM - 10K, 0.25W	E	A-1-72692	R20	-25
-26 R14 A-6-44507 E RESISTOR, FIXED, FILM - 1.5K, 0.5W	1	RESISTOR, FIXED, FILM - 1.5K, 0.5W	E	A-6-44507	R 14	-26

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No.	Fig. & Index	Desig-		Inden-		
-28 R21 A-67-72691 E RESISTOR, FIXED, FILM - 1.5K, 1 -29 CR5 A-1-82673 E DIODE - same as CR4 Ref -30 Q2 A-1-83243 E TRANSISTOR - same as Q6 Ref -31 R11 A-79-72691 E RESISTOR, FIXED, FILM - 4.7K, 1 0.25W -32 CR3 A-1-82573 E DIODE - same as CR4 Ref -33 R13 A-19-44507 E RESISTOR, FIXED, FILM - 680 ohms, 1 0.5W -34 R12 A-37-72691 E RESISTOR, FIXED, FILM - same as Ref R16 -35 C5 A-30-71984 E CAPACITOR - same as C2 Ref -36 Q1 A-1-83242 E TRANSISTOR - same as Q6 R87 R8 A-47-44507 E RESISTOR, FIXED, FILM - 300 ohms 1 0.5W -38 R1 A-3-48082 E JUMPER No. 22 PVC wire 1 -39 C1 A-30-71984 E CAPACITOR - same as C2 Ref -39 C1 A-30-71984 E CAPACITOR - same as C2 Ref -40 R2 A-3-93416 E RESISTOR, POTENTIOMETER - 1	No.	nation	Part No.	ì	Description	
-28 R21 A-67-72691 E RESISTOR, FIXED, FILM - 1.5K, 0.25W -29 CR5 A-1-82673 E DIODE - same as CR4 Ref -30 Q2 A-1-83243 E TRANSISTOR - same as Q6 Ref -31 R11 A-79-72691 E RESISTOR, FIXED, FILM - 4.7K, 0.25W -32 CR3 A-1-82573 E DIODE - same as CR4 Ref -33 R13 A-19-44507 E RESISTOR, FIXED, FILM - 680 ohms, 0.5W -34 R12 A-37-72691 E RESISTOR, FIXED, FILM - same as Ref R16 -35 C5 A-30-71984 E CAPACITOR - same as C2 Ref -36 Q1 A-1-83242 E TRANSISTOR - same as Q6 Ref -37 R8 A-47-44507 E RESISTOR, FIXED, FILM - 300 ohms 0.5W -38 R1 A-3-48082 E JUMPER No. 22 PVC wire 1 -39 C1 A-30-71984 E CAPACITOR - same as C2 -40 R2 A-3-93416 E RESISTOR, POTENTIOMETER - 1	-27	Q4	A-1-83243	E	TRANSISTOR - same as Q3	Ref
-30 Q2 A-1-83243 E TRANSISTOR - same as Q6 Ref -31 R11 A-79-72691 E RESISTOR, FIXED, FILM - 4.7K, 0.25W -32 CR3 A-1-82573 E DIODE - same as CR4 Ref -33 R13 A-19-44507 E RESISTOR, FIXED, FILM - 680 ohms, 0.5W -34 R12 A-37-72691 E RESISTOR, FIXED, FILM - same as Ref R16 -35 C5 A-30-71984 E CAPACITOR - same as C2 Ref -36 Q1 A-1-83242 E TRANSISTOR - same as Q6 Ref -37 R8 A-47-44507 E RESISTOR, FIXED, FILM - 300 ohms 0.5W -38 R1 A-3-48082 E JUMPER No. 22 PVC wire 1 -39 C1 A-30-71984 E CAPACITOR - same as C2 -40 R2 A-3-93416 E RESISTOR, POTENTIOMETER - 1	-28	R21	A-67-72691	E		
-31 R11 A-79-72691 E RESISTOR, FIXED, FILM - 4.7K, 0.25W -32 CR3 A-1-82573 E DIODE - same as CR4 Ref -33 R13 A-19-44507 E RESISTOR, FIXED, FILM - 680 ohms, 0.5W -34 R12 A-37-72691 E RESISTOR, FIXED, FILM - same as Ref R16 R16 -35 C5 A-30-71984 E CAPACITOR - same as C2 Ref -36 Q1 A-1-83242 E TRANSISTOR - same as Q6 Ref -37 R8 A-47-44507 E RESISTOR, FIXED, FILM - 300 ohms 0.5W -38 R1 A-3-48082 E JUMPER No. 22 PVC wire 1 -39 C1 A-30-71984 E CAPACITOR - same as C2 Ref -40 R2 A-3-93416 E RESISTOR, POTENTIOMETER - 1	-29	CR5	A-1-82673	E	DIODE - same as CR4	Ref
-32 CR3 A-1-82573 E DIODE - same as CR4 Ref -33 R13 A-19-44507 E RESISTOR, FIXED, FILM - 680 ohms, 0.5W -34 R12 A-37-72691 E RESISTOR, FIXED, FILM - same as Ref R16 -35 C5 A-30-71984 E CAPACITOR - same as C2 Ref -36 Q1 A-1-83242 E TRANSISTOR - same as Q6 Ref -37 R8 A-47-44507 E RESISTOR, FIXED, FILM - 300 ohms 0.5W -38 R1 A-3-48082 E JUMPER No. 22 PVC wire -39 C1 A-30-71984 E CAPACITOR - same as C2 Ref -40 R2 A-3-93416 E RESISTOR, POTENTIOMETER -	-30	Q2	A-1-83243	E	TRANSISTOR - same as Q6	Ref
-33 R13 A-19-44507 E RESISTOR, FIXED, FILM - 680 ohms, 0.5W -34 R12 A-37-72691 E RESISTOR, FIXED, FILM - same as Ref R16 -35 C5 A-30-71984 E CAPACITOR - same as C2 Ref TRANSISTOR - same as Q6 Ref R8 A-47-44507 E RESISTOR, FIXED, FILM - 300 ohms 0.5W -38 R1 A-3-48082 E JUMPER No. 22 PVC wire 1 -39 C1 A-30-71984 E CAPACITOR - same as C2 -40 R2 A-3-93416 E RESISTOR, POTENTIOMETER - 1	-31	R11	A-79-72691	E	RESISTOR, FIXED, FILM - 4.7K, 0.25W	1
-34 R12 A-37-72691 E RESISTOR, FIXED, FILM - same as Ref R16 -35 C5 A-30-71984 E CAPACITOR - same as C2 Ref -36 Q1 A-1-83242 E TRANSISTOR - same as Q6 Ref -37 R8 A-47-44507 E RESISTOR, FIXED, FILM - 300 ohms 0.5W -38 R1 A-3-48082 E JUMPER No. 22 PVC wire 1 Ref -39 C1 A-30-71984 E CAPACITOR - same as C2 Ref -40 R2 A-3-93416 E RESISTOR, POTENTIOMETER - 1	-32	CR3	A-1-82573	E	DIODE - same as CR4	Ref
-35 C5 A-30-71984 E CAPACITOR - same as C2 Ref -36 Q1 A-1-83242 E TRANSISTOR - same as Q6 Ref -37 R8 A-47-44507 E RESISTOR, FIXED, FILM - 300 ohms 0.5W -38 R1 A-3-48082 E JUMPER No. 22 PVC wire -39 C1 A-30-71984 E CAPACITOR - same as C2 Ref -40 R2 A-3-93416 E RESISTOR, POTENTIOMETER - 1	-33	R13	A-19-44507	E		1
-36 Q1 A-1-83242 E TRANSISTOR - same as Q6 Ref -37 R8 A-47-44507 E RESISTOR, FIXED, FILM - 300 ohms 0.5W -38 R1 A-3-48082 E JUMPER No. 22 PVC wire 1 -39 C1 A-30-71984 E CAPACITOR - same as C2 Ref -40 R2 A-3-93416 E RESISTOR, POTENTIOMETER - 1	-34	R12	A-37-72691	E		Ref
-37 R8 A-47-44507 E RESISTOR, FIXED, FILM - 300 ohms 0.5W -38 R1 A-3-48082 E JUMPER No. 22 PVC wire 1 -39 C1 A-30-71984 E CAPACITOR - same as C2 Ref -40 R2 A-3-93416 E RESISTOR, POTENTIOMETER - 1	-35	C5	A-30-71984	E	CAPACITOR - same as C2	Ref
-38 R1 A-3-48082 E JUMPER No. 22 PVC wire 1 -39 C1 A-30-71984 E CAPACITOR - same as C2 Ref -40 R2 A-3-93416 E RESISTOR, POTENTIOMETER - 1	-36	Q1	A-1-83242	E	TRANSISTOR - same as Q6	Ref
-39 C1 A-30-71984 E CAPACITOR - same as C2 Ref -40 R2 A-3-93416 E RESISTOR, POTENTIOMETER - 1	-37	R8	A-47-44507	E		1
-40 R2 A-3-93416 E RESISTOR, POTENTIOMETER - 1	-38	Rl	A-3-48082	E	JUMPER No. 22 PVC wire	1
The state of the s	- 39	Cl	A-30-71984	E	CAPACITOR - same as C2	Ref
	-40	R2	A-3-93416	E	RESISTOR, POTENTIOMETER - 200 ohms, 1W	1
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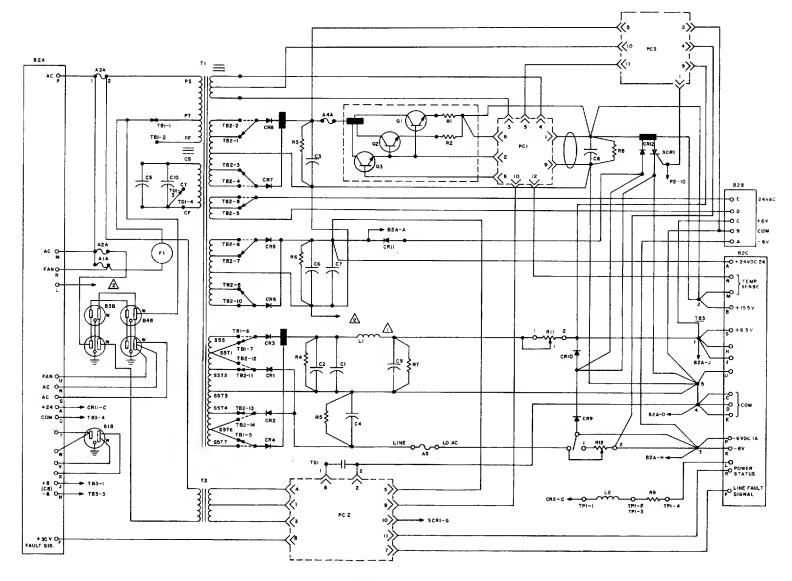


Figure 5-19. Basic Power Supply Schematic, Acme Model PS-2-59307

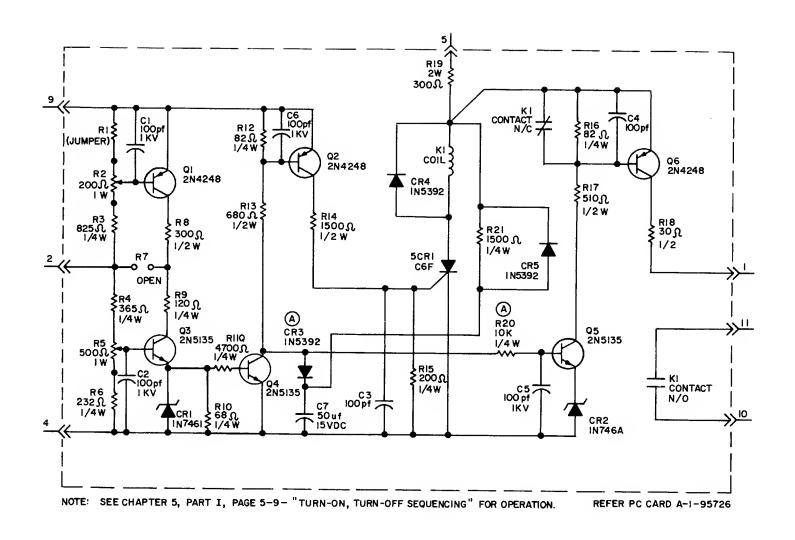


Figure 5-20. Sequencing Circuit Schematic (Printed Circuit Board A-1-95726) (PC3)

ADDENDUM TYPE 316/716 POWER DISTRIBUTION UNIT

SECTION 1 INTRODUCTION

GENERAL DESCRIPTION

The Type 316/716 Power Distribution Box is designed to provide 120 Vac onc-phase 60 Hz power to Type 316/716 drawers, μ -PAC option drawers and various peripheral devices via standard parallel blade duplex outlets.

The unit takes two phases of a three-phase system and splits it into two single-phase branch circuits, on which are contained five individual fused outlets.

SPECIFICATIONS

Electrical Specifications

<u>Input Voltage</u>. -- The input voltage to the power distribution box is a 208 Vac three-phase 60 Hz 5 wire service.

<u>Input Current</u>. -- Loading on the input lines will be from phase to neutral on two-phase only. The maximum load current per phase will be 24A, and there is no provision or procedure for balancing the load on the phase. The unused phase is terminated at the input connector and for possible future expansion.

Output Voltages and Currents. -- The voltage provided by each output connector is normally 120 Vac one-phase 60 Hz, and the maximum current that can be obtained from each duplex connector is 15A.

Power On/Off. -- The power distribution box is turned on and off by means of a 120 Vac control line from a Type 316/716 power supply or similar source which controls a two-pole contact within the box.

Mechanical Specifications

The dimensions of the power distribution are:

Length: 16.475 inches

Width: 19 inches
Height: 5.22 inches

The power distribution box consists of the following:

Sheet metal chassis

Input converter

Contacts

Five output converters

Five output Edison base fuses

Input circuit breaker

Input and output RFI filters.

The input and output connectors are mounted on the rear of the PD box: the circuit breaker and fuses are on the front. The contactor is attached to the inside of the front panel, and the RFI filters are located near the right side at the bottom of the box.

SECTION 2 OPERATING PROCEDURES

CONTROLS AND INDICATORS

There are no controls or indicators on the power distribution box.

OPERATING GUIDES

For personnel safety, do not replace fuses with the input circuit breaker in the $\,{\rm ON}\,$ position.

SECTION 3 FUNCTIONAL THEORY OF OPERATION

BLOCK DIAGRAM ANALYSIS

The block diagram of the power distribution box is shown in Figure A-1.

The ac input power enters the power distribution box through J8 and passes through an RFI filter to the circuit breaker. From there it goes to the contactor and J7 via a fuse. When the contactor is energizing by J6, power is provided to J1 through J5 via 15A fuses. J1 has an additional RFI filter for load which could generate noise onto the ac line.

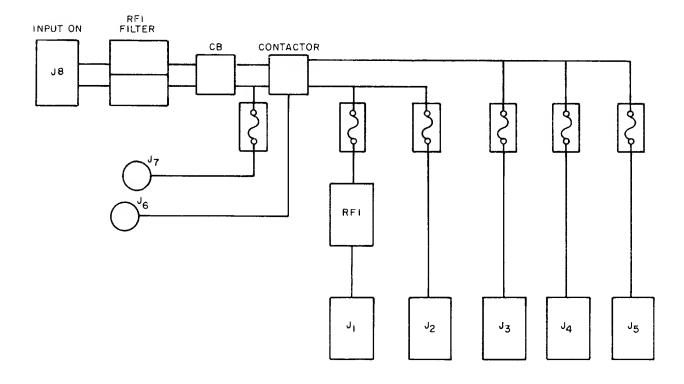


Figure A-1. Power Distribution Unit Block Diagram

SECTION 4 DETAILED THEORY OF OPERATION

DETAILED LOGIC DESCRIPTION

Refer to Figure A-3 for schematics. The power distribution box is designed to take two phases of a three-phase input power line and divide into two single-phase branch circuits for the operation of any Type 316/716 equipment which requires 120 Vac via a standard parallel blade plug.

J8 brings into the box two phases, neutral and earth ground. Earth ground (pin GR) is connected to the box by an integral stud which is also connected to the ground terminals of J1 through J7. The neutral line, Pin W, is wired directly to "cold" side of each connector (silver colored terminal). The two phases (pins X and Y) are each wired to a pi section RFI filter and then to a two-pole community circuit breaker. Thus, if a fault occurs in one phase, the other will also be disconnected. The breaker will trip for currents in excess of 24A. The output of the circuit breaker is wired to a two-pole contactor and one leg is also wired to J7 through a 15A fuse. The output of the contactor is wired to the "hot" side of the duplex outlet (brass color). When used in a Type 316/716 system, a Type 316/716 power supply is plugged into J7 and a cable from the duplex outlet on the Type 316/716 power supply is plugged into J6. With the circuit breaker in the ON position, power is applied to J7 and the switch on the Type 316/716 control panel which is plugged into J7 via the power supply. When the switch is turned on, the duplex outlet on the supply energizes the contactor through J6 thus applying power to J7 through J5 on the PD box. Conversely, when the switch on the control panel is turned off, power is also removed from the outlet on the PD box.

INTERFACE

Primary Power Interface

The ac input connector on the power distribution box, J8, mates with a Hubbell Model No. 25414 or equivalent.

Output Power Interface

Jl through J5 will mate with any parallel blade plug (i.e., Hubbell Cap. 5200 series or 5900 series).

Control Interface

J7 mates with any parallel blade plug (i.e., Hubbell Caps, 5200 series or 5900 series). J6 mates with a Hubbell Model No. 4730-K twist lock connector or equivalent.

SECTION 5 INSTALLATION

PRELIMINARY INFORMATION

Service personnel should be familiar with the complete installation procedure and safety precautions before attempting to install the Type 316/716 power distribution box.

Tools and Test Equipment

A medium size screwdriver is all that is required to install the Power Distribution Unit.

Space and Environmental Requirements

The space and environmental requirements are presented in the Mechanical Specification paragraph.

INTERFACE CONSIDERATIONS

Interface considerations are presented in the Electrical Specification.

INSTALLATION PROCEDURE

Mechanical Procedure

Refer to Figure A-2.

Electrical Interconnections

Refer to the Site Planning Manual (order no. AD71) for the input ac connection. For additional cabling information, refer to Table A-1 (wire list).

CHECKOUT PROCEDURE

Initial Checkout

Before plugging in power, check all fuses. Check that circuit breaker is in the OFF position, and check that all plugs to the Type 316/716 power supply are firmly seated in their pockets.

Cycle-up Checkout

Plug in ac connector and operate power switch on control panel. Check for $120 \mathrm{Vac}$ with ac voltmeter at each duplex output.

On-Line Checkout

Connect cables to duplex outlet and apply power via control panel. Check each device plugged into box for presence of ac power.

SECTION 6 MAINTENANCE

EQUIPMENT CONFIGURATION

Figure A-2 presents the installation and accessories drawing.

SECTION 7 TROUBLESHOOTING

TROUBLESHOOTING PROCEDURES

The box should be given a good visible inspection for damage to internal parts and input and output connectors.

Recommended Test Equipment

Ac voltmeter, ac ammeter.

Check Procedure

If there is no output at any of the connectors, check the following:

- a. Voltage present at input connector.
- b. Blown 15A fuse of Type 316/716 power supply.
- c. Control panel to Type 316/716 power supply cable not connected.
- d. Loose cables at J6 and J3.
- e. Defective contactor.
- f. Defective circuit breaker.

If there is no voltage at an individual output connector, check 15A fuses on front of PD box.

If individual fuse blows continuously, check for overload or shunt at output connector.

WIRE LIST

The wire list is presented in Table A-1.

Refer to Interface paragraph for interface connections.

Table A.l. PDU Wire List

From	To	Wire Color and Gage
XXAJ8J0X	XXA1001	BLK #10
XXAJ8J0Y	XXA1101	
XXAJ8J0W	XXAJ1J04	
XXA1102	XXB07-CB04	
XXA1102	XXB07-CB03	
XXB07-CB01	XXB0802	
XXB07-CB02	XXB0801	#10
XXBF6F01	XXB0802	BLK #14
XXB0808	XXAJ6P01	BLK
XXB0807	XXAJ6P02	BLK
XXBF1F02	XXA0901	RED
XXAJ2J04	XXAJ7J01	BLK
XXBF2F02	XXAJ2J02	RED
XXBF3F02	XXAJ3J02	RED
XXA0902	XXAJ1J02	BLK
XXBF2F01	XXB0805	BLK
XXBF3F01	XXB0806	BLK
XXBF4F02	XXAJ4J02	RED
XXBF4F01	XXB0806	BLK
XXBF5F01	XXB0806	BLK
XXBF5F02	XXAJ5J02	RED
XXBF6F02	XXAJ7J02	BLK #14
XXAJ1J03	XXAJ2J03	#10
XXAJ8J0W	XXAJ3J03	#10
XXAJ3J04	XXAJ4J04	# 1 O
XXAJ4J03	XXAJ5J03	#14
XXBF1F01	XXB0805	BLK #14
XXAJ8JGR	XXA12-GR01	GRN #10
XXA12-GR01	XXAJ01-J05	#14
XXAJ01-J05	XXAJ02-J05	
XXAJ02-J05	XXAJ03-J05	
XXAJ03-J05	XXAJ04-J05	
XXAJ04-J05	XXAJ05-J05	
XXAJ05-J05	XXAJ07-J03	
XXAJ07-J03	XXAJ06-J03	GRN #14

SECTION 8 REFERENCE DATA

PD UNIT SCHEMATIC (Figure A-3.)

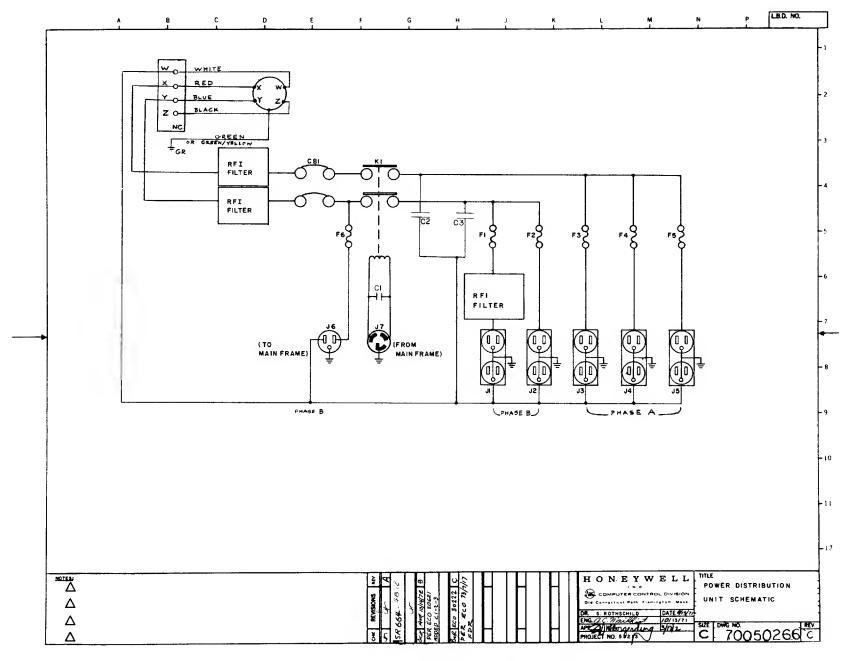


Figure A-3. Power Distribution Unit Schematic (Ref. Drawing C70050266, Rev. C)

SECTION 9 ILLUSTRATED PARTS BREAKDOWN

This section contains illustrated parts lists for the following power distribution unit assemblies.

	Table No.	Figure No.
Chassis Assembly	A-2	A-4
Coding Drawing	_	A-5

Table A-2. Chassis Assembly Parts List (See Figure A-4)

<u>Item</u>	Part Number	Description	Qty 702
01	7001954-702	CHASSIS, DET/ASSY	001
02	7001953-701	PANEL, FRONT DET/ASSY	001
03	70031806-701	COVER, PDU DET/ASSY	001
04	70942407-002	LINE FILTER	003
06	70960060-013	CIRCUIT BREAKER, CB 1	001
07	70982112-001	PLATE, IDENT	001
09	70941163-001	CONNECTOR, RECEPTACLE, ELECT, J7	001
10	70941323-001	CONNECTOR, RECEPTACLE, ELEC, J1-J5	005
11	04670063 - 029	FUSE-FUSTAT F1-F6	006
12	04670062-013	FUSE-HOLDER-FUSTAT	006
13	70901400-009	NUT, SHEET SPRING	010
15	70941334-001	CONNECTOR, RECEPTACLE, J6	001
17	70901005-002	NUT, #10-32	007
18	70902050-012	WASHER, FLAT, #10	007
19	70902006-043	WASHER, LOCK, #10	007
20	70963027-002	RELAY, SOLENOID, KI	001
21	70902006-042	WASHER, LK, #8-32	016
22	70902050-010	WASHER, FLAT, #8-32	016
23	70904113-046	SCREW, #8-32	006
24	70960060-102	CIRCUIT BREAKER, MTG BRKT	001
27	70032069-702	GROUND STRAP	001
28	70902003-032	WASHER, EXT, TOOTH #10	007
30	70032183-000	ONE-LINE DIAGRAM	001
31	70982128-003	PLATE, IDENT	001
32	70982131-001	PLATE, IDENT	001
33	70906164-001	CLAMP, CAP	003
34	70901003-006	HEX, NUT, 8-32	006
35	70908052-131	SPACER	001
36	04310020-015	CAP	003
37	70032761-702	CABLE, POWER	001
38	03510051-003	CLAMP, CABLE	001
39	70908035-004	CLIP, ELECT	001
40	70937506-005	BOARD, TERM	001
43	70031997-702	WIRE LIST	001
44	70033072-000	SCHEMATIC PDV	REF
45	70033073-000	CODING, DWG	REF
46	70982006-005	PLATE, DESIG	001

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